

News

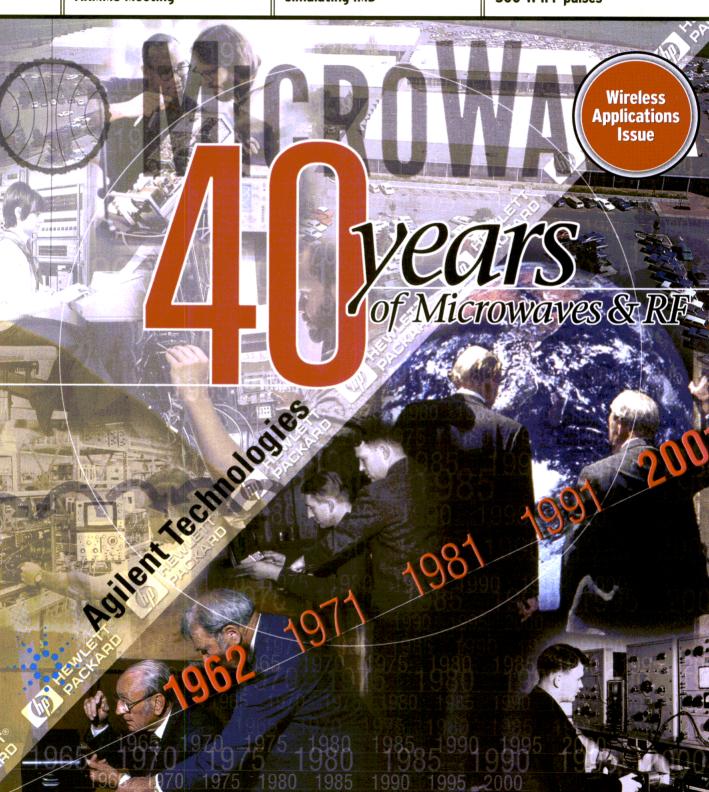
Report from the ARMMS Meeting

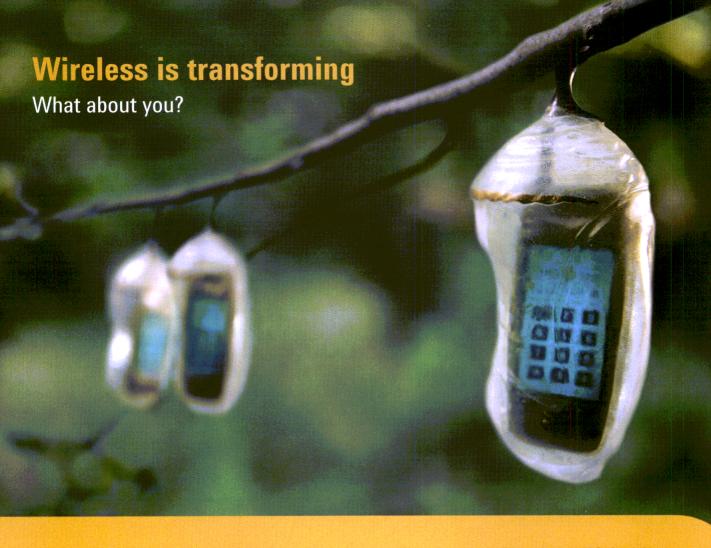
Design Feature

Techniques for simulating IMD

Product Technology

LDMOS device drives 500-W IFF pulses





www.anilent.com/find/3n

u.s. 1-800-452-4844, ext. 7325 canada 1-877-894-4414, ext. 7389 Will you keep pace with 3G, or will you set it? Profound change confronts the wireless world. Technologies are migrating fast and furiously toward 3G. Agilent has been spurring this evolution since the beginning, as a driving force on the test standards boards. So in collaborating with us, you'll propel yourself quickly ahead of the development curve. Not only are our solutions 3G compliant, they're infused with industry insight you'd expect from the company who helps define the test standards. Whether you're designing, verifying, or manufacturing, you'll have the solid foundation needed to focus on executing quickly. And, no matter where in the world your team is working, they'll have access to that expertise—whether it's W-CDMA, cdma2000, or EDGE. Dreams made real.



FULLY RELIABLE ALUMINUM

TRIDE

- Power Resistors
 - ◆ 10 200 Watt Models
 - Values 50 & 100 Ohm
 - 5% Tolerance Standard

Attenuators

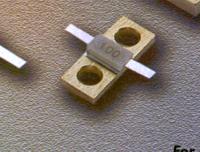
- ◆ 40 100 Watt Models
- Attenuation Values 1-30 dB

Terminations

- Power Up To 1000 Watts
- Excellent Broadband VSWR
- Coaxial Versions Available SMA, Type N, 7/16 & Others

Featuring

- · Flanged & flangeless configurations
- · BeO & lead free
- All welded leads
- Super high grade aluminum nitride (AIN)
- · Thin-film/thick-film
- Copper and copper/tungsten mounting flanges
- · High temperature attachment
- · Nickel, silver and gold plating



u III H SO 9001

For additional information, contact Paul Davidsson at 631-439-9348, fax 631-439-9333 or email pdavidsson@miteq.com

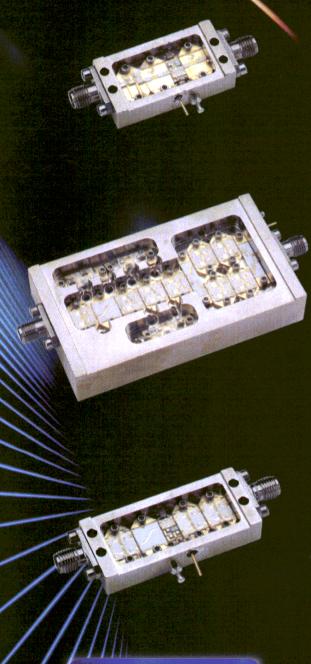
100 Davids Drive Hauppauge, NY 11788 TEL.: (631) 436-7400 • FAX: (631) 436-7430

www.miteg.com



AIIIPLIFIE

for every application



JCA TECHNOLOGY

DELIVERY IN 2-4 WEEKS ARO

4000 Via Fescador, Camarillo, CA 93012 (805) 445-9888 Fax: (805) 987-6990 email: jca@jcatech.com • www.jcatech.com

Enter No. 242 at www.mwrf.com

ULTRA BROAD BAND reg, Range Gain N/F Gain 1 dB Comp. 3rd Order VSWR

Model	Freq. Range GHz	Gain dB min	N/F dB max	Gain Flat +/-dB	1 dB Comp. pt. dBm min	3rd Order ICP typ	VSWR In/Out max	DC Current
JCA018-203	0.5-18.0	20	5.0	2.5	7	17	2.0:1	250
JCA018-204	0.5-18.0	25	4.0	2.5	10	20	2.0:1	300
JCA218-506	2.0-18.0	35	5.0	2.5	15	25	2.0:1	400
JCA218-507	2.0-18.0	35	5.0	2.5	18	28	2.0:1	450
JCA218-407	2.0-18.0	30	5.0	2.5	21	31	2.0:1	500

MULTI OCTAVE AMPLIFIERS

Model	Freq. Range GHz	Gain dB min	N/F dB max	Gain Flat +/-dB	1 dB Comp. pt. dBm min	3rd Order	VSWR In/Out max	DC Current
JCA04-403	0.5-4.0	27	5.0	1.5	17	27	2.0:1	550
JCA08-417	0.5-8.0	32	4.5	1.5	17	27	2.0:1	550
JCA28-305	2.0-8.0	22	5.0	1.0	20	30	2.0:1	550
JCA212-603	2.0-12.0	32	5.0	3.0	14	24	2.0:1	550
JCA618-406	6.0-18.0	20	6.0	2.0	25	35	2.0:1	600
JCA618-507	6.0-18.0	25	6.0	2.0	27	37	2.0:1	800

MEDIUM POWER AMPLIFIERS

Model	Freq. Range	Gain dB min	N/F dB max	Gain Flat +/-dB	1 dB Comp.	3rd Order	VSWR In/Out max	DC Current
JCA12-P01	1.35-1.85	35	4.0	1.0	33	41	2.0:1	1000
JCA34-P02	3.1-3.5	40	4.5	1.0	37	45	2.0:1	2200
JCA56-P01	5.9-6.4	30	5.0	1.0	34	42	2.0:1	1200
JCA812-P03	8.0-12.0	40	5.0	1.5	33	40	2.0:1	1700
JCA1218-P02	12.0-18.0	22	4.0	2.0	25	35	2.0:1	700

LOW NOISE OCTAVE BAND LNA'S

Model	Freq. Range GHz	Gain dB min	N/F dB max	Gain Flat +/-dB	1 dB Comp. pt. dBm min	3rd Order ICP typ	VSWR In/Out max	DC Current
JCA12-3001	1.0-2.0	40	0.8	1.0	10	20	2.0:1	200
JCA24-3001	2.0-4.0	32	1.2	1.0	10	20	2.0:1	200
JCA48-3001	4.0-8.0	40	1.3	1.0	10	20	2.0:1	200
JCA812-3001	8.0-12.0	32	1.8	1.0	10	20	2.0:1	200
JCA1218-800	12.0-18.0	45	2.0	1.0	10	20	2.0:1	250

NARROW BAND LNA'S

Model	Freq. Range	Gain dB min	N/F dB max	Gain Flat +/-dB	1 dB Comp.	3rd Order	VSWR In/Out max	DC Current
JCA12-1000	1.2-1.6	25	0.75	0.5	10	20	2.0:1	80
JCA23-302	2.2-2.3	30	0.8	0.5	10	20	2.0:1	80
JCA34-301	3.7-4.2	30	1.0	0.5	10	20	2.0:1	90
JCA56-401	5.4-5.9	40	1.0	0.5	10	20	2.0:1	120
JCA78-300	7.25-7.75	27	1.2	0.5	13	23	2.0:1	120
JCA910-3000	9.0-9.5	25	1.2	0.5	13	23	1.5:1	150
JCA910-3001	9.5-10.0	25	1.2	0.5	13	23	1.5:1	150
JCA1112-3000	11.7-12.2	27	1.1	0.5	13	23	1.5:1	150
JCA1213-3001	12.2-12.7	25	1.1	0.5	10	20	2.0:1	200
JCA1415-3001	14.4-15.4	35	1.4	1.0	14	24	2.0:1	200
JCA1819-3001	18.1-18.6	25	1.8	0.5	10	20	2.0:1	200
JCA2021-3001	20.2-21.2	25	2.0	0.5	10	20	2.0:1	200

Features:

- Removable SMA Connectors
- Competitive Pricing
- Compact Size

Options:

- Alternate Gain, Noise, Power, VSWR levels if required
- Temperature Compensation
- Gain Control



Maintaining Phase Stability Can Be a Real Balancing Act.

Introducing Phase Master™ A phase stable cable series from Storm

The Phase MasterTM series from Storm Products is ideally suited for demanding test, radar, and space applications where phase vs. temperature or phase vs. flexibility is critical. The cable offers superior performance made possible by Storm's unique MicroFormTM construction, which withstands the harmful effects of temperature and flexure.

- Unique MicroFormTM construction significantly improves stability over temperature and flexure
- Light weight—unarmored cable weighs only 17g/ft
- Excellent VSWR, low insertion loss, and high velocity of propagation

Phase Master $^{\scriptscriptstyle\mathsf{TM}}$. . . when stability hangs in the balance.



For more information on how Phase Master™ can benefit your program, visit www.stormproducts.com/microwave or call 630-323-9121 or 1-888-347-8676 (in U.S.).



Worth switching to...

■ ■ ■ Want to save more real estate in your cordless phone,

UPG158TB

Shown actual size, these low voltage L-Band SPDT switches are available now in low cost 6-pin 2.0 x 1.25 x 0.9 mm "super minimold" package.

PCS, and digital cellular handset designs? Our ultraminiature GaAs SPDT switches deliver wide bandwidth, low insertion loss

and high P_{1dB} , plus the quality and consistency you've come to expect from NEC.

Best of all is the price. At less than 50 cents each in production quantities, they're switches worth switching to!

Ultraminiature GaAs Switches, from 49¢.

Want more information? You can download data sheets for our NEC switches directly from our website.

	UPG158TB	UPG137GV
FREQUENCY RANGE	100 MHz to 2.5 GHz	100 MHz to 2.5 GHz
INSERTION LOSS	0.4dB @ 2GHz	0.55 dB @ 1 GHz 0.65 dB @ 2 GHz
P _{1dB}	+27 dBm	up to +35 dBm
CONTROL VOLTAGE	+3V to +5V	+3V to +5 V
PACKAGE	6-pin super minimold	8 Pin SSOP
PRICE*	49¢	95¢

*100K Piece Qty.

They can all be found in our RFIC Selection Guide

Shown 3X actual size.

under GaAs RFICs at:

www.cel.com/prod/prod_rfics.asp

www.cel.com



Congratulations Microwaves & RF

CEL California Eastern Laboratories

NEC

 4590 Patrick Henry Drive
 Santa Clara, CA 95054
 408 988-3500

 DISTRIBUTORS: Arrow (800) 525-6666
 Reptron Electronics (888) REPTRON

 Mouser Electronics (800) 346-6873
 Electro Sonic (800) 567-6642 (CANADA)

AUGUST 2001 • VOL. 40 • NO. 8

Visit us at www.mwrf.com

Departments

13 **Feedback**

21 **Editorial**

26 The Front End

70 **Editor's Choice**

Financial News

76 People

78 Educational Meetings

80 **R&D Roundup**

102 Bookmark

183 **Application Notes**

208 **New Products**

216 **New Literature**

223 Infocenter

224 Looking Back

224 **Next Month**



COVER STORY

Garage Gives Birth To Measurement Giant

The story of Hewlett-Packard Co.. and subsequently Agilent Technologies, is a capsule history of test-andmeasurement techniques and equipment for the microwave industry.

News

ARRMS Meeting Melds **Simulation And** Testina

Special Section



- 85 Simulate IMD In RF **Amplifiers With Memory Effects**
- Construct An FMCW Front End For **Anticollision Radar**
- 107 CMOS SOS Switches Offer Useful Features, High Integration
- 122 EDA Software **Improves Accuracy** Of Microstrip Filter **Designs**
- 127 Parameter Describes Mixer IM Performance
- 133 Design A Low-Noise Synthesizer Using YRO Technology
- 147 Wideband VCO **Designs Are** Independent Of **Circuit Parameters**

Product Technology

- 185 LDMOS Delivers 500 W For IFF Systems
- 193 RF Subsystem **Enables Cable Telephony**
- 196 PLLs Shine With Sapphire Technology
- 199 SAW Filter Screens **GPS Receive Signals**
- 200 Simulator Tackles **Tricky EM Problems**
- 203 System Speeds Assembly Of RF **Power Devices**
- 204 SPICE-Based **Software Fine-Tunes Designs**





SUBSCRIPTION ASSISTANCE AND INFORMATION POSTMASTER:

Please send change of address to Microwaves & RF. Penton Media. Inc., The Penton Building, 1300 E. 9th St., Cleveland, OH 44114-1503. For other subscription information or assistance, please call (216) 696-7000 and have a copy of your mailing label handy

Microwaves & RF (ISSN 0745-2993) is published monthly, except semi-monthly in December. Subscription rates for US are \$80 for 1

year (\$105 in Canada, \$140 for International). Published by Penton Media, Inc., The Penton Building, 1300 E. 9th St., Cleveland, OH 44114-1503. Periodicals Postage Paid at Cleveland, OH and at additional mailing offices.

Canada Post International Publications Mail (Canadian Distribution Sales Agreement Number 344311). CAN. GST #R126431964.





WIERNE

INTERNET SITE #1

AVAILABILITY OF PRODUCT

Digi-Key®

#1

DELIVERY OF PRODUCT

1-800-DIGI-KEY www.digikey.com

© 2001 Digi-Key Corporation

The distributor Internet site most frequently visited by respondents in the Distributor Evaluation Study, Beacon Technology, October 2000. The distributor with the highest rating for Delivery of Product in the Distributor Evaluation Study, Beacon Technology, October 2000. The distributor with the highest rating for Availability of Product in the Distributor Evaluation Study, Beacon Technology, October 2000.

Enter No. 229 at www.mwrf.com

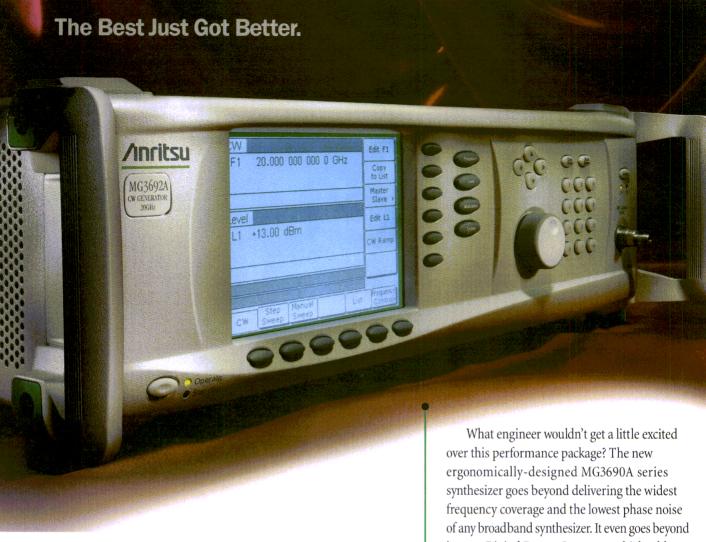




5305 Spectrum Drive, Frederick, Maryland 21703-7362 800-638-2048 • Tel: 301-846-9222 • Fax: 301-846-9116

e-mail: sales@weinschel.com • Web: www.weinschel.com





It's Quieter. It's Sleeker. It's Sexier.

(well, to an engineer)

its new Digital Down-Converter which adds uncompromising RF coverage to its already exceptional microwave performance. This nextgeneration Anritsu synthesizer takes you to a whole new level in engineering design.

It's not just about a sleek new body either. We're talking practical improvements like a larger display, fewer buttons, accessible menus and an intuitive interface. We've also made it 20 pounds lighter and trimmed off 6 inches in depth. And even with the MG3690A's powerful engine, you'll be amazed how quietly it runs.

For more information call 1-800-ANRITSU or go directly to our website product page at www.us.anritsu.com/adsmailers/MG3690A.asp. The MG3690A Broadband Synthesizer. When it comes to your Local Oscillator needs, the best has indeed gotten better.



MG3690A Broadband Synthesizer

©2001 Anritsu Company Sales Offices: United States and Canada, I-800-ANRITSU, Europe 44(01582)433200, Japan 81(03)3446-1111, Asia-Pacific 65-2822400, South America 55(21)527-6922, http://www.us.anritsu.com

Discover What's Possible™

What Goes In Comes Out.



And Nothing More.

If you're testing a driver amp or other piece of wireless equipment, you know the value of "nada". Because AR "S" Series amps are uniquely linear, the output signal is nothing more than an amplified, faithful representation of the amplifier's signal input.

"S" Series amplifiers also offer newly improved third-order intercept points and reduced spurious noise figures—so adjacent channel power is kept to a minimum. The required guard band between carriers is minimized. And you get the most from the precious available RF spectrum. An unusually broad frequency range accommodates cellular, PCS and Bluetooth frequencies as well as future frequency allocations. They're the market's most ideal amplifiers for telecommunications multi-tone input test applications.

"S" Series amplifiers. 0.8 to 4.2 GHz. 1 to 200 watts. Part of our microwave line found at www.amplifiers.com/ampmicro.cfm

ISO 9001 Certified

Copyright© 2001 Amplifier Research. The orange stripe on AR products is Reg. U.S. Pat. & Tm. Off.



Our wirewound RF chip inductors run circles around the competition



Higher Q Compared to non-wirewound chip coils, most Coilcraft parts have Q factors that are 50% to 150% higher.

Lower DCR Put as much as 3 times the current through our chip inductors thanks to their low DC resistance.

Higher SRF Ceramic construction shifts SRFs to much higher frequencies than multilayer or ferrite designs.

Tighter tolerance Precision manufacturing techniques let us consistently produce parts with 2% inductance tolerance. Our most popular values also come in 1% tolerance.

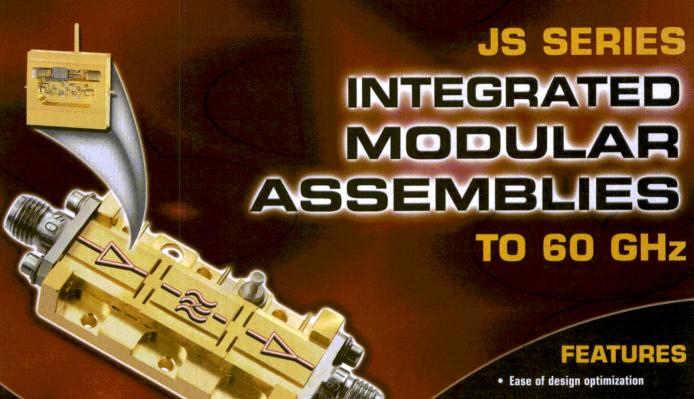
Better support From our engineer-friendly web site to our global manufacturing capabilities, Coilcraft is just plain easier to do business with.

ORDER YOU,

Visit us at www.coilcraft.com for technical data, free samples, simulation models and more.







MODULE TYPES

- Ultra-Broadband Amplifiers
- Medium Power Amplifiers
- High-Gain Amplifiers
- Low-Noise Amplifiers
- Frequency Multipliers
- High-Pass Filters
- Band-Pass Filters
- PIN Attenuators
- Power Dividers
- · Input Limiters
- IF Amplifiers
- Couplers

- Proven JS amplifier technology
- Superior noise and phase performance
- All modules contain internal regulation
- Module sizes are 0.45" L x 0.40" W x 0.11" H
- Compact assembly sizes fit most system applications

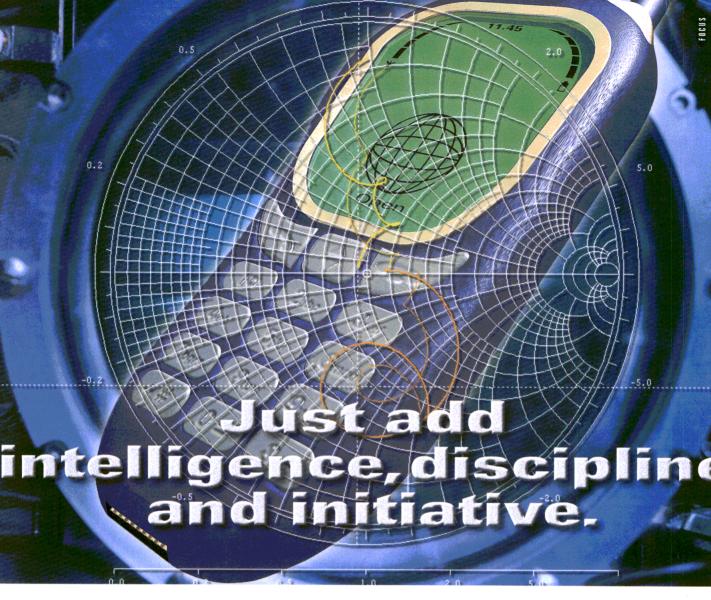
OPTIONS

- Combined isolated gain modules for up to 75 dB of total gain
- Integrated filtering to reduce noise bandwidth and I.M. distortion
- Ultra-low noise and medium power module pairings for high dynamic range
- PIN attenuators to enhance system flexibility
- Front-end RF limiters to protect against high level inputs
- A single-broadband input can be divided into multiple sub-bands



100 Davids Drive, Hauppauge, NY 11788 TEL.: (631) 436-7400 • FAX: (631) 435-7470/436-7430 miteg.com

6-7430 q.com



Want to know the secret of success in the land of Linux and Nokia? It's APLAC. An industrial-strength simulation technology that combines the functionality of Spice with the utility of an advanced RF simulator. APLAC, and only APLAC, provides the accurate IC- and board-level models and precise methods to analyze non-linear circuit behavior

demanded by top RF and analog designers. The only approach up to the complex design challenges ahead: 3G, Bluetooth, and beyond.

APLAC gives you something unique - the freedom to do things right. All you do is supply the three ingredients mentioned above.

To learn more about APLAC, why not download a student version from our website www.aplac.com and contact us at APLAC Solutions.





APLAC

APLAC Solutions Inc 320 Decker Dr, Suite 100, Irving, TX 75062 tel. 972-719-2562 www.aplac.com e-mail: sales@aplac.com APLAC Solutions Corporation
Atomitie 5 C, FIN-00370 HELSINKI, Finland tel. +358-9-540 450 00
www.aplac.com e-mail: sales@aplac.com

The Freedom To Do Things Right.

Enter No. 217 at www.mwrf.com

((feedback))

Article Credibility

▶▶PLEASE TELL ME that the article "Raise Bandwidth Efficiency With Sine-Wave-Modulation VMSK" in the April 2001 issue (p. 79) was just an April Fools' joke. Something tells me that it is not, however, because other credulous articles about VMSK have appeared for years in this and other trade publications—even the IEEE Transactions on Broadcasting.

When I first learned about VMSK in an August 2000 article of EDN, I found that elementary signal theory was enough to completely debunk the bandwidth and performance claims of Harold Walker and his equally confused colleagues. See the website: www.people.qual comm.com/karn/papers/vmsk.

I encourage Microwaves & RF to keep utter nonsense like this article from getting into print and confusing readers who do not know any better.

Phil Karn

Defends Article

▶▶PHIL KARN OF Qualcomm has been on a one-man crusade to prove that VMSK and similar "Ultra Narrow Bandwidth" modulation methods do not work. The reason for this is rather obvious-if a satisfactory method were proven in the marketplace, Qualcomm would be out of business. Karn, however, denies any Qualcomm interest.

VMSK is not the only narrowband method. It has predecessors going back 16 years. VMSK just happens to be the first one to be successfully tried over the air. Two cellular operators have made frequencies available for VMSK testingafter they witnessed the first successful demonstrations. Over-the-air tests are continuing in the US and Europe. Karn is very annoyed that we will not mention names so that he can pester them.

I would like to quote Dr. W.C.Y. Lee from his latest book, Essentials of Wireless Communications (McGraw Hill), "AlphaCom technology can also be used. It can send a 48 kb/s MD3 data stream through a 2 kHz filter and receives with good quality. The idea is to slightly mark the states of the modulation using VMSK so that less distortion of the carrier waveform can be achieved. Of course, we know that the undistorted CW carrier only needs a 1 Hz filter in principal." Having been present when Dr. Lee made his own VMSK measurements at Vodafone. I can say that he had adequate test equipment and demo hardware available.

VMSK does work. The only question is how well? Those who wish to participate in the debate should visit <VMSK.org>. Karn's comments are posted there also. His negative comments have been helpful to many experimenters, professors, and students. I personally congratulate K.H. Sayhood and Wu Lenan on their eye-opening paper.

H.R. Walker





TABLE OF CONTENTS

PlanetEE, the global resource for electronics engineers, is the home base for Penton Media Inc.'s Electronics Group. We focus on your needs by offering a rich blend of news, in-depth articles, educational tools, product writeups, and other resources. We've also separated the electronics industry into ten "technology communities," which corral all of a specific technology's material into core areas. Some of what you'll find on Planet EE includes:

TECHNOLOGY COMMUNITIES

- Analog/Mixed-Signal
- Components & Assemblies
- Embedded Systems
- Power Control & Supplies
- Digital ICs & ASICs
- Electronic Design Automation
- Interconnects/Packaging & Materials
- · Communications/Networking
- Computing & Information Appliances
- Test & Measurement

PRODUCT LOCATOR PLUS

- EE Product News' Product Locator
- Microwaves & RF's Product Data Directory
- VITA VMEbus/ESOFTA Product Indexes

RESOURCES

- Breaking Industry News
- Career Forum
- Ideas For Design
- Literature
- Events Calendar
- Education Center

Sign Up For PlanetEE's "Alert" E-Newsletters

- Bluetooth Alert
- Communications Alert
- Display Alert
- DSP Alert
- EDA Alert
- Netronics Alert
- Power Alert

PlanetEE's series of FREE focused email technology newsletters deliver expert analysis, the latest products, design tips, tutorials, and market information to aid you in developing your design projects. The "Alerts" are backed by the veteran editorial strength of the Penton Media Electronics Magazine Group: Electronic Design's David Morrison, Ashok Bindra, Louis Frenzel, and David Maliniak; Wireless Systems Design's Cheryl Ajluni; and Microwave & RF's Jack Browne, just to name a few. Go to www.PlanetEE.com and sign up now!



















Ideal for broadcast and cable systems test and measurement

CCR-33M10 SPDT Switch

- DC 3.0 GHz
- Mini SMB (MSMB) Pin Connectors
- Latching or Failsafe
- Actuator Voltage: +5, +12, or +28 VDC
- 20 msec Switching Time
- Indicator Circuits and TTL Options

ISO-9001









A Teledyne Technologies Company

Teledyne Wireless, 1274 Terra Bella Avenue, Mountain View, CA 94043, Phone: 800.832.6869, Fax: 650.962.6845

For Faster Information e-mail: switches@teledyne.com

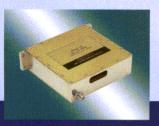
www.teledynewireless.com

Enter No. 291 at www.mwrf.com



Technologies Innovative Designs for the Future

Elcom's automated, high volume manufacturing capabilities reduce response time in order to keep your project cost-effective and on schedule.



RUGGED FREQUENCY SYNTHESIZERS

A series of rugged frequency synthesizers designed for high capacity MW and MMW digital radios up to 38 GHz. With an emphasis on **Guaranteed Zero Phase Hits**TM, the DFS Series offers extremely low microphonics and wide operating temperature range.

DC Power consumption below 4 watts is maintained by utilizing low power components resulting in low junction temperatures and overall high reliability.

r chabine,

SPECIFICATIONS

- Frequency Range: 0.5-23 GHz
- Tuning Bandwidths up to 1000 MHz
- Switching Speed: <25 ms
- Phase noise meets 16, 32, 128 & 256 QAM requirements
- Output Power Range: 12-18 dBm
- Load VSWR 1.5:1
- Step Sizes: 0.125-10.0 MHz



MICROWAVE FREQUENCY SYNTHESIZERS

This line of compact frequency synthesizers employs a single module design implemented with CMOS, ASIC, advanced RF MMIC and a dedicated microcomputer. A Ku-band synthesizer with I KHz step, 2.2 GHz bandwidth and integrated L-band LFLO consumes only 8 watts—a 65% savings compared to competing units.

Very low phase noise makes the MFS Series ideal for applications in Satcom converters (L, X, C, Ku and Ka Bands), Instrumentation and Wireless Communications

SPECIFICATIONS

- Output Frequency: I-23 GHz
- Frequency Bandwidth: I-2.25 GHz
- Phase Noise 20 dB Better than IESS
- Step Size: I KHz or I25 KHz
- · Switching Speed: 50 ms
- Power Output: 12-16 dBm
- Load VSWR: 2.0:1
- · In-Band Spurious: -70 dBc
- Out-of-Band Spurious:
 -82 dBc
- Fixed L-Band Output: Freq. Range: 0.5-3.0 GHz Pwr. Out.: 12 dBm ±2 dBm Spurious: -95 dBc
- · Low Profile: 0.73" high
- Meets IESS, Eutelsat and MIL-STD-188/146



PHASE LOCKED

OSCILLATORS

The PDRO series of oscillators employ a unique technique to phase-lock DROs to a crystal reference of 5 to 100 MHz. Several models in the series require only a single loop for reliable phase-lock performance. By utilizing just one loop, size and power consumption are minimized and multiple frequencies can be realized from the same reference. The low profile and small size (2.5" x 3.5" x 0.65") features ultra low phase noise and low DC power consumption with a ruggedized design and wide operating temperature range.

SPECIFICATIONS

- Frequency Range: 0.5-18 GHz
- Fractional Reference Multiplicator
- · -100 dBc Spurious
- Meets MIL-STD-188 & IESS 308
- Integrated Reference Optional (Same Package)



MINIATURE
PHASE LOCKED
OSCILLATORS

The miniature MPDRO sources employ a unique technology to phase-lock DRO to a crystal reference of 5 to 100 MHz. The technique requires only a single loop for reliable phase-lock performance. By using just one loop, size, power consumption and cost are minimized.

SPECIFICATIONS FOR THE MPDRO Series

- · 0.5 to 26 GHz Operation
- Single Loop, locks to 5 to 100 MHz Reference
- Ultra Low Phase Noise
- · Integrated Buffer Amplifier
- - 100 dBc Spurious
- Ruggedized
- Low DC Power Consumption
- Small 2.25" x 1.4" x 0.8"
- Meets MIL-STD-188 and IESS 308

Both the PDRO and MPDRO series of Phase Locked Oscillators are ideal for applications in Satcom Converters, Digital Radios and Instrumentation. In addition, the MPDRO series has applications as a fiber optic clock generator.

ADDITIONAL PRODUCTS PLANNED FOR ELCOM

- Clock Encoders and Decoders for DWDM Fiber Optic Networks up to 40 GHz
- Synthesized Clock Generator for DWDM Fiber Optic Networks up to 40 GHz
- Clock Recovery Modules for DWDM Fiber Optic Networks up to 40 GHz
- Dual Output Frequency Synthesizer for Digital Radios

Since 1995, Elcom Technologies, Inc., has experienced a rapid growth rate. We have always set the highest standards for quality, service and reliability with our products. As a result of our success, we are moving to a new, 32,000 sq. ft. modern facility in order to maximize our ability to meet our ever growing customer needs.

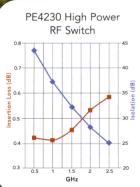


Technologies

11 Volvo Drive • Rockleigh, NJ 07647 (201) 767-8030 • Fax (201) 767-6266

For detailed information and data sheets, please visit www.elcom-tech.com
Enter No. 233 at www.mwrf.com





Rise above the noisy crowd and simplify your next wireless design with the world's first family of high performance, low insertion loss CMOS RF switches. Their exceptional >36dB isolation at 1 GHz and a CMOS/TTL compatible, singlepin control lets your wireless systems clearly perform better. Get clearer communications from Sapphire CMOS technology. For details visit our web site or call 858-455-0660.

3mm x 4.9mm

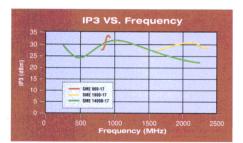


Available in +10 dBm Pada +21 dBm P_{1dB} or +31 dBm P_{1dB}





High IP3 Performance! Meet your cost and IP3 goals with WJ's SME Mixers.



High IP3 performance over frequency separates WJ mixers from the rest.

High IP3 and low conversion loss make the SME mixer a perfect choice for your cellular, PCS, 3G and broadband requirements. The SME draws no current and requires only 17 dBm LO drive to deliver an IP3 of 29 dBm.

		Ŋ	J HIG	H IP3 N	IIXER:	8		
Mixers	Freq	uency Range (I	ЛHz)	LO Power	P1dB	IIP3	Conversion	Isolation
MIAGIS	RF	LO	IF	(dBm)	(dBm)	(dBm)	Loss (dBm)	(I-R) (dB)
SME 900-17	820-960	720-940	20-100	+17	+14	+29	6.2	34
SME 1400B-10	1-2200	1-2200	1-2000	+10	+6	+19	6.5	30
SME 1400B-13	1-2200	1-2200	1-2000	+13	+9	+22	6.5	30
SME 1400B-17	1-2200	1-2200	1-2000	+17	+13	+27	6.5	30
SME 1900-17	1600-2400	1400-2390	10-250	+17	+14	+29	7.4	26

Get more details today. Call our toll free number, fax us at 408-577-6620 or e-mail us at sales@wj.com. Data sheets are available in PDF download files by visiting our web site at www.wj.com.

The Communications Edge™



Visit us on the web at www.wj.com

1-800-WJ1-4401

wj communications

Distributed In U.S.A. by **Nu Horizons Electronics**: 888-747-6846; **Richardson Electronics**: 800-737-6937
In Europe call **WJ:** +44-1252-661761 or your local Distributors: **Richardson Electronics-Worldwide**: 800-737-6937 Web Site: www.rell.com/gen_sales_locations.asp and **BFI Optilas-Europe**: Telephone (44) 1622 883467 Web Site: www.bfioptilas.avnet.com.





The Power to Turn your Ideas On

At K&L Microwave we provide real solutions for real people. As a global manufacturer and world leader in the production of RF and Microwave filters, we can satisfy your requirements from the most basic microminiature bandpass up to an integrated assembly. K&L Microwave has the technology to enhance your position in the global market by providing engineering solutions, technical support, quality products and global logistics. Our next generation design will help support your developing systems. Our recent capacity expansion enables us to maintain our outstanding delivery performance as customer demand increases.

WHETHER YOUR REQUIREMENTS ARE HIGH END MILITARY OR HIGH VOLUME COMMERCIAL... K&L HAS THE POWER TO TURN YOUR IDEAS ON.

2250 Northwood Drive * Salisbury, MD 21801 * Phone: 410-749-2424 * Fax: 410-749-5725 www.klmicrowave.com * sales@klmicrowave.com Enter No. 243 at www.mwrf.com



You asked for more power...



MMA 701 PERFORMANCE

More Power +27 dBm

High Linearity +48 dBm

• PAE>50%

Available from stock

NEW MMA-700 FAMILY

The MMA701-SOT89 is a low cost packaged InGaP HBT ideally suited for Cellular, PCS, 2.5/3G, MMDS, WLL and other types of wireless infrastructure applications where flat gain and good linearity are required. This device offers an exceptional combination of performance, efficiency, and versatility to quickly bring a superior solution to market

The MMA710-SOT89 is a broadband fully matched packaged InGaP HBT ideally suited for narrow or broadband performance applications. This device offers a flat gain/power response from 1 MHz through 5 GHz, with usable gain to 6 GHz. This device delivers an outstanding combination of broadband P-1dB compression, linearity, and efficiency and is ideally suited as a general purpose gain block or driver.

These devices have been designed and tested to offer the highest standards of reliability and performance you have come to know from Metelics.

...we delivered.

HBT AMPLIFIERS

Model	Frequency Range (GHz)	Vcc (V)	lcc (mA)	Gain* (dB)	P-1dB** (dBm) Typical	IP3** (dBm) Typical	Thermal Resistance (°C/W)
MMA701-SOT89	0.001-4.0	7.0	130	16.0	+27	+48	80
MMA710-SOT89	0.001-5.0	7.0	95	12.5	+22	+37	130

^{*} Matched SSG at 2.0 GHz

^{**} Measured at 2.0 GHz



These parts are available at

800.225.7434



975 Stewart Drive • Sunnyvale, CA 94085 PH 408.737.8181 • FX 408.733.7645 sales@metelics.com • www.metelics.com

from the editor

Learning From A History Lesson

HISTORY LESSONS CAN be instructive and insightful. Assembling this 40th Anniversary issue required a look back through four decades of articles, news events, products, companies, technologies, and people. And sometimes we forget that there may be people around us who If you are may be able to teach us the greatest lessons of all.

To learn from history, numerous visits were made to different companies on both Coasts, to a variety of individuals usually with considerable tenure at their companies. Originally, these "company histories" were to appear in this issue. A few do, such as the story of ARRA (Bay Shore, NY) and the Isaacsons. But the majority of these company histories, companies such as Anritsu/Wiltron (Morgan Hill, CA), M/A-COM (Lowell, MA), Raytheon (Lexington, MA), and even learn what you a few companies that didn't survive through the years, such as Avantek (Santa Clara, CA), will appear in subsequent issues in 2001. Apologies to all those companies and people who took the time to sit before our tape recorders in the hopes of appearing in August—we

will run your stories, but later than expected. It is a way to extend our 40th Anniversary celebration throughout the rest of the year!

There is much to learn from some of the "elder statesmen" in this industry. Compiling these stories provided an opportunity to sit with some knowledgeable people, such as Bob Traut of Rogers Corp. (Rogers, CT), Tom Rose of M/A-COM, and Phil Cheney of Raytheon Co. In terms of longevity, Bob Traut would be an award winner in most contests, with more than 51 years at Rogers.

Similarly, Phil Cheney, who will retire from his spot as Vice President of Engineering for Raytheon at year's end, has enjoyed 40 years at the company, bridging the years from when vacuum tubes were king and transistors were first developed to our current technologies of microminiaturization and solid-state integration.

In sitting with people like Bob Traut, Tom Rose, and Phil Cheney, there is always that one additional detail that one would like to extract from these "living history books." It was certainly cherished time spent with these folks. On this magazine, there have been a number of these teachers over the years, people like Howard Bierman, Stacy Bearse, and that legendary salesman, Harry Dolan.

Perhaps the lesson for today is this: If you are fortunate to work alongside of a Bob Traut or a Phil Cheney, do not take the time for granted. Learn what you can from these valuable resources. For they have been where you are going, and they have done what you are trying to do, and this wisdom is never easy to come by.

Jack Bro



fortunate to work alongside a Bob Traut or a Phil Cheney, do not take the time for granted; can from these valuable resources.



Enter NO. 458 or visit www.mwrf.com



Enter NO. 449 at www.mwrf.com

Model 9640 Dual HF Receiver

Frequency Range — 0.56 to 32 MHz

Instantaneous Bandwidth - 10 MHz

Noise Figure — 10 dB Maximum

Gain — 48 dB ±2 dB

Synthesizer Control - RS-232C Interface

Synthesizer Tuning Speed — 100 µs Maximum

Frequency Synchronous or Independent Operation



Interad Ltd.

18321 Parkway • Melfa, VA 23410 Phone: 757-787-7610 • Fax: 757-787-7740 E-mail: interad@interadltd.com

Enter NO. 424 at www.mwrf.com

ICTOWAVE

HIGH-SPEED ELECTRONICS GROUP

Group Publisher Craig Roth, (201) 393-6225 • croth@penton.com Publisher/Editor Jack Browne, (201) 393-6293 • jbrowne@penton.com Managing Editor Peter Stavenick, (201) 393-6028 • pstavenick@penton.com Senior Editor Gene Heftman, (201) 393-6251 • gheftman@penton.com Senior Editor Don Keller. (201) 393-6295 • dkeller@penton.com Associate Managing Editor John Curley, (201) 393-6250 • jcurley@penton.com Special Projects Editor Alan ("Pete") Conrad

Copy Editor Mitchell Gang • mgang@penton.com Editorial Assistant Dawn Prior • dprior@penton.com Contributing Editors Andrew Laundrie, Allen Podell

MANUFACTURING GROUP

Director Of Manufacturing Ilene Weiner Group Production Director Mike McCabe **Customer Service Representative** Dorothy Sowa, (201) 393-6083, FAX: (201) 393-0410 Production Coordinator Eileen Slavinsky

ART DEPARTMENT

Art Director Armand Veneziano • aveneziano@penton.com Group Design Manager Anthony Vitolo • tvitolo@penton.com

Circulation Manager Nancy Graham—(216) 696-7000 Reprints Sue McCarty—(845) 228-4896 • Maureen Tighe—(845) 225-5370

EDITORIAL OFFICE Penton Media, Inc.

611 Route #46 West, Hasbrouck Heights, NJ 07604 Phone: (201) 393-6286, FAX: (201) 393-6227

PENTON TECHNOLOGY MEDIA

President David B. Nussbaum Vice President, Finance Keith DeAngelis Director, Information Technology Steven Miles VP, HR and Organizational Effectiveness Colleen Zelina Vice President/Group Director John G. French



Chairman & Chief Executive Officer Thomas L. Kemp President & Chief Operating Officer Daniel J. Ramella Chief Financial Officer Joseph G. NeCastro Chief Technology Officer R. Thomas Jensen **Executive Vice President & President,** Penton Technology Media David B. Nussbaum **Executive Vice President & President,** Penton Industry Media James W. Zaremba **Executive Vice President & President.** Penton Retail Media William C. Donahue **Executive Vice President & President.** Penton Lifestyle Media Darrel Denny Senior VP, Human Resources & Executive Administration

Katherine P. Torgerson Vice President & Controller Jocelyn A. Bradford Vice President, Investor Relations Mary E. Abood

International editions are shipped via several entry points, including: Editeur Responsable (Belgique), Vuurgatstraat 92, 3090 Overijse, Belgique. Microwaves & RF is sent free to individuals actively engaged in high-frequency electronics engineering. In addition, paid subscriptions are available by writing to: Penton Media, Microwaves & RF, c/o Bank of America, Subscription Lockbox, P.O. Box 96732, Chicago, IL 6093; Tel.: (216) 931-9188, FAX: (216) 696-6413. Prices for non-qualified

subscribers are:

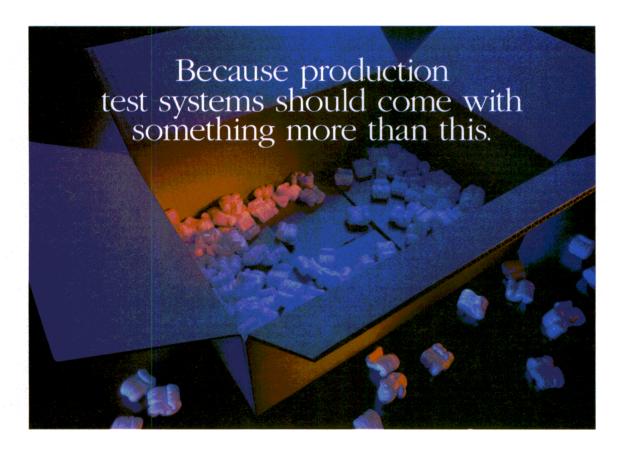
Single Copies

	1 Yr. (Surface)	1 Yr. (Air Mail)	Regular Issues	PDD Only	
U.S.	\$ 75.00	_	\$10.00	\$100.00	
Canada	\$100.00	\$135.00	\$12.00	\$125.00	
Mexico	\$120.00	\$174.00	\$14.00	\$125.00	
All other countries	\$135.00	\$243.00	\$16.00	\$125.00	

Reprints can be ordered from Reprints Services at (651) 582-3800

Back issues of MicroWaves and Microwaves & RF are available on microfilm, microfiche, 16-mm, or 35-mm roll film. They can be ordered from Xerox University Micro-films, 300 North Zeeb Rd., Ann Arbor, MI 48106. For immediate information, call (313) 761–4700. Copying: Permission is granted to users registered with the Copyright Clearance Center, Inc. (CCC) to photocopy any article, with the exception of those for which separate copyright ownership is indicated on the first page of the article, provided that a base fee of \$1.25 per copy of the article plus 60 cents per page is paid directly to the CCC, 222 Rosewood Dr., Danvers, MA 01923. (Code 0745–2993/01 \$1.25 +.60) Copying done for other than personal or internal reference use without the expressed permission of Penton Media, Inc., is prohibited. Requests for special permission or bulk orders should be addressed in writing to the publisher.

Copyright © 2001 by Penton Media, Inc. All rights reserved. Printed in the U.S.



If it seems like most instruments you order today come with little more than the materials they're packed in, you

should know that Keithley has a better idea. Every solution we develop comes with the rich experience of Keithley people who are eager to work with you, and to lend the kind of support today's applications demand. We go beyond manufacturing the fastest, most accurate instruments you can find—and beyond what most people seem

willing to do. Instead of offering the same things as everyone else,

we're combining broadband signal routing (RF and high speed digital signals), battery simulation, and audio testing in whole

new ways that help our customers get products to market in less time, and with fewer defects. We stick around afterward, too, providing a level of ongoing support even our most conscientious competitors don't seem to deliver. To learn more, download your FREE Telecommunications

Application Kit at keithley.com/ideas.

Or call 1-888-534-8453 to learn

about exciting, new products that truly show how we think out of the box.



Learn more at 1.888.KEITHLEY or www.keithley.com



A GREATER MEASURE OF CONFIDENCE



Impaine Meeting All Your RF Requirements

at One Source

All products are produced in-house to meet the growing demands of today's customers.

provides a full range of RF and microwave products from basic components to complete systems including RF switches, filters, combiners/dividers, front-end units, tower top amplifiers, repeaters, thin film products and more. From machining to assembly, all products are produced includes.

The advanced technology and seamless quality of KMW enable us to provide the best solutions for your needs. KMW will save you time, effort, money, and will support you with top quality, competitive pricing and fast turnaround time.

Switchable Power Combiners / Dividers

Contactless Phase Shifters

Continuously Variable Attenual

Step-Rotary Attenuators

RF Switches

Filters & Filter Units

Power Splitters

Amplifiers

Directional Couplers

Circulators / Isolators

Tower Top Amplifiers

Front-End Units

Repeaters

Connectors & Cable Assemblies

Ceramics & Thin Film Products

ISO9001 Certified

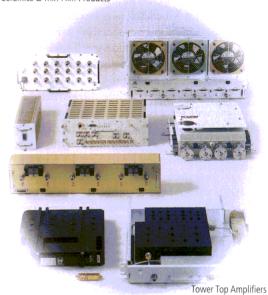
When planning for your project, plan with confidence, plan with



Switchable Power Combiners / Dividers
Contactless Phase Shifters
Continuously Variable Attenuators
Step-Rotary Attenuators
RF Switches
Filters
Power Splitters
Amplifiers
Directional Couplers
Circulators / Isolators
Connectors & Cable Assemblies
Ceramics & Thin Film Products

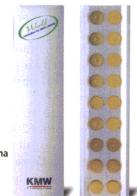


Optic Repeater Microwave Repeater Miniature Repeater In-Building Repeater



Combiner Divider Unit Switchable Combiner Unit Filter Unit Channel Combiner Unit Thin Film Products

New Products



Multi-Line Phase Shifter for Electrical Tilting Antenna



KMW has a special offer on the Thomas Register website www.thomasregister.com, which includes the following items: Contactless Phase Shifters / Continuously Variable Attenuators

Step-Rotary Attenuators / RF Switches / Filters and more

3-Way Beam Control Antenna

- Vertical Down Tilting
- Horizontal Steering
- · Beamwidth Switching



KMW Inc. (HQ, Korea) Tel: +82-31-370-8674 Fax: +82-31-376-9588 E-mail: info@kmwinc.com KMW U.S.A Inc. Tel: 1-562-926-2033 Fax: 1-562-926-6133 E-mail: vchung@kmwinc.com KMW Japan Inc. Tel: +81-45-478-2202 Fax: +81-45-478-2210 E-mail: izumi@kmwinc.co.jp KMW China Inc. Tel: +86-21-5899-9145 Fax: +86-21-5899-9413 E-mail: kmwsha@online.sh.cn

the front end

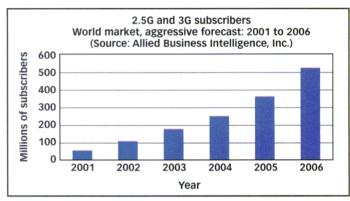
News items from the communications arena.

2G And 3G Evolution Will Pay Off

OYSTER BAY, NY—Despite the negativity surrounding second-and-a-half generation (2.5G) and third generation (3G) that has been created by pessimists without patience, the evolution of second-generation (2G) networks will provide very positive results for many involved in the wireless industry once the migration is complete, according to a 2.5G and 3G study from Allied Business Intelligence, Inc. (ABI).

2.5G and 3G operators will realize approximately \$300 billion worldwide in subscriber revenues from an audience of more than half a billion 2.5G and 3G subscribers in 2006 (see figure), while infrastructure vendors will see over \$100 billion in infrastructure sales of 2.5G and 3G base stations through 2006.

"The key is realizing that this is an upgrade path in many cases, and the building of new networks by large carriers with a sizable customer base in others," says Larry Swasey, ABI's president and the report's main author.



"In both cases, subscribers can be turned over to new services rather easily, but like any other evolution in technology it will take some years to complete the transition."

More than half of all handset shipments will be 2.5G and 3G compliant, while over three-quarters of all handsets will have some type of data connectivity by 2006, according to ABI's report, "2.5G and 3G—The Evolution of the Wireless Network."

InP Process Enables OC-768 Performance

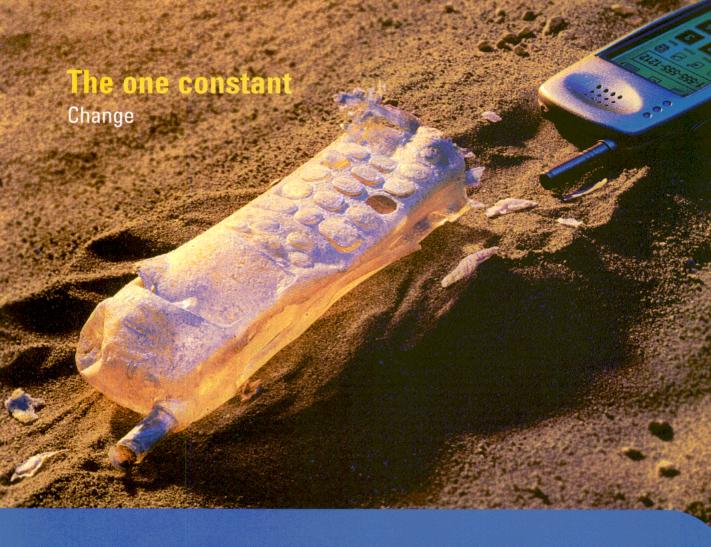
CAMARILLO, CA-Vitesse Semiconductor Corp. has announced its latest process technology for the manufacture of analog and digital integrated circuits (ICs) for data transmission at rates in excess of 40 Gb/s. The process is built around indium-phosphide (InP) heterojunction bipolar transistors (HBTs). The first generation of the InP HBT process will be used to manufacture physical-layer ICs for Synchronous Optical Network (SONET) OC-768 applications and circuitry for 10-Gb/s systems that use returnto-zero (RZ)-encoded data. Succeeding generations will provide ICs with up to 100-Gb/s levels of performance and integrated optical devices, thereby providing the capability to manufacture true monolithic optical ICs (OEICs).

The first generation of the InP HBT process uses a vertical, mesa-isolated NPN bipolar transistor having a demonstrated peak f_{au} of 150 GHz and a peak f_{max} of 160 GHz. The trans

sistor performance is consistent with the bandwidth and edge-rate requirements of circuits operating from 40 to 50 Gb/s.

"InP is the only IC technology that combines the high-frequency performance and high breakdown voltage required to implement all transmit, receive, and clock-recovery functions for 40-Gb/s systems," states Alan Huelsman, Ph.D., Vitesse's director, InP Program. "All other IC technology choices result in compromises in system performance or complications in architecture for thermal or functional partitioning considerations. In addition, InP is the only IC technology that provides a path to monolithic integration of long wavelength optical sources and detectors."

Vitesse began development of InP HBT technology in January 2000, using the company's 4-in. (10.16-cm) gallium-arsenide (GaAs) production line in Camarillo, CA. Approximately 50 percent of the line has been converted to process InP wafers. First HBT devices were successfully completed in December 2000.



www.agilent.com/find/wireless

u.s. 1-800-452-4844, ext. 7319 canada 1-877-894-4414, ext. 7322 And with every new format, technology, or player to enter your market, the pressure increases to keep ahead of pace. Now, perhaps more than ever, choosing the right people to collaborate with is critical. Consider someone who knows where the wireless world is heading. Agilent. We've been heavily involved with the standards boards since day one. And we're committed to giving you insight from which to base your design and manufacturing processes that's as sophisticated as your new technology. And solutions that work together across disciplines. With worldwide support and expertise wherever your teams need it. Suddenly, those market windows don't seem quite so small. **Dreams made real**.



Australia 1-800-629-485 * Australia 3-125125-7006 * Belarus 375-17-209-6341 * Belgium 32-2404-9340 * Bulgaria 359-2-953548 * Denmark 45-70131515 * Egypt 20-2301-53-52 * Finland 358-10855-2100 * France 33-825010700* * Germany 49-1805-246330** Grace 301-7569000 * Hong Arg 38-1317-889 * Hungary 36-1382-6006 * India 91-11-682-6862 * Ireland 353-1615-8222 * Israel 972-3-6892-570 * Isiay 39-02-9269-8484 * Japan 81-426-56-7832 * Kazahtsan 7-3272-582-200 * Korea 822-2004-5114 * Kuwait 985-243-2565 * United 4405-413 * Makiyai 1-800-88-868 * Morrocco 12-223-12-2-0** United 482-256-11-12-2014 * Norway 47-2273-5759 * Oman 968-70-77-27 * Philippines 1-800-1651-0170 * Poland 4822-608-11-12-2014 * Norway 47-2273-5759 * Oman 968-70-77-27 * Philippines 1-800-1651-0170 * Poland 4822-608-11-300-315-2014-222-12-2014 * Norway 47-2273-5759 * Oman 968-70-77-27 * Philippines 1-801-1501-0170 * Poland 4822-608-11-300-315-310

the front end

CTIA Signs Agreement With Chinese Counterpart

washington, DC—The Cellular Telecommunications & Internet Association (CTIA) announced that it has signed a Memorandum of Understanding with the Chinese Institute of Communications (CIC), the pre-eminent telecommunications trade association in China. The agreement, which was signed in Beijing, China, recognizes that "a close, cooperative relationship between the two organizations will contribute to the sound growth of the wireless communications industries of the United States and China, the two largest wireless markets in the world."

"China and the United States are the two largest wireless countries in the world. With five million new subscribers per month, the size of the Chinese wireless industry will soon pass that of North America," says Tom Wheeler, CTIA's president and CEO. "This agreement establishes strong cooperative ties between those two powerhouse markets and pledges that CIC and CTIA will work to build successful relationships between the carriers and suppliers of the two countries. It is the foundation for opening even more doors and advancing the wireless industry to benefit both regions."

The memorandum further states, "CTIA and CIC pledge to work together to support development of the wireless industry in both the United States and China through a variety of means, including the exchange of information, joint seminars and shows, study programs, and regular meetings."

Electronic-Chemical Demand To Grow 10 Percent Annually Through 2004

CLEVELAND, OH—World demand for electronic chemicals is forecast to grow more than 10 percent per year to \$17.6 billion in 2004, outpacing gains in electronic-component shipments due to an above-average performance in the key semiconductor segment and a steady shift toward higher-performance chemicals. After a relatively weak showing in 1998 and early 1999 due to a slump in the global semiconductor industry, electronic-chemical suppliers should benefit from aggressive spending on new and upgraded chipmaking facilities, particularly facilities dedicated

to next-generation 300-mm wafers and sub-0.25-µm design technology. Based on imperatives to invest in this new technology, long-term prospects for chemicals remain favorable despite periodic volatility in the semiconductor industry, such as the weakness that emerged in the first quarter of 2001, particularly in the US. These and other trends are presented in *World Electronic Chemicals*, a study from the Freedonia Group, Inc., an industrial market-research firm.

Photoresists will post the strongest longterm growth as the industry shifts from conventional g-line resists to advanced I-line and deep-ultraviolet (DUV) resists. Constant improvements in the performance parameters of photoresists are directly linked to the ability of chipmakers to squeeze an increasing number of transistors onto their chips (thus increasing processing speed), making this segment the focus of much of the industry's research-anddevelopment (R&D) efforts. For instance, even as DUV resists are just gaining widespread use, a consortium of suppliers and government labs is working on a new generation of extreme-UV (EUV) resists, which should hit the market in approximately 2005 and offer features down to the 30-nm level.

Digital Head-End Systems To Be Delivered And Integrated

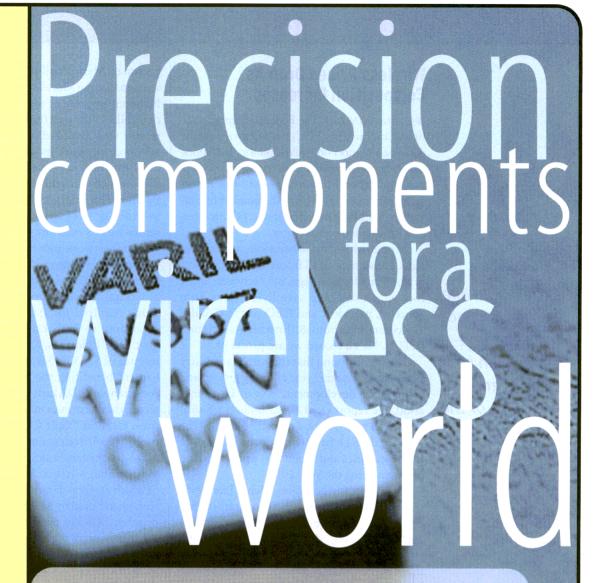
DENVER, CO AND SUNNYVALE, CA—Broadband network provider WINfirst has selected Harmonic, Inc. open-system solutions for digital head ends in Sacramento, CA and Dallas, TX where WINfirst is building a fiber-to-the-home network.

Harmonic has also contracted to provide professional services, including system design and integration with other third-party technologies supporting the WINfirst interactive TV platform.

The WINfirst deployment features Harmonic's digital-TV (DTV) head-end systems, including the DiviCom family of encoders, MN20 multiplexers, SimulCrypt conditional-access interfaces, the Narrowcast Services Gateway for video-on-demand applications, and the InterSect Internet-protocol (IP) set-top gateway. These systems will enable WINfirst to offer more than 200 channels of video and audio, enhanced pay-per-view, and video-on-demand services.

China and the United States are the two largest wireless countries in the world. With five million new subscribers per month, the size of the Chinese wireless industry will soon pass that of North America."

AMPS CDMA **CDPD** DAMPS DCS1800 ECM **EDGE** EW GEO **GPRS** GPS GSM900 HFC IFF LEO LMDS LMR MMDS NPCS PCS PCS1900 RADAR RFID RLL SMR TDMA **TETRA** UMTS WAP WBA **WCDMA** WLAN



As demand in the wireless telecommunications industry nears 3G protocols, precision engineering and manufacturing become essential to the success of RF design engineers. We offer a variety of precision commercial VCOs, PLLs, and RF Passive Components designed to meet the stringent needs of today's and tomorrow's wireless applications.

To find out how Vari-L can "have a part in your future," please visit our website or send us an email at sales@vari-l.com.



4895 Peoria Street Denver, Colorado 80239 303.371.1560 303.371.0845

WLL

WWAN

sales @ vari-l.com

PLL Synthesizer Modules PRODUCTS

Wideband RF Transformers

Couplers

Voltage Controlled Oscillators

Power Dividers/Combiners



PROUDLY MADE IN THE USA

ISO9001 Certified

Contact the Vari-L Sales Department for your special microwave and RF component assembly needs.

Vari-L

OUR

INCLUDE:

the front end

Wireless Prices Drop As Competition Increases

WASHINGTON, DC—The Federal Communications Commission (FCC) has released a report detailing a number of wireless industry indicators, including price per minute, number of competitors per market, and minutes of use. The report reflects increased growth in the number of consumers, climbing minutes of use, falling rates, and heightened competition.

"The growth of the wireless industry has benefited consumers on all fronts, delivering lower prices, broader coverage, new services, and a tool which can help save lives," says Tom Wheeler, president and CEO of the Cellular Telecommunications & Internet Association (CTIA). "It's a record we are proud of."

The report found that the wireless industry experienced "another year of strong growth and competitive development." As of December 2000, the report cited 109.5 million US subscribers, a penetration rate of 39 percent. The FCC cited US Department of Labor Bureau of Labor statistics and found that prices fell 12.3 percent during the year 2000.

The report further states, "Since late 1999, seven major mobile-telephone operators have begun offering mobile data services, including "wireless web," short-messaging service, and e-mail on mobile-telephone handsets. Four of those seven operators reported their mobile Internet usage at the end of 2000 and had a combined total of 2.5 million mobile Internet users."

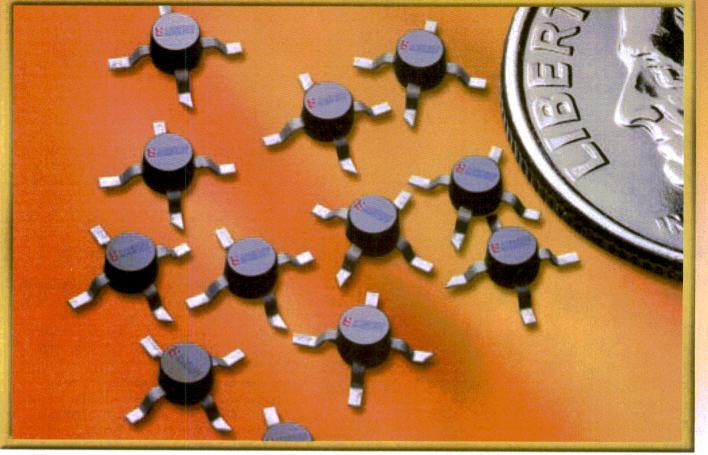
CTIA has asked the FCC for more spectrum to make room for the expected growth of the industry in voice and wireless data. Specifically, CTIA would like to see US spectrum for next-generation services aligned with that of the rest of the world, which is migrating to the 1710-to-1855-MHz band.

Kudos

Flarion announced that Rajiv Laroia, its founder and CTO, was selected for the BUSINESS NEWS New Jersey "40 Under 40." BUSINESS NEWS New Jersey bestows "40 Under 40" recognition every year to business achievers, including entrepreneurs and corporate executives, willing to take risks and assume responsibility. Laroia was recognized for researching and developing the next generation of mobile wireless technology...The US House of Representatives has approved a resolution by Con-

gressman Mark Udall (D-CO) and Congresswoman Connie Morella (R-MD) honoring the National Institute of Standards and Technology (NIST) on its 100th anniversary...Tektronix was awarded a Gold Medal for its advanced network-monitoring system at the 2001 International Telecommunication Show (ITS), which was held earlier this year in Lodz, Poland. The Intertelecom Gold Medal, first awarded in 1994 to innovative products presented by ITS exhibitors, recognizes Tektronix' Net-7 network-monitoring system as one of the "most interesting products or technology solutions demonstrated at the ITS"...International Crystal Manufacturing has met the standards required for ISO-9002 certification, according to Beth Freeland, ICM's president...ITT Industries, Cannon announced that revenue of \$265,000 was raised at a golf tournament benefiting the Muscular Dystrophy Association (MDA) attended by many companies in the electronics industry. The ITT Industries, Cannon "Golf Classic" is the longestrunning golf tournament held on behalf of MDA, a voluntary health organization dedicated to eradicating 40 neuromuscular diseases, some of which are fatal. Funds raised at the ITT tournament are used by MDA for patient care and research...Global distributor Avnet, Inc. has garnered seventh place among Computerworld magazine's annual listing of the "100 Best Places to Work in IT"...Cambridge Silicon Radio (CSR) has won the award for Best Bluetooth Component 2001 at the Bluetooth Congress in Monaco. CSR's BlueCore[™] single-chip solution was awarded the winning trophy at the Special Award Ceremony, which took place at Monte Carlo's Hotel de Paris preceding the Bluetooth Congress exhibition...Valtronic was honored at Mentor Graphics 15th Annual PCB Technology Awards. Each year, Mentor Graphics hosts a competition that includes entrants from the computer, consumer-electronics, industrialcontrol, military/aerospace, transportation, telecommunications, data-communications, and wireless-communications industries. Valtronic's winning entry in the industrial-controls category, a Picture Reader for Barcode 2D, was designed by Gabriel Gay and Van Ly Mai of Valtronic's Switzerland facilities...Agere Systems announced that the ORiNOCO® USB Client is the first and only universal-serial-bus (USB) wireless-networking radio on the market to receive the Wi-Fi and USB Compliance Test certifications. MRF

ctil would like to see US spectrum for next-generation services aligned with that of the rest of the world, which is migrating to the 1710-to-1855-MHz band."



NGA gain blocks are delivered in miniature SOT-86 packages.

Big Upgrade? Small Solution!

Now there's a simple way to upgrade your existing design with InGaP/GaAs gain blocks from Stanford Microdevices.

SMDI's NGA Series gain blocks feature reduced thermal resistance, lower junction temperatures and improved reliability compared to competing devices.

And, they can be dropped right into many existing sockets.

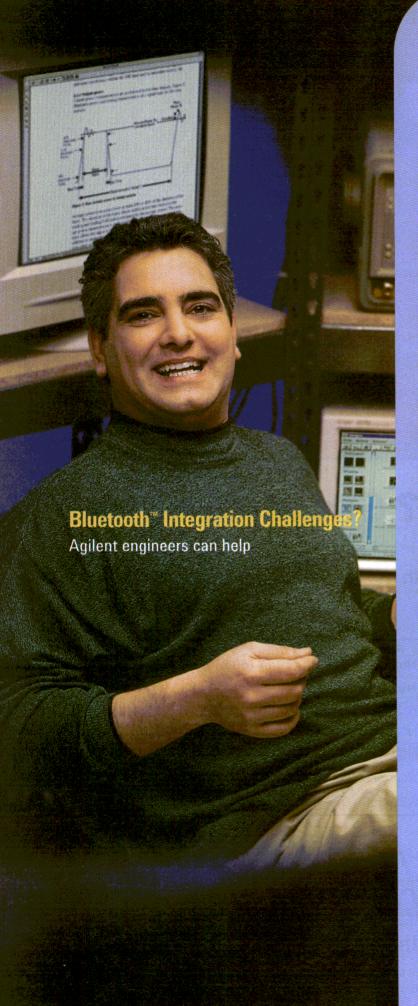
They deliver higher OIP3 and higher MTTF—a winning combination!

For more information, visit us at stanfordmicro.com.

Part Number	Freq (GHz)		OIP3 (dBm)			Vd, Id (V, mA)	Rth (°C/W)
NGA-186	DC-8.0	14.7	31.7	12	4	4.1, 50	120
NGA-286	DC-6.0	15	31.2	15	3.4	4.0, 50	120
NGA-386	DC-4.0	15	27	19	2.7	4.0, 35	144
NGA-486	DC-8.0	17.5	39.5	14.5	4.5	4.2, 80	118
NGA-586	DC-6.0	19	38	19	4.5	5.0, 80	121
NGA-686	DC-4.0	19.2	35	11	6.1	5.9, 80	121



www.stanfordmicro.com • 800.764.6642



It probably started with a conversation over in marketing: "Bluetooth wireless technology is the next big thing! We have to put it in all our products! Details? Bah, all you do is add an antenna. The engineers will figure it out. Let's go see if they're finished yet."

And now you and a few thousand other engineers are figuring out that *Bluetooth* integration is not a trivial task. From baseband DSP to RF interference, you've got an integration challenge worthy of legendary King Harald himself.

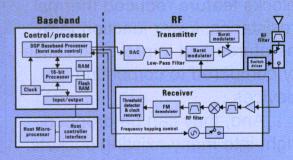
Welcome to the wild world of RF. New to RF? We've pooled the talents of our digital, DSP and RF experts to identify the most important signal checks you'll need to make when integrating *Bluetooth* designs. Our online resources include everything from an RF basics seminar to advanced measurement techniques.

Something for the RF experts, too. If you have the luxury of approaching *Bluetooth* from an RF background, we can offer advice on the most-efficient test procedures and toolsets to tackle a wide range of *Bluetooth* measurements.

The *Bluetooth* big picture. Most of the *Bluetooth* work we're seeing today involves the integration of a *Bluetooth* module into a new product design:

- · Evaluating module performance and characterizing interoperability
- Understanding host-module integration issues
- · Designing and debugging the host-module interface
- · Conducting pre-qualification RF testing
- · Getting Bluetooth Qualification
- · Manufacturing quality products

Some of the more interesting problems show up in the second stage, as you bring the RF transceiver into your host products.

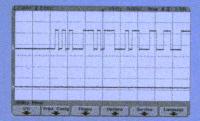


Watch out for some interesting interoperability problems when you integrate a Bluetooth module into your host device

u.s. 1-800-452-4844, ext. 7571 canada 1-877-894-4414, ext. 7471

Baseband signal integration. Challenges here include verifying transmission and receipt of data packets, viewing the actual data values transmitted, quantifying system bottlenecks, identifying logic errors, and resolving DSP and mixed-signal issues.

For instance, once you've found the preamble, you can identify the entire bit stream, including the access code, header and payload. Learn more in our free *Bluetooth* baseband application note.



The first two pulses in this idealized transmit signal correspond to the 0101 pattern of the preamble; the access code follows immediately after

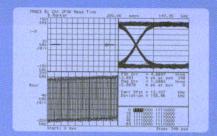
RF receiver tests. RF receiver performance is key to both *Bluetooth* qualification and overall product performance. For example, a sensitive radio that is immune to interference will reduce file transfer times and therefore increase battery life. You need to make sure the RF receiver will not be adversely impacted by the harmonics of high-frequency digital signals or other noise sources likely to be present in your system.

Receiver performance is tested in a number of ways for qualification, including carrier/interference and blocking tests. You probably won't need to run all the tests if you're integrating someone else's module, but they can be complicated so clear information and simplified procedures are important.

RF transmitter tests. The *Bluetooth* specification covers a wide range of transmitter tests, some to insure interoperability between *Bluetooth* devices (e.g., modulation characteristics) and others to meet regulatory limits (e.g., spurious emissions). Given the concerns about interference with other wireless systems, output spectrum tests are also important.

Integrating a module can create problems that affect transmitter performance, sometimes in unexpected ways. For example, power supply ripple coupled through your system can degrade the modulation characteristics.

You must be able to show that your device stays within both *Bluetooth* and regulatory limits, and the more of this work you can do on your



Bluetooth measurement tools range from powerful design analysis to fast, automated tests for the production line. Above, a modulation characteristics test verifies proper performance of the modulation circuitry to ensure reliable data transfer over the Bluetooth communication link.



At left,
an automated test
combines pass/fail
indications with
numerical readouts

design bench, the better. Some of the tests are complex and potentially time-consuming to understand and perform. Our free online application resources can help you look for and fix problems quickly.

Get the complete *Bluetooth* test story—FREE. Talk to one of our *Bluetooth* measurement specialists to learn more or tap into our free technical resources at www.agilent.com/find/bt.

Among the features you'll find there:

- A comprehensive measurement guide: Performing Bluetooth RF Measurements Today featuring descriptions and examples of the many RF measurements you might need
- Interactive measurements that show some key Bluetooth measurements in action, starting with frequency drift and frequency settling—explore these real-life measurements before you need to make them on your own system

We can't do much about your enthusiastic friends in marketing, but we can definitely help you through the *Bluetooth* integration experience.

Visit www.agilent.com/find/bt for a FREE Bluetooth CD-ROM packed with application notes, measurement tips and solution guides.



Lowest Power Consumption Dual PLLs on Earth

National's LMX23xxU Family: PLLatinum™ PLL Performance with up to 43% Power Savings

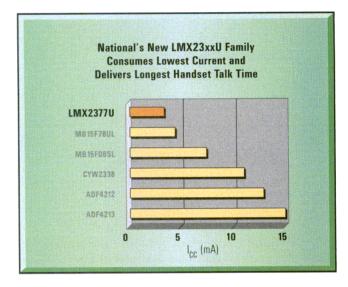
- Ultra Low Current Consumption
- Fastlock Mode
- LMX2377U: Low Voltage MICROWIRE Interface (1.8V up to V_{CC})
- Upgrade, Pin and Software Compatible to LMX233xL Family and LMX2370
- Synchronous and Asynchronous Power Down Modes
- CSP-24 and TSSOP-20 Packages (LMX2335U in CSP-16 and TSSOP-16)

Ideal for all Portable Wireless Applications

For More Information on LMX23xxU: wireless.national.com 1-800-272-9959

Free CD-ROM Data Catalog Available at: freecd.national.com

WEBENCH™
- READY On-line Simulation



ľ	lew Generation 'U	' Family
Product	Active I _{cc} (Typ © 3V)	Operating Frequency
LMX2330U	3.3 mA	2.5 GHz / 600 MHz
LMX2331U	2.9 mA	2.0 GHz / 600 MHz
LMX2332U	2.5 mA	1.2 GHz / 600 MHz
LMX2335U	2.5 mA	1.2 GHz / 1.2 GHz
LMX2336U	3.5 mA	2.0 GHz / 1.2 GHz
LMX2377U	3.4 mA	2.5 GHz / 1.2 GHz
Pro	evious Generation	'L' Family
Product	Active I _{cc} (Typ @ 3V)	Operating Frequency
Product LMX2330L		
	(Typ @3V)	Frequency
LMX2330L	(Typ @3V) 5.0 mA	Frequency 2.5 GHz / 510 MHz
LMX2330L LMX2331L	(Typ @3V) 5.0 mA 4.0 mA	2.5 GHz / 510 MHz 2.0 GHz / 510 MHz
LMX2330L LMX2331L LMX2332L	(Typ @ 3V) 5.0 mA 4.0 mA 3.0 mA	Frequency 2.5 GHz / 510 MHz 2.0 GHz / 510 MHz 1.2 GHz / 510 MHz

© National Semiconductor Corporation, 2001. National Semiconductor and 🗗 are registered trademarks and WEBENCH and PLLatinum are



Garage Gives Birth To Measurement Giant

The story of Hewlett-Packard Co., and subsequently Agilent Technologies, is a capsule history of test-and-measurement techniques and equipment for the microwave industry.



eginning in 1939 with only \$538—an amount that today barely covers a month's electric bill in Palo Alto, CA—Bill Hewlett and Dave Packard started a company in the garage behind the home they shared at 367 Addison Rd. These two Stanford University graduates were responsible not only for starting a test-and-measurement technological revolution, but for a business philosophy that has been taken to heart by Silicon Valley's most accomplished companies.

JOHN L. MINCK

Consultant

642 Towle Pl., Palo Alto, CA 94306-2535; (510) 493-3955.

BARRY MANZ

Presidentt

Manz Communications, Inc., 350 Main Rd., Montville, NJ 07045; (973) 316-0999, E-mail: barry@manzcom.com.

And it is comforting to remember that RF and microwave technology was HP's primary driver for more than 25 years, and that this technology and the HP philosophy live on today, in the form of Agilent Technologies.

The story of HP's foray into microwave technology, and the development of its RF and microwave products have been chronicled less frequently than the story of how Walt Disney provided the company with its first big boost by ordering eight of its model 200B audio oscillators for use in the film *Fantasia*. Or the story of how Packard created "management by walking around," or even the story of the role played by Stanford professor Frederick Terman in shaping the "HP Way" and his vision of an electronics industry knowledge center in the Valley. Nevertheless, that foray

and its subsequent developments were every bit as important for the US economy, for the tens of thousands of people who participated in them, and for what the microwave industry has become today.

The company's entry into the RF and microwave instrumentation marketplace came about gradually. Soon after the company's founding in 1939 (Fig. 1), Hewlett entered the US Army Signal Corps for technical assignments in radar at Ft. Monmouth, NJ. Packard remained in Palo Alto, managing the fledgling company and its wartime production operation. The company's entire product line consisted of the 200A audio oscillator, the 400A voltmeter, an audio signal analyzer, and some crystal-stabilized frequency standards.

The company produced its first RF measurement product in 1943. The Model A signal generator covered 500 to 1350 MHz, and was designed for the US Navy. A commercial version, the 610A ultra-high-frequency (UHF) signal generator, was introduced in 1948. In the late 1940s, Varian Associates, founded in Palo Alto by Russell and Sigurd Varian, inventors of the klystron tube, offered HP a small line of waveguide test equipment. The Varian brothers felt that development of the line would detract from their tube business. The product line consisted of some waveguide slotted lines and other components such as directional couplers.

In the same period, the US Naval Research Laboratory contracted with HP to design klystron signal generators, which led to a commercial product, the 616A signal generator, with coverage to 4.2 GHz. It was followed by generators working to 21 GHz.

By 1950, the product line had grown to include the 430A power meter and a double-tuned 475 bolometer sensor. Other innovations expanded the HP line of coaxial equipment, such as the 805A "parallel-slab" slotted line, which cleverly constrained the RF fields mostly at the side walls, and effectively made the 3/4-in. (1.91-cm) open-slot function as a slot only a few thousands of an inch wide.

Part of the reason for HP's continued attention microwave research was Hewlett's recruiting of several engineers from wartime research facilities on the Fast Coast (Fig. 2). Several of these engineers would ultimately become primary participants in the company's future. Bruce Wholev, who later advanced to Microwave Division Manager in 1962, came from Terman's Radio Research Lab at Harvard, working in electronics

had been working in radar at MIT's Radiation Lab.

countermeasures. Art Fong

From the early days of thermistor power sensors, HP heeded the cry for a thermistor sensor that would not respond to the warmth of the human hand, introducing the 431A temperature-compensated power meter in 1961.

When Hewlett was setting up European distribution for this product, he bought the patent rights to a novel noise-figure measurement concept from the Swedish company Magnetic AB. This led, in 1958, to the 340A noise-figure meter. Later, the 524B frequency counter, with its plug-in versatility, launched HP into the frequency and time business.

By the mid 1950s, the proliferation of product lines was creating problems in managing different product and business strategies. To provide more specialization, the corporate research-and-development (R&D) lab was divided in 1958 into four product groups: audiovideo, frequency and time, microwave, and oscilloscopes. Total worldwide business in 1959 was \$47.7 million, and HP's 165-page catalog that year boasted 150 products.

Focusing on individual product lines in the design labs worked well, and by 1962 the company's sales had grown \$109 million. Manufacturing operations expanded to Europe and Colorado, and several technology-company acquisitions were made. This reorganization continued in 1962, as the four major product lines became full operating divisions, of which the microwave division was one. Bruce Wholey was named general manager, but soon acquired other

responsibilities.

1. The starting place

for a multibillion-dollar

international company

was a simple garage

in Palo Alto.

In 1964, John Young became division manager of the microwave division, and filled out his management team with John Doyle in manufacturing and Paul Ely in R&D. John Minck became marketing manager. Ely was already known for his microwave management experience at Sperry Microwave in Florida. Young managed the Microwave Division for approximately six years, and then progressed through various vice-presidential positions to become the company's CEO in the 1980s.

The Microwave Division hit its stride in the 1960s, and its new product lines changed the face of microwave measurements. In 1964, the Model 8551 spectrum analyzer put HP into the spectrum-analyzer market and, in the process, expanded the market five-fold, since it made measurements in ranges that previous analyzers could not reach.

In 1968, the 8410 vector-networkanalyzer (VNA) product line revolutionized microwave-component design with the concept of characterizing the scattering parameters of test devices. The project's slogan was "stamp out slotted lines." Major accomplishments



Linearity. Reliability. Power!

Stanford Microdevices' SXA-289 and SXT-289 amplifiers offer the infrastructure-equipment designer a rare combination of efficient ¹/₄-watt power with high linearity in a low-cost, surface-mountable SOT-89 package. Both products feature SMDI's high-reliability GaAs heterojunction bipolar transistor (HBT) technology sot-89 Package and deliver high output 3rd order intercept

The wide frequency range and power efficiency of our SXA/SXT amplifiers make them an excellent choice for driver

performance of better than 40 dBm.

functions in repeaters and other infrastructure equipment covering the cellular, PCS, WLL, GSM, WCDMA, UMTS, ISM, IF and LO bands. And, exceptional linearity makes them an ideal option for multicarrier digital applications.

Find out how the SXA-289 and SXT-289 can satisfy the power-amplifier requirement in your equipment design.

For more information, visit us at stanfordmicro.com.

Part Number	Frequency Range (MHz)	P1dB (dBm)	IP3 (dBm)	Gain @1950 MHz	Supply Voltage (V)	Current (mA)
SXA-289	5-2000	+24	+42	15.5	5.0	105
SXT-289	1800-2500	+24	+41	15.0	5.0	105



www.stanfordmicro.com • 800.764.6642

were also made in signal generators, sweepers, power meters, and measurement components.

A crucial element of HP's success was a management innovation started by the Microwave Division in the mid-1960s. This was the now well-accepted "triad" management concept, which focused three-person teams from marketing, R&D, and production-on-product planning. Those product teams, consisting of young engineers, devised product strategies based on their combined knowledge of the market, applications, and technology, and then presented the strategy to division management for approval.

This approach contrasted with the strategy of many companies of that time, which created product plans from a central planning group. The genius of the arrangement was that the best creative ability of all team members was used, while also employing the insight

of the company's marketing and business upper management during the reviews. Many of those young team members of the 1960s went on to become division and executive managers throughout the corporation.

HP has contributed heavily to the development of new technologies, most of which have found their way into the company's products. The step-recovery diode was one of HP's more important contributions to signal synthesis. In the early 1960s, engineer Frank Boff was working on harmonic-comb generators to extend the range of counter frequency converters. One circuit showed nonintuitive results, with high-frequency harmonics that were more powerful than what seemed theoretically possible from a nonlinear resistive device such as a diode.

To investigate further, he borrowed an early lab prototype of the HP sampling oscilloscope to display a timedomain picture of what was producing such rich signals in the frequency-domain. When Boff finally got the fuzzy picture focused, he did not see the expected chopped-off top of a sine wave produced by a diode, but rather, he saw a sine wave that rose smoothly to approximately full amplitude, then suddenly crashed to near-zero amplitude.

At that point, serendipity entered the scene. Boff remembered seeing a paper in the *IEEE Proceedings* which theorized that this waveform might exist if a device exhibited a nonlinear charge-versus-voltage curve instead of the nonlinear current-versus-voltage curve that defined a diode. Boff reviewed the article, looked again at the strange wave shape, and proclaimed that what he had taken to be a nonlinear resistor or diode was actually a nonlinear capacitor under certain conditions.

What he had developed was a variation of the well-known P-N diode that

Today's signal paths.....

Seven-day turn-around on your semirigid cables, bent and manufactured from your e-mailed Pro-E, Catia, Me-30, Solid Works, and other output files. All Manufacturing processes performed with tools from the technology leader.



Take routes only the High Tech can follow!

"The Tool Makes the Difference"
ISO 9001
www.semi-rigidcables.com





Trying to squeeze more hours out of the day? It's time you talked to Anritsu.

In the lab, on the production line, or in the field...we make every second count.

Keeping up with the explosion of new technologies becomes a bigger challenge all the time. So where do you turn to squeeze more hours out of the day?

Turn to Anritsu. We come to the table with solutions that cover all of your wireless signal analysis needs.

Whether you're manufacturing products for today, or developing products for 3G, Anritsu offers a cutting-edge solution at every level. And no one has a brighter history of innovation. For example, Anritsu manufactured the first true broadband VNA, covering the range of 40 MHz to 110 GHz. We also created the world's first true handheld spectrum analyzer.



In addition, Anritsu is the only provider of a single solution that can measure handsets based on all the major wireless standards.

So, whether you need to test a power amplifier in the lab, a handset on the production line, or a tower in the middle of nowhere, you can rely on Anritsu.

Don't waste another minute.

Find out what a solutions-driven partner can mean for your business, today. Talk to Anritsu and you'll "Discover what's possible"... in no time. Call us at I-800-ANRITSU, or check out our Web site at www.us.anritsu.com/Discover

MICROWAVE • WIRELESS • OPTICAL • TELECOM • NETWORKING



enhanced the stored carrier phenomenon and achieved an abrupt transition from reverse-storage conduction to cutoff. The device was able to switch tens of volts or hundreds of milliamps in less than a nanosecond. The result was the ability to generate milliwatts of harmonic power at 10 GHz from stable oscillators running at 200 MHz. The device

was called the "Boff diode"

for a number of years, and later changed to the more generic "step-recovery-diode."

HP capitalized on this new capability. HP counters used the harmonic-comb signals to downconvert test signals for counter coverage to 18 GHz. The 8410 series network analyzer used a two-channel version to downconvert microwave signals for characterizing S-parameters to 18 GHz. Sampling oscilloscopes used the diode to generate the large sampling impulses needed to measure transitions in the picosecond range. A generation of HP signal generators and sweepers used those harmonics to stabilize microwave signals, via indirect frequency synthesis.

HP also became the world leader in exploiting a family of sophisticated feedback loops, using synthesis techniques such as programmable "divide-by-N" loops. Not only did they discipline microwave oscillators and reduce their phase noise, they provided exact and programmable output frequencies.

Another variation of the P-N diode was the PIN version, which acted at low frequencies like a regular diode, but at RF/microwave frequencies similar to a programmable microwave resistor. This became the centerpoint for broadband control of signal amplitudes for leveling loops, and for a pulse generator with nanosecond rise and fall times.

HP also pioneered the development



2. The founders of Hewlett-Packard Co., Dave Packard (seated) and Bill Hewlett, worked with very little operating capital but quickly built a giant test and measurement business.

of sophisticated phase-locked loops (PLLs), which were optimized for fast switching, high stability, and spectral purity for extremely-low single-side-band (SSB) phase noise. It was a neverending quest, and HP later designed specific instruments for characterizing SSB phase noise, as well as analysis of loop gain and stability.

The 40-year history of *Microwaves* & *RF* magazine coincides with a period of enormous advancement in test and measurement. The contributions of HP were large and broad, as were the contributions of the people who brought them to fruition.

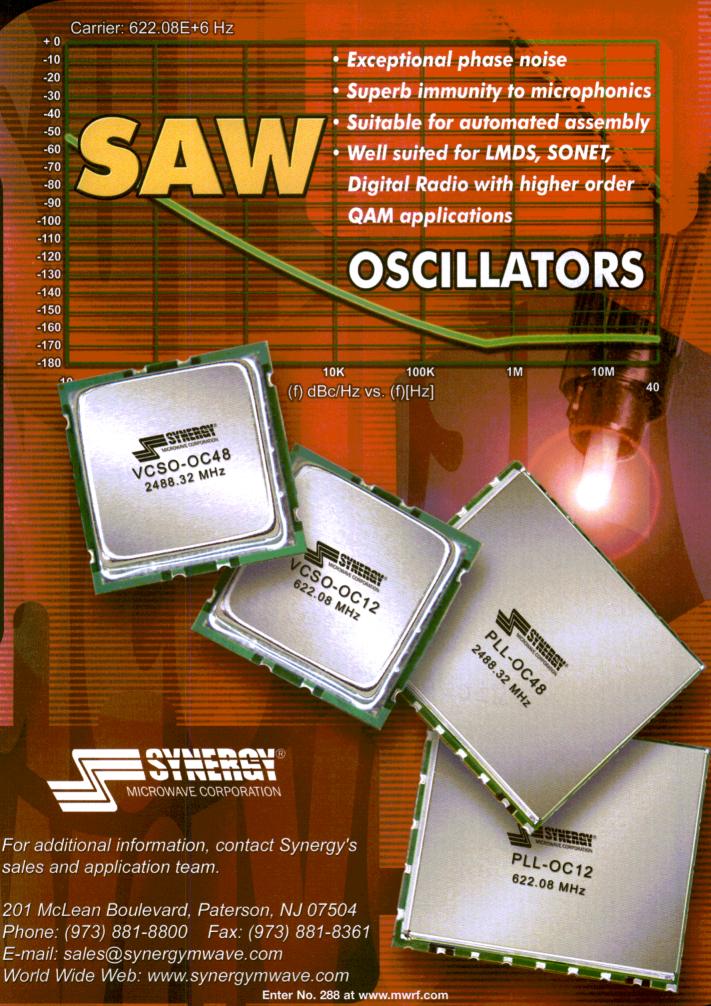
The distinction between signal generators, sources, and sweepers (or swept-signal generators) always seemed to confuse customers. Signal generators were intended for signal simulation, carrying modulation such as amplitude modulation (AM)/frequency modulation (FM)/pulse, and later phase and digital modulation. Later, in wireless test sets, the modulation would include the entire system of handshakes, protocols, and other functions. In contrast, sources were pure continuous-wave (CW) oscillators, generally without

modulation, used for general-purpose and bridge drivers. Sweepers allowed the signal to be swept over a range of frequencies, and have been dominant in component design. In recent decades, with the power of microprocessors, the distinction between the basic types blurred as instruments were created that could perform multiple tasks.

Probably the most popular signal generator of the 1950s and 1960s was the 608C/D family. HP built tens of thousands of these very-high-frequency (VHF) instruments, and their vacuum-tube oscillators and power amplifiers (PAs) provided superior spectral purity and stability. Their semiconductor replacements, the 8640A/B of 1973, had cavity purity, with phase locking and a frequency counter.

What went unsaid was the superiority of vacuum tubes, including klystrons, for signal generation. The oscillator voltages of those tuned tank circuits or cavities provided outstanding signal-tonoise characteristics that took years for solid-state generators to match. Yet, the operating advantages of microwave transistors and yttrium-iron-garnet (YIG)-tuned oscillators in reliability and size were too much to resist, and after much development, methods such as phase-locking greatly improved spectral purity.

In its transition into synthesizer technology, HP found a way to stabilize PLLs with a VHF instrument, the 8708A. It was used to discipline and add narrowband FM to the 608E/F. However, the first integrated indirect synthesized signal generator was the 8660A unveiled in 1971, with versatile plug-ins that allowed its owner to choose from many modulation formats and frequency bands to 2.6 GHz. It was also programmable. The microwave synthesizer that revolutionized automated test systems with its general-purpose -inter-





25 years ago, who'd have th

Congratulations

Microwaves & RF Magazine

on 40 years.



nt that this would lead to this?

We did.

We're Avnet's RF and Microwave Division, your one source for RF and microwave semiconductors and components. For over 25 years, we've been bringing OEMs the industry-leading RF and microwave components on which cutting edge products are built ... plus superior service.

Our extensive field-based technical staff applies years of RF expertise to your design, component and application requirements. Our value-added services span parametric testing and hi-rel processing, to custom hybrid development and thin-film assembly services. And when your needs go beyond straightforward component selection, we offer complete integrated materials services and design services, helping you navigate the entire supply chain, from design to production.

If you're looking for a partner who brings an innovative RF and microwave product and service approach to the market, look no further than Avnet. Who knows where we'll take your next product?

(866) Avnet RF or (866) 286-3873 www.em.avnet.com/rfm



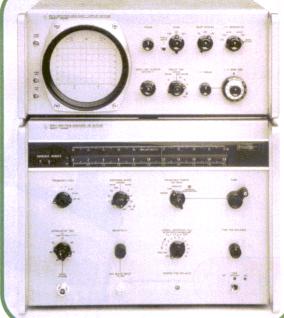
face-bus (GPIB) programming bus was the 8672A. Introduced in 1977, it covered 2 to 18 GHz.

Continuing developments yielded products such as Agilent ESG-series of digital signal generators, which generate the most complex modulation formats used in modern communications systems, including Global System for Mobile Communications (GSM), code-division multiple access (CDMA), time-division multiple access (TDMA), Digital European Cordless Telecommunications (DECT), Enhanced Data rates for Global Evolution (EDGE), as well as broadband inphase/quadrature (I/Q) modulation.

The Model 5100A frequency synthesizer introduced in 1964 was developed in response to the US Navy's need for a fast-switching, direct-synthesized, high-resolution signal source for secure communications. The product covered DC to 50 MHz with a resolution of 0.01 Hz and crystal frequency stability of one part in 10¹⁰.

The emergence of high-frequency digital circuits provided HP with the tools to create powerful digital-direct-synthesis (DDS) generator technology for use in secure communications. The Model 8770A arbitrary waveform synthesizer in 1988 created completely arbitrary waveforms from DC to 50 MHz using a fast digital-to-analog converter (DAC). This frequency-agile technology made it possible to hop from one frequency to another in 8 ns, the time that is required to move to a different sequence. Next, came fixed upconverters that could translate this 50-MHz band to microwave frequencies.

In 1991, the Model 8791A frequency-agile signal simulator (FASS) added frequency-agile upconverters that achieved a typical 100-ns agility to 18 GHz. In addition to impressive carrier agility, FASS used a special waveform-generation language that allowed users to program wide-bandwidth modulation of arbitrary formats such as nonlinear chirps, TDMA, and CDMA. These powerful simulators were able to recreate entire



3. HP's first spectrum analyzer in 1964, Model 8551/851A, became a frequencydomain oscilloscope, indispensable for RF and microwave workbenches.

channels of signals, noise, and interference, providing real-life signal environments for the qualification of receivers (Rxs).

As source technology moved from the backward-wave oscillators (BWOs) of the 1960s to solid-state YIG oscillators, sweepers for the more advanced network analyzers had to be programmable, as well as frequency repeatable, so that data-correction routines could be ensured. To do this, synthesized sweepers were required.

Synthesized signal generators were also required for automatic test systems that were designed to evaluate electronic-warfare (EW) Rxs. These tests required simulated modulations and programmable test frequencies. Landmark sweepers such as the 8340A and, more recently, the Agilent 8360, packed remarkable functionality into user-friendly packages.

Wholey launched HP into the spectrum-analyzer market in 1964, partly driven by pressure from field sales engineers who were looking for a new market area. The business was dominated by the Polarad Co. (Long Island City, NY), which was a prime contractor for military analyzers. They mostly used sin-

gle-band, tunable klystrons as the first local oscillator (LO), with a sweeping second LO for 100-MHz sweep width (dispersion, in the jargon of the day). The Panoramic Co., also on Long Island, was soon building a multiband unit, capable of 2 to 12 GHz, downconverted with harmonics of the first LO.

The project engineer assigned to the HP analyzer was Fong, whose experience at MIT had involved signal generators and spectrum analyzers, including waveguide components. By designing a sweeping first LO using a

BWO for the source, it was possible to provide a sweep width of 2 GHz. The BWO used a tracking, phase-locked, VHF sweeping oscillator in the narrowband mode that quieted the noise of the BWO tube.

The prototype of the first HP spectrum analyzer, the Model 8551/851A (Fig. 3), was first shown to key customers during the 1963 IEEE show in New York City, in a private suite in the Essex House Hotel. The unit was draped with a tablecloth to conceal the powerful fan connected to a laundry dryer hose that piped cool air to the bulky circuitry. The customers left impressed and HP had a year before the launch date to work out any problems. One year later, production units were on display at the IEEE show in the New York Coliseum. Within the first year of production, HP sold more than 75 a month, and it soon became the company's first \$1 million-a-month product.

The performance of this product was demonstrated by application engineer Lyle Jevons, who uncovered an interesting application at Edwards AFB, approximately 50 miles north of Los Angeles. The problem faced by the Air Force was that three long-range S-band surveillance radars operated by National Aeronautics and Space Administration (NASA), the Air Force, and the Federal Aviation Administration (FAA) that were located on mountain peaks in the area interfered with each other. The colonel's job was to sort out the signals.

THE POSSIBILITIES ARE INFINITE FUITSU



Fujitsu innovation has brought us a product breadth that includes 800MHz to 76GHz, low noise to high power, low cost to space hi-rel, plus laser diodes and receivers for long haul communications.

1991

The world's largest GaAs wafer fabrication facility was completed in Yamanashi Prefecture, Japan.

1984

Fujitsu Yamanashi Electronics(later named Fujitsu Quantum Devices)was established as a wholly-owned subsidiary of Fujitsu to specialize in the manufacture of compound semiconductors.

1973

Fujitsu develops world's first GaAs FET used for microwave radio link system in 1976.

1962

Fujitsu was already in its 27th year of existence and its 3rd year of semiconductor mass production.

www.fcsi.fujitsu.com

FUJITSU COMPOUND SEMICONDUCTOR, INC. 2355 ZANKER RD., SAN JOSE, CA 95131 PH: (408) 232-9500 FAX: (408) 428-9111



North American Distributor of products for Fujitsu Compound Semiconductor, Inc. (800) 777-7334 www.cdiweb.com To help, Jevons, accompanied by the US Air Force colonel who was the frequency-control officer at Edwards, parked alongside a phone booth at a desert intersection north of the base, where they could monitor the signals and the colonel could call his radar technicians.

The Model 8551, with its broad 2-GHz sweep, could experience all of the signals at once, and its 60-dB dynamic range also identified the sidelobes that overlapped each other. The colonel stepped into the phone booth, called each radar technician, and quickly unsorted the signals. Jevons reported that the colonel offered him \$100,000 to keep the analyzer.

It was little wonder that this instrument was soon merchandised as a "frequency-domain oscilloscope," since it could display baseband frequencies from 10 to 2000 MHz, and it became an indispensable instrument for RF and microwave engineers. In succeeding

generations, smaller size, absolute amplitude calibration, and innovative features such as tracking generators made frequency-response measurements simpler. Solid-state LOs made the products more stable, reliable, and portable.

The 8566 and 8568 spectrum analyzers of the late 1970s were a new generation of instruments that took advantage of microprocessors—and each employed three. These analyzers had better frequency-tuning accuracy, narrower resolution, lower phase noise, and better phase-lock stability.

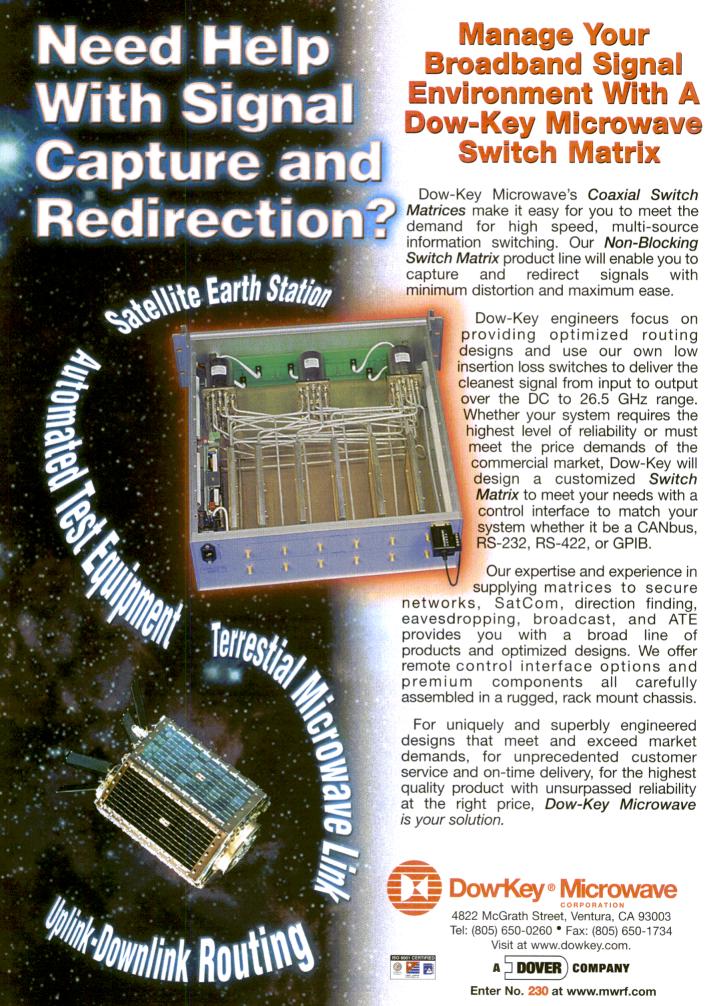
Their most impressive feature was their human interface. These were among the first instruments with a lower panel that looked like a calculator keyboard. A single rotary knob provided a selectable analog feel for tuning, but the keyboard offered digital precision. More important, they offered powerful onboard signal data computation.

A fellowship grant made to Al Bagley,

a young graduate student at Stanford University in 1948, led to the development of HP's frequency-counter business. Hewlett and Packard personally asked Bagley to study the measurement needs of the nuclear-physics industry. From that study came requirements for a faster nuclear-pulse-counting technology that could resolve two nuclear events only 0.1 ms apart. Bagley determined that new, low-capacitance semiconductor diodes might enable faster digital circuitry. He built a prototype for the project—and asked for a job at HP.

From that work came the model 520A high-speed decimal scaler, which was able to condition very short nuclear pulses occurring at up to 10 MHz, and to divide down by factors of 10 or 100. Although the 520A had only minimal commercial success, Hewlett envisioned a different measurement process that gated those scaled-down, high-speed pulses into a slower-speed





accumulator (counter). Thus, the frequency counter was born.

Frequency counters were a huge commercial success and in great demand from the 1950s onward. They were used to measure everything from transmitter (Tx) frequencies to the accelerometers on which ballistic missile-guidance systems were based. HP became the industry leader in electronic counting in the early 1950s with the 524A frequency counter, which boasted a 0.01-Hz-to-10-MHz measuring range.

In 1954, plug-in downconverters were introduced as the model 524B electronic counter. Plug-ins eventually extended the measurement range to 18 GHz after the introduction of the steprecovery-iunction diode.

RF-interference (RFI)-measuring Rxs of the 1970s were generally mechanically tuned and cumbersome. By modifying some early spectrum analyzers, HP was able to enhance the RFI measurement technology with the addition of common antennas and probes. The 85650A quasi-peak adapter (circa 1982) was an early example of an instrument which, when added to spectrum analyzers, provided a broad electronic sweep capability and offered the designer a wide bandwidth in which to search for leakage signals. It also provided precise, calibrated data.

The earliest power-measuring techniques were primitive by today's standards. The story has been told that Russell Varian cleverly drilled a small hole at the appropriate position in the klystron cavity wall and positioned a fluorescent screen alongside it. The screw provided a gross indication that the cavity was in oscillation.

A major improvement to this measurement technology was made in 1961, when the 431A power meter, with a dual-thermistor design to reduce drift 100-fold, could measure power levels as low as 1 μ W. The 478/86A line of power sensors covered 100 kHz to 40 GHz, and later to 110 GHz.

The next big step in microwave power measurement came in 1974 with the introduction of the Model 435A power meter and its associated power-

sensor family. This sensor family was a clever exploitation of a silicon (Si)-chip fabrication process that placed a broadband microwave termination on one side of a thin Si web, and a sensitive metallic thermopile on the opposite side. The meter measured the absorbed heat down to 3 μW and up to 20 mW. Since the sensor was a true heat-sensing device, it provided "square-law" linear response over its entire range.

In 1997, the latest family of power meters and sensors was introduced. The Agilent EPM-series power meters took advantage of new ultra-wide-dynamic-range sensors (the E-series power sensors), to measure from -70 to +20 dBm in a single sensor.

The 185A and 187A sampling oscilloscopes (circa 1960) were giant leaps ahead in RF and digital measurements. Using sampling technology, they permitted engineers to measure exceedingly fast transition times for repetitive, pulsed waveforms. They featured sophisticated triggering circuitry for viewing actual RF waveforms to 1 GHz.

The ability to view the time-separated reflections from a coaxial transmission structure enabled engineers to diagnose reflections from individual elements. For example, the individual attenua-

tion elements of the model 355A VHF attenuator could be seen and each tweaked for exact $50-\Omega$ performance. If all were lumped together in a standing-wave-ratio (SWR) measurement, no corrective adjustments could be made. The advancement helped circuit engineers working on components that relied heavily on coaxial and stripline transmission structures.

Picture a mechanical, motor-driven klystron signal source, driving two back-to-back directional couplers, two diode detectors, and a 1-kHz ratio meter. This was the state of reflectometers in 1954. Scalar parameters were considered entirely adequate for production-line test assurance, and these analyzers measured SWR and reflection coefficient, as well as transmission parameters. Systems were developed for waveguide bands from 2.6 to 40 GHz, and for most coaxial bands.

Next came the 890-series sweep oscillators, which exploited BWOs for signal generation, making the sweep electronic. This led to oscilloscope displays with calibrations grease-penciled onto the cathode-ray-tube (CRT) screen. The 1416A SWR display (circa 1966) offerd a scope plug-in with calibrated reflection and transmission data.

ABOUT THE AUTHORS

ohn L. Minck joined Hewlett-Packard Co. in 1958 and retired in 1995, enjoying a rich 37-year career with the company. He held technical-marketing assignments, mostly in microwave areas, and was RF and microwave marketing-communications manager for several decades. In the early 1970s, Minck managed a venture product group that designed and introduced light-emitting diodes (LEDs) to the market, contributing LEDs to HP's first Model HP-35 pocket calculator. Since 1972, Minck has been active with NCSL International, a trade association, with interest in metrology and calibration issues. He was National President of NCSLI for 1977, and since 1979 has been editor of the organization's NCSLI Newsletter. Minck lives in Palo Alto, CA, with Jane, his wife of 45 years. He has three grown children.

arry Manz is president of Manz Communications, Inc., of Montville, NJ, which he founded in 1986. The company conducts media relations campaigns and produces technical print and Web-based editorial for companies in the electronics industry. Manz was editor of Microwaves & RF magazine during the 1980s. He can be reached at (973) 316-0999 or barry@manzcom.com.

RF Peak Power Meter Selection Meeting

Requirements:

Widest peak measurement band-width Full band-width over entire dynamic range Speed

Accuracy

Interactive graphical display

Ease of use

Automatic capture of waveform

Things to avoid:

Glitches

Ranging and associated errors, delays, slowdowns

Conclusion: BOONTON ELECTRONICS 4530 RF PEAK POWER METER.

Action Item: Call Boonton Electronics ASAP!





The Boonton 4530 RF Peak Power Meter brings peak power measurement capabilities to both the laboratory and production, making Peak, CW Power and RF Voltage measurements at high speed from 10 Hz to 40 GHz.

Contact Boonton Electronics for all of your power measurement testing needs.

Phone: 973-386-9696 Fax: 973-386-9191 Email: sales@boonton.com Web: www.boonton.com Boonton Electronics P.O. Box 465

Parsippany, NJ 07054-0465

BOONTON

Other families of sweep oscillators followed, with the 8690 series and eventually the 8620A series (circa 1970), which featured solid-state YIG oscillator sources for the first time. HP's microwave-component research labs contributed coupling microwave transistors with YIG

technology to yield exceptionally stable and high-power sources. Later came the 8350- and 8340-series signal sources.

HP continued to introduce new RF and microwave scalar analyzers, starting with the 8755 frequency-response measuring system of 1972. This was a

plug-in for the 180-oscilloscope family, which was specifically designed as a system for scalar parameter testing. The 8756A and 8757A scalar network analyzers followed in turn, each with more measuring capability and higher frequency ranges, ultimately reaching 60 GHz in 1985.

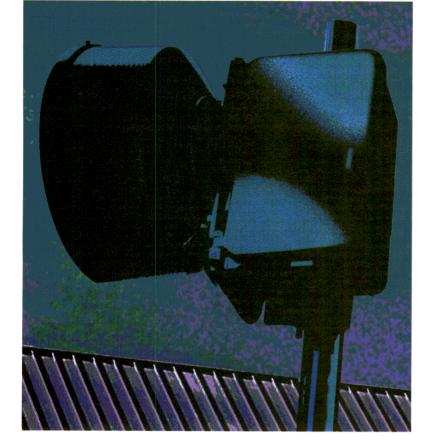
Following 1967's two-channel 8405A vector voltmeter, the 8410A VNA in 1968 revolutionized the characterization of microwave components from 10 MHz to 12 GHz, and soon to 18 GHz (Fig. 4). With its swept microwave source and signal-separation test sets, it easily exceeded its original objective—to stamp out slotted lines. Before this, engineers had to use tedious slotted-line measurements to compute a Smith chart plot, frequency by frequency.

The availability of the VNA popularized the design concept of scattering parameters: characterization data in complex impedance format for twoport and N-port microwave components. Provided with actual Smith-chart oscilloscope displays or phase-gain plots versus frequency, component designers gained powerful insights into their circuitry. In the microwave semiconductor revolution of the 1970s, designers raced to develop thin-film-on-sapphire integrated-circuit (IC) technology to combine the power of microwave transistors with a variety of circuit elements, including directional couplers, filters, mixers, converters, terminations, and lumped-circuit components such as inductors and capacitors.

The 8510A network analyzer of 1985 built on the tremendous insight that component design engineers first realized with the 8410A. Combining the new power of the microprocessor with the earlier analyzer's extensive capability for characterizing components and systems, the 8510A launched a revolution. For example, it could process frequency-domain data and render a time-domain characteristic of the signal passing through a complex subsystem on a chip.

Agilent's latest network-analyzer family, the PNA series, is built on the legacy of the 8510 family. However, these





Pual RF Output, Internal Reference YIG-Based Synthesizers for Digital Radios



"Look to the leader in YIG-Technology"



Generation II YIG-Based Synthesizers

Micro Lambda, Inc. a leader in the development of next-generation YIG devices introduces the second generation of YIG-Based Frequency Synthesizers covering the 2-12 GHz frequency range. Designed specifically for Digital Radio ODU's and harsh commercial environments, these latest synthesizers offer dual RF outputs and/or Internal Crystal reference oscillators yielding excellent integrated phase noise characteristics over carrier offset frequencies from 10 kHz to 10 MHz.

Tunable bandwidths of either 2 GHz or 3 GHz are available as standard products. This results in fewer numbers of synthesized sources required for a variety of Digital Radio frequency plans. Millimeter-Wave frequencies can easily be obtained using frequency multipliers to obtain output frequencies between 24 GHz through 44 GHz.

Applications include QAM and QPSK modulated Digital Radio's and a multitude of general purpose applications.

FEATURES

- · 2-12 GHz Frequency Coverage
- Excellent Integrated Phase Noise Characteristics
- · Dual RF Outputs
- · 3-Line Serial Interface
- Internal Crystal Reference
- 500 kHz Step Size
- Internal Memory (last frequency programmed - recall)

MLSL-SERIES SYNTHESIZERS

These series of synthesizers utilize an internal 10 MHz crystal reference oscillator to generate tunable frequencies covering the 2-12 GHz range. Dual RF output power levels of +8 dBm to +10 dBm are offered depending on frequency, with a standard tuning step size of 500 kHz. Input tuning commands are via 3-Line Serial interface. The size of these compact units is 2.5" x 2.5" x 1.0" without mounting plate and consume less than 6 watts of prime power. The units have an internal memory capability which "recalls" the last frequency programmed when the prime power is removed and reapplied. Standard models include 2-4 GHz, 4-6 GHz, 5-7 GHz, 7-9 GHz and 9-11 GHz. Specialized frequency ranges are easily implemented utilizing the versatile synthesizer architecture.







are totally new products, and some of the first to truly take the integration of microprocessor and microwave instrument to its highest level. They employ the Windows 2000 Professional operating system that brings the full complement of personal-computer (PC) and networking capabilities to the world of microwave instruments, and employ powerful digital signal processing (DSP) to implement 160 digital resolution bandwidth filters.

The measurement capability provided by the 8510T network-analyzer system was combined with RF and microwave circuit-design modeling software. This process provided the verification feedback needed to confirm that circuits and fabrications worked according to the design model. EEsof (later acquired by HP) and pioneers such as Les Besser, then with Super-Compact, delivered sophisticated microwave circuit-design models that have never stopped improving. As new computing power became available. more powerful modeling followed. Agilent's Advanced Design System (ADS) software suite currently brings microwave computeraided-design (CAD) performance and functionality to its highest level.

The 340A noise-figure meter was designed for radars, not for characterizing components, a clear need that had been mentioned by customers. Based on a 1982 landmark market-research study led by

Mike Cuevas, a new noise-figure product was envisioned. The resulting 8970A noisefigure analyzer pleased circuit designers since they could measure and display the gain and noise-figure parameters of amplifiers, mixers, and converters at the same 4. A young John Minck is shown with time. the 8410A vector net-

work analyzer, an

revoloutionized the

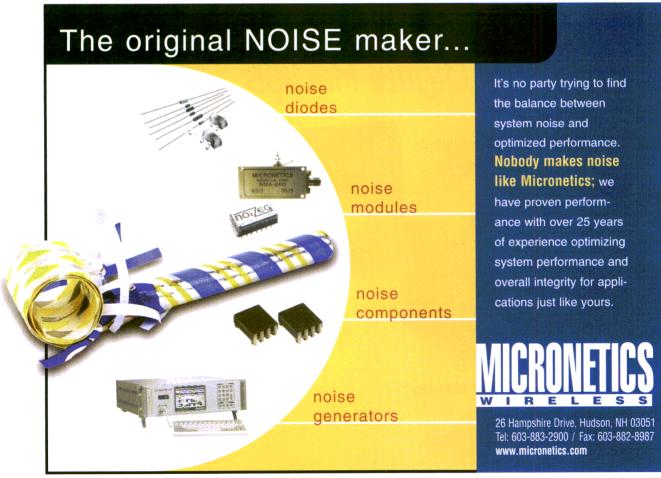
way that microwave

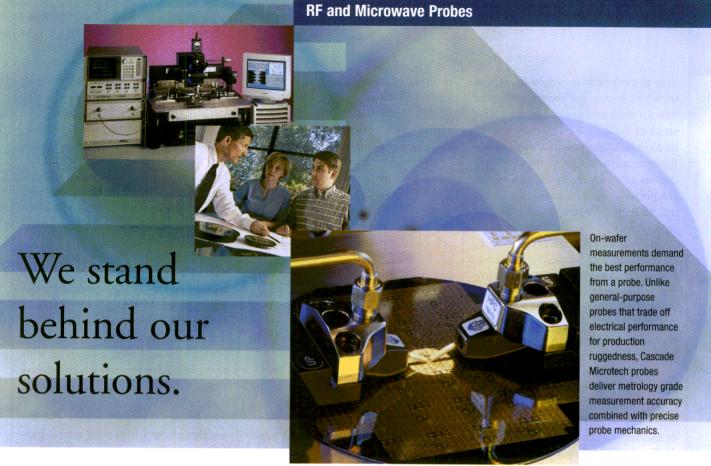
components were

characterized.

instrument that

Since circuit designers will gladly trade-off gain to improve the noise figure of an input amplifier, this capability proved popular for applications such as satellite Rx front ends. The 8970A had enough sensi-





So nothing will stand between you and your measurements.

The probe you buy is only as reliable as the company that stands behind it.

Cascade Microtech is not just the world's largest manufacturer of probes; we also produce probe stations, probe cards, accessories, and software used in analytical testing and R&D characterization of semiconductor devices on-wafer.

All of our probes have one thing in common, our no-compromise Air Coplanar™ probe technology. This innovation plus our years of extensive probing experience and superior manufacturing techniques, guarantees you accurate measurements...the first time...every time. What's more, our probes are available in the industry's most comprehensive range of tip configurations and mounting styles to fit your needs.

Most important, when you need answers, Cascade Microtech is there for you with leading-edge solutions to your tough probing challenges and the superior application support you just can't get from a probes-only discounter.

Find out more at www.cascademicrotech.com.
Or call 503-601-1000 or 1-800-550-3279 (USA & Canada).
Japan: 03-5478-6100. Europe: +44 1295-812828.



Channel Partner



Innovating Test Technologies

©2001 Cascade Microtech, Inc. The Cascade Microtech logo and Air Coplanar are trademarks of Cascade Microtech, Inc.

tivity to measure its own noise figure, and thereby compute out the error effect of its own front-end noise. Agilent's NFA series of noise-figure analyzers continue to expand the possibilities of noisefigure measurement, providing a real-time display of noise figure or gain versus frequency, easy measurement set up, built-in data storage, and printer connectivity.

In the late 1970s, HP began to focus on testing mobile transceivers. By combining a desktop computer, signal generator, frequency counter, power meter, various modulation sources, power supplies, and switching, the 8950A transceiver test system (Bigfoot) was born. It provided all of the measurement capability necessary to completely characterize an FM mobile transceiver.

HP had traditionally supplied general-purpose instruments for transceiver measurements. But starting around 1979, the 8901A modulation analyzer directly targeted the mobile Tx test market. The analyzer was essentially a 1-GHz-calibrated Rx that accurately and precisely measured the AM, FM, and phase modulation of mobile Txs.

By combining the 8901A with the 8662A microwave synthesizer and 8903A audio-modulation analyzer, along with some signal switching, specialized test systems such as the 8957S cellular-radio test system were created. In 1992, HP launched a family of compact, portable cellular test sets, many of which are still in use today. The Agilent 8920A RF communications test set combines 22 instrument functions for transceiver testing of land-mobile and cellular applications.

Yet another system, the Model 8924C, targeted CDMA. Test sets were customized for GSM/digital-communications-services(DCS)/pulse-codemodulator (PCM) DECT, and pager applications. Today, base-station testing is accomplished with the Agilent 8935-series base-station test sets for CDMA and TDMA technologies.

With the 10 wireless communications test sets of the Agilent 8960 series that were introduced in 1999, mobilephone manufacturers could achieve breakthrough speed that improved test throughput up to 300 percent in a system designed to test multiple communications formats.

HP has always played a commanding role in the computerization of instrumentation. The 2116A instrument computer that was introduced in 1968 yielded its first major application in the 8540A automatic network analyzer. Despite an interface which used a clacking teletypewriter and programming with punched paper tape on the floor, component designers were awed at the power of data-corrected measurements, and the insight they got into their circuit performance. By coupling the 2116A to HP spectrum analyzers, the 8581 automatic spectrum monitor was born. It enhanced long-term signal characterization for satellites and antennas.

True egalitarian automation became reality with the IEEE approval of the IEEE-488 GPIB of 1962. This emerged as desktop computers were becoming popular, and priced so that every test bench could afford them. HP led development of the bus technology, and arranged for an industry committee to take over and make it an open system.

Today's communication technology relies heavily on synchronized transmission frequencies, and cellular base stations, broadcast-television stations, and GPS satellites must reference these precise and stable standards. In fact, cesium beam standards can arguably be credited with standardizing the technology clocks of the world. HP engineers undertook the first "Flying Clock" project in 1964, flying two atomic clocks to Europe to precisely compare the US Naval Observatory time and the national standards at the National Bureau of Standards (NBS) with official clocks in Switzerland.

Atomic frequency standards had been developed in many countries to serve as



Features

- Wide frequency coverage
- Compact size/lightweight
- Max. handling power: 80 watts
- Power absorption: 30watts

Flat-package mounting (up to 38GHz) also available

FDK AMERICA, INC. BOSTON OFFICE

411 Waverley Oaks Road, Suite 324, Waltham, Massachusetts, 02452-8437, U.S.A. TEL: (1) 781-899-7700 FAX: (1) 781-899-7701

FDK CORPORATION

5-36-11, Shinbashi, Minato-ku, Tokyo 105-8677, Japan (Hamagomu Bldg.) TEL: (81) 3-5473-4672 FAX: (81) 3-3431-9436

FDK ELECTRONICS GMBH

Heerdter Lohweg 89, 40549 Düsseldorf, Germany TEL: (49) 211-591574 FAX: (49) 211-593549

Enter NO. 416 at www.mwrf.com

Microwave radio equipment

Radars/wireless LAN/Mobile

Microwave amp/osc

• Satellite comm/broadcast egpt.





Introducing... instant online information. Go to www.spectrumcontrol.com and enter the Speclink number.









PATCH ANTENNA ELEMENTS



Spectink #H0385

complete connectivity. To help make your designs a reality, turn to SPECWave inductors, capacitors, filters and antennas. The SPECWave family of wireless components deliver high performance in ever smaller sizes . . . exactly what you need for evolving applications like telematics, bluetooth and cellular communications.

And now we've added some new tools to our website with SpecLink instant product information, DesignDirect - an online design system, and our new OnLine Catalog – a way to build your own part number.

To see how we can help Keep Your Wireless Connections Clear, check us out @ www.spectrumcontrol.com Speclink #H0380 or call 814-474-1571.



SPECTRUM CONTROL INC. A Control Products and Systems Company

Signal Products Group

www.spectrumcontrol.com Phone: 814-474-1571 • FAX: 814-474-3110

Enter No. 282 at www.mwrf.com

the basic reference based on the atomic resonance principle, unvarying and fundamental. The 5060A became the first commercial product of choice in industrial primary-standards labs.

HP celebrated its 60th birthday in 1999 in a whirlwind of change. For a

quarter century of the company's history, test and measurement was its core business, and within it RF and microwave measurements played an enormous role in the company's success. Over those 60 years, HP had recorded an impressive record, includ-

ing a compound annual growth rate of 18 percent.

But the marketplace, and HP's role within it, had changed. The company that dedicated itself so steadfastly to test and measurement had become a leader in many other areas of electronics technology, most notably in computing. The question for the future of HP became increasingly how to continue its success in every market area.

Agilent Technologies was the answer. In March 1999, HP announced that it would split the company, with Agilent focusing on communications and life sciences, and HP focusing on computers and imaging. Agilent CEO Ned Barnholt encapsulates the opportunity:

"The split gave us a greater strategic focus. We were a communications and life-science company trapped in the body of a computer and imaging company. We now had an opportunity to go out and tell our story, and to focus more aggressively on our markets. We felt, and I think this has been proven to be true, that we've become a lot faster and more responsive. So anything we want to change, anything we want to do differently, we can do. We decided to bring forward the best of the HP values and culture, and to look also at new ways to become more successful."

Although less than two years have passed since Agilent was formally created, the results of this line of thinking have already borne fruit—perhaps most noticeably in the area of RF and microwave instrumentation. Agilent is introducing significant new RF and microwave instruments that solve key measurement problems, at a rate much faster than when it was HP.

Agilent recently made the decision to sell its life-sciences interests. So, as it was for so long at HP, test and measurement is Agilent's primary focus.

Editors note: Readers can request a copy of a 36-page Agilent brochure that reviews a broad array of HP and Agilent communication test products, starting with the model 200A by requesting literature number 5890-2090E from the website at www.agilent.com.



FROM COMPONENTS TO SYSTEMS

AMPLIFIERS TO 60 GHz

- Octave to ultra-broadband
- Noise figures from 0.35 dB
- Power to 10 watts
- Temperature compensated
- Cryogenic

MIXERS TO 60 GHz

- · Single-, double-, and triple-balanced
- Image rejection and I/Q
- Single-sideband, BPSK and QPSK modulators
- · High dynamic range
- Active and passive frequency multipliers

INTEGRATED SUBASSEMBLIES TO 60 GHz

- Integrated up/downconverters
- Monopulse receiver front ends
- PIN diode switches
- Ultra-miniature switch matrices
- Missile receiver front ends
- Switched amplifier/filter assemblies



FREQUENCY SOURCES TO 40 GHz

- Free-running VCOs/DROs
- Phase-locked cavity oscillators
- Phase-locked coaxial resonators
- Synthesizers for SATCOM
- Fast-tuning communication synthesizers



IF AND VIDEO SIGNAL PROCESSING

- Logarithmic amplifiers
- Constant phase-limiting amplifiers
- Frequency discriminators
- AGC/VGC amplifiers
- I/Q processors
- · Digital DLVAs



SATCOM EARTH STATION EQUIPMENT TO KG-BAND

- Synthesized up/downconverters
- Test translators
- LNA systems
- 1:N redundancy units
- INMARSAT products
- FM modems



FAX: (631) 436-7430

100 Davids Drive, Hauppauge, NY 11788 www.miteg.com KDI/Triangle's Resistor Products Group offers



- Price Differential AIN, same price as BeO
- Delays & Excuses Delivered from stock
- Capacity Limitations
 Over 1 million delivered

free samples of

Aluminum Nitride Products

- Resistors
- Attenuators
- Terminations

N/C=



An ISO 9001 Company \bullet Power Levels 5–600 Watts \bullet 50 & 100 Ω standard (other values available)



KDI resistor products are distributed by Richardson Electronics, Ltd.



ARMMS Meeting MeldsSimulation And Testing

The most recent gathering of a British-based RF and microwave technical society covered a wide range of topics, including component and system modeling and testing.

echnical societies offer their members the opportunity to share ideas in a relatively noncompetitive environment. One of the small, but important RF and microwave societies in the UK is the ARMMS RF & Microwave Society, with two meetings each year devoted to the design and measurement of devices and products operating at RF and microwave frequencies. The most recent meeting/

conference, held from April 30 to May 1, 2001 at Burleigh Court, Loughborough University (Loughborough, England), featured 16 talks on design, simulation, and test of devices, components, and automotive systems.

The technical program was coordinated by Steve Evans-Pughe of Applied Wave Research, Inc. (El Segundo, CA). To start things off, Malcolm Edwards of Applied Wave Research explored the design automation of RF and microwave computer-aided engineering (CAE) based on Microsoft's component-object-model (COM) capability. The COM is a technology that allows multiple programs resident in a computer's random-access memory (RAM) to communicate with each other simply and effectively. The COM capability can be used for a number of purposes, such as extending the capability of an existing software program by adding functions that were not originally included in the program.

The COM capability is built into the Microwave Office suite of CAE

tools from Applied Wave Research and can be controlled from any programming language or scripting

engine such as Visual Basic, Java Script, or a compiled language such as Visual C++. The Microwave Office program includes a scripting language that uses standard Visual Basic syntax that allows advanced users to automate the design process through the creation of macros and utilities.

The built-in scripting language allows operators to explore concepts and perform tests on new functions before extending the process into the realm of compiled code. This capability can help speed the design process as part of a Rapid Application Development (RAD) environment. The automated approach was demonstrated on measurements and analysis of the resonator and the source of negative resistance for a microwave oscillator.

As a sequel to Edwards' presentation, Chris Potter of P&H Technology Consultants (Cambridge, England) also addressed COM with an examination of automated prototype testing. Potter notes that it is fairly straightforward to write RF test sequences by

JACK BROWNE
Publisher/Editor

Finding a better way.





Long Laminates



Tight Tolerances



Low Cost Substrate

There's a world of difference between our laminates and the competition's

When it comes to designing and manufacturing high performance laminates, we've always been finding a better way.

Taconic is the company that introduced:

- PTFE/woven glass
- Tighter tolerances
- Long laminates
- Low cost commercially oriented microwave substrate
- Shorter lead times
- Duplicate manufacturing and service centers: US, Ireland and Korea

Our experienced sales and technical staff aren't just order takers, they're problem solvers. They don't just react, they anticipate problems and offer solutions.

That's why our customers are really our best sales people. They know what a critical difference we make in a fast paced, highly competitive marketplace.

TACONIC

Finding a better way.

Visit our website: www.4taconic.com Corporate Headquarters, Petersburg, NY

Enter No. 299 at www.mwrf.com

Taconic congratulates the Staff of *Microwaves and RF* magazine for serving the high-frequency industry with a quality publication for 40 years.

Taconic was founded in 1961 under the leadership of Mr. Lester T. Russell, the acknowledged inventor of the process for applying PTFE coating to fiberglass fabric. Mr. Russell pioneered this process while working for DuPont in the early 1950's. This is the central process for producing nearly all of the products that Taconic sells. Taconic is the largest worldwide coater of PTFE fiberglass fabric.

Taconic is a diversified company serving electronics, industrial, and architectural markets. We are a manufacturing organization with facilities in New York, California, Ireland, England, France, and South Korea with total employment of approximately 400 people.

Taconic has kept ahead of the growing demands for product and services world-wide. We are the first to have duplicate manufacturing facilities in the US and Europe. Additionally, Taconic is moving ahead with plans to produce laminate materials in Korea.

Since the introduction of the TL series (TLY, TLX, and TLT materials), Taconic has delivered the tightest dielectric-thickness and dielectric-constant tolerances in the industry.

Taconic leads the industry with innovation. We developed the first capabilities to produce laminates up to three meters in length. This technology allowed the development of long printed circuit antennas for mobile telephone infrastructure and microwave landing systems.

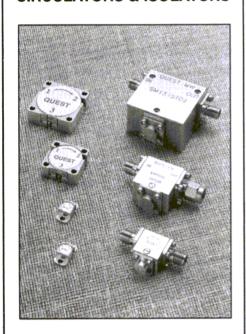
We recognized in the early 1990's that the growth of the wireless industry required a new substrate material. Taconic changed the market by delivering the TLC product as the lowest-cost substrate in the world. Not only was it low cost, but the material also exhibits improved thermal and mechanical properties. Since then, the industry has continued to benefit from iterations of new products based around the TLC concept. The newest offerings by Taconic capture the benefits of Organic and Ceramic substrates in the ORCER family including the RF-35, CEr-10, RF-60, and RF-30 materials.

At Taconic, we pride ourselves on offering the best service and shortest lead times in the industry. Our trained and qualified staff strives to meet and exceed the needs of our customers worldwide. Taconic is committed to investing in the growth and improvements in the high-frequency market.



NEIS

CIRCULATORS & ISOLATORS



QUEST for Quality, QUEST for Performance, QUEST for the BEST:. .JOIN US.

Quality products with quick delivery at competitive prices are our standard.





225 Vineyard Court
Morgan Hill, CA 95037
Phone 1 408 778 4949
Fax 1 408 778 4950
Toll Free
1 877 QUESTMW (783 7869)
Website: www.questmw.com
E-mail: circulators@questmw.com

Enter NO. 444 at www.mwrf.com

applying COM with programs such as Microsoft Excel, Microsoft Word, Agilent VEE, and National Instruments' Test-Stand. He adds that the SoftPlot program and its COM interface is well-suited to RF test automation. SoftPlot can take care of a general-purpose interface bus (GPIB) and ask it to send command strings to an instrument.

At the system level, J.A. Flint and A.R. Ruddle of MIRA (Warwickshire, England) detailed Guidelines for Electromagnetic Compatibility modeling for Automotive Requirements (GEM-CAR). This is a three-year European project aimed at producing guidelines for the numerical modeling of automotive EMC situations. One goal of the project is to highlight the potential uses of modeling in the design and test phases of the vehicle-development life cycle. Another goal is to define the practical issues which need to be addressed before embarking on modeling the automotive environment. The GEMCAR document is meant to be a two-way learning tool for EM software developers and the automotive industry.

Advances in computational EMs (CEM) and computing power have allowed these systems to be applied not only to microwave devices and components, but also to the simulation of complex designs, such as automobiles and aircraft. CEM methods used in automotive modeling include the transmission-line-modeling (TLM) method, the finite-difference-time-domain (FDTD) method, the method of moments (MoM), the boundary-element (BE) method, and the finite-volume (FV) technique.

The authors described two of the simplest of the GEMCAR validation models: an antenna model and a vehicle model. The antenna model is based on a log-periodic-dipole-array (LPDA)/biconical hybrid design. The widely available antenna type is commonly used for immunity-type EMC testing. The particular antenna for modeling spans 20 MHz to 1 GHz, which is the main band of interest in the European Automotive EMC Directive 95/54/EC.

Engineers at MIRA placed the anten-

na into a semianechoic chamber and used it to illuminate a volume of space. The electric field strength was then measured at various points in front of the antenna in horizontal and vertical polarizations. These points were chosen to represent the envelope of a vehicle that would be placed. A reference point was chosen in the chamber and the relative field strength at each of the other calibration points was recorded for use in a comparison with the model. A model was constructed of the experimental setup and a prediction for the relative field strength was calculated.

Since a vehicle represents an extremely complex three-dimensional (3D) model, the computer-aided-design (CAD) data for the vehicle were simplified before any attempts were made to apply meshing techniques for numerical modeling. For a TLM analysis, the vehicle data were discretized on a tartan mesh, essentially a Cartesian grid with variable cell dimensions. Surface currents were computed for a vertically polarized plane-wave incident on the front of the vehicle.

Both models were found to agree closely with the measured data, except at lower frequencies. Below 100 MHz, the effects of the chamber walls dominated the measurement results due to the poor low-frequency response of the absorbing material. At higher frequencies, the accurate placement of the measurement probes becomes a major issue due to the decreasing wavelengths of the test signals. The various modeling techniques yielded similar results, although with some methods requiring greater computational resources and processing time. For example, the MoM approach is well-suited for analyzing the antenna, but is less effective when modeling geometrically complex structures such as the vehicle. These are some of the issues that the GEM-CAR program must address.

In a less complex vein, Mats Jansson of Nera Networks AS (Kokstad, Norway) spoke about the design of waveguide filters using a 3D simulator. Jansson explained that although many EM computer programs exist for the design



LOWER COST MICROWAVE CIRCUITS

UP TO 40%
SAVINGS OVER
THIN FILM

MICROSTRIPS MULTILAYERS

FILTERS
INDUCTORS
LANGE COUPLERS



Amitron

The Future of Thick Film Technology www.amitron.com 978.686.1882

Enter No. 207 at www.mwrf.com



of waveguide filters, these programs are limited to specific filter topologies or coupling structures. Due to these limitations, there is still a real need for a general-purpose tool for waveguide design. His solution is based on applying well-known circuit-theory synthesis methods in combination with the High Frequency Structure Simulator (HFSS) from Ansoft (Pittsburgh, PA). By optimizing one dimension of the waveguide structure in each step, the simulation can be performed quickly with fast convergence. Couplings are optimized for the correct K-inverter values at the desired center frequency. Resonators are optimized by calculating the resonator length and then performing fine tuning until the structure resonates at the center frequency.

The approach was applied to the design of a waveguide filter with inductive posts for use at 15.35 GHz. The filter, which is tunable from 14.90 to 15.35 GHz, was measured at 15.32 GHz. Measurement results agreed closely with the simulation data.

Bernhard Wagner of Computer Simulation Technology (Darmstadt, Germany) offered a presentation on Perfect Boundary Approximation (PBA). The PBA is an extension to the time-domain modeling technique of finite integration (FI). The PBA approach provides accurate simulation of thin objects without requiring long computation times. It avoids the small time-integration step width of other time-domain modeling methods and avoids the poor matrix conditions for certain structures that result from the use of some frequency-domain methods. Compared to conventional FI and finite-element (FE) methods, the PBA approach can perform complex calculations on 3D structures in a fraction of the time. The technique was applied successfully to a number of different structures, including a planar patch-antenna array, a diplexer, and a human-body specific-absorption-rate (SAR) study.

Kelvin Clarke of Ansoft spoke on modeling and optimizing photonic-bandgap (PBG) structures. The behavior of these devices is analogous to the character-

istics of atomic crystal structures in optical and solid-state physics. These structures can occur in bulk form (as substrates) or in a surface form (as circuits with or without ground planes). The surfaces of these devices reflect incident waves in phase rather than as out-of-phase images. These structures have a type of array symmetry which results in repeating signal characteristics. Also, they do not propagate EM waves at certain frequencies within the bandgap region. Clarke notes that PBGs could be useful as novel transverse-EM (TEM) model waveguide for feed structures, as reducedloss antenna substrates, as dielectric-filled waveguide feeds with built-in bandrejection filtering, and as non-imaging ground planes to improve antenna-element performance.

Since the HFSS program includes certain features, such as a full-featured finite-element-analysis (FEA) solver, linked boundary conditions, an Eigenmode solver, and a field calculator, the software is well-suited to the analysis of PBGs. Several modeling methods are possible with HFSS, including the use of the direct-transmission method (for 3D PBGs), the use of the dispersion diagram method (for surface PBGs), and the use of the reflection-phaseanalysis method (also for surface PBGs). The latter two approaches also employ the use of the company's Optimetrics parametric-sweep program for analysis of unit cells.

The direct-transmission method generates S-matrix data which can be used to obtain the PBG "forbidden band," where EM transmission does not occur. Of course, the transmission parameters are only accurate for the direction of propagation that is modeled; propagation in the other direction must be modeled separately. Also, the transmission parameters are only accurate for a number of periods in the direction of propagation that is modeled. The approach was applied to the modeling of a dielectric-rod PBG substrate with a top frequency of 15 GHz.

In the dispersion diagram method, the Optimetrics program is used to generate a parametric sweep using a nominal HFSS project design. A dispersion curve is generated by plotting Eigensolutions versus appropriate input variables in Optimetrics. The results are plotted as Eigenmodes versus boundary-condition phases. As a sample project, the dispersion diagram method was used to model a high-impedance PBG lattice etched on a dielectric substrate with a dielectric constant of 2.2.

In the reflection-phase analysis method, an HFSS nominal project is a unit cell of the repeating PBG circuit or structure, imaged with linked boundaries on each side. Incident plane-wave excitation is directed toward the PBG surface, and an additional integration plane is identified internal to the radiation boundary face for use with phase-data extraction.

The PBG structures offer great promise for microwave and millimeter-wave design, and they can be modeled with the HFSS. But Clarke notes that the choice of modeling approach should be guided by finding the simplest solution possible, obtaining a good starting design, not using too many variables at once, and using a well-adapted mesh for the quickest possible convergence.

Mark Eidem of Castle Microwave (Twyford, Berkshire, England) explored the nature of passive intermodulation (IM), which can cause poor performance in cellular base stations. It can be caused by bad solder joints, poor alignment of parts, inadequately torqued screws and fasteners, poor plating processes, the nonlinear behavior of ferrite materials, and environmental degradation. Forms of passive IM include reflected or reverse IM and through or forward IM. Passive IM is measured by injecting multiple signals to a device under test (DUT), boosted by a linear power amplifier (PA), and measured with a sensitive receiver (Rx) [capable of -140 dBm or better sensitivity]. One of the trends in passive-IM testing is a move toward swept-frequency testing, rather than static two-tone tests, to reveal the true passive-IM behavior of microwave components. Swept tests were performed on a personal-communications-services (PCS)-band diplex-

What's New,

What's Next, What Works.

Look for It At

Internet World Fall 2001

Today, businesses are looking for practical solutions to help increase productivity, cut costs, become more customer focused and in the end, increase profits. Companies will continue to look for the latest, most relevant technologies. They will look for technologies that offer the best solutions to solve their business problems and also create new opportunities.

Internet World Fall is where your business can find those solutions it's looking for, through its in-depth conference program and exhibit floor brimming with companies showing the latest technologies. Join us at Internet World Fall 2001 and discover what's new, what's next and most importantly, what works — for your business.

NINTH ANNUAL



INTERNET WORLDFall 2001

Co-Located With:



Sponsored By:





Featuring:



Sponsored By:



For more information, visit www.internetworld.com. For information about exhibiting, e-mail: eventsales@iw.com or call 203-559-2866

Internet World Fall 2001 Conference: October 1-5 Exhibits: October 3-5 Jacob K. Javits Convention Center New York City

Produced By:



Official Sponsors:



INTERNET WORLD.COM

Wireless Enterprise • Small Business E-Commerce • Enterprise Streaming • Security • One-to-One Marketing • Extended Supply Chain Services Effective Outsourcing • Content Management • Peer-to-Peer Networking • Advanced E-Business Practices • E-Procurement • Storage Area Networking • Electronic Customer Relationship Management

CRYSTAL PRODUCTS

N 5 DAYS



Chances are if you order your crystals on Monday you can have them by Friday. Sound too good to be true? Not if you use ICM's Expedite Delivery.

We realize that time is money and you can't wait endlessly for the crystals you need. That's why ICM delivers some standard and custom crystal products in as little as 5 days. Not only that, but most of our products are manufactured here in the United States and meet ISO standards.

Think you'll need your crystal product quicker than 5 days? We can handle that too. We have a 3 day expedited delivery option on some products, just let our customer service staff know your delivery date when you place the order.

We've been in business for 50 years, manufacturing quality crystal products and meeting or exceeding the expectations of our customers. So if you need crystals in 5 days, give us a call. We look forward to doing business with you.

Exceptional service...

Exceptional products



Enter NO. 425 at www.mwrf.com

This is what we do for suppression of RF energy...

Eliminate unwanted RF interference by using the C-RAM product line of microwave absorbers from Cuming Microwave Corporation. Whatever your requirements, you will find exactly what you need in our complete line of rubber-based and lossy foam absorbers for RFI suppression:

- Rubber-based absorbers from 800 MHz to > 40 GHz
- Lossy foam absorbers from 2 GHz to > 40 GHz
- · Peel & stick adhesive for convenient mounting
- · Custom fabrication to part configuration drawings
- High-volume, cost-effective solutions
- Custom application services

Request our RF Problem Solver Kit containing an assortment of sample materials for engineering evaluation. Keep it handy in your lab to speed the selection of absorbers for your application needs as they arise.

This is who we are.



T: 508 580-2660 • 1 800 432-6464 • F: 508 584-2309 • email: mwsales@cumingcorp.com

● Enter NO. 434 at www.mwrf.com

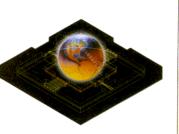
NEWS

er filter to show differences in results from static-IM testing. Tests were performed with a test system from Summitek Instruments, Inc. (Parker, CO) consisting of an agile Rx and an integrated RF module with frequency synthesizers, diplexers, filters, PAs, a power combiner, and a low-noise amplifier (LNA). The system supports measurements of IM products as a function of frequency or as a function of time.

In other presentations, Richard Ranson of Filtronic (Keynes, Bucking-hamshire, England) provided an introduction to third-generation (3G) cellular systems, reviewing frequency allocations, air interfaces, and coding. Kal Kalbasi and Steve Tucker of Agilent Technologies (Santa Rosa, CA) offered a detailed examination of digital intermediate-frequency (IF) design for 3G systems, while Yngve Thodeson of Nera Networks ASA detailed a new field-effect-transistor (FET)-based frequency tripler with 13-GHz output signals.

Finally, Dominic FitzPatrick of Milmega Ltd. (Ryde, Isle of Wight, England) reviewed the benefits of solidstate versus traveling-wave-tube (TWT) amplifiers for various applications. He compared output-power levels, efficiency, distortion characteristics, noise, gain, and reliability. In addition, Emil Entchev and associates from Farran Technology Ltd. (Bodmin, Cornwall, England) addressed the design of highpower amplifiers using commercial gallium-arsenide (GaAs) monolithic microwave integrated circuits (MMICs) and a waveguide-based power combiner. They achieved better than 2-W (+33-dBm) output power from 36.00 to 37.25 GHz.

The next meeting of ARMMS is scheduled for November 12 and 13, 2001 at the Hilton Hotel, Bracknell, Berkshire, England. For more information about ARMMS, please contact the society's Secretary, Duncan McIntosh, ARMMS RF & Microwave Society, P.O. Box 1215, Shirley, Solihull B90 4JH, England; 01212-432694, FAX: 01983-616864, e-mail: duncanmcintosh@ieee.org, Internet: www.armms.org.



When Performance and Reliability Are Your Number One Packaging GoalsTHE ONLY SOLUTION IS STRATEDGE.

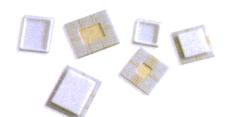
HI-SPEED WIRELESS DEVICES You've designed the perfect microwave circuit for high performance and reliability, now you need the package to keep it perfect. One company has been designing, building and delivering microwave packaging solutions longer than anyone: StratEdge. The result is millions of packages delivered to commercial and Hi-Rel customers just like you.

paramount.

- ISO 9002 Certified
- Volume Production Since 1992
- Innovative, Patented Technology
- Complete Simulation and Design Capability
- Test and Assembly Services
- Microwave and mmWave Packages
- Production Packages from DC thru 50 GHz
- Single Chip MMIC Power Amp Packages
- High Speed Digital Packages
- MCM Packages
- Commercial & Hermetic Packages
- Leadless, Leaded & SMT Designs
- Glass and Ceramic Dielectrics

4393 Viewridge Avenue San Diego, California 92123 858-569-5000 Ext.202

www.stratedge.com/mwrf



SE50 Series - Offering the widest operational bandwidth available today; DC through 50 GHz! Perfect for Point-to-Point, Point-to-Multipoint radio, LMDS, and any other application where price and performance are

LCC Series - The VSAT industry benchmark.

Operational from DC to 23 GHz, the
LCC offers leads for easy next level interconnect, with the ability to handle tremendous power. The LCC has found success in VSAT,
optical and instrumentation systems.

0C-768 Packages - If you're tasked with the challenge of packaging OC-768 devices, only StratEdge engineers have the experience and technology required for designing broad bandwidth High Speed Digital packages through 50 GHz.

OG-192 Packages - StratEdge was the first to develop High Speed Digital, OC-192 packaging. Whether you choose a ceramic wall, or glass side wall package from the PTI Division of StratEdge, our microwave design engineers can deliver a leaded or surface mount solution that will meet any budget.







ONNOVATION

Facing a ferocious marketplace?

Let RFMD tame your challenges.

We dare to be different by providing highly integrated solutions that help meet stringent system requirements and reduce your bill of materials.

RFMD employs **innovation** to develop **next-generation** processes, circuits, architectures, standards and packaging **in advance of the marketplace**.

Our deep design resources and extensive manufacturing capacity enable us to design a wide range of best-in-class components for all your RFIC needs.

Because true success has no competition.

DARING innovation – it sets us apart.



Proprietary, State-Of-The-Art RF Integrated CircuitsSM

7628 Thorndike Road Greensboro, NC 27409-9421

Phone 336.664.1233

Fax 336.931.7454

Visit us at European Microwave Week 2001, Booth #124

Mention daring when contacting us.



editor's choice

VCO serves cablemodem market

THE MODEL V585ME24 VCO can generate frequencies from 1568 to 1971 MHz for low-noise applications such as cable modems. The device generates its entire band of frequencies within a voltage tuning range of +1 to +20VDC, and has an average tuning gain of 33 MHz/V. Its typical SSB phase-noise performance is -102 dBc/Hz at 10kHz offset from the carrier. Power output is 6.5 ± 1.5 dBm into a $50-\Omega$ load. Second-harmonic suppression is -9 dBc. The VCO minimizes pulling to less than 10 MHz with a 14-dB return loss, and pushes less than 5 MHz/V with a 5-percent change in the supply voltage. It draws 16 mA of current from a nominal +10-VDC power supply, and operates from 0 to 75°C.

Z-Communications, Inc., 9939 Via Pasar, San Diego, CA 92126; (858) 621-2700, FAX: (858) 621-2722, Internet: www. zcomm.com

Enter No. 73 at www.mwrf.com

Leaded packages target VSAT applications

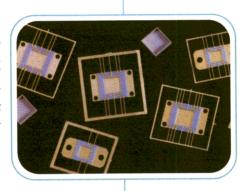
THE LCC FAMILY of ceramic packages for DC-to-23-GHz amplifiers serves C- and Ku-band VSAT applications. The packages feature two or more RF leads and multiple DC leads, and claim to provide easy and cost-effective attachment to the next level of the system while maintaining the integrity and electrical performance of an IC. They combine a Cu composite base with a patented microstrip-embedded, microstrip-to-microstrip transition design. The composite base provides thermal conductivity and expansion coefficient compatible with GaAs chips. A plastic lid with epoxy preform protects the device within.

StratEdge, 4393 Viewridge Ave., San Diego, CA 92123; (858) 569-5000, FAX: (858) 560-6877, Internet: www. stradedge.com

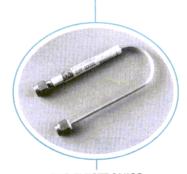
Enter No. 74 at www.mwrf.com



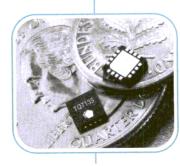
Z-COMMUNICATIONS VCO



STRATEDGE CERAMIC PACKAGES



RLC ELECTRONICS CABLE FILTERS



TRIQUINT POWER AMPLIFIER

Cable lowpass filters built to specifications

A FAMILY OF coaxial-cable low-pass filters is built to meet customer specifications for cutoff frequency, rejection, and mechanical requirements. The U-shaped filters are available with four specifiable characteristics: cutoff frrequency, number of sections, connector spacing, and cable diameter. Cutoff frequencies range from 100 MHz to 26 GHz. Multiple sections achieve different values for 3-dB point, 30-dB point and 60-dB point. The connector spacing—the distance between the SMA connectors at the ends of the "U"—supports a user's specific mechanical requirements. The two diameter values available [0.141 in. (0.358 cm) or 0.086 in. (0.218 cm)] yield different cable-loss constants and minimum bend radii. The filters can handle up to 2 W of average RF power.

RLC Electronics, Inc., 83 Radio Circle, Mt. Kisco, NY 10549; (914) 241-1334, FAX: (914) 241-1753, Internet: www.rlcelec tronics.com.

Enter No. 75 at www.mwrf.com

PA covers CDMA/AMPS

THE MODEL TQ7135 PA is a +3-VDC, twostage SiGe HBT amplifier designed for use in IS-95/98 and AMPS-compliant mobile phones. The amplifier boasts an efficiency of 40 percent and a gain of 28 dB. It has two power modes to minimize quiescent current consumption: a highcurrent setting of 94 mA and a lowpower setting of 72 mA. Its ACPR is -49 dBc and its alternate-channel power is -56 dBc. VSWR is 10:1 for supply voltages under +4.5 VDC. The amplifier is housed in a 4-mm² surface-mount, 16pin, fine-pitch leadless plastic package, providing phone designers with a low-profile solution.

TriQuint Semiconductor, 2300 NE Brookwood Parkway, Hillsboro, OR 97124; (503) 615-9000, FAX: (503) 615-8900, Internet: www.triquint.com.

Enter No. 76 at www.mwrf.com

performance Carrier: 820.00E+6 F -20 -30 -40 -50 -60 -70 -80 -90 -100 1M 10M SMC CRO-S-1030 CRO, CFO & MFO Series Ceramic resonator based Extremely low phase noise High stability Frequency range: 350 MHz to 2100 MHz For additional information, contact Synergy's sales and application team.

Phone: (973) 881-8800 Fax: (973) 881-8361 E-mail: sales@synergymwave.com World Wide Web: www.synergymwave.com

201 McLean Boulevard, Paterson, NJ 07504





Broadband Giants Slug It Out

Number 3 tries to take over number 1 and war breaks out for the control of CATV services in the US. Comcast Corp., the third largest cable provider

recently made an unsolicited \$58 billion bid to take over the cable operations of AT&T Broadband, the largest cable company. About a week later, AT&T's

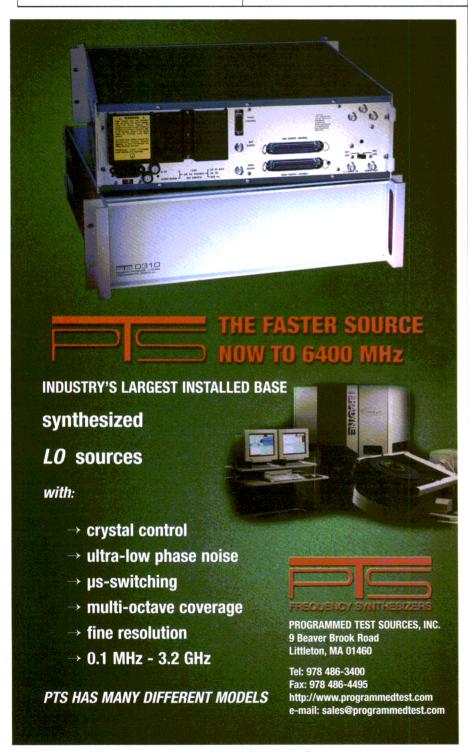
board of directors rejects the bid saying that it does not reflect the full value of its cable unit. Comcast attempts to sidestep AT&T's board by getting stockholders to pressure the board into making the deal, now considered a hostile takeover move.

At stake in the battle is king-of-thehill status in the broadband business. A Comcast-AT&T merger would give the combined company 22 million subscribers, one-third of the US market. AOL Time Warner, in second place, has 12.7 million customers.

The deal is clouded by the highly unsettled state of AT&T's businesses. The company is splitting itself into four separately traded businesses, one of which is the Broadband unit. While it is ostensibly looking for either a sale or partnership with a cable company, another option is spinning off Broadband into a separate business unit. However, the spinoff move did not take place when AT&T rejected Comcast's offer, which is considered a positive step toward the eventual merger of the two companies.

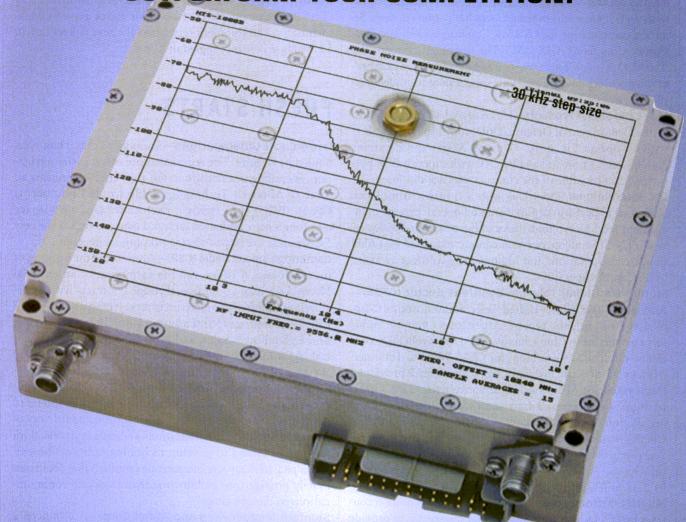
When the dust settles, Comcast will probably get its way. For one thing, it has a very good track record of integrating previous acquisitions and running a profitable operation, while AT&T does not. It claims that the savings on AT&T's combined cable operations could amount to more than \$1 billion per year. Second, when Comcast's offer was announced, AT&T's stockholders responded positively by sending the stock up 12 percent (Comcast's shareholders did not do likewise, sending the stock down by 7 percent). Under the terms of the Comcast offer, AT&T stockholders would own shares in the new company, and maintain their shares in the core AT&T stock.

When all of the maneuvering ends, Comcast will likely have to sweeten the deal by many billions to keep AT&T from looking for different suitors or using a number of delaying tactics at its disposal.



ELIMINATE PHASE HITS ...

OUTPERFORM YOUR COMPETITION!



THE DRS SYNTHESIZER

SPECIFICATIONS

Frequency Range: 4 - 15 GHz in bands

Bandwidth: to 1200 MHz Step Size: 10 kHz to 10 MHz

Power: +13 to +17 dBm Spurious: <70 dBc typ.

Dimensions: 4.6 x 4.0 x 1.16 in.

The DRS Synthesizer... compact, cost effective, with low phase noise optimized for high data rate digital radio applications with complex modulation schemes up to 256 QAM ... its the perfect solution for your system! Now you can outperform your competition...get PHASE HIT FREE performance at a price you can afford. Call our applications engineers to discuss your requirements and needs.



9 Whippany Rd. • Whippany, NJ 07981 TEL: 973-884-2580 • FAX: 973-887-6245 www.cti-inc.com • e-mail: sales@cti-inc.com

financial news

CONTRACTS

BAE SYSTEMS—Will be upgrading countermeasures systems on US Navy and Marine Corps helicopters under a \$6 million contract from the US Army Communications and Electronics Command (CECOM). The upgraded system—the AN/ALQ-144A Countermeasures Set-provides comprehensive protection against a wide spectrum of Ir-guided missile threats.

M/A-COM SIGINT Products—Has received a contract award by the Department of Defense (DoD) for 71 microwave Rxs with an option for up to 71 more. Major specifications involve a collection and analysis Rx with superior BER performance. The value of the contract was not disclosed.

LCC International, Inc.—Has won a contract from Click Vodafone to perform deployment and overall project-management services for phase three of Egypt's nationwide network. The \$16 million, one-year contract extension is in addition to the Operations and Maintenance contract awarded to LCC in October 2000.

Motorola's Global Telecom Solutions Sector (GTSS)-Announced that China United Telecommunications Corp. (China Unicom), the second-largest telecommunications service operator in China, has awarded Motorola three contracts, totaling \$141 million, for GSM-900 and 1800 network expansion and installation in China's three provinces. Deployment of Motorola's Horizonsystems GSM infrastructure solutions will start soon for the expansion and installation of China Unicom's GSM networks in three of China's major provinces—Jiangsu, Shandong, and Xinjiang. The expansion projects, which are slated for completion by this October, will increase the capacity in the three provinces by 2.68 million subscribers.

Mu-Del Electronics, Inc.—Was awarded a \$3.4 million contract by ITT Industries. The two-year contract is to provide the Rx frequency generator and pulse-forming circuits for a new ITT radar program.

EMS Technologies, Inc.—Announced the award of a sevenyear contract with the US Department of Transportation (DoT) for technical services relating to wireless technologies and network services. The contract was awarded by the DoT's Transportation Administrative Services Center (TASC) under a new program known as STATUS-Specialized Technical and Technology User Services. STATUS is designed to provide all government agencies-federal, state, and localwith immediate access to specialized technical expertise in a number of information-technology and infrastructuresupport areas, including artificial intelligence, geographic/geospacial information systems, e-learning and learningmanagement systems, operational maintenance support, and wireless technologies/networks. Under the contract, EMS will compete in the Wireless Technologies/Networks area for task orders submitted by various government customers to perform wireless communications and connectivity systems and services.

Harris Corp.—Has completed initial shipment of its Falcon II AN/PRC-117F(C) multiband/multitransmission manpack radios to the US Air Force's Tactical Air Control Party (TACP) squadrons at Hanscom Air Force Base in Massachusetts. The shipment represents the first delivery of an \$11 million contract signed in March.

FRESH STARTS

PowerCache Ultracapacitors—Announced that it has overhauled its website. The redesigned site offers easier navigation, including a search function that cross-references all three of Maxwell Technologies' Electronic Components Group (ECG) sites (www.powercache.com, www.space electronics.com, and www.sierrakd.com), as well as the new ECG portal site (www.electroniccomponents.com).

Cambridge Silicon Radio (CSR)—Announced the opening of its San Jose, CA office and the formation of an external North American sales force, through contracts with several well-established manufacturers representative companies: EIR, J-Squared, and SSI (Eastern region); Beta Technology, Bonser-Philhower Sales, and Luscombe Engineering (Central region); Luscombe Engineering, Moulthrop Sales, and Westrep (Western region); and J-Squared (Canada).

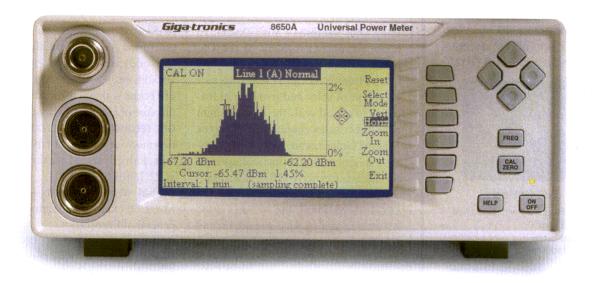
SRI International and GeoLink Corp.—Have signed a Memorandum of Understanding where the companies intend to work together to advance the sophistication and delivery of pervasive satellite-communications and radar systems. Both companies intend to develop technology for small-formfactor phased-array satellite-antenna terminals that could ultimately provide true mobile broadband satellite communications to the consumer.

Stanford Microdevices and Atmel Corp.—Announced a joint-development agreement, where the two companies will collaborate on the design and development of wireless communications products based upon silicon-germanium (SiGe) products.

Tru-Connector—Unveiled their new website, which was designed by Strand Marketing. Located at www.tru-con.com, the site offers telecommunications, wireless, semiconductor, and military designers a variety of standard and custom connectors and cable assemblies to choose from. In addition to a completely redesigned user interface, visitors can use Tru-Connector's "Build Your Own Connector" tool that takes them through a step-by-step specifications process and enables submission directly to Tru-Connector's technical sales team for price and delivery.

Mitel Corp.—Has introduced a new global identity—Zarlink Semiconductor under which it will deliver communications-connectivity solutions to the world's leaders in voice and data networking. Zarlink will provide highly specialized ultralow-powered chip sets for use in medical applications. MRE

Proven.



The fast, easy and accurate 8650A, because there's still no substitute for experience.

Download a data sheet at **www.gigatronics.com** or call **1(800)726-GIGA**

Crest Factor

Histograms, CDF, CCDF

Strip Charts, Peak Hold

WCDMA, CDMA 2000, CDMA, TDMA, and GSM/EDGE ready

1,750 readings/second CW, 800 readings/second modulated

Patented NIST traceable on-board calibration system

Modulation, CW, Peak and Average Power measurements

Automatic and manual Time Gating with graphical display

90 dB dynamic range in a single sensor

4-line graphic display

100 kHz to 40 GHz



Harmonic (Comb) Generators for Output

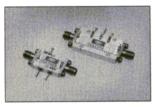


You can now select *any* input frequency from 10 MHz to 10 GHz and obtain output frequencies up to **50 GHz***



GC Series

- No Bias Required with Specified 1/2 Watt Drive
- Miniature Sizes
- · Drop-In Modules or with Connectors



GCA Series
with Integral Preamplifier

- 0 dBm or +10 dBm Input
- Drop-In Modules Available
- +5 V DC Power Supply or Integral Regulator for +12V or +15V Bias

*Please call factory for limits

Your Source for the Most Complete Line of Comb Generators

Other Herotek Products:

Detectors • Limiters • Amplifiers • Switches • Multipliers •

Subassemblies



The microwave

products source

Herotek, Inc.
155 Baytech Drive
San Jose, CA 95134
Tel: (408) 941-8399
Fax: (408) 941-8388
Email: info@herotek.com
Website: www.herotek.com





DY 4 Systems Names Quinly As President

TOM QUINLY has been appointed to the position of president at DY 4 Systems, Inc. Mr. Quinly has been with DY 4 for four years, most recently serving as DY 4's acting vice president of operations. He will be located in the Leesburg, VA office.

Enea OSE Systems—MIKE DAGER to CEO; formerly president of the US-based division.

I-Bus/Phoenix—ULRICH DIEHL to vice president of sales and marketing; formerly involved with the development of indirect sales channels at Wavetek Wandel Goltermann. Also, ANDY CONWAY to global marketing manager for broadcast; formerly OEM sales manager for the UK operation.

LCC International, Inc.—CARLO BAR-AVALLE to senior vice president and CEO of the Europe, Middle East, Africa, and Asia Pacific operations; formerly managing director responsible for the development and management of international operations at Exchange, plc. Scott Specialty Gases—DAVID HER-MANCE to director of national accounts; formerly vice president of sales and marketing for the US Gauge Division of Ametek Corp.

The Cellular Telecommunications & Internet Association (CTIA)—DIANE CORNELL to vice president for regulatory policy; formerly associate bureau chief at the FCC's Wireless Telecommunications Bureau.

Quake Global—POLINA BRAUNSTEIN to vice president of operations; formerly director of operations at Space Electronics. Also, JENNIFER FORMAN to business development director; formerly marketing manager.

CTS Corp.—VINOD M. KHILNANI to senior vice president and CFO; formerly vice president and CFO at Simpson Industries, Inc.

REMEC, Inc.—DAVID L. MORASH to executive vice president and CFO; formerly CFO for Wireless Knowledge.

ITT Industries, Cannon—PAUL H. ESLING

to director of contract equipment manufacturing (CEM); formerly director of sales and marketing for Celestica Corp. **Tecknit**, **Inc.**—JOHN CROSBY to president of Tecknit's global companies; formerly director of European activities.

GHz Technology, Inc.—CHARLES WEEKES to senior vice president of marketing and sales; formerly served in a similar position at ZF Linus Devices.

Global Opticom, Inc.—RAYMOND NIEDZWIECKI to COO; formerly director general of Eurostar.

Andrew Corp.—PAUL R. COX to group president for communication products; formerly vice president of communication products.

Hybrid Networks, **Inc.**—ANAND KHOKHA to the board of directors; remains as president of Durkee/Sharlit Associates.

Celerity Digital Broadband Test—DAVID SPRENKLE to Eastern regional sales manager; formerly marketing specialist with RDL, Inc.

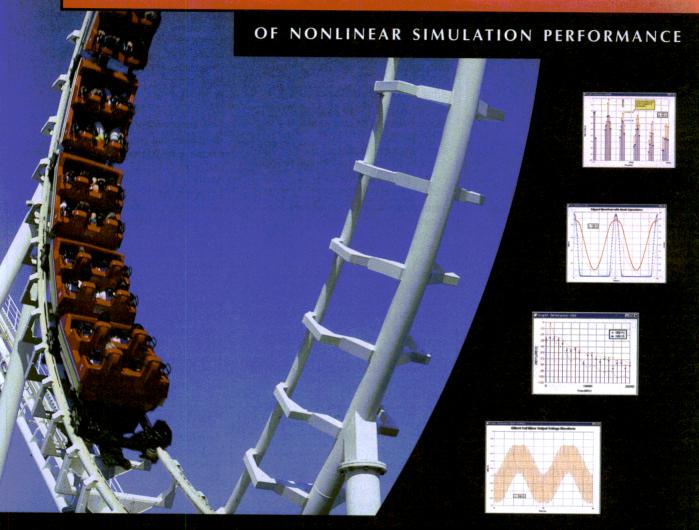
Century Tel, Inc.—ANDREW AULTZ to vice president for the southern region; formerly vice president of the Competitive Local Exchange Co. (CLEC) at Alltel.





Zentrix Technologies, Inc.—KENNETH COLEMAN, JR. to vice president of sales; formerly president of Technical Sales and Solutions.

RIDE THE POWER CURVE



ower, Accuracy and Speed. That's what you get with Eagleware's new harmonic balance mulator, HARBEC[™]. From real-time tuning, to application of artificial intelligence techniques, to co-simulation with ectromagnetics, HARBEC does it all ... with a powerful set of features that includes:

bust Simulation

- unlimited, arbitrary circuit topology
- wide range of nonlinear device models (diodes, JFET, BJT, MOSFETS, MESFETS)
- wide range of sources (voltage, power, current, waveform)
- DC analysis and optimization
- unlimited tone harmonic balance analysis and optimization

EM Co-simulation

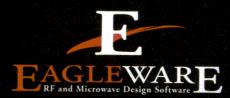
High Performance Design

- Al performance optimization
- fast tuning

Spice Model Import
Extensive Parts Library
Equations and Post Processing

nd it's fully integrated into the GENESYS suite of synthesis, S-parameter, electromagnetic and physical design tools.

o Grab a Seat and Hold On! With nonlinear modules priced at \$4990, they're going fast. And so will your design.



Enter No. 232 at www.mwrf.com

www.eagleware.com



Mid-Atlantic RF Systems offers creative solutions for your most demanding requirements for RF microwave components and systems.

Mid-Atlantic Products

Amplifiers
Switches
Power Dividers
Hybrid Couplers
Directional Couplers



PO Box 745, Forest Hill, MD 21050

Tel.: 410/893-2430 Fax: 410/638-5193

email: info@midatlanticrf.com www.midatlanticrf.com

education

► SHORT COURSES

IEEE Topical Workshop on Power Amplifiers for Wireless Communications

September 10-11 (San Diego, CA)
IEEE Microwave Theory and Techniques Society (MTT-S) in collaboration with the UCSD
Center for Wireless Communications
University of California-San Diego
Michell Parks

(858) 534-2498

e-mail: parks@ece.ucsd.edu

The Software Defined Radio (SDR) Forum

September 11-13 (Madrid, Spain)

Bock Communications, Inc.

(714) 540-1030 ext. 15, FAX: (714) 540-1060

e-mail: rsilverio@bockpr.com Internet: www.sdrforum.org

Introductory RF and Microwaves

September 20-21 (Lake George, NY)

R.A. Wood Associates

1001 Broad St., Suite 450

Utica, NY 13501

(800) 966-3606, FAX: (315) 735-4217

e-mail: RAWood@rawood.com

Internet: www.rawood.com

Future Directions in IC and Package Design Workshop (FDIP)

October 27 (Royal Sonesta Hotel,

Cambridge, MA)

Components, Packaging and Manufacturing

Technology Society

Paul Baltes

(520) 621-3054, FAX: (520) 621-1443

e-mail: epd@engr.arizona.edu

Internet: www.cpmt.org/conf/

fdip01/fdip.html.

Principles of Modern Radar

October 29-November 2 (Atlanta, GA) Georgia Institute of Technology, Continuing Education

Atlanta, GA 30332-0385

(404) 385-3502

e-mail: conted@gatech.edu

Internet: www.conted.gatech.edu.

►MEETINGS

2001 IEEE Emerging Technologies Symposium on Broadband Communications for the Internet Era

September 10-11 (Dallas, TX) IEEE Dallas Section

Jon Veihl

IEEE ETS

P.O. Box 852492

Richardson, TX 75085-2492

(972) 952-0011, FAX: (972) 952-0054

CTIA Wireless IT and Internet 2001

September 11-13 (San Diego Convention

Center, San Diego, CA)

The Cellular Telecommunications Industries

Association (CTIA)

Michelle Solomon, Registration Manager

(202) 736-3244

e-mail: msolomon@ctia.org

Silicon Monolithic Integrated Circuits in RF Systems

September 12-14 (Ann Arbor, MI)
IEEE MTT-S, NASA Glenn Research Center,
the National Science Foundation and the
Army Research Office
Center for Professional Development
University of Michigan, College of
Engineering

Beth Hillis, Program Coordinator (734) 647-7200, FAX: (734) 647-7182

34th International Symposium on Microelectronics (IMAPS 2001)

October 9-11 (Baltimore Convention Center, Baltimore, MD)

IMAPS

611 2nd St. NE

Washington, DC 20002

(202) 548-4001, FAX: (202) 548-6115

e-mail: IMAPS@imaps.org Internet: www.imaps.org

2001 IEEE GaAs IC Symposium

October 21-24 (Renaissance Harborplace Hotel, Baltimore, MD)

IEEE MTT-S, Electron Devices Society, and

Solid State Circuits Society

2001 IEEE GaAs IC Symposium

Piscataway, NJ 08855

Mary Clemente (732) 562-5350, FAX: (732) 981-1203

e-mail: m.e.clemente@ieee.org.

►CALL FOR PAPERS

58th ARFTG Microwave Measurements Conference: RF Measurements for a Wireless World

November 29-30 (San Diego, CA) Automatic RF Techniques Group (ARFTG), IEEE Microwave Theory and Techniques Society (MTT-S)

Dr. J. Stevenson Kenney, Technical Program Chair

nair

School of Electrical and Computer Engineering, Georgia Institute of Technology Atlanta. GA 30332-0250

(404) 894-5170, FAX: (404) 894-4641 e-mail: iskenney@ece.gatech.edu

Internet: www.arftg.org

Deadline for Abstracts: September 10

IEEE MTT-S International Microwave Symposium

June 2-7, 2002 (Seattle, WA)

IEEE Microwave Theory and Techniques Society (MTT-S)

Technical Program Chairs:

Eric Strid, Cascade Microtech, Inc.

e-mail: eric@cmicro.com

Ed Godshalk, Maxim Int. Prod.

e-mail: ed_godshalk@or.mxim.com

Internet: www.ims2002.org

Deadline for technical paper summaries in

.DOC format: November 26

You are on a power trip...

you design amplifiers and every last dBm counts.

rely on Harmonica

You don't want any surprises when the part that performed so well during simulation is built and tested. No shifted gain. No premature saturated power or unaccounted spectral regrowth...and certainly no oscillations.

Successful amplifier designs demand optimal ACPR, power, IP3, nonlinear stability and yield. That's why many engineers are turning to

Harmonica, the most powerful high-frequency circuit design solution available for the PC desktop. With physics-based distributed

models and a time-tested
Harmonic Balance engine,
Harmonica delivers superior
speed, accuracy, power and
functionality. And as a part of
Ansoft's Serenade Design
Environment, Harmonica
offers seamless links to

layout, system simulation, electromagnetics, and third-party tools.

After all, every dBm counts.

Discover the difference Harmonica makes in the design of amplifiers, mixers, oscillators, filters, matching networks and other components in your wireless design.

For your free evaluation copy of Harmonica or any of the tools in Ansoft's Serenade Design Environment call 412-261-3200 or send e-mail to info@ansoft.com.

Power Trip

ANSOFT

high performance EDA

www.ansoft.com

R&D roundup

CMOS deltasigma modulator samples IF in digital FM radio Rx

IN DIGITAL RADIO Rxs, baseband signals have traditionally been processed using analog techniques. But development trends for these Rxs are pushing toward full integration onto a single CMOS chip, which would permit complete mixed-signal (analog and digital) processing on a single device. And moving the analog-to-digital interface closer to the antenna would permit IF digitization. This would confer several advantages to the Rx. Mainly, it would maintain the quality of downconversion by avoiding analog imperfections, 1/f noise, and DC offsets. But IF digitization can become a bottleneck for the system, and requires highperformance analog-to-digital conversion. Since the analog-to-digital conversion is performed prior to channel-selection filtering, the ADC must have a wide dynamic range to guarantee sufficient signal resolution, especially in the presence of a large adjacent channel. Paolo Cusinato of Texas Instruments, Davide Tonietto of Conextant Systems, Fabrizio Stefani of STMicroelectronics, and IEEE Senior Member Andrea Baschirotto have devised a sigma-delta modulator for this type of ADC. The sixth-order bandpass sigma-delta modulator operates at 42.8 MHz over a 200-kHz bandwidth with a dynamic range of 74 dB. The modulator was fabricated using standard 0.35- µm, 3.3-VDC CMOS technology. See "A 3.3-V CMOS 10.7-MHz Sixth-Order Bandpass $\Sigma\Delta$ Modulator with 74-dB Dynamic Range," IEEE Journal of Solid-State Circuits, April 2001, Vol. 36, No. 4, pp. 629-638.

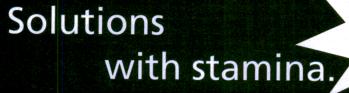
Piezoelectrically actuated microstrip antenna offers variable frequency, bandwidth, and gain

MICROSTRIP ANTENNAS ARE used in many military and commercial applications because they conform to surfaces, are durable, and easy to manufacture. But they are limited to applications that support relatively narrow banwidths and low antenna gain. Some tuning techniques have yielded moderately increased bandwidth, but with an accompanying reduction in efficiency and no increase in instantaneous bandwidth. Parasitic elements, added to a microstrip antenna to increase gain, can also affect the antenna's bandwidth. To overcome these limitations, IEEE Member Jennifer T. Bernhard, E. Keily, and Gregory Washington of Ohio State University have developed a variable-bandwidth microstrip antenna that is actuated by layers' piezoelectrical material. The antenna's resonant frequency, bandwidth, and gain change as a function of the vertical spacing between the primary radiator and its parasitic director. The researchers found that this method provides good mechanical performance while avoiding electromagnetic interference. The vertical spacing between antenna and parasite was varied from 2.28 to 10.2 mm using a stack of high-deflection, piezoelectrical actuators. The antenna's resonant frequency generally increased, and the bandwidth generally decreased, as the space between the plates increased. Also, at the smaller spacing values, the instantaneous bandwidth was larger than that for a single patch antenna or comparable varactor-tuned patch antennas. See "A Smart Mechanically Actuated Two-Layer Electromagnetically Coupled Microstrip Antenna with Variable Frequency, Bandwidth, and Antenna Gain," IEEE Transactions on Antennas and Propagation, April 2001, Vol. 49, No. 4, pp. 597-601.

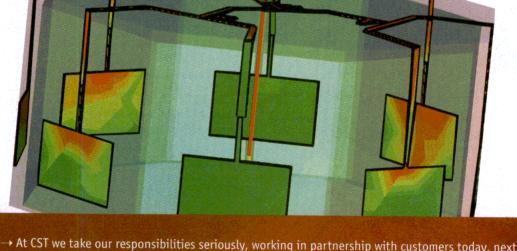
SiGe RF front end achieves GaAs performance while conserving power

WIRELESS COMMUNICATIONS SYSTEMS continue to stimulate demand for a semiconductor process that would support high integration and high performance at a reasonable price tag. For low-noise RF front ends, the process of choice traditionally has been GaAs. But the outstanding performance of GaAs MESFETs comes at the expense of a relatively high price and high DC power consumption, especially in LNA design. CMOS has become a more economical alternative for higher integration, and significant progress has been made in designing inexpensive CMOS RF front ends—but their performance is limited. Searching for an alternative, substantial research effort has

been put into the development of SiGe bipolar technology. IEEE Student Member Osama Shana'a, IEEE Member Ivan Linscott, and IEEE Fellow Len Tyler have developed a SiGe bipolar RF front end that achieves GaAs-like performance but consumes much less DC power. The circuit is a scaled 1.8-GHz front end built on a 30-GHz SiGe bipolar process. The authors also developed a low-noise Gilbert active mixer. Both circuits use a frequency-scalable optimization technique to ensure the best noise factor for a given DC power. See "Frequency-Scalable SiGe Bipolar RF Front-End Design," IEEE Journal of Solid-State Circuits, June 2001, Vol. 36, No. 6, pp. 888-895.



Agilent HFSS users call CST for a limited time SPECIAL OFFER!



→ At CST we take our responsibilities seriously, working in partnership with customers today, next week, and over the years to come. Our aim is not simply market leadership, but to be there for you on the road to success, offering consistent, reliable, fast and accurate solutions and advice. Over 20 years experience in the area of numerical field calculation has already been invested in the development of our 3D EM simulation tools.

CST MICROWAVE STUDIO™ is used world-wide by market leaders such as:

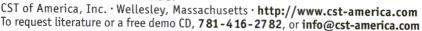
- · Raytheon
- · Radio Frequency Systems
- · Lucent Technologies
- · Nokia
- ·Sony

Typical applications include:

- · Waveguides, filters, power splitters
- · Planar structures, switches
- · Couplers, multiplexers, LTCCs
- · MMIC packages, RLC-extraction
- · Coax and multipin connectors
- · All kinds of antennas







If You Need to Switch Don't Fight It!!



Pass Bands (GHz)

Insertion Loss (DC-24 GHz) Switching Speed 10.3 - 11.715.8 - 17.7 18.8 - 19.7 6.0 dB max

200 ns max

70 dB min

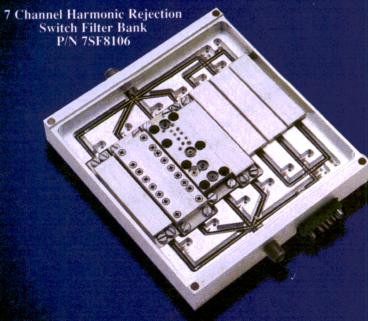
SP4T PIN Diode Switch 2.0 to 18 GHz P/N 4S3068



Specifications

Frequency Range Insertion Loss Isolation **VSWR** Switching Speed

2.0 - 18 GHz 2.9 dB max 55 dB min 2.0:1 max 50 ns max



Specifications

0.5 - 0.8Pass Bands (GHz) 0.8 - 1.31.3 - 2.02.0 - 3.53.5 - 6.06.0 - 10.410.4 - 18.0

6.0 dB max Insertion Loss 2.0:1 max **VSWR** 2nd Harmonic Reject. 50 dBc min 65 dBc max Harmonics

MVS) Microwave & Video Systems, Inc.

87B Sandpit Road Danbury, CT 06810 TEL (203) 792-7474 FAX (203) 792-7475

...join the Big Easy with (MVS)



High Performance PIN Diode Switches & Switch Filter Banks

- Available from 0.1 to 26 GHz.
- RF & Microwave Applications

SPDT PIN Diode Switch 0.3 to 20 GHz P/N 2S3025



Frequency Range Insertion Loss Isolation **VSWR** Switching Speed

0.3 - 20 GHz 3.0 dB max 70 dB min 2.0:1 max 100 ns max

2 Channel Switch Filter Bank Miniature P/N 2SF3170

Specifications

Pass Bands (GHz)

Insertion Loss **VSWR**

Switching Speed Size(Inches)

6.66 - 7.667.66 - 8.66

> 3.0 dB max 2.0:1 max 100 ns max

 $3.0 \times 1.1 \times .35$

10 Channel Switch Filter Bank 1 to 18.5 GHz P/N 10SF3181-1



Dual Outputs Low Freq Input High Freq Input Insertion Loss Rejection Range(55 dB)

1.0 -18.5 GHz

6 Pass Bands (1-10.5 GHz) 4 Pass Bands (10.5-18.5 GHz)

9 dB max DC - 19 GHz

"Quality by Design"

(MVS) also specializes in Microwave Integrated Assemblies. Think of us for your packaging and assembly integration needs.

Enter No. 260 at www.mwrf.com

Get the devil out of the details

High Frequency Planar EM Software Solutions from Sonnet®

Do your high frequency designs act as though they're possessed by parasitics? Are your amplifiers tempted to oscillate and your oscillators to amplify? Are package resonances demonizing your circuit performance?

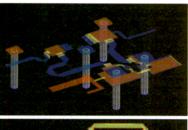
Sonnet can exorcize those oscillating amplifiers, correct your wayward filters, rebuke misbehaving matching circuits and put a fork into those pesky packaging problems, all before you ever build them.

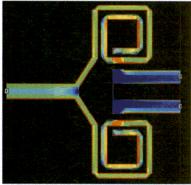
Sonnet offers a heavenly array of electromagnetic software solutions for your challenging planar circuit and packaging designs.

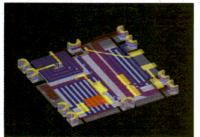
The Sonnet em^{\otimes} Suite has been an industry standard for accuracy and reliability in high frequency planar 3D EM analysis software for over 10 years. All EM vendors quickly say they are "accurate", but only Sonnet quantifies it. Struggling with $\pm 5\%$ error from other EM software? With Sonnet $\pm 1\%$ is easy, and better than $\pm 0.1\%$ is possible.

Sonnet has the power and experience you need for analysis of the most demanding applications in planar circuit and package technologies. And our technical support is so solid you'd be tempted to think it was from Above.

Contact us about taking the devil out of your high frequency design details...don't tempt fate!







Free Download:

Try Sonnet Lite for your 1- and 2- layer circuit designs...FREE.
See our web site for details.
ww.sonnetusa.com



Sonnet Software, Inc. toll free: 877/7-SONNET 877/776.6638 phone: 315/453.3096 fax: 315/451.1694 info@sonnetusa.com



Simulate IMD In RF Amplifiers With Memory Effects

This article presents a model that provides helpful predictions of multi-tone IMD in systems having long time-constant memory effects.

pectral regrowth resulting from nonlinear distortion in RF amplifiers is a tremendous problem for designers and users of digitally modulated and multicarrier communication systems. Intermodulation distortion (IMD) occurs when mixing two or more carriers and is caused by the nonlinearities of the active devices used in the mixing circuits. Today, IMD in multi-tone spectral communication systems is evaluated

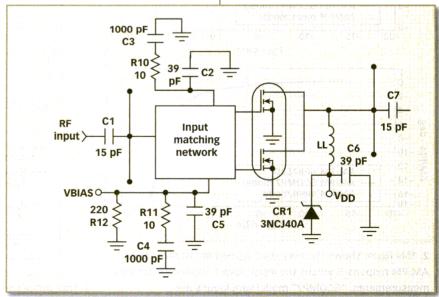
relations between them and the more-familiar, two-tone, third-order intercept point (IP3) and single-tone ampli-

tude-modulation/amplitude-modulation (AM/AM) and AM/phase-modulation (PM) standards.²⁻⁴ In ref. 5, it is shown that NPR can be accurately predicted with a current commercial system simulator, such as OMNISYS, by

using figures of merit such as adjacentchannel power ratio (ACPR) or noisepower ratio (NPR). Commercial measurement systems are now available for these multi-tone figures of merit¹ and many studies continue to clarify cor-

PASCAL DELEMOTTE, FRÉDÉRIC BUÉ, AND YVES CROSNIER

Institut d'Electronique et de Microélectronique du Nord, IEMN, UMR CNRS 8520, Av. Poincaré, BP 69, 59652 Villeneuve d'Ascq, France; 33 03 20 43 65 09, FAX: 33 03 20 43 65 23. e-mail: delemotte@univ-lille1.fr



1. A block diagram of the OMNISYS-based Memory Effects simulation is shown here.

using the measured AM/AM and AM/PM characteristics of the RF amplifiers under test as input data. Nevertheless, this approach concerns only quasimemoryless systems—that is, systems where the amplitude and phase distortions at a particular instant depend only on the input signal level at that instant. Most systems exhibit a quasimemoryless behavior, except those that have large time constants due to biasing circuits, feedback loops, or thermal effects. Several works have been performed on that subject, giving rise to specific measurement techniques and simulations.^{6, 7} The purpose of this article is to provide a simulation approach that features three advantages: it can be implemented easily in most commercial system simulators, it allows any designer to perform a systematic analysis, and it provides helpful predictions of multitone IMD in systems where long timeconstant memory effects are identified or suspected. As in ref. 5, this article makes use of the functions and models avail-

able in the OMNISYS software from Hewlett-Packard Co. (Palo Alto, CA). It presents a specific model where amplitude and phase distortions are controlled, affording a time-delay representation of memory effects. To illustrate the model's capabilities, the article presents two analyses describing the expected behavior of commercial amplifier modules in the presence of memory effects—first in the case of two-tone excitation, then in the case of a mutitone excitation—to investigate NPR.

Model Configuration

The model, which is built in order to monitor the complex distortion of a particular amplifier, is based on the assumption that the AM/AM and AM/PM characteristics have been previously measured and that the time-

constant τ of the memory effect has been clearly evaluated. With these

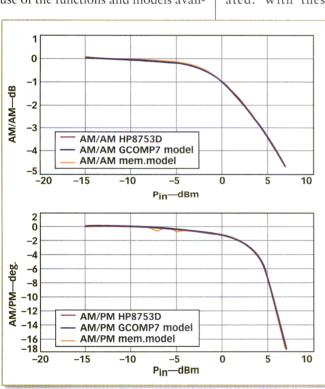
requirements fulfilled, the principle of the model lies in the realization of the following relationship:

$$\begin{aligned} V_{out}(t) &= V(t)\cos[\omega t + \phi(t)] = \\ V(t)\cos(\omega t)\cos(\phi(t) - V(t)\sin(\omega t)\sin(\phi(t)) \end{aligned} \tag{1}$$

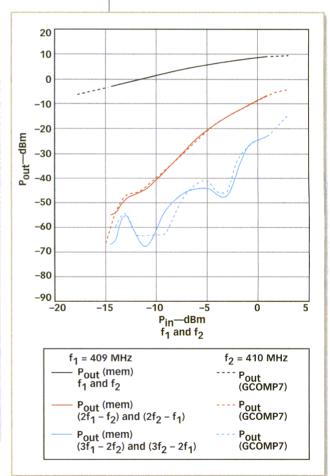
This represents the amplifier's output voltage V_{out} at time t.

In this relationship, the memory effect can be taken into account by making the voltage amplitude V(t) and the phase deviation $\varphi(t)$ depend on the input voltage V_{in} at instant $t-\tau_1$ and at instant $t-\tau_2$, where τ_1 and τ_2 are delays characterizing memory time constants. **Figure 1** shows the complete block diagram built with OMNISYS elements to achieve these functions.

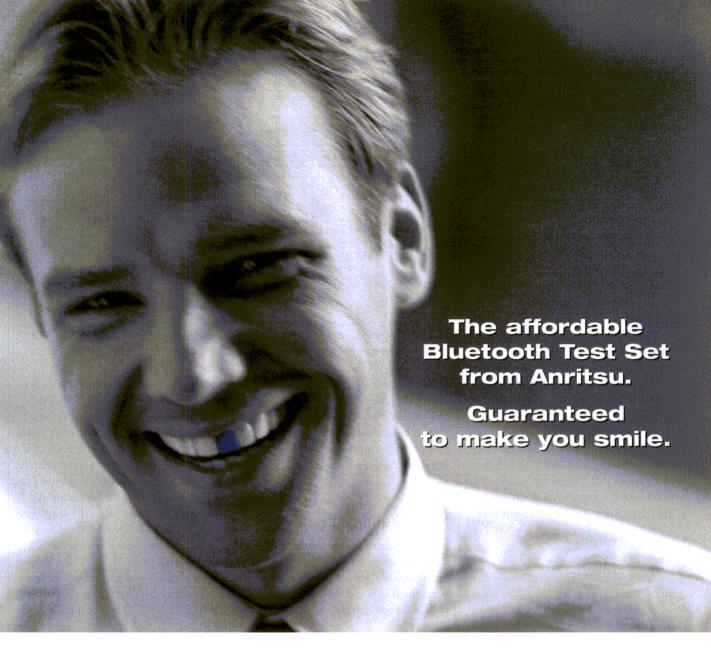
In this simulation setup, V(t) is compressed by the gain-controlled ampli-



2. This figure shows the very good agreement of AM/AM and AM/PM responses versus the input power obtained from VNA measurements. "GCOMP7" model simulations and "mem.model" simulations for the module "MAR 3" from Mini-Circuits at 410 MHZ are illustrated above.



3. This comparison shows the good fit between IM responses obtained with the "GCOMP7" model and "mem.model" for the module "MAR 3."



Only Anritsu brings you Bluetooth RF Test Spec V0.09 in one powerful, economical package.

There's only one Bluetooth Test Set specifically designed to perform manufacturing and interoperability tests to RF test spec V0.09. And that's Anritsu's MT8850A. So what's our secret?

The core of Anritsu's measurement system is a reference Bluetooth transceiver, not an off-the-shelf radio. That means we can deliver a higher level of performance, offering full user control of a variety of test parameters including test frequency,

hopping ON and OFF, loopback or TX test modes and number of measured packets.

The MT8850A wins again when it comes to flexibility. It measures both Bluetooth chip sets as well as the actual consumer products that use a Bluetooth radio.

The Bluetooth Test Set from Anritsu is also easy to use and even easier to afford. It's perfectly priced for a wide variety of production line applications.

The Bluetooth Test Set from Anritsu. It's going to make a lot of people smile. Call us for details at 1-800-ANRITSU, or visit us at www.us.anritsu.com/bluetooth









DESIGN

fier element "VGAIN2." This is tabulated according to the equivalent voltage gain (assuming a $50-\Omega$ standard) of the device under test (DUT) derived from its power gain. The "VGAIN2" control loop is fed by the input signal through a delay element of duration τ_1 and an envelope detector. Achieving the phase deviation, $\phi(t)$ is slightly more complex. The input signal is first delayed through a delay element of duration τ_2 . Then, the phase deviation $\phi(t)$ is extracted by using the phase comparator element "PCOMP." For this operation, the working signal is divided into two paths. One consists of a direct transmission without phase shift to play the role of reference. The other comprises a "GCOMP7" element conditioned with unity gain and a phase response with respect to the signal level identical to the AM/PM characteristic of the DUT. Then, the sine and cosine functions of $\phi(t)$ are synthesized using a splitter element, "CSPLIT," followed by two "EQN1" elements where two polynomial voltage-transfer functions are implemented. The functions are:

$$\cos \phi(t) = 1 - \left[\phi(t)\right]^2 / 2 \tag{2}$$

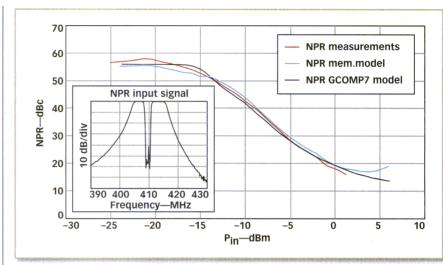
and

$$\sin \varphi(t) = \phi(t) - \left[\phi(t)\right]^3 / 6 \tag{3}$$

Another splitter element, CSPLIT, and a +90-deg. phase-shifter element provide the amplitude-modulated RF signal V(t) cos ω t and its quadrature form V(t) sin wt. Two "EQN2" elements, where the multiplication operation is implemented, produce the products V(t) cos ω t cos φ (t) and -V(t) sin ω t sin φ (t). Finally, a summation element "CSUM" yields the desired output RF voltage:

$$V_{out} = V(t)\cos \omega t \cos \phi(t) - V(t)\sin \omega t \sin \phi(t) = V(t)\cos[\omega t + \phi(t)]$$
 (4)

Note that this modeling supports separately delaying $(\tau_1 \text{ and } \tau_2)$ of the



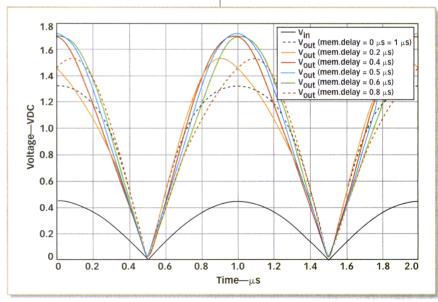
4. This comparison shows the good fit between the measured and simulated NPR responses versus the total input power for the module "MAR 3."

memory effects, influencing the amplitude and phase of the RF signal. In fact, this capability should be used sparingly since a particular memory effect generally affects amplitude and phase with the same delay, which results in: $\tau_1 = \tau_2 = \tau$.

Model Validation

To check the fitness of the previously mentioned model, known as "mem.model," three kinds of tests were performed. They consist of a comparison between simulations performed

with this model and simulations performed with the OMNISYS "GCOMP7" standard amplifier model for three different types of input signal: single tone, two tone, and multi tone. In each case, the working frequency is approximately 410 MHz and the delay τ is assumed to be equal to zero in the "mem.model." The DUT in these tests is the amplifier module "MAR3" from Mini-Circuits Laboratories, Inc. (Brooklyn NY), already used in ref. 5. Its AM/AM and AM/PM characteristics are drawn from measurements performed with an HP8753D VNA. The computing pro-



5. This is the signal envelope obtained under two-tone excitation with the memory delay τ varying from 0 to 1 μs for the module "MAR 3."

<u>muRata</u>

Innovator in Electronics

MURATA's RF and wireless innovations open the door to design freedom

Murata PN: MM8430-2600

Description: RF Switch
Connector. One of the most exciting microwave products to come along in years. This low cost test switch has virtually universal RF and microwave design appeal. It solves many design and production test problems at a low cost. Applicable to all RF applications under 3GHz (3000MHz). Test probes: Works with Lab test probe MXGM76RL1000 and mass production test probe MM126030. Reel size/Stock quantity: 1000 pcs. I reel. Order PN: MM8430-2600TB I

Murata PN:

LFSN25N19C2450B New Global PN: LFB322G45SN1A504

Description: 2450MHz Band Pass Filter, Miniature (3.3 x 2.5mm) ultra low cost Ceramic LC Chip type BPF. This low cost BPF makes an ideal interstage filter. Small enough and low cost enough to be used in several positions on the same board! Reel size/Stock quantity: 2000 pcs. I reel. Order PN: LFSN25N19C2450B

Murata PN: MOE920-2450

Description: 2450MHz miniature (7.8 x 6mm) surface mount VCO. For use in all 2.4GHz Wireless LAN applications. Low cost. Reel size/Stock quantity: 3000 pcs. I reel. Order PN: MQE920-2450-T7

Murata PN: DFC21R57P002HHA

New Global PN: DFCB2 IG57LDJAB **Description:** 1.57GHz Band Pass Filter (BPF) for GPS applications. Ceramic Monoblock miniature low cost surface mount. Used as the primary RF filter by the USA's leading manufacturers of commercial GPS receivers, this filter has performance and low cost in a standard miniature package. Ceramic BPFs like this form the backbone of Murata's. Microwave product line. Since 1950, ceramic electronic components have been Murata's key focus. Reel size/Stock quantity: 2000 pcs. 1 reel. Order PN: DFC21R57P002HHA-TA2120



Enter No. 237 at www.mwrf.com

With advanced e-commerce supply chain solutions, state-of-the-art

design centers, technical support teams of qualified engineers all around the world and a partner like Murata, the experts at

Future Electronics give you the freedom to go further.



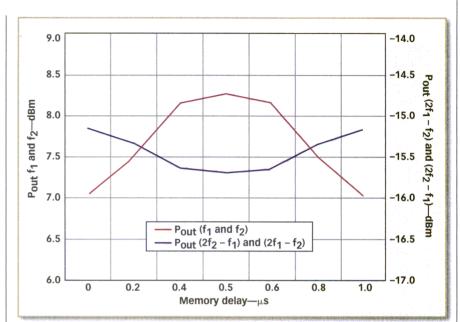
DESIGN

cedure used for all the simulations is the Fast Fourier transform (FFT).

The single-tone test led to very good agreement between the models and the measurements. Indeed, as shown in **Fig. 2**, AM/AM and AM/PM results obtained from "GCOMP7" simulations, "mem. model" simulations, and vector-network-analyzer (VNA) measurements are quasi-identical.

The two-tone test was also very satisfactory, as demonstrated in **Fig. 3** by the fundamental-, third-, and fifth-order power responses resulting from the two models. Slight discrepancies became perceptible only for the fifth-order response.

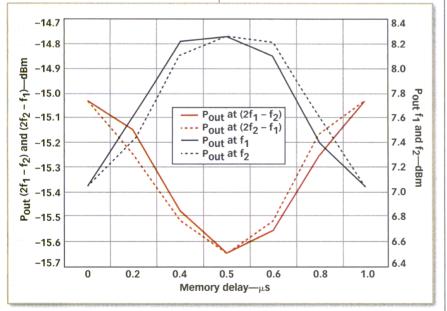
For the multi-tone test, an NPR spectrum excitation was chosen. It consisted of a 10-MHz-wide white-noise band with a 1-MHz-wide, 50-dB-deep notch centered at 410 MHz. The test was first performed through real measurements with a practical setup based on an avalanche-diode noise source similar to that described in ref. 5, but with filtering centered to 410 MHz. Then the simulation was performed with the "GCOMP7" model and with the "mem.model" using the simulation setup of ref. 5 after appropriate modifications of the filtering band and the



6. This figure shows the two-tone output-power spectrum versus the memory delay τ with only AM/AM distortion for MAR3 as DUT. $P_{in\ total}$ = 0 dBm, f1 = 409 MHz, f2 = 410 MHz.

multi-tone "RFCOMB" source. Remember that this test, to be similar to bandpass Gaussian white noise, consists of a large number of equal-amplitude, equally spaced carriers having independent, random phases. For the "GCOMP7" model, this number is 10,000, but is limited to 600 for "mem.model" due to its higher com-

plexity. Consequently, it required more computer random-access memory (RAM) [HP 9000C200]. Despite the substantial differences between the operating conditions of the measurements and the two simulations, NPR results obtained in the three cases were all in good agreement. As shown in Fig. 4, discrepancies between these results are within a margin of a few decibels on the major part of the input-power range. So the NPR test, as well as the single-tone and two-tone tests, show that the developed "mem.model" is fully valid. Therefore, it is now reasonable to make use of its potential for delaying amplitude and phase distortions and to apply it to the analysis of memory effects in two cases of great interest: the two-tone excitation and the NPR excitation.

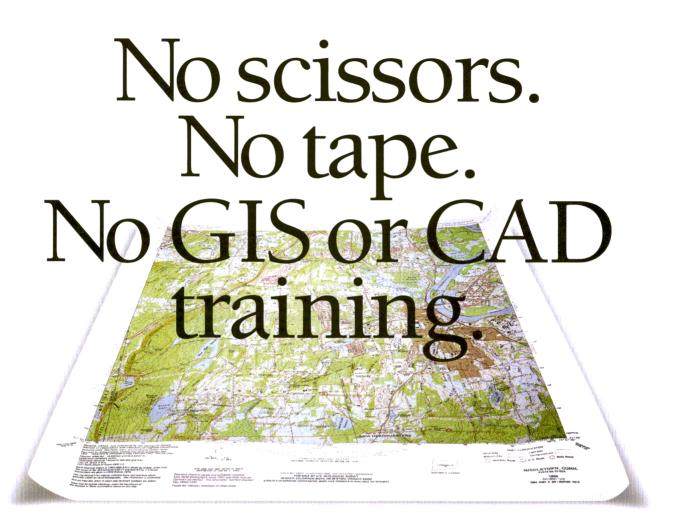


7. This figure shows the two-tone output-power spectrum versus the memory delay τ with AM/AM and AM/PM distortions for "MAR3" as DUT. P in total = 0 dBm, f1 = 409 MHz, f2 = 410 MHz.

Two-Tone Excitation

In this study, the "mem.model" is applied to the "MAR3" module and the input is driven by the "RFCOMB" source with two equal-amplitude carriers at 409 and 410 MHz. The computing procedure is still the FFT.

The first aspect to be examined lies in modifications to the signal envelope caused by memory effects. This is shown



Now, without fuss or special know-how, you can produce customized paper "topos" – computer quick. For pennies!

With Maptech's Terrain Navigator software series, it's a snap.

(If you know Windows®, you're already an expert!)

Simply install our digital versions of USGS topos in your computer. Each Super Region CD includes over 4,000 sharp, high-quality maps. Access the ones you want,

and automatically stitch together adjacent maps to cover any size project.

Next, edit your topos, adding notations and drawings. Hook up a handheld GPS to input field measurements. Then use our simple tools to create profiles and 3-D renderings.

Finally, copy your maps into MS Word® or PowerPoint® for reports or presentations, print them on any office printer, or email them to your client.

The cost? Not \$4 to \$7 like a paper USGS topo, but under 4¢ per map! For a product "tour" see our website. © 2001 Maptech, Inc.



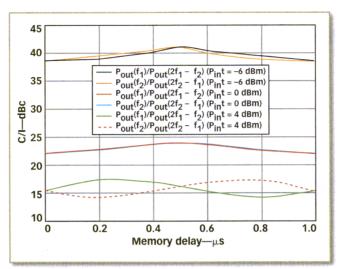
The leader in digital mapping

DESIGN

in Fig. 5, in the case where the total input power is 0 dBm. Without any memory effect that is, with $\tau = 0$ —the output voltage Vour is clearly affected by a hard compression which, from Fig. 3, corresponds to a power-gain compression of approximately 2.5 dB. But as τ varies from 0 to 0.5 µs, it can be seen that the Vous compression decreases progressively. At $\tau = 0.5 \mu s$, which is half the beat period between 409 and 410 MHz, Vout is almost exempt from compression and the corresponding power-gain value is very close to that of the linear zone in Fig. 3. For τ varying from 0.5 to 1.0 µs, an inverse

evolution can be seen and $\tau=1$ µs leads, as expected, to a situation identical to that of $\tau=0$. This example clearly shows how the presence of memory effects can completely confuse the understanding of the familiar two-tone test. It must be pointed out that only the AM/AM distortion is involved in these envelope modifications. AM/PM distortion plays no role. This is supported by the fact that, in the previous examples, the envelope shape has exactly the same appearance at the final output and at the "VGAIN2" output of the "mem.model."

The second aspect to be considered deals with spectrum modifications resulting from memory effects. Contrary to the case of the signal envelope, AM/AM and AM/PM distortions are involved in these spectrum modifications. Nevertheless, the AM/AM distortion still has a major contribution. This is illustrated in Fig. 6, which presents the variations of the fundamental and third-order spectrum components versus the memory delay τ at "VGAIN2" output—that is, with only the AM/AM contribution. An important piece of information that is provided in this figure lies in the symmetry of the spectrum with respect to the center frequency, and the symmetry of the spectrum variations with respect to the τ value 0.5 μs. Curiously, this symme-



8. This figure shows the two-tone C/I ratio versus the memory delay τ with AM/AM and AM/PM distortions for MAR3 as DUT. $P_{in\ total}=-6$ dBm, 0 dBm, and +4 dBm, f1 = 409 MHz, f2 = 410 MHz.

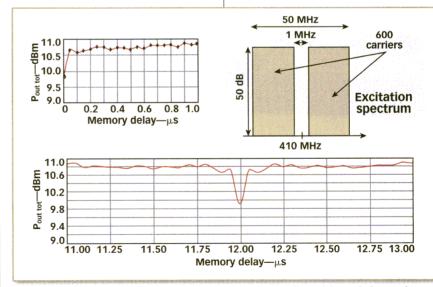
try is somewhat disturbed with the introduction of the AM/PM distortion contribution, as shown in **Fig. 7**, which provides the complete spectrum at the final output of the "mem.model." Comparing this figure with Fig. 6 makes it clear that the only contribution of the AM/PM distortion is the addition of a slight asymmetry to the spectrum at a particular value of the delay τ and a slight asymmetry of the variations of this spectrum versus τ , except for the particular values 0, 0.5, 1.0 μ s, and their multiples.

To conclude these investigations, it would be of great interest to see to what extent carrier/intermodulation (C/I) measurements can be exploited in the presence of memory effects. Figure 8 reveals the answer to this question. It shows three examples of C/I variations versus the delay τ obtained at the final output of the "mem.model." They correspond to input-power levels of -6, 0, and +4 dBm. Note that many variations of the ratio C/I are possible, depending on the power level and the value of the delay τ . Deviations, with respect to the case where $\tau = 0$ (no memory effect), can reach approxi-

mately 2 dB at worst, which is far from negligible.

NPR Excitation

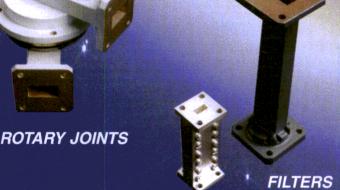
In this study, the "mem.model" is always applied to the "MAR3" module but its input is now driven by an NPR excitation. This is provided by the "RFCOMB" source and has a 50-MHz bandwidth centered around 410 MHz and is filled with 600 carriers having Continued on page 207



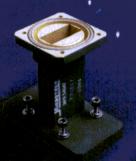
9. This figure deals with an NPR simulation on a "MAR3" module and shows the variations of the total output power versus the memory delay τ , with the previously discussed excitation spectrum and 0-dBm total input power.

The Future Is Now! The Leader in Microwave Components









RIGID WAVEGUIDE SPECIAL



FLEXIBLE WAVEGUIDE **ASSEMBLIES**





WAVEGUIDE TO COAX ADAPTERS

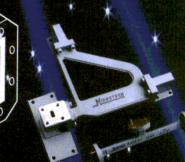




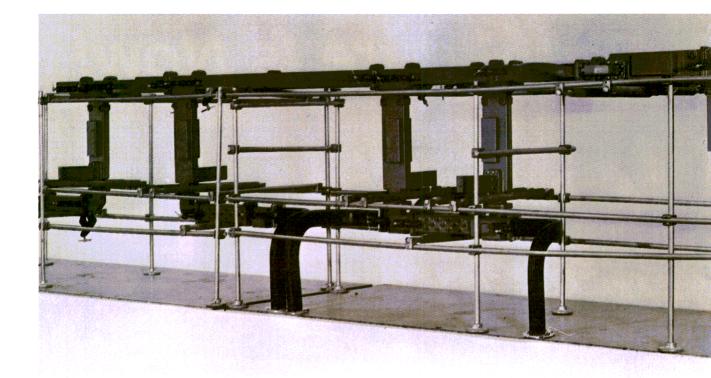
1425 Highland Avenue Cheshire, CT 06410 USA 203-272-3234 • Fax 203-271-0352

E-Mail: sales@microtech-inc.com Visit us at: http://www.microtech-inc.com

Enter No. 259 at www.mwrf.com



DIPLEXERS



The





smaller



we get,



For over 50 years, Microwave Development Laboratories has stayed ahead of the industry, anticipating new technologies and responding with imaginative and innovative microwave coupling solutions.

It all started with the Riblet Coupler back in 1948. From there, we designed a thin wall monopulse comparator for the Lunar Excursion Module in the 1960s. The 1970s saw us developing waveguide feed and monopulse networks for F-14 and F-15 aircraft. As we moved into the 1980s, we introduced internally milled technology to reduce the size and weight, and improve the performance, of our products for the F-18 and B-1 radar systems.

Today, as designs demand even higher frequencies and smaller, more precise waveguides for Apache helicopters and satellite communications, MDL's computer design technology keeps us out front. That's what makes us the leader. You could say the smaller we get, the bigger we become.

the bigger we become.







With over 35 years experience designing and manufacturing microwave components, Lorch Microwave provides filtering solutions to the commercial market

- from base station to microwave radio links
- from less than 1MHz to 40GHz
- from high volume to small custom runs

Diverse engineering and manufacturing capabilities allow Lorch Microwave to quickly respond to customer needs and provide custom tailored solutions, all with trademark service and satisfaction.



1725 North Salisbury Blvd. · PO Box 2828 Salisbury, Maryland 21802

Tel: 800.780.2169 · Fax: 410.860.1949

E-mail: lorchsales@lorch.com Web: http://www.lorch.com

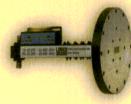
Enter No. 248 at www.mwrf.com

Commercial,
High Performance
& Custom-Designe
Products



WIRELESS FILTERS AND DUPLEXERS

- cellular and PCS base stations filters, duplexers and assemblies
- delay assemblies for feed forward amplifier application



WAVEGUIDE DIPLEXERS

- point-to-point microwave radio links to 40 GHz
- terrestrial communication networks



CERAMIC FILTERS

- filters and diplexers to 5.8 €
- specialized cellular and PCS applications
- diplexers and finite pole placed topologies available

OTHER COMMERCIAL AN MILITARY APPLICATIONS

- cavity filters
- discrete filters
- tunable filters
- other signal processing products



Construct An FMCW Front End For Anticollision Radar

This novel front end uses a GaAs MESFET VCO for high output power and wide tuning range, as well as a balanced resistive mixer for low IM and 1/f noise.

nticollision radar plays one of the most important roles in developing intelligent traffic systems (ITS). In this application, the distance between moving vehicles and other obstacles must be measured accurately, so frequency-modulation continuous-wave (FMCW) radar is usually employed. This article describes the design and performance of a low-cost, X-band, integrated front end that can

be used in an FMCW anticollision radar system. Its main components are a voltage-controlled oscillator (VCO), a buffer, a circulator, and a mixer. The system operates at 9 GHz and has a linear tuning range of more than 300

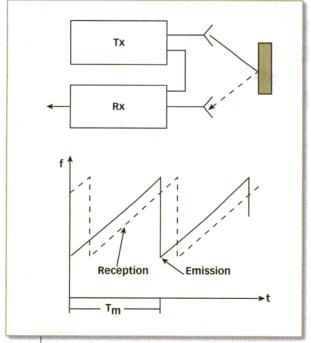
MHz. The VCO employs a galliumarsenide (GaAs), metal-semiconductor field-effect transistor (MESFET) and

> strikes a good balance between high output power and wide tuning range. A GaAs FET balanced resistive mixer provides low intermodulation (IM) and low 1/f noise even at very low intermediate frequencies (IFs) [down to tens of Hertz].

Basically, the frequency of an emitted signal varies according to the known time function $\phi(t)$ (Fig.1). Ignoring the Doppler effect, any additional modulation by the target or the amplitude difference, the received signal has a time delay $T_d = 2d/c$ when compared with the emitted signal. By mixing the emitted and received signal, this small time difference is replaced by a frequency difference f_b. Compensation for the inevitable Doppler frequency shift f_d is described in the ensuing text.

XIAOBO YANG, CHUNGUANG JING, AND TAO YANG

Microwave Center, University of Electronic Science & Technology China (UESTC), Chengdu Sichuang, P.R. China 610054; 86-28-3202480 FAX: 86-28-3202538, e-mail: xbyang@uestc.edu.cn



1. This figure shows the principle of distance measurement.

The distance between the vehicles can be deduced from the following relationship:

$$|f_b| = f_d + KT_d \tag{1}$$

when:

$$f_d = 0, |f_b| = KT_d = \frac{2\Delta f d}{T_{cc}C}$$
 (2)

then:

$$d = \frac{cT_m f_b}{2\Delta f} \tag{3}$$

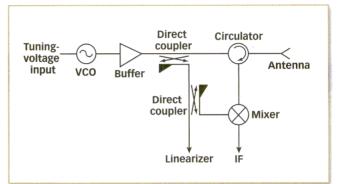
 f_d = the Doppler frequency shift, f_b = the frequency difference,

 T_d = the time delay, and

 $K = \Delta f / T_m =$ the frequency-modulation (FM) slope.

Circuit Design

The integrated transceiver presented here has a single antenna and a circulator to isolate the emitted and received



2. This block diagram shows the front end designed for use in an anticollision radar system.

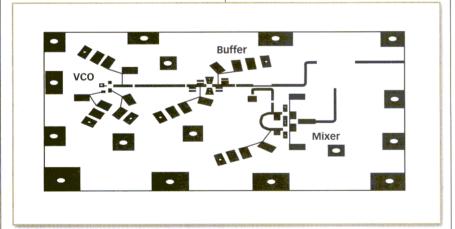
signals. It includes a varactor-tuned VCO, a buffer amplifier, a single balanced resistive mixer, as well as a circulator (Fig. 2).

The varactor-tuned VCO contains a GaAs FET common-source capacitivefeedback oscillator that is tuned by changing the varactor's capacitance. An NE76084 FET was chosen as the active device for this particular design since it has sufficient high-frequency power output. The specification for the oscillator involves a single-polarity bias supply, so a self-bias circuit was used

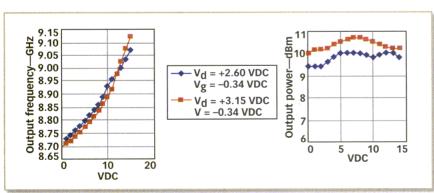
to supply the FET's gate voltage.

The VCO output signal must be made insensitive to load variations, otherwise the output frequency and power would vary with the load and the radar's normal operation would be affected. A good solution to this problem is adding a GaAs FET small-signal amplifier as a buffer at the VCO's output terminal. It provides high isolation (-47 dB) and, as a bonus, a small amount of gain (approximately 4 dB). The most important factor to consider is the absolute stability of the buffer. So, unlike the VCO's self-bias circuit, a double bias is used to supply the buffer FET with suitable voltages and currents.

To maintain excellent performance, FMCW radar requires that the receiver (Rx) has very low IM and noise. However, the Schottky-barrier diode that is used in most microwave mixers cannot provide these required characteristics because it is a strongly nonlinear device. This system that is described here employs a new type of resistive mixer (linear mixer) that uses the timevarying channel resistance of a GaAs MESFET to achieve frequency mixing. Due to the very weak nonlinearity of this resistance when no DC bias is applied to the FET's drain, the mixer generates very low IM as well as lower noise when compared with a diode mixer having the same conversion loss. Two FETs with well-matched I/V characteristics are chosen for the single balanced mixer. The FET gates are driven with a 180-deg. local-oscillator (LO) phase difference that is achieved by a loop of transmission line, which causes the channel resistance to show a

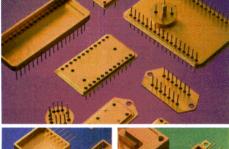


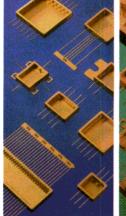
3. This photograph shows the front end's PCB layout.

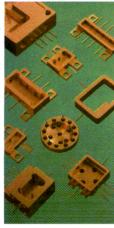


4. These graphs show the output characteristics of the front end.











ADVANCED TECHNOLOGY GROUP INC.

ISO-9002 CERTIFIED

THE HIGHEST QUALITY HYBRID AND MICROELECTRONIC PACKAGES AT COMPETITIVE PRICES

ATG offers fast delivery, competitive pricing and consistently high quality. Our "Design Adaptation Formula" gives us the ability to work quickly and efficiently to build the most cost effective part to meet *your* specifications. Our streamlined manufacturing and highly motivated people allow us to keep costs down and quality high by the continual monitoring of parts through in-coming, in-process and final inspections.

ATG is your dedicated source for:

Hybrid Packages • Power Packages

- Microwave Packages
 Fiber Optic Packages
- Dual In-line Headers Saw Packages
- Unibody Packages TO-46, TO-5, TO-8 Headers

CALL US TO DISCUSS YOUR REQUIREMENTS.

www.advtechgr.com

time-varying characteristic. The drains are in parallel at the RF and are fed through a quarter-wave transformer that matches the 50-Ω RF input to the 25- Ω input impedance of the parallel channels. The IF currents in the channels are 180-deg. out of phase. Therefore, they are combined using a 180-deg. combiner in the form of a super-

low-noise operation amplifier. The mixer demonstrates superior performance, even at very low IF (down to tens of Hertz).

Simulation And Fabrication

Each functional circuit within the integrated front end, as well as the entire

Each functional circuit within the front end, as well as the entire front end as a whole, were designed and simulated in a computer using CAD software.

front end as a whole, were designed and simulated in a computer by using advanced HP EEsof RF CAD software until the design targets were met.

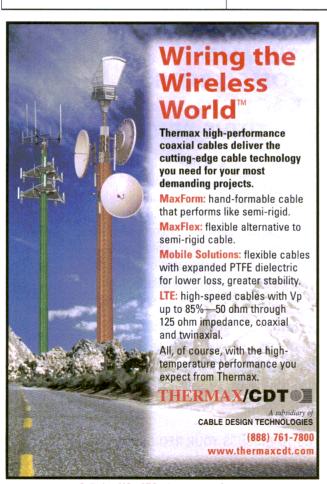
The circuit, including the circulator and coupler, as well as the main functional units mentioned earlier, was fabricated on a substrate (having $\epsilon_r = 2.65$ and H = 0.5 mm) and housed

in an aluminum (Al) box along with DC power-supply circuits and an IF amplifier. The entire package size measures 60 \times 30 \times 20 mm. All of the active devices that are used in this front end are GaAs MESFETs (NE76084) to ensure consistent operation. Figure 3 shows the printed-circuit-board (PCB) layout of the front end. Figure 4 shows the front end's output frequency and power versus tuning voltage.

The front end of FMCW anticollision radar described in this paper operates across the frequency range of 8.8 to 9.1 GHz. Its FM linearity is better than 3 percent due to the constant ν varactor diode used as the VCO's tuning element (ν is the index of the rate of the varactor's capacity to voltage). The output power of the transceiver is +10.3dBm (± 0.3) since it provides 10-dBm LO power to the mixer. The conversion loss of the resistive mixer is 8 dB at 9 GHz, MRF

FOR FURTHER READING

- 1. "VORAD Collision Warning Radar," IEEE International Radar
- 2 "GaAs Monolithic Circuit for EMCW Radar " IEEE Microwave and Millimeter-wave Monolithic Circuits Symposium, 1988.
- 3. "Noise Calculations and Experimental Results of Varactor Tunable Oscillator with Significantly Reduced Phase Noise, IEEE MTT-43, No. 2, 1995.
- 4. "A GaAs MESFET Balanced Mixer with Very Low Intermodulation," IEEE MTT-S Digest, 1987
- 5. Stephen A. Maas, The RF and Microwave Circuits Design Cookbook, Artech House, Boston, 1998



Enter NO. 453 at www.mwrf.com

BASE STATION FILTERS AMPS, DCS, GSM, PCS, UMTS

BANDPASS



MULTIPLEXERS

HIGHPASS



DIPLEXERS



BANDSTOP VOLTAGE TUNED

LF, RF and MW Filters, 100 KHz to 18GHz designed to your specifications.

E-Mail: sales@ana-tech.com

Web site: www.ana-tech.com

Please contact us for our full catalog of capabilities. Let us look at your current filters rquirements our experienced force will direct you to the best solution.



ECTRONICS

70 Outwater Lane, Garfield, NJ 07026 Tel: 973-772-4242 Fax: 973-772-4646

You need to design communication systems with speed and flexibility.

succeed with Symphony

Encode, multiplex, modulate, upconvert, filter, amplify, transmit, receive, reverse and recover. Symphony's end-to-end communication system design suite lets you simulate your baseband, transceiver and channel with speed and flexibility.

Make key architectural decisions and component specifications at any stage of your development. Optimize performance such as noise figure, BER,

ACPR, or SINAD with a comprehensive library of RF and

DSP behavioral models, along with

frequency, discrete-time

domain and mixed mode analyses.

Symphony provides the speed and power for simulating systems such as GSM, CDMA and 3G. As a part of

Ansoft's Serenade Design

Environment, Symphony provides a seamless link to circuit simulation, 3D and planar electromagnetics in addition to Matlab co-simulation.

Design with speed and flexibility.

Discover the difference Symphony makes in your system development and component specification.

For your free evaluation copy of Symphony, or any of the tools in Ansoft's Serenade Design Environment call 412-261-3200 or send e-mail to info@ansoft.com.

Rapid Deployment



high performance EDA

www.ansoft.com

Introduction To 3G Mobile Communications

JUHA KORHONEN, Editor

THIRD-GENERATION (3G) mobile communications systems represent the future of cellular technology. Ushering in an era of digital multimedia handsets with high data-transmission rates, 3G will take the end user beyond the realm of basic

cellular services and into the brave new world of wireless communications.

Juha Korhonen's Introduction To 3G Mobile Communications provides the reader with an easy-to-understand primer on 3G-technology principles, concepts, and applications. The first chapter covers the history of mobile cellular systems from first generation to the present. The overview examines proposals for 3G Standard, including WCDMA, Advanced TDMA, OFDM, and IMT-2000, as well as addressing 3GPP and 3GPP2.

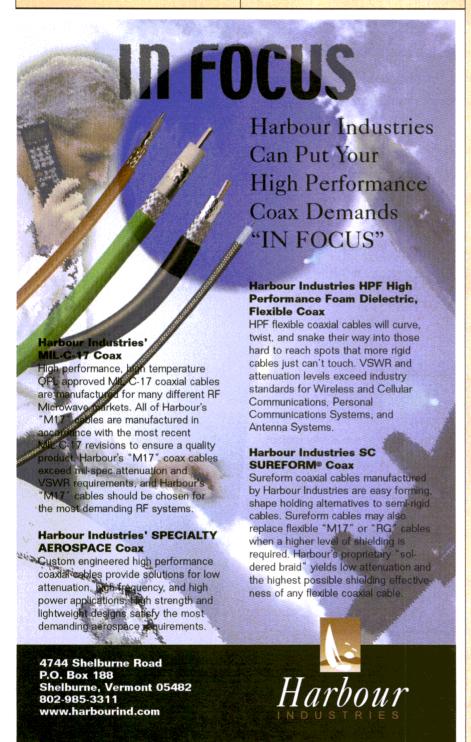
Chapter 2 highlights principles of CDMA, radio-channel access schemes, spread spectrum, power control, and TDD. Chapter 3 examines the physical layer of WCDMA air interface. Chapter 4 concentrates on modulation techniques and spread spectrum.

Chapter 5 features orthogonal, pseudo-noise, and synchronization codes, as well as auto-correlation, cross-correlation, and intercell interference. Chapter 6 examines channel-coding processes and theories, including block codes, convolutional codes, turbo codes, and channel coding in UTRAN. Chapter 7 investigates the Protocol Stack of WCDMA air interface.

Chapters 8, 9, and 10 focus on network basics, planning, and management, respectively. In these chapters, UMTS and GSM radio-access networks are analyzed, interfaces are discussed, and telecommunications-management architecture is explored.

Chapter 11 examines RRC, random-access, and radio-bearer procedures; data transmissions; and handovers. Chapter 12 introduces new concepts in the UMTS network, including location services, opportunity-driven multiple access, super and turbo chargers, and multimedia messaging services. Chapter 13 explores 3G services, including teleservices, bearer services, supplementary services, QoS classes, and service capabilities.

Chapter 14 lists examples of 3G applications, including voice, messaging, Internet access, and location-based applications. Finally, Chapter 15 offers examples of the future of 3G mobile communications. A glossary of acronyms is included. (2001, 559 pp., hardcover, ISBN: 1-58053-287-X, \$95.00.) Artech House, 685 Canton St., Norwood, MA 02062; (800) 225-9977, (781) 769-9750, FAX: (781) 769-6334, Internet: www.artechhouse.com.



What the ireless World is Coming To...

WirelessDeveloper 2001

Westin Hotel, Santa Clara, CA

THE MONEY

August 20-24, 2001

WirelessDeveloper

If you're interested

in developing tomorrow's must-have wireless applications, this is the event that you must attend in 2001.

If you're...

A Professional Developer creating applications for resale in the market.

A Corporate Developer creating applications for your company's internal use.

A Content Developer focused on presenting information services (content) to users.

You don't want to miss the largest event dedicated to wireless development.

WirelessDeveloper 2001 will:

- Provide an in-depth look into the top technologies & platforms
- Review current developer tools (SDK's, training, equipment availability)
- Demonstrate current state-of-the-art applications
- Offer hands-on coding examples Describe developer support and certification options
- Discuss application testing opportunities
- Introduce successful developers
- Explain business support options
- Teach you about VC financing and mergers & acquisition options to growing your business

You'll be able to attend the official full-day DevCons from companies like:

Compag **AT&T Wireless**

Openwave PacketVideo



LOW COST NEW HIGH PERFORMANCE **OPERATING TO 26 GHz**





DESIGNED FOR COST SENSITIVE PROGRAM

D14-SERIES

HIGH PERFORMANCE AND RELIABILITY FROM

DUCOMM TECHNOLOGIES, INC.

A SUBSIDIARY OF DUCOMMUN INCORPORATED

23301 Wilmington Avenue, Carson, CA 90745-6240

Phone 310-513-7200 • Fax 310-513-7298

e-mail: sales@ductech.com

www.ductech.com

SPECIFICATIONS	DC-18	18-26 GHz		
V.S.W.R. (max)	1.2:1	1.4:1		
Insertion loss (max)	.2 dB	.4 dB		
Isolation (min)	70 dB	60 dB		
RF Power CW	50 W	20 W		
Switching Time	15 msec max			
Operating Mode	Failsafe or Latching			
Environmental	Temp: -35°C to 85°C			
	Humidity: 95% Rh			

COMMERCIAL SWITCHES • CUSTOM FILTERS • SPACE QUALIFIED SWITCH

RF Microwave Product Line History

- UZ	1969-1978
D oto oto /UZ	1070 1004
Dynatech/UZ	1978-1984
Dynatech Microwave Technologies	1984-1995
Jay-EI/DMT	1995-1998
Ducommun Technologies, Inc.	1998-
A Subsidiary of Ducommun Incorporated	1849-



Same Prestigious Company • Same Renowned Quality • Same Responsive Service

RF/Microwave Product Line

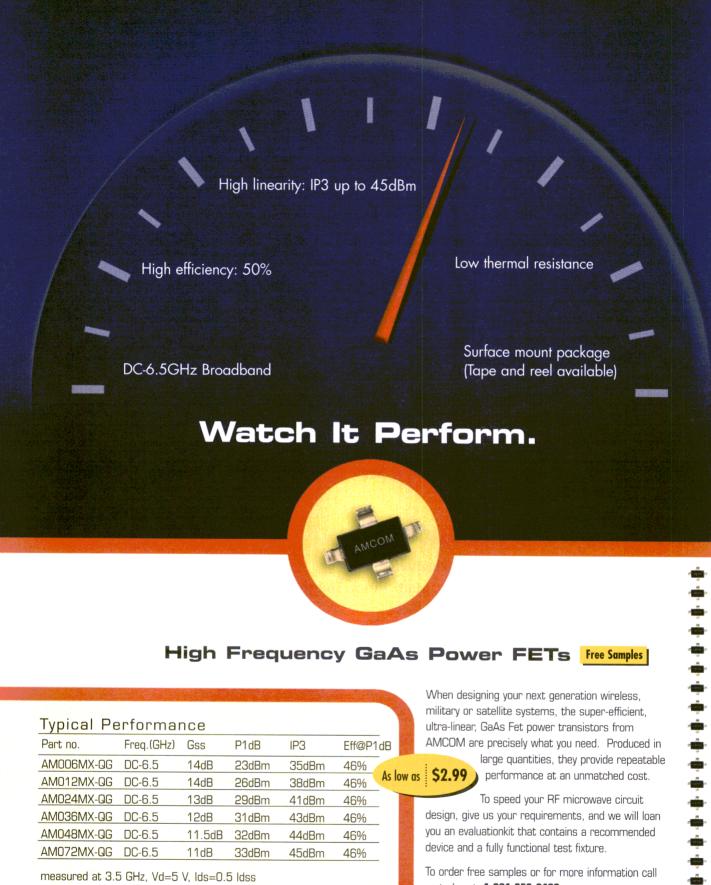
- Wireless and Hi-Rel Applications
- Single Pole Double Throw, Multi Throw, Transfer, T-Switch and ATE Switches
- TCAS Coaxial Antenna Switches
- Military Notch Filter and Switch Filter

Illuminated Switch Panel Product Line

- Engineered Lighting, Panel and Switch Solutions
- COTS and Military Components
- Military NIVS Compatible
- Primary Displays and Control Display Unit Bezel and Front End Assemblies
- Cockpit Switches
- Switch Assemblies/Annunciator Panel Assemblies

Electromagnetic Product Line

- Severe Environments Motion Control Specialists
- BDC, DC + Stepper Motors/Actuators
- Motor Options Include Brakes, Planetary + Harmonic Drive Gears
- High Accuracy Resolvers



High Frequency GaAs Power FETs Free Samples

Typical Performance

.,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	,, , , , , , , , ,	100					artir a milicar
Part no.	Freq.(GHz)	Gss	P1dB	IP3	Eff@P	1dB	AMCOM a
AMOO6MX-QG	DC-6.5	14dB	23dBm	35dBm	46%	450	C0.00
AM012MX-QG	DC-6.5	14dB	26dBm	38dBm	46%	As low as	\$2.99
AM024MX-QG	DC-6.5	13dB	29dBm	41dBm	46%		
AM036MX-QG	DC-6.5	12dB	31dBm	43dBm	46%		design, giv
AM048MX-QG	DC-6.5	11.5dB	32dBm	44dBm	46%		you an eva
AM072MX-QG	DC-6.5	11dB	33dBm	45dBm	46%		device and

measured at 3.5 GHz, Vd=5 V, Ids=0.5 Idss

When designing your next generation wireless, military or satellite systems, the super-efficient. ultra-linear, GaAs Fet power transistors from AMCOM are precisely what you need. Produced in

> large quantities, they provide repeatable performance at an unmatched cost.

To speed your RF microwave circuit design, give us your requirements, and we will loan you an evaluationkit that contains a recommended device and a fully functional test fixture.

To order free samples or for more information call us today at: 1-301-353-8400.

22300 Comsat Drive, Clarksburg, MD 20871 tel: 301-353-8400 • fax: 301-353-8401

email: info@amcomusa.com • www.amcomusa.com





CMOS SOS Switches Offer Useful Features, High Integration

Understanding the basic theory and characteristics underlying CMOS SOS switch technology opens the door to numerous RF and microwave applications.

witching RF and microwave signals is a fundamental function in all radio applications. Accordingly, there are a great variety of switch products and forms, from the basic single pole, single throw (SPST) to a large crosspoint matrix. This article explains basic RF semiconductor switch functionality and reviews switch parameters and limitations. It examines the basic theory of an RF switch and the

trade-offs between power handling, insertion loss, and isolation.

Although there are diode-type switches, the focus here is on complementary-metal-oxide-semiconductor (CMOS) metal-oxide-semiconductor field-effect-transistor (MOSFET) types, the main technology for wireless applications. Switches can also be classified as reflective and absorptive, but this article addresses only the reflective type.

Most high-frequency switches use gallium-arsenide (GaAs) technology.

Peregrine Semiconductor's Ultra-Thin-Silicon (UTSi) Technology enables the realization of quality RF switch-

es using dielectric isolation between UTSi MOSFETs that are fabricated in CMOS. UTSi is a Si-CMOS process that is fabricated on a sapphire insulator, known as Si-on-sapphire (SOS). This enables the manufacture of simple to highly integrated RF switches with modest-to-high-power capability (+10 to +37 dBm). Stacking devices allows UTSi RF switches to handle any practical power level. The complete isolation afforded by UTSi makes this switch impossible to fabricate in convention-

al Si-CMOS, bipolar CMOS (BiCMOS), and Si-germanium (SiGe) technologies. UTSi switches can be further integrated with complex digital CMOS control and other components in order to realize excellent on-chip isolation and insertion loss over a broad range of frequencies and supply voltages.

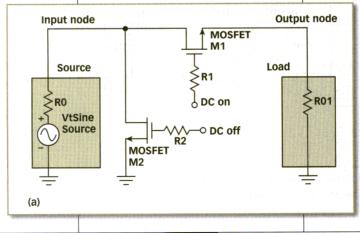
Simple mathematical expressions can be used to describe the operation of MOS-

MARK L. BURGENER

Senior Staff Scientist

Peregrine Semiconductor Corp., 6175 Nancy Ridge Dr., San Diego, CA 92121; (858) 455-0660, FAX: (858) 455-0770.

1a. The basic MOSFET SPST switch consists of two devices (M1 and M2) that either pass or block an RF input signal depending on the bias voltages that control M1 and M2.



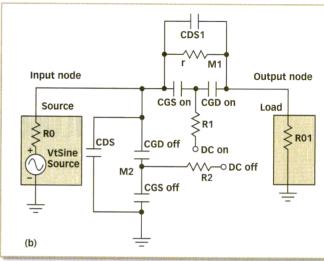
FET switches. An SPST switch schematic is shown in **Fig. 1a**. An RF signal presented at the input node is either blocked from or passed through to the output node, depending on the DC bias of MOSFETs M1 and M2. Actual values of DC bias depend on the polarity and threshold of the MOSFETs. Resistor R0 isolates the bias from the AC signal and is essential for optimal switch action. The on- and off-states of the switch are explained using **Figs. 1b** and c.

Figure 1b illustrates the equivalent small-signal values of MOSFETs M1 and M2 when the RF switch is on. M1 is primarily resistive, with a through coupling of r, while M2 is primarily capacitive, with coupling to ground through capacitors CGS off, CGD off, and CDS. The importance of the gate resistor R1 is clearly illustrated. If R1 is too small, the gate node of M1 would be held at the DC bias voltage, resulting in negative feedback via capacitors CGS on and CGD on. This feedback has the effect of increasing r, resulting in larger Ohmic loss. A small value of R2 prevents the voltage dividing action of M2 capacitors CGS off and CGD off, reducing the 1-dB compression point up to 6 dB (as explained later). R, therefore, needs to be large enough so that RF signals feeding onto the gate node are AC isolated from the DC bias. That is:

$$f_{min} = 5 / \pi R C_{offp} \sqrt{2}$$
 (1)

where:

R = the series resistor of the gate node (Fig. **1b),** and $f_{min} =$ the minimum frequency at which the switch can operate. Since R is much larger than 50 Ω , C_{offp} for M2 is the parallel value of CGS off and CGD off (the offcapacitance was chosen since it results in the largest f_{min}). It is important to real-



1b. The equivalent small-signal parameters of M1 and M2 in Fig. 1a show the dominant characteristics of each device. M1 is primarily resistive while M2 is capacitive.

ize that Eq. 1 is based on simple resistive-capacitive (RC) calculations and has no lower limit due to semiconductor material limitations. By contrast, GaAs switches may have switching speed limitations as a result of slow states that may be present in the GaAs.

The insertion loss of the switch is the difference between the maximum available power at the input and the power delivered to the output. At low frequencies, most of the power is lost across r, resulting in the following expression for insertion loss:

$$IL = 10LOG_{10} \left[\left(1 + \frac{r}{2R0} \right)^2 + \left(\frac{\omega C_{offs}(R0 + r)}{2} \right)^2 \right] (in \, dB) \quad (2a)$$

where:

R0 = the impedance of the source and load (50 Ω),

r = the resistance of M1 when the switch is on, and

 C_{offs} = the series value of CGS off and CGD off in parallel with CDS of M2.

Equation 2a becomes invalid when the capacitive reactance of M2 becomes comparable to r. However, Eq. 2a can serve as a guide in estimating insertion loss. Usually, r is much less than R0 in real switches. Equation 2a is simplified as follows:

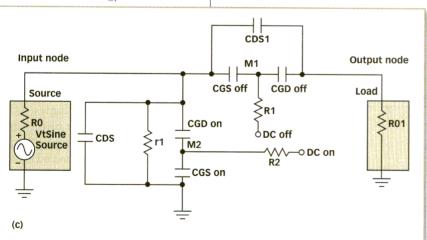
$$IL \approx \frac{10r}{R0ln(10)} \approx$$

$$0.087r \qquad (2b)$$

within 5 percent at low frequencies ω \times C \times R0 \leq 0.1 for r <10 Ω and R0 = 50 Ω

Thus, at low frequencies, a 3- Ω value for r will result in approximately one-quarter-of-a-decibel insertion loss.

The small-signal equivalent circuit for the off-state of the switch in Fig. 1a is provided in Fig. 1c. For simplification, M1 and M2 are chosen identically, so



1c. In the normal off-state, M1 is turned off and M2 is turned on, thus blocking the input signal from the output node. M2 serves to increase the input-to-output isolation of the switch.

TOGETHER, TAKING OEM PERFORMANCE TO A HIGHER LEVEL.



A NEW BRAND OF RF AMPLIFIER FOR OEM.

Combining the top talent in engineering from AR and Kalmus, AR/Kalmus brings a new level of technology and field-proven integrity to the OEM marketplace, meeting the most demanding customer needs in military, communications and Industrial/Scientific/Medical applications.

No other brand offers this product range or depth, this much experience or guaranteed performance. AR/Kalmus amplifiers are all backed by best-in-the-business warranties and a worldwide support and service network.





the values of capacitance and resistance are identical to those in Fig. 1b. However, for an actual circuit design, M1 and M2 may have different sizing for overall performance optimization.

In the off state, M1 has the role of blocking the input from the output. When turned off, M1 is primarily capacitive with feedthrough of the input determined by the series/parallel values of CGD off, CGS off, and CDS. Feedthrough of the signal is undesirable and is related to the isolation of output to input when the switch is turned off. To reduce the magnitude of the feedthrough (i.e., increase the isolation), M2 comes into play.

M2 is turned on when M1 is turned off. In this condition, M2 is primarily a resistor with value r. By design, this value is much less than the characteristic impedance of the RF source, so r greatly reduces the voltage at the input of M1. When the value of r is much less than R0 and the feedthrough capacitive

reactance of M2, isolation can be easily calculated. Isolation for the offswitch is the difference between the maximum available power at the input to power at the output. The circuit analysis results in the following equation for isolation:

$$IS = -10LOG_{10}$$

$$\left[4r^2\omega^2C_{offs}^2\right] /$$

$$\left(1 + \frac{r}{R0}\right)^2 + \omega^2C_{offs}^2R0^2$$

$$\left(1 + \frac{2r}{R0}\right)$$
(3a)

For the condition r <0.1 R0, and $\omega r C_{\rm ons}$ <0.1, where:

 ω = the frequency of the RF input, R0 = the impedance of the source (50 Ω),

 C_{offs} = the feedthrough capacitance of M1 in the off condition,

r =the on resistance of M2 in the on

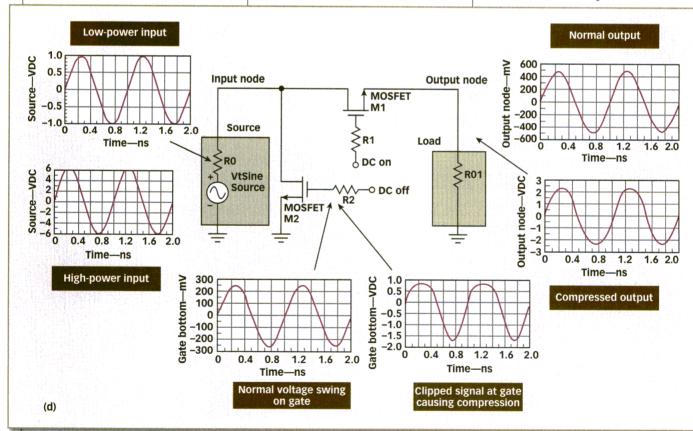
condition, and

 $C_{\rm ons}$ = the shunt capacitance of M2 in the on condition. Equation 3a is derived by assuming that the coupling to ground is primarily through r. For small values of frequencies and r, the equation for isolation can be further simplified:

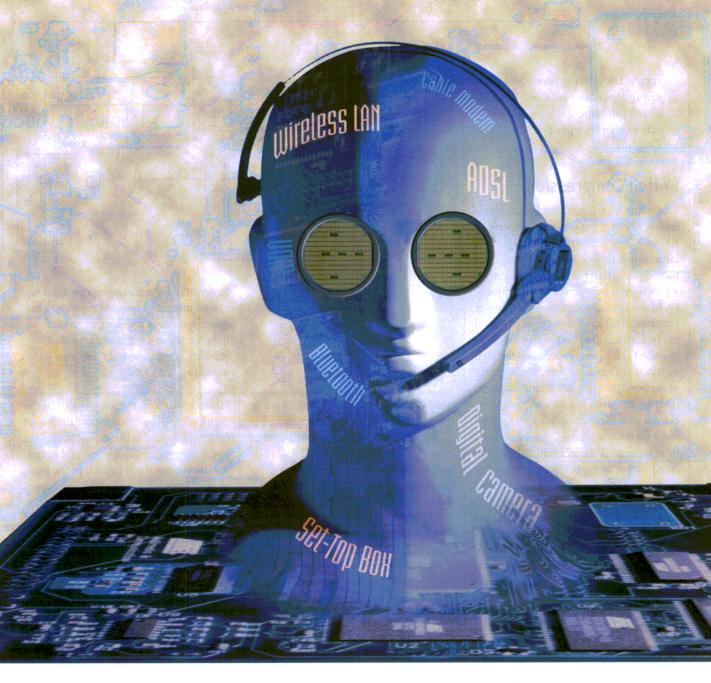
$$IS = -20LOG_{10} (2r\omega Ct) \quad (3b)$$

for the condition, r <0.1 R0, and ωrC_s <0.1 and $\omega R0C_{offs}$ <0.1

Eqs. 2b and 3b can now be used to estimate values of r and C_t if target insertion loss and isolation are known. For an insertion loss of 0.6 dB, r must be less than $7\,\Omega$ in a $50\text{-}\Omega$ system. For the same switch, a target isolation of 35 dB at 1-GHz C_{offs} must be less than 0.25 pF. Usually, the values of C_{offs} and r cannot be decoupled and both are determined by the geometry of the device. Thus, the limits of insertion loss and isolation of the switch in Fig. 1a can be determined for a particular device



1d. Various types of compression result in the circuit shown in Fig. 1a, depending on the bias voltages at the gates of M1 and M2. A compressed output is caused by the turning on of the shunt switch (M2), thereby diverting the input signal from appearing at the output node.



Making Imagination and Vision a Reality

Atmel's Multimedia and Communications group designs and delivers total solutions for many diverse markets including digital cameras, video set-top boxes, high-definition TV, wireless LANs, wireless PANs, VoIP, Dolby® Digital decoder, multi-protocol network processors and complete Bluetooth™ solutions.

Shorten your product introduction cycles by using our comprehensive reference designs (which come complete with type and regulatory approvals) plus high-quality firmware and software drivers. Our offering of logic and tailored memory solutions provide the vital components needed to build intelligent high-performance end products.

Let Atmel expand your mind with our next generation of communication system-on-chip solutions.

For more information, go to: www.atmel.com/ad/multimedia02.html

www.atmel.com

Fax-On-Demand: (800) 292-8635 (North America) • (408) 441-0732 (International)

Atmel and the Atmel logo are registered trademarks of Atmel Corporation in the United States and other countries.

Bluetooth is a trademark of Telefonaktiebolaget LM Ericsson and used under license. Dolby is a registered trademark of Dolby Laboratories Inc.

© 2001 Atmel Corporation. All rights reserved.



geometry. Usually, the product of r and $C_{\rm t}$ are independent of the MOSFET width, so fundamental isolation of the switch is also independent of MOSFET width.

Switch Compression

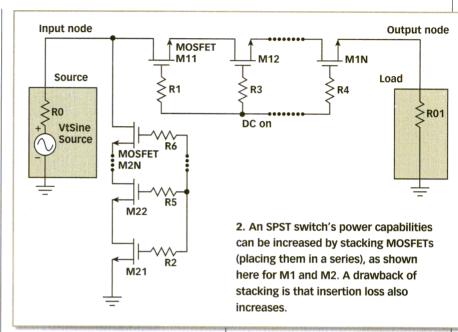
In addition to insertion loss and isolation, another important parameter of RF switches is their ability to handle large input power when the switch is turned on, so that the insertion loss is not a function of power at a fixed frequency. Many applications require that power transmitted through an on switch should not be distorted. If two tones that are closely spaced in frequency are passed through a switch at the same time, nonlinearity of the switch can produce intermodulation (IM) and create a false tone in adjacent channels. If these channels are reserved for information signals, power in these false tones must be as small as possible. A measure of the power in these false tones is known as the input third-order intercept point (IP3). Switches with large IP3 values produce little power in adjacent channels, which is important in applications such as antenna switches. IP3 is usually 17 to 20 dB larger than the largest input power a switch can handle without distortion.

An indicator of a switch's ability to handle power is known as the 1-dB compression point (P1dB). It is defined as the input power at which the insertion loss has increased by 1 dB from its low-power value.

$$IL(P1dB) - IL(P \to -\infty)$$

$$= 1.0 dB$$
 (4)

To understand what causes compression, voltage levels at various nodes are drawn for the simple switch in Fig. 1a in the on-state and presented in **Fig. 1d**. The source is represented by a sine wave with a peak-to-peak amplitude of 2 V_o . DC levels required to turn the MOSFETs on and off are V_{on} and V_{off} , respectively. A normal, uncompressed signal is shown on the output node, as well as curves showing the compression modes at the output. To understand



how compression occurs, operation of the MOSFET must be understood.

MOSFETs require a gate-to-source bias that exceeds the threshold voltage, V_t , to turn on. Likewise, the gate-to-source bias must be less than V_t for the switch to be off. V_t is positive in "type-N" MOSFETs and negative for "type-P" MOSFETs. For the switch in Fig. 1a, "type-N" MOSFETs were chosen. The source of an "type-N" MOSFET is the node with the lowest potential.

The reason for the first type of compression can now be explained using the previous concepts. If a transient voltage on M2, shown in Fig. 1c, results in turning on M2 during part of the cycle, input power will be routed to ground and lost to the output. This loss of power becomes larger for larger input powers and will cause compression. P1dB for this case can be estimated.

Assuming CGD and CGS are simi-

lar or the same in value, only half of the transient voltage change on the input node will appear at the gate node of M2. Eventually, the negative swing of the input will dip below the potential of the gate, as well as below ground (thus becoming the source). When this difference becomes V_t, M2 begins to turn on and compression begins. P1dB from this effect is:

$$PIdB_{VT} = 10LOG_{10}$$

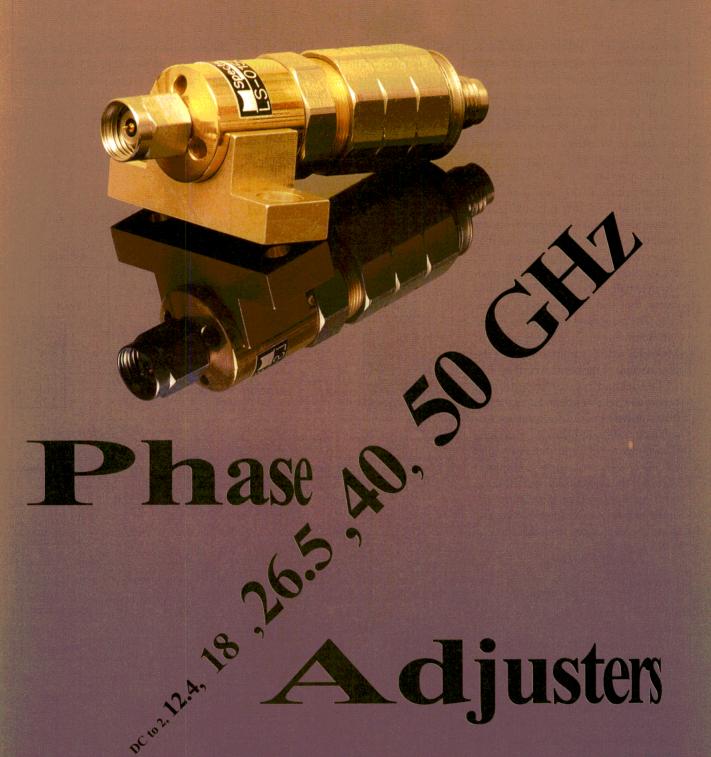
$$\left(\frac{2(V_t - V_{off})^2}{R0}\right) + 30 \ (in \ dBm) \ (5)$$

where:

 $P1dB_{VT}$ = the onset of compression for the switch in Fig. 1a.

This compression is caused by the turning on of a normally off gate in the shunt leg of the switch. Suppose V_t is approximately +0.7 VDC and $V_{\rm off}$ is cho-

Power capability versus insertion-loss trade-offs									
Number in stack	Vth (VDC)	V _{on} / V _{off}		IS at 1 GHz		IS at 2 GHz	IL at 4 GHz	IS at 4 GHz	Onset of comp. (dBm)
1	0.7	3.0/0	0.16	41	0.24	35	0.55	30	13
3	0	3.0/ -3.0	0.39	41	0.40	35	0.43	29	31
6	0	3.0/ -3.0	0.75	42	0.75	36	0.76	30	37
C _{offs} = 0 r = 1.									



Spectrum GmbH

80905 Munich, Germany P.O. Box 45 05 33

Fax:{49}-(89)-354-804-90,

Telephone: {49}-(89)-354-804-0

http/www:spectrum-et.com e-mail: specelek@CompuServe.com

sen to be 0 VDC. Substituting in Eq. 5, compression will begin at approximately +13 dBm. A negative value for V_{off} of -1 VDC will increase the compression to approximately +21 dBm. For the circuit in Fig. 1d, compression can be greatly increased by using a negative supply to turn off the devices. Note that for normal low input power, half of the source voltage is dropped across the output load. With low input power, the potential on shunt MOSFET gate never exceeds +0.7 VDC, thus ensuring that it does not turn on. At high-power input, the voltage swing on the output is much less than half of the source voltage, indicating that the compression is occurring. The compression is caused by the extreme swing in gate voltage on shunt MOSFET, which turns it on during the positive half of the input cycle (Fig. 1d).

The second type of compression occurs when the source and drain of M2 break down at excessive voltages. For submicron Si-on-insulator (SOI) devices, this voltage may be approximately only +1 VDC above the supply. Clipping occurs at the two extremes of the large transient input voltage. If the source-to-drain breakdown voltage is V_{bk}, the onset of compression from this effect is:

$$P1dBbk = 10LOG_{10}$$

$$\left(\frac{V_{bk}^{2}}{2R0}\right) + 30 \ (in \ dBm) \tag{6}$$

where:

 $V_{\rm bk}$ = the source-to-drain breakdown, and

 $P1dB_{bk}$ = the estimate of compression for a switch where the source and drain of the off leg break down at large input voltage excursions. For example, suppose the switch in Fig. 1a has the following characteristics:

$$V_{\text{off}} = -3.0 \text{ VDC},$$

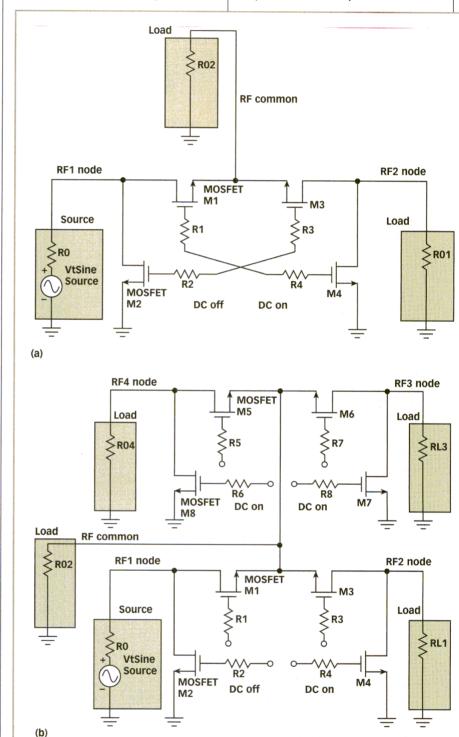
 $V_{\text{t}} = +0.7 \text{ VDC},$ and
 $V_{\text{bk}} = +4.0 \text{ VDC},$

What will cause compression and what will its value be? To answer that, Eqs. 5 and 6 are used to calculate P1dB $_{\rm vt}$ = +27 dBm and P1dB $_{\rm bk}$ = +25 dBm. Since P1dB $_{\rm bk}$ <P1dB $_{\rm vt}$ for this example, the cause of compression will be source-to-drain breakdown and compression

will be approximately +25 dBm.

Equations 5 and 6 set clear limits on the power-handling capabilities of

the switch as shown in Fig. 1a. For power levels above +22 to +25 dBm, there may be a limit set by source-to-drain



3. The basic SPST switch is the building block of more-complex switches such as the SPDT type shown here. Stacking can also be used here to increase power-handling capability (a). A more complex switch than that shown in Fig. 3a is the SP4T type that appears here. In this example, RF1 is turned on. Integrating devices of this complexity in ICs is not complex using UTSi technology (b).

114

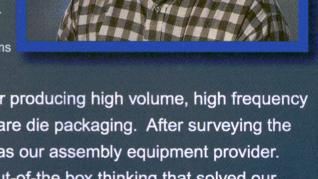
We needed an automation solution that could handle assembly and interconnect of our RF devices today and in the future. Palomar Delivered!"





Palomar Technologies 3500-II assembly for the Triton Network Systems LMDS receiver.

Joseph Kreuzpaintner Production Manager Triton Network Systems



"At Triton Network Systems", our factory for producing high volume, high frequency RF modules has the added challenge of bare die packaging. After surveying the industry, we chose Palomar Technologies as our assembly equipment provider. Palomar delivered proven software, with out-of-the box thinking that solved our technical issues and met our accelerated production schedule."

PALOMAR TECHNOLOGIES



U.S. HEADQUARTERS 2230 Oak Ridge Way Vista, CA 92083-8341 Phone: (800) 854-3467, (760) 931-3600 Fax: (760) 931-3444 www.palomartechnologies.com PALOMAR TECHNOLOGIES EUROPE Am Weichselgarten 30/B 91058 Erlangen Germany Phone: 49-9131-48009-3 Fax: 49-9131-48009-55 PALOMAR TECHNOLOGIES (S.E. ASIA) PTE LTD Block 192, Pandan Loop, Unit 07-08/09 PanTech Industrial Complex Singapore 128381 Phone: 65-779-2766 Fax: 65-779-7939 breakdown. If not, the difficulty of producing negative supplies below $-V_{\rm dd}$ (-3 VDC) demands other circuit solutions. Also, there is the very real issue of placing too much electrical-field stress across a gate oxide. If the simple switch can stand off, by +30 dBm for example, at with a negative supply of -3 VDC, the gate oxide will experience up to +8 VDC. For a 100- 1 gate oxide, this will pose a reliability problem.

Figure 2 is a SPST switch with N MOSFETs placed in series (or stacked) for the through and shunt legs. This switch has the advantage of increased power-handling capability, which is traded off against increased insertion loss. Layout of stacked devices is simple and does not require any contacts at the diffusion connection of the MOSFETs, thus device-area penalty is moderate. Each gate has its own resistor R that AC-isolates the MOSFETs from DC bias.

Using small-signal analysis similar to that used in Fig. 1a, the insertion loss for the on-state of a stacked SPST switch is derived. In general, stacked devices will have less off capacitance (by 1/N) and greater resistance than a single device. Thus, the insertion loss becomes:

$$IL(N) = 10LOG_{10}$$

$$\left\{ \left(1 + \frac{Nr}{2R0} \right)^2 + \left[\frac{\omega C_{offs}(R0 + Nr)}{2N} \right]^2 \right\}$$
(7)

where:

IL(N) = the calculated insertion loss of the stacked switch in Fig. 2.

For small values of r, doubling it will double the insertion loss at low frequencies, while at higher frequencies, feedthrough through capacitor C_{offs} to ground will begin to increase IL further.

The calculation of the isolation of

stacked devices is made in a similar fashion as insertion loss. Since the net value of capacitance for the off-leg is proportional to 1/N and the on-value of resistance in the on-leg is proportional to N, Eq. 7 predicts that the isolation of a stacked switch will be insensitive to the number of stacked devices (at least to zero order). Including the effect of N thereby creates:

$$IS = -10 \times LOG_{10}$$

$$\left[4r^2\omega^2 C_{offs}^2 / \left(1 + \frac{Nr}{R0}\right)^2 + \frac{\omega^2 C_{offs}^2 RO^2}{N^2}\right]$$

$$\left(1 + \frac{2Nr}{R0}\right)^2$$
(8)

for $N_{r}\!<\!0.R0, \omega r C_{onp}\!<\!0.1$ where:



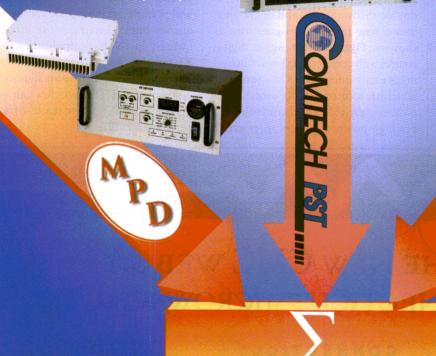
116

THE COMBINED POWER OF 3 COMPANIES INTO 1

PST is your single LARGEST SOURCE for High Power RF Amplifiers, Switches and Complete Power Amplifier Sub-systems. PST's proven power amplifier products with the acquisition of MPD's Military, Satellite and Medical Power Amplifier products

and Hill Engineering's Solid State
Switch products give you the most
powerful combination that you can
depend on. Innovative Amplifiers using
the latest technologies to supply you
with the highest reliability... that's
what the Power of 3 can do.

Athir Engineering Inc.







105 Baylis Road, Melville, NY 11747 Tel: 631-777-8900 Fax: 631-777-8877 E-mail: info@comtechpst.com Web: www.comtechpst.com



 C_{offs} = the capacitance of a single through device in the off-state and r =the resistance of a single shunt device in the on-state.

The Table illustrates that stacking devices and the ability to generate negative onboard voltage sources enables the realization of high-power, high-isolation, and low-insertion loss switches in UTSi technology. With actual packaged parts, inductances and mutual coupling become the limiting factors in isolation and insertion loss. When a part is packaged, care must be taken in order to achieve proper matching, so the final part can approach the theoretical limits of the technology. A balance between target costs and final packaged switch characteristics must be made. However, values that are outlined in the table are more easily realized in highly integrated applications where RF switching is only required between two on-chip locations. In these applications, point-to-point inductances are

much smaller than those in wirebonded parts.

The process that is used to build this type of SPST switch lends itself to high levels of integration. Since the process is based on standard CMOS process flows, digital interfaces can be created with little impact on area, design time, or yield. For example, matrix switches that have three-wire serial-to-parallel interfaces are simple to implement, and, when combined with NAND-NAND-type logic, complex control can now be integrated on-chip. SPST switches can be combined into more complex switch functions, including single-pole, double-throw (SPDT) and single-pole, four-throw (SP4T) configurations as shown in Figs. 3a and b. Again, digital control with correct digital-to-RF buffering is easily integrated. Gate resistors. which are located near RF switch components, provide excellent isolation. For high-power applications, negative supply generators are integrated by using standard techniques. These techniques require low frequency and lowcurrent oscillators. With proper layout, they are isolated from RF. Sidebands from the negative supply generators are too small to be measured in the laboratory.

The availability of low threshold voltages enables the realization of lowvoltage parts in UTSi. For example, switches can operate below +2 VDC with trade-offs in RF characteristics. For +1-VDC applications, onboard voltage triplers can be used to realize the full potential of a switch as shown in the table with a trade-off in chip area. Low-frequency digital interfaces are affected little by low-voltage applications. As RF integrated solutions move toward lower voltages, such as in Bluetooth applications, UTSi switches can still be used with modest trade-offs in performance. MRF



MPP4201

High Frequency >12GHz Flip Chip PIN Diode

FEATURES

- 0.2 pF Capacitance
- Rs of 2.5 Ohms
- Vb of 70 Volts
- Operating Freq up to 12GHz
- Handles 10 Watts of RF power
- Patented hermetic flip chip
- Flip Chip is tape and reel compatible

APPLICATIONS

- ISM Band Antenna Switching
- 802.11a 5GHz antenna switching
- MMDS and LMDS Antenna Switching
- 3G Fixed Microwave Infrastructure
- 2.4GHz High Frequency Switches



UPP1001

High Isolation, Low Loss Low Distortion Power PIN Diode

FEATURES

- 100, 200, and 400V versions
- Patented Powermite Surface Mount
- Low Bias Current requirements
- High Zero Bias Impedance
- 0.75 Ohm resistance
- 1.6 pF Capacitance rating
- Handles 2.5 Watts of RF power
- Full metal bottom eliminates flux entrapment in automated assembly

APPLICATIONS

- Two way radio antenna switch
- High density Wireless messaging



Visit our website for all our RF devices, data sheets, and application notes: WWW.Microsemi.com/rf



© 2001 Microsemi Corporation

USB6B1



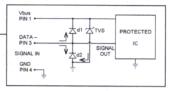
ESD I/O Port Protection

FEATURES

- Single and Two-Line protection
- Stand-Off 5.0 Volts max
- Breakdown 6.0 Volts min
- Clamping 9.8 Volts max
- Capacitance 5 pF typical
 Temp Coefficient 3mV/°C max
- IEC-6000 ESD compliant

APPLICATIONS

- PDAs USB Port Protection
- Data line Protection



SMP6LCXX



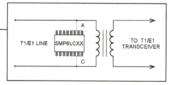
T1/Ethernet Line Protection

FEATURES

- Rugged 600 Watt device
- 10/1000µs surge protection
- Breakdown 6.0-13.3 Volts min
- Clamping 9.6-19.9 Volts max
- Capacitance 30 pF typical
- Peak Pulse Current 10 Amp max
- Standby Current 300µA max

APPLICATIONS

- T1/E1 Protection
- Data line Protection



NEW! Design Guide



Visit our web site for all our TVS devices, data sheets, and application notes:

www.Microsemi.com/tvs



© 2001 Microsemi Corporation

MWS11-PH41

InGaP HBT WCDMA Power Amplifier



The MWS W-CDMA is a high-efficiency linear amplifier targeting 3V mobile handheld systems. The device is manufactured in an advanced InGaP/ GaAs Heterojunction Bipolar Transistor (HBT) RF IC fab process. It is designed for use as a final RF amplifier in 3Volt W-CDMA and CDMA2000, spread spectrum systems, and other linear applications in the 1800MHz to 2000MHz band. There are two 16-pin package versions for this power amplifier. One is a 3mm x 3mm chip scale package (CSP) with external input/output match and the other is an internally I/O matched module.

FEATURES

- Single 3V Supply, 70mA Idle Current
- 27 dBm Linear Power Output
- 26 dB Linear Gain
- 40% Linear Efficiency
- 70mA Idle Current
- 3mm 16 Pin MLP or Flip Chip

APPLICATIONS

- 1920-1980 MHz W-CDMA Handsets
- 1850-1910 MHz CMDA2000 Handsets
- Spread Spectrum Systems



MRF5812

Surface Mount Bipolar RF Mobile Radio Transistor

Designed for high current, low power, low noise amplifiers up to 1.0 GHz. Broad MRF Series can cover applications ranging from 2MHz to 4GHz.

FEATURES

- Low noise: 2.5dB @ 500 MHz
- Associated gain: 15.5 dB @ 500 MHz
- Ftau: 5.0 GHz @ 10 V, 75 mA

APPLICATIONS

- Two way radio power amplifiers
- High density wireless messaging

Visit our website for all our RF devices, data sheets, and application notes: www.Microsemi.com/rf



© 2001 Microsemi Corporation

Introducing Gore Blind Mate Interconnects... For Your System to System Interconnect Needs.





Gore Blind Mate Connectors:

- Compliant with SMP1 and GPOTM Connectors
- Sample Kits Available for Immediate Delivery
- 24 Hour Turn-Around for Sample Orders
- \$3.95/Piece for Introductory Price
- 25 Piece Sample Packages- Under \$99

Innovative Solutions, Defining Technology...



www.gore.com/electronics

1 800 445-GORE



EDA Software Improves Accuracy Of Microstrip Filter Designs

The simulation and optimization of microstrip coupled-line filters for WCDMA are quick and simple by using a popular EDA package.

esearch work has focused recently on the development of wideband-code-division-multiple-access (WCDMA) mobilecommunication systems throughout the world. RF filters are important components in WCDMA base-station transceivers (BTS) to reject unwanted signals. In an RF receiver (Rx), a filter is generally required between the lownoise amplifier (LNA) and the downconverter to reject

size and cost of the components should be taken into consideration during the design. Microstrip interdigi-

image noise. In an RF transmitter (Tx). tal filters feature low loss, high out-ofband rejection, and small size. The traverter to reject image spurs, local-oscil-

ditional microstrip interdigital filter, however, is DC shorted, so high-frequency capacitors are needed as DC blocks when the filter is used with active circuits where a DC bias exists. The traditional interdigital filter is modified in this article. The modified filter has a simpler configuration that requires less computation and is DC opened, making it suitable for direct integration with active circuits.

Simulation and optimization of the filter is carried out with the aid of elec-

JIANYI ZHOU, WEI JIANG. LING TIAN, AND WEI HONG

State Key Lab. of Millimeter Waves, Southeast University, Nanjing, 210096, People's Republic of China: FAX: +86-25-3792096, e-mail: ivzhou@seu.edu.cn

Compared with RF surface-acoustic-wave (SAW) filters and RF dielectric filters, microstrip filters have advantages such as low cost, high-power rating, and good flexibility. Since the frequency of WCDMA is high, the dimensions of microstrip filters are reduced and can be integrated with other RF circuits such as LNAs and mixers. In

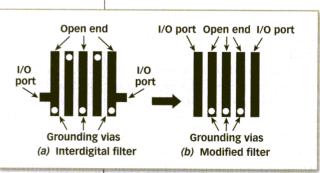
mobile-communication systems, the

a filter is also required after the upcon-

lator (LO) leakage, and other unwant-

ed signals.

1. A conventional interdigital filter has DC-shorted I/O ports (a), whereas the modified version for this design has DC-open I/O ports (b).



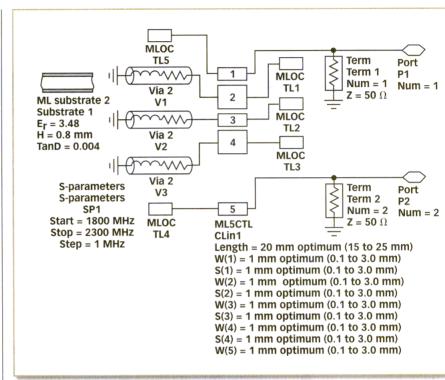
tronic-design-automation (EDA) software. Traditional synthesis tools have limitations, and do not yield acceptable results. They require more trials, tuning, and adjustments. With the aid of advanced EDA software and selecting accurate models, one can obtain satisfactory filter designs quickly and easily. The accuracy of the simulation is improved significantly by employing proper models for microstrip multiple-coupled lines and discontinuities, and the losses introduced by the substrate and metallization are taken into account. The simulation results agree closely with experimental results.

Using EDA software such as the Agilent Technologies Advanced Design System (ADS), accurate models for microstrip multiple coupled lines can be developed.

Simulating A Filter

There are many types of microstrip bandpass filters, including parallel side-coupled line filters, interdigital filters, and others. Generally, interdigital filters have smaller size, lower insertion loss, and good out-of-band rejection. Since the input/output (I/O) ports of the traditional interdigital filter are DC shorted, the configuration provided here is slightly modified so that the I/O ports are DC opened. The schematic of a conventional interdigital filter and the modified version are shown in Figs. 1a and b. Ambala and

It was found that the size of the modified filter is appreciably smaller than the conventional type. Since the structure of the modified filter is simpler, the computation time of simulation and optimization are reduced, which is very important for the optimization



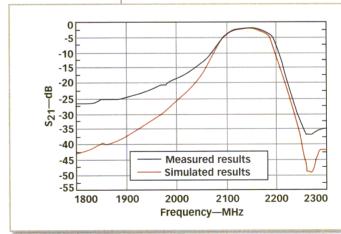
2. The schematic of the microstrip filter as depicted in the ADS format shows the range of values of the filter dimensions along with the optimized value for each dimension.

procedure. Moreover, those filters are DC blocked, so no additional capacitors are needed when they are used with other circuit components, especially active circuits that need DC bias. This makes the implementation very simple.

Traditional analysis and synthesis methods are available for these filters.

Since the coupling of non-neighboring lines, losses in the substrate, metallization, and other discontinuities are neglected in traditional methods, the simulated results are not sufficiently accurate. Using EDA software such as the Agilent Technologies Advanced Design System (ADS), accurate models for microstrip multiple coupled lines can be developed. The accuracy of the simulation can be improved by considering the effect of discontinuities such as grounding vias, open ends, and others which are simulated by ADS. The schematic of the filter as described in ADS is shown in **Fig. 2**.

Using the optimization tools pro-



3. Experimental (measured) and simulated curves of the transmit filter show almost perfect agreement in the passband, but the out-of-band performance of the simulated filter is better than that of the physical filter.

SAWTEK OSCILLATORS REALLY DELIVER

Sawtek...Your Total SAW Solution!

Sawtek's voltage controlled SAW oscillators deliver the specs your need for low g-sensitivity, very low noise floors and low phase noise. The differential output Emitter Coupled Logic (ECL) clock is perfect for the low jitter requirements of SONET, Ethernet and network servers. Sawtek's new single-ended sine wave oscillator is ideal for broadband



applications such as SONET, LMDS/MMDS point-to-point and multi-point microwave systems. When your designs demand vibration immunity and aggressive cost-effectiveness, demand oscillators from Sawtek...they deliver.

Differential ECL Clock VCSO

- Frequencies from 600 MHz to just over 1 GHz
- Surface Transverse Wave (STW) technology offers very low jitter at high fundamental frequencies (<.3 pS RMS)

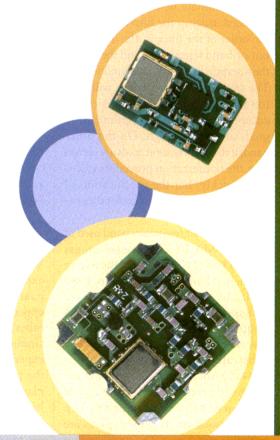
Single-Ended Sine Wave VCSO

- Frequencies from 300 MHz to 2.5 GHz
- STW technology offers low phase noise (-120 dBc/Hz to -135 dBc/Hz at 10 kHz, -165 dBc/Hz at 1 MHz) and exceptional high frequency jitter performance (<5 fS RMS)



www.sawtek.com

Phone: (407) 886-8860 • Fax: (407) 886-7061 E-Mail: info@sawtek.com

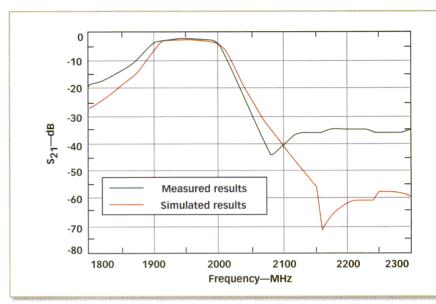




vided by ADS, the filter design can be executed without tightly restricting the initial values of approximately all of the important parameters, such as the length of the coupled lines, the width of each strip, and the gap between two neighboring lines. The computation time of the optimization routine can be shortened considerably if a reasonable range of values of the parameters is provided. For example, the initial value of the length of the coupled lines can be selected near the quarter-wavelength of the central frequency in the passband.

The optimization goals are determined by the required passband loss and out-of-band rejection. These goals are very important and should be carefully selected. It is highly recommended that an estimate be calculated for the specified order of the filter. The higher the order of the filter is, the higher the out-of-band rejection is, and the higher the insertion loss in the passband will be. The optimization procedure will take too much calculation time to yield an acceptable result if the optimization goals are set too high. On the other hand, if the optimization goals are set too low, the optimization procedure calculates quickly, but the specification of the filter will not be satisfied for the specific application.

The transmit frequency band used in the WCDMA BTS transceiver ranges from 2110 to 2170 MHz and the receive frequency band spans 1920 to 1980 MHz. According to this, two filters are designed—one for the forward-channel frequency band, and the other for the reverse-channel frequency band. The substrate used in the simulation is RO4350 from Rogers Corp. The initial length of the coupled lines is 20 mm, while the strip width of each line and the gap width between two neighboring lines are initially set to 1 mm. The optimization ranges of these parameters are given, as shown in Fig. 2. Five-coupled line is used in the design of the filters. The corresponding optimization goal of the passband insertion loss is 3 dB, and the optimization goal of the out-of-band rejection is more than 20 dB.



4. A comparison of the experimental (measured) and simulated curves of the receive filter is similar to that of the transmit filter (shown in Fig. 3) in terms of passband and out-of-band performance.

With the optimized results, five receive filters and five transmit filters were created on the RO4350 substrate. The dimension of each filter is 15 to 25 mm, quite a bit smaller than that of either a parallel side-coupled-line filter or a traditional interdigital filter. The coincidence of these filters is perfect. The comparison of the experimental results and the simulated results is shown in **Figs. 3 and 4**.

Simulated Versus Real

When comparing the simulated and experimental results, the results in the passband of the simulation and the experiment perfectly agree with each other. The out-of-band rejection in the simulation is better than that in the experiment. One possible reason is that the physical filters have finite ground planes, while the filters in the simulation have infinite ground planes. Actually, in this experiment, to reduce size of the filter, the area of the ground plane is a little larger than that of the coupled lines. A finite ground plane affects the out-ofband rejection significantly, especially in the lower frequency band. Another possible reason is the radiation coupling between the lines, which is neglected in the simulation. Accurate simulation of radiation requires three-dimensional (3D) electromagnetic (EM) solvers. The optimization procedure may become impossible since the computation time is too long if 3D EM solvers are used in the filter design.

Although the out-of-band performance of the actual filters is not as good as the simulated results, these filters are usable for many applications. In the transmit filter, the insertion loss in the passband is approximately 3 dB, while the rejection in the receive band is more than 20 dB, which is acceptable as an image and LO leakage-rejection filter. In the receive filter, the insertion loss in the passband is approximately 3 dB, while the rejection in the transmit band is more than 35 dB, which is suitable for rejecting image noise and transmit noise. In a word, these filters are suitable for image-rejection filters or spur-rejection filters in WCDMA BTS RF transceivers and other infrastructure of WCDMA RF systems. MRF

REFERENCES

- 1. R.J. Wenzel, "Printed Circuit Complementary Filters for Narrow Bandwidth Multiplexers," *IEEE Transactions*, Vol. MTT-16, pp. 147-157, March 1968.
- 2. J.D. Rhodes, "The Generalized Interdigital Linear Phase Filter," *IEEE Transactions*, Vol. MTT-18, pp. 808-818, June 1970.
- 3. J. Zhou and W. Hong, "Design of Compact Microstrip Duplexers for 3G Mobile Communication Systems," *IEEE AP-S*, Italy 2000
- 4. HP Advanced Design System Documentation, Hewlett-Packard Co., 1999.

INCAN I VOIALIANVI Q13.5mm¹¹¹ Quick lest • Excellent Repeatability/ Connectors & Adapters* Low VSWR

 Quick & Easy Push-On/ Pull-Off Design

 Guide Sleeve **Design For** Automated **Applications**

 Designed for Long



No Nut



3/8" Nut





ELECTRICAL SPECIFICATIONS

MODEL	FROM	TO	FREQ RANGE (GHz)	VSWR (GHz)	
8006E1	QT3.5mm™ (m) with no nut	3.5mm (f)			ig.
8006E11	QT3.5mm™ (m) with 3/8" dia. nut	3.5mm (f)	page 100 miles	DC - 16.0, 1.05	
8006E21	QT3.5mm™ (m) with 9/16" dia. nut	3.5mm (f)	DC - 26.5**	16.0 — 26.5, 1.08	
8006Q1	QT3.5mm [™] (m) with guide sleeve	3.5mm (f)		10.0 _ 20.5, 1.08	

REPEATABILITY

REPEATABILITY	DC - 18.0 GHz	18.0 - 26.5 GHz
Push-On Mode	> 45 dB	> 40 dB
Torque Mode	> 50 dB	> 50 dB
Hand Torque	> 50 dB	> 50 dB

Other available configurations include:

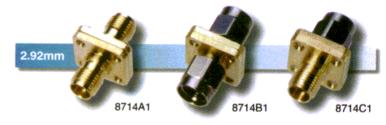
- 7mm
- NMD3.5mm (f)
- TYPE N (f & m)
- NMD2.4mm (f)

ALSO AVAILABLE FROM MAURY

In-Series Precision Adapters

- Low VSWR / Low Loss
- DC to 50 GHz
- Minimize VNA Test Port Wear
- Phase Matched / Minimum Length
- Bulk Head & Panel Mount Configurations Available
- Between-Series Adapters Are Also Available

2.4mm



3.5mm 8021C2

ELECTRICAL SPECIFICATIONS

MODEL	FROM	то	FREQ RANGE & MAX. VSWR
7921A	2.4mm Q (f)	2.4mm Q (f)	DC — 26.5 GHz. 1.06
7921B	2.4mm Q (f)	2.4mm Q (m)	26.5 — 40.0 GHz, 1.10
7921C	2.4mm Q (f)	2.4mm Q (m)	26.5 — 34.0 GHz, 1.15
8714A1	2.92mm K (f)	2.92mm K (f)	DC 4.0 GHz, 1.05
8714B1	2.92mm K (m)	2.92mm K (m)	4.0 — 20.0 GHz, 1.08
8714C1	2.92mm K (f)	2.92mm K (m)	20.0 — 40.0 GHz, 1.12
8021A2	3.5mm (f)	3.5mm (f)	DC — 18.0 GHz. 1.05
8021B2	3.5mm (m)	3.5mm (m)	18.0 — 26.5 GHz, 1.08
8021C2	3.5mm (f)	3.5mm (m)	26.5 — 34.0 GHz, 1.12

Between-Series configurations include: • 2.4mm to 2.92mm (K)

- 2.4mm to 3.5mm

* U.S. PATENT #6210221

MAURY MICROWAVE CORPORATION 2900 Inland Empire Blvd., Ontario, CA 91764, USA

For more information contact our **SALES DEPARTMENT** at Tel: (909)987-4715 • Fax: (909) 987-1112 Email: maury@maurymw.com

Visit us on the World Wide Web at http://www.maurymw.com

Enter No. 250 at www.mwrf.com

^{**}Slightly reduced VSWR specifications to 34 GHz.



switch filters

- Excellent electrical performance
- High isolation
- Low loss and low VSWR

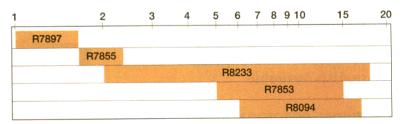
RF and Microwave Switch Filters are available as modifications to over 100 existing Microphase designs or in customer specified configurations. They provide reliable high performance, multi-throw, multi-octave switched filtering in compact packaging.

Most switch filters feature one input and one output, with two or more selectable filter paths. However, multiple inputs and outputs may be specified to alternately route the signal, or to inject BIT signals.

The integrated switches are PIN diode or GaAs FET designs with internal drivers controlled through TTL compatible inputs.

TYPICAL SPECIFICATIONS

Frequency Range	10MHz to 26 GHz
Number of Channels	2 to 12
Insertion Loss	2 to 8 dB
Isolation	40 to 75 dB
VSWR	1.3:1 to 2.0:1
Switching Speed	10 nsec to 1µsec
Input Power	up to +27 dBm CW
Control	TTL Binary Coded Decimal
Power Supply	+5 volts
	-5, -12 or -15 volts
Size	1 x 1.25 x .35 (.44 in ³)
	to 7 x 4.6 x 1.63 (52 in ³)



PART NO.	TYPE	FREQUENCY (GHz)	DIMENSIONS (in)
R7897	SP4T	1.1-1.7	$2.0 \times 1.5 \times 0.25$
R7855	SP2T	1.7-2.4	$4.0 \times 2.0 \times 0.50$
R8233	SP3T	2.0-18.0	1.0 x 1.25 x 0.35
R7853	SP3T	5.0-15.0	$3.0 \times 1.7 \times 0.50$
R8094	SP8T	6.0-17.0	$4.0 \times 2.8 \times 0.64$



587 Connecticut Avenue PO Box 960 Norwalk CT 06854-096 203 831-2255 fax:203 866-6727 www.Microphase.com

Call: John Filakovsky 203 831-2228

Enter No. 257 at www.mwrf.com



Parameter Describes Mixer IM Performance

A new figure of merit known as IP3 efficiency, or E-factor, can be helpful in evaluating the effective IM performance of FET-based and diode-based mixers.

ixers perform the critical frequency-translation chores in modern communications systems. With the increasing use of complex, phase-based modulation schemes in communications, dynamic range has become a key performance parameter in comparing mixers. While third-order intercept point (IP3) has served as a measure of dynamic range in mixers, the specification can be misleading. A proposed new

figure of merit for mixer dynamic range is IP3 efficiency.

To achieve increased subscriber capacity, modern receivers (Rxs) and transmitters (Txs) must handle multiple-carrier signals (desired or not). When multiple carriers arrive at the input of a mixer, they combine with each other to generate intermodulation (IM) products. The most troublesome product to remove by filtering is the third-order IM product. The tolerable level of this product is dictated by the system requirements. Higher IP3 performance, within limits, can be obtained in a mixer by careful design or at the expense of local-

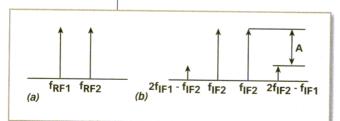
oscillator (LO) power in a particular design. But an increase in LO power also requires an increase in DC

power and additional hardware. By accurately evaluating the IP3 performance of a mixer, however, it may be possible to avoid unwanted power consumption and expense in a communications system's design, by using IP3 efficiency as a figure of merit.

It may be useful to first define IP3. When two RF signals of equal amplitude arrive at a mixer's input, IM frequencies are generated due to the nonlinearity of the mixing device. Figure 1a shows a spectrum of two RF signals f_{RF1} and f_{RF2}-that are close in frequency. Figure 1b shows a simplified spectrum at the intermediate-frequency (IF) output of a mixer. The third-order products, $2f_{IF1} - f_{IF2}$ and $2f_{IF2} - f_{IF1}$, are predominant IM frequencies, closest to the desired IF output. The spacing between IM products and the adjacent carrier is the same as the spacing between the carrier signals. For example, if the carriers are 1 MHz apart, the IM product will be 1 MHz from the nearest carrier. If the carriers are spaced 1 kHz apart, then the IM product will

Engineering Dept.

Mini-Circuits, P.O. Box 350166, Brooklyn, NY 11235; (718) 934-4500, FAX: (718) 332-4661, Internet: www.minicircuits.com.



1. This diagram illustrates a two-tone signal that is processed at the input of a mixer (a), with the resulting signals (b) produced at the mixer's IF output port.

be only 1 kHz removed from the nearest carrier. If the two carriers are close, it is difficult to filter the unwanted IM product.

If the difference in power level between the main signal and the generated IM product is A dB (Fig. 1b), then IP3 can be defined as:

Input IP3
$$(dBm) =$$

$$P_{in} (dBm) + A / 2$$
 (1)

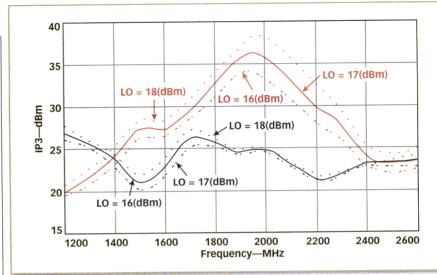
Within the linear region of a mixer, in most cases, the IM product decreases by 3 dB for every 1-dB decrease in RF power. From Eq. 1, it can be seen that this relationship leads to IP3 being insensitive to RF power level. As a result, IP3 has been used as a parameter to describe mixer IM performance.

In general, a lower level of IM product leads to better Rx or Tx performance. Lower-level mixer IM can be achieved in two ways: by an increase in LO power or by improved mixer design. Unfortunately, there has been no easy way to quantify the effectiveness of a design in terms of IM performance. But it may be possible to use a new figure of merit, IP3 efficiency or E, for this purpose. Parameter E can be defined by Eq. 2 as:

$$E = [IP3 (dBm) - LO power (dBm)] / 10$$
 (2)

As a rule of thumb, the IP3 of a well-designed mixer is 10 dB above the LO power. Substituting this relationship into Eq. 2 leads to an E value of 1. A value of E that is higher than 1 signifies a mixer with superior IM performance.

Table 1 lists a series of FET-based mixers that were developed by Mini-Circuits (Brooklyn, NY). The IP3 performance levels of these mixers range from +21 to +38 dBm. At first glance, it is easy to dismiss the mixer with +21-dBm IP3 performance as substandard. On closer examination, however, it can be seen that the LO power used by this mixer is only +7 dBm. For a +7-dBm mixer, IP3 performance of +21 dBm can be considered very good. Still, the IM per-



2. These plots show the IP3 performance as a function of frequency for HJK-19H (red curves) and SYM-25H 9 (black curves) mixers.

formance of the mixer has not been quantified by simply evaluating its LO power and IP3 performance. For this mixer, the E-factor is 1.4, which is considerably above the unity value established for a normal mixer with reasonable IM performance. By using the E-factor, selecting mixers with high IP3 efficiency can be simplified.

Table 1 contains FET-based mixers with E-factor values in the range of 1.4 to 2.1. These values are considerably higher than the E-factor values exhibited by conventional diode-based mixers **(Table 2).** In an examination of typical

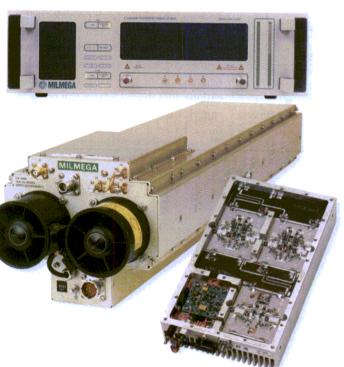
diode-based mixers, the E-factor is typically 0.8 except for one narrowband model (SYM-10DH). FET-based mixers can be produced with very repeatable performance compared to diodebased mixers, and require no tuning to meet their specified performance levels. As a result, for a given set of performance characteristics, the cost of manufacturing FET mixers is considerably less than that of diode-based mixers.

To compare the swept performance of the FET-based and diode-based mixers, the two types of mixers were tested across their RF ranges. **Figure 2** shows

	Table 1: High-efficiency FET mixers							
MODEL NO.	RF FREQ. (MHz)	LO FREQ. (MHz)	IF FREQ. (MHZ)	LO POWER (dBm)	IP3 (dBm) typical	E- FACTOR		
HJK-9	818 to 853	753 to 778	40 to 100	+7	+22	1.5		
HJK-19	1850 to 1910	1780 to 1840	70 to 130	+7	+21	1.4		
HJK-21	1850 to 1910	2090 to 2150	180 to 300	+7	+22	1.5		
HJK-9LH	818 to 853	753 to 778	40 to 100	+10	+27	1.7		
HJK-19LH	1850 to 1910	1780 to 1840	70 to 130	+10	+25	1.5		
HJK-21LH	1850 to 1910	2090 to 2150	180 to 300	+10	+25	1.5		
НЈК-9МН	818 to 853	753 to 778	40 to 100	+13	+31	1.8		
НЈК-19МН	1850 to 1910	1780 to 1840	70 to 130	+13	+30	1.7		
HJK-21MH	1850 to 1910	2090 to 2150	180 to 300	+13	+29	1.6		
нук-зн	140 to 180	160	0.5 to 20	+16	+37	2.1		
HUD-3H	140 to 180	160	0.5 to 20	+16	+37	2.1		
НЈК-9Н	818 to 853	753 to 778	40 to 100	+17	+33	1.6		
HJK-19H	1850 to 1910	1780 to 1840	70 to 130	+17	+34	1.7		
HJK-21H	1850 to 1910	2090 to 2150	180 to 300	+17	+36	1.9		
HUD-19SH	1819 to 1910	1710 to 1769	50 to 200	+19	+38	1.9		

HIGH POWER Microwave Amplifiers

Milmega's strength lies in our ability to produce a family of high quality octave band solid state microwave amplifiers, and yet maintain the flexibility to design and build high quality amplifiers/amplifier systems to meet your specific requirements. This strength has created Milmega's global reputation as experts in the field of high power microwave engineering.



Our standard products and custom designs can be found in many leading edge applications including:

Physics research

Colliding electrons and positrons in the search for quarks and the testing of nuclear theory.

Electromagnetic Compatibility (EMC) testing

Providing wide frequency ranges and producing field strengths over 200V/m.

Defence

Operating over wide temperature ranges in rugged environments, Milmega amplifiers are built into sophisticated jamming systems.

Communications testing

Where Milmega amplifiers are often used in pairs for Passive Intermodulation (PIM) testing.



Designers and Manufacturers of High Power Microwave Amplifiers and Systems

Milmega Ltd, Ryde Business Park, Nicholson Road, Ryde, Isle of Wight, PO33 1BQ, UK
Tel: +44(0) 1983 618000 Fax: +44(0) 1983 616864
E-mail: sales@milmega.co.uk Web: www.milmega.co.uk

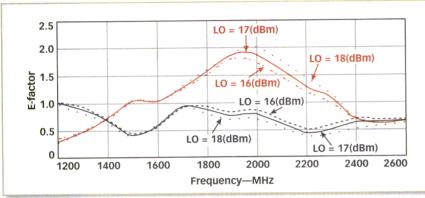
DINTY QUALITY MANAGEMENT 013

 $1\mathsf{GHz}$

10GHz

Enter No. 261 at www.mwrf.com

Table 2: Conventional diode mixers							
MODEL NO.	RF FREQ. (MHZ)	LO FREQ. (MHZ)	IF FREQ. (MHz) (dBm)	LO POWER typical	IP3 (dBm)	E- FACTOR	
SYM-10HJ	400 to 1000	400 to 1000	DC to 400	+17	+25	8.0	
SYM-10DH	800 to 1000	800 to 1000	20 to 200	+17	+31	1.4	
SYM-25H	10 to 2400	10 to 2400	1 to 1100	+17	+25	8.0	
SYM-36H	1500 to 3600	1500 to 3600	DC to 600	+17	+25	0.8	



3. These plots show the E-factor as a function of frequency for HJK-19H (red curves) and SYM-25H 9 (black curves) mixers.

YOU'RE FAST AND

INNOVATIVE.

www.advanced-control.com

the IP3 performance of FET-based (HJK-19H) and diode-based (SYM-25H) mixers. The IP3 of the FET-based mixer is approximately 7 to 10 dB higher than that of the diode-based mixer in the 1800-to-2000-MHz personal-communications-services (PCS) frequency region. With increasing bandwidth, the IP3 performance of the diode and FET mixers tends to be similar.

Figure 3 shows the E-factor values for the same two mixers. The IP3 efficiency or E-factor for the FET-based mixer is 0.6 to 0.9 higher than that of the diode mixer in the 1800-to-2000-MHz range. Over a wider frequency range, however, the diode mixer provides higher E-factor values than the FET-based mixer. In addition, the diode mixer has a more constant E-factor over a wider bandwidth. Thus, for narrowband applications, FET-based mixers can provide superior dynamic range compared to diode-based mixers. MRE



SO ARE WE.

market. Call us today, or visit us at www.advanced-control.com. Your ideas can't wait, . . . and we can't wait to help you.

DETECTORS

Schottky, Tunnel and Zero-Bias Schottkys. Frequency ranges from 1 KHz up to 40 GHz. Schottkys offer a wide linear dynamic range with high sensitivity. Tunnels offer extremely stable operation (V out vs. temperature)

LIMITER-DETECTORS

Limiter protection allows for exposure to higher input power levels by increasing the burn-out power level. Schottky Detectors can also include video protection from EMI & ESD.

LIMITERS

ACC manufactures a wide variety of input protection Limiters. The range of input power capability is dependent on frequency, package style, pulse widths, temperature range and a variety of other factors.

AMPLIFIER - DETECTORS

ACC has broadband RF-Microwave Amplifier stages coupled with detectors which offer sensitivity values not achievable with detectors alone

DETECTOR-AMPLIFIERS

This family of devices combines the Detector with a Video Amplifier.

SWITCHES
Standard Pin-Diode SPST, SP2T,
SP3T, SP4T, SP5T, and Transfer switche
covering the frequency range of 10 MHz
through 18 GHz. These cost-effective
switches have been optimized for high performance including low loss, high isolation, and fast switching.

ATTENUATORS

ACC offers a standard series of 4- through 6-bit Pin-Diode digital attenuators, covering the frequency range of 1 GHz through 4 GHz with up to 63 dB of attenuation. The attenuators have been optimized for high performance including low loss, attenuation accuracy and flatness, fast switching, and compact size.

CUSTOM CONTROL COMPONENTS

ACC designs and manufactures custom Pin-Diode and GaAs FET based switches, Digital Attenuators, Variable Attenuators, Phase Shifters, Switch-Limiters, Switch Matrices, Threshold-Detectors, Coupler-Detectors, Super-Components, and Multi-function Sub-assemblies, operating from DC to beyond 18 GHz.

GET THE COMPONENTS YOU NEED FAST FROM



20 Meridian Rd., Eatontown, NJ 07724 Tel 732 460-0212 Fax 732 460-0214

Enter NO. 401 at www.mwrf.com

ISO 9001 CERTIFICATE NO. 99-088



"Leading edge circuit design says less is more. Small is never small enough, and it has to do more. More is the operative."

"My ideal materials company has to give me more. More products, more ideas, more support. Now."



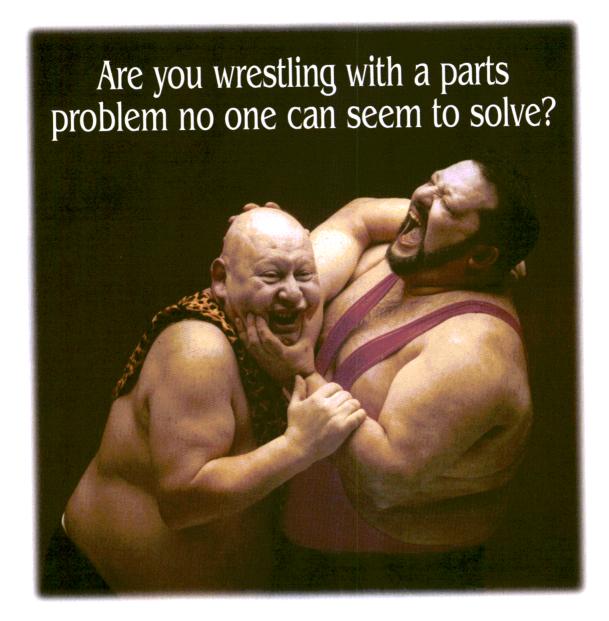
Done.

"Done?"



Done. We've combined our flex circuit materials and microwave materials divisions to offer a sweeping array of high performance circuit materials for demanding applications, plus global capabilities, unrivaled technical expertise, and unsurpassed service. To find out more, visit www.rogers-corp.com/acm/info6.htm. Or call 480-961-1382.

The new Advanced Circuit Materials Division at ROGERS



From standard to custom, KDI can make your parts!

Looking for a single-source heavyweight in the RF/microwave arena? You've found it. Whether you want components or finished subassemblies, KDI will never leave you on the ropes.

We offer the most comprehensive line of passive components and subassemblies in the industry, as well as the speed and flexibility you need from a technology partner.

KDI quality assurance standards are first-in-class and we are recognized for continuously improving our processes and technology. Surfpac technology is just one example. Now being

implemented throughout our product line, this breakthrough surface mount process has significantly reduced the size and cost of switches, attenuators, amplifiers and phase shifters. The benefits go right to our customer's bottom line.

Add to these product categories KDI's world-class manufacturing capability, and your decision to go single source



becomes even easier. Our extensive production experience with a wide variety of processes and materials from thick-film hybrids to passive and active circuits makes KDI your partner-of-choice in RF/microwave manufacturing.

Whether your needs are in cellular or PCS base stations, analog or TDMA, 3G, GSM or CDMA, KDI is totally capable. Don't let the wrong vendor put a "stranglehold" on your parts supply...call KDI today!

For application assistance or more information, call 973-887-8100 Ext. 500, or fax us at 973-884-0445.





KDI-INTEGRATED PRODUCTS

60 South Jefferson Road, Whippany, NJ 07981 • Tel: 973-887-8100 • Fax: 973-884-04-Web site: www.kditriangle.com • e-mail: sales@kditriangle.com



Design A Low-NoiseSynthesizer Using YRO Technology

This article describes the advantages of the YIG replacement oscillator, and offers a design for a low-noise, fast-switching YRO synthesizer.

ttrium-iron-garnet (YIG)-based oscillators are renowned for their ability to generate clean sine waves at very high frequencies, but they are not known for their frequency agility. Nor are they immune to vibrational effects such as microphonics, phase hits, and frequency-modulation (FM) effects. This article describes a novel device called a YIG-replacement oscillator (YRO), which can serve as a

formance, albeit with the associated manufacturing difficulties for repeatable performance in high volume at low cost.

DRO-based radios have limited util-

DRO-based radios have limited utility in the LMDS market due to their fixed-frequency nature. To be useful in LMDS applications, they must be combined with additional frequency-agile sources such as VCOs. However, combining DROs and VCOs increases the cost beyond LMDS price points and performance. The fixed-frequency nature of the DRO also precludes their widespread use or adoption in the test-and-measurement market.

To solve the frequency-agility issue, radio manufacturers that serve the point-to-point and point-to-multipoint markets would prefer to use a synthesized application that could emulate the good phase-noise performance of a DRO, yet eliminate the crude DRO-VCO combinations and deliver much higher transmission speeds.

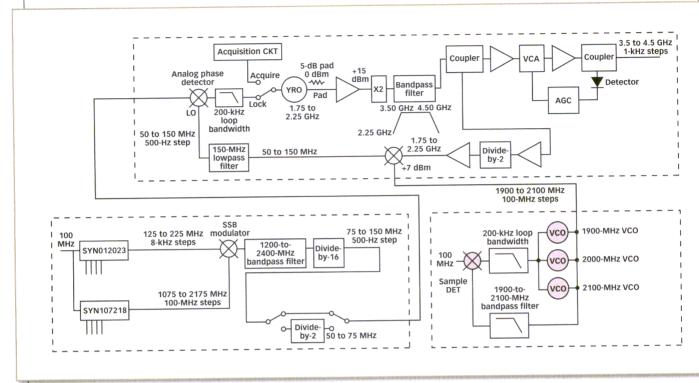
One major technological challenge to increase data rates and improve modulation schemes for digital-radio manufacturers is synthesizing the high-frequency "carrier" wave. To achieve that

ELIOT FENTON AND ANDY GODDARD

APA Wireless Technologies, 4050 N.E. 5th Ave., Fort Lauderdale, FL 33334; (954) 563-8833, FAX: (954) 563-7127, e-mail: efenton@apawireless.com, asgoddard@apawireless.com

direct substitute for YIGs and dielectricresonator oscillators (DROs) in applications such as frequency synthesizers, upconverters, downconverters, phaselocked oscillators, microwave communications, test equipment, radar, local multipoint-distribution systems (LMDS), and multichannel multipointdistribution systems (MMDS). This article describes voltage-controlled oscillators (VCOs), DROs, and YIGs, and points out the advantages that YROs have over these devices. It also describes the design of a fast-switching, lownoise, 3.5-to-4.5-GHz synthesizer that makes use of a YRO.

Traditionally, digital-radio and testequipment manufacturers used one of two types of oscillators for their products: DROs or YIGs. Mechanically adjustable DROs are used for fixedfrequency applications. Although effective, these components do not have the frequency agility needed for radio manufacturers who build and test their own products. Initially developed for military applications in the 1960s, DROs



The three loops that comprise the synthesizer are illustrated above.







www.PlanetEE.com

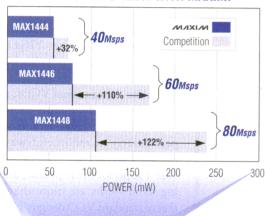


WORLD'S LOWEST POWER 3V, 10-BIT 80Msps ADC DELIVERS 73dBc SFDR

New 10-Bit 40Msps/60Msps/80Msps/105Msps ADCs are Ideal for Portable Imaging and Communications

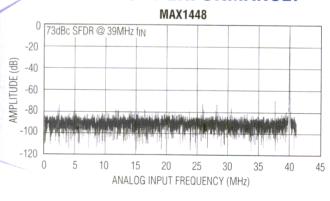
LOWEST POWER!

SAVE 32% TO 122% WITH MAXIM!



- ♦ 59dB SNR @ f_{IN} = 20MHz
- ♦ 2.7V to 3.3V Operation
- ♦ Tiny 5mm x 5mm TQFP Package
- On-Chip Internal/External Reference
- ♦ Shutdown (<5µA @ 3V)
- Pin-Compatible 40Msps, 60Msps, 80Msps and 105Msps Versions
- Differential Input T/H with 400MHz FPBW

HIGHEST PERFORMANCE!





2-PIN TOR

Smm x 5mm

FREE High-Speed ADC/DAC Design Guide—Sent Within 24 Hours! Includes: Reply Cards for Free Samples and Data Sheets

SMALLEST

PACKAGE

CALL TOLL-FREE 1-800-998-8800 for a Design Guide or Free Sample 6:00 a.m. – 6:00 p.m. Pacific Time



www.maxim-ic.com

Get Price, Delivery, and Place Orders
Online at www.maxim-ic.com

2001 EDITION! FREE FULL-LINE DATA CATALOG ON CD-ROM

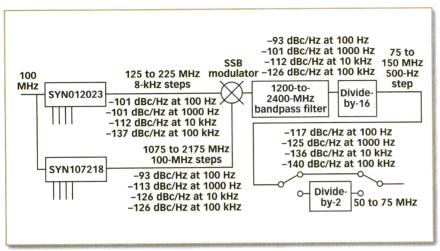




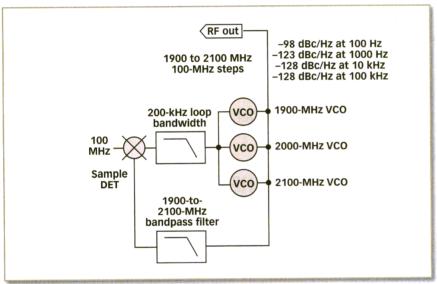
Maxim Integrated Products, 120 San Gabriel Drive, Sunnyvale, CA 94086, (408) 737-7600, FAX (408) 737-7194.

Distributed by Maxim/Dallas Directt, Arrow, Avnet Electronics Marketing, CAM RPC, Digi-Key, Elmo, Nu Horizons, and Zeus.

Distributed in Canada by Arrow and Avnet Electronics Marketing.



2. This diagram shows the synthesizer's reference loop.



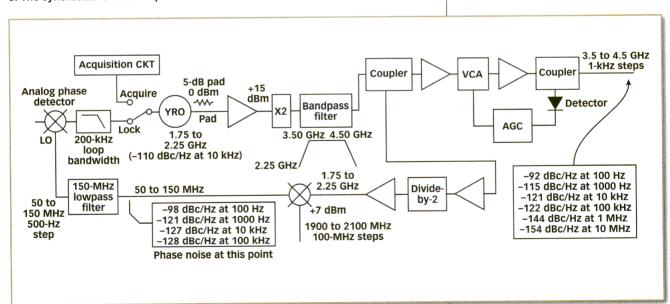
3. The synthesizer's fixed loop is shown here.

objective, LMDS manufacturers have turned to YIG oscillators. These "analog" devices are capable of generating very-high, very-clean microwave signals that are critical to data transmission. However, YIGs incorporate a rare-earth material that can be difficult to obtain, and the devices must be properly configured in a machined metal housing to be effective.

YIG-based technology has been in use for many years, but it has several inherent weaknesses. For example, YIGs are very expensive to manufacture because they require a substantial amount of manual labor and are prone to manufacturing defects. Also, YIGs can be tuned to different frequencies, but only very slowly.

Unlike conventional VCOs, a YIG-based oscillator's quality-factor (Q) performance increases with frequency, particularly at millimeter-wave frequencies. YIG-based synthesizers provide a superior noise profile, and tuning bandwidths are more than twice that of standard VCO designs. However, YIGs require a significant amount of power, which generates excessive heat that may harm the other electronic components in the transceiver. YIGs also require an environment that is free from vibration and electromagnetic interference (EMI).

In outdoor settings such as a rooftop,

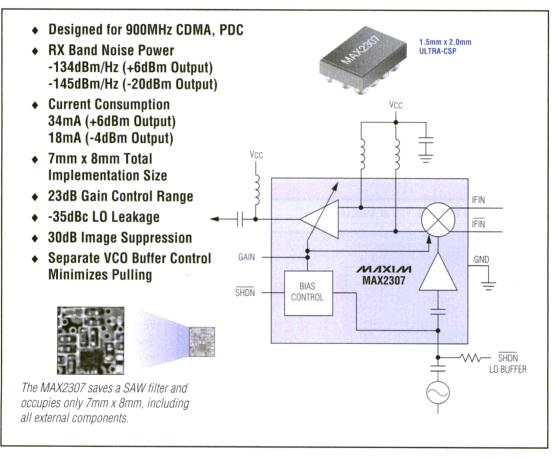


4. The synthesizer's main loop can be seen here.

MINIATURE CELLPHONE UPCONVERTER/ DRIVER IC ELIMINATES SAW FILTER, **USES ONLY 18mA!**

Ultra-CSP IC Puts Out +6.5dBm While Measuring Only 1.5mm x 2mm

The MAX2307 is designed for Japanese N-CDMA and PDC 900MHz applications. Its unique upconverter architecture eliminates a SAW filter at the expense of just one low-cost inductor. The device is packaged in an ultra-small CSP package and draws less current than comparable discrete designs, especially at 10dB backoff from peak power, the typical CDMA output power used for talk-time calculations.





FREE Wireless Design Guide—Sent Within 24 Hours! **Includes: Reply Cards for Free Samples and Data Sheets**

CALL TOLL-FREE 1-800-998-8800 for a Design Guide or Free Sample 6:00 a.m. - 6:00 p.m. Pacific Time





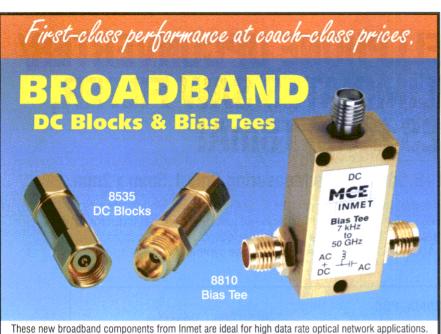
2001 EDITION! FREE FULL-LINE DATA CATALOG ON CD-ROM





Maxim Integrated Products, 120 San Gabriel Drive, Sunnyvale, CA 94086, (408) 737-7600, FAX (408) 737-7194, Distributed by Maxim/Dallas Direct!, Arrow, Avnet Electronics Marketing, CAM RPC, Digi-Key, Elmo, Nu Horizons, and Zeus. Distributed in Canada by Arrow and Avnet Electronics Marketing

IN INTERIOR IN INTERIOR INTERI



These new broadband components from Inmet are ideal for high data rate optical network application: The 8535 series of DC Blocks operate from 7 kHz to 50 GHz and pass RF signals with nominal attenuation. The 8810 family of Bias Tees operate from 7 kHz to 50 GHz and handle up to 250mA of bias current with a DC-RF isolation better than 30 dB across the frequency band.

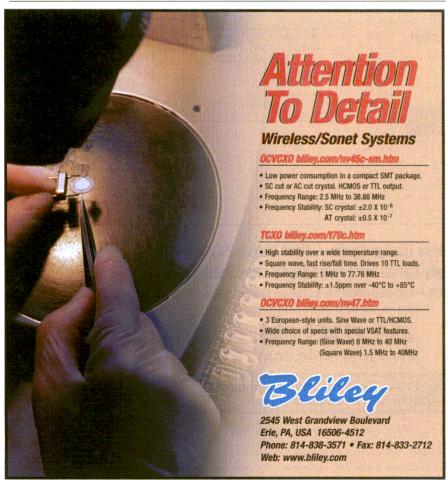




Manufacturer of Attenuators • Adapters • Bias Tees • DC Blocks • Equalizers • Terminations
300 Dino Drive • Ann Arbor, MI 48103 USA • Phone 888-244-6638 or 734-426-5553 • FAX 734-426-5557
Visit us on the Web at www.inmetcorp.com

ISO 9001 CERTIFIED

Enter No. 423 at www.mwrf.com



DESIGN

YIGs are prone to wind, vibration, rain, and lightning, all of which have a detrimental effect. For example, YIGs in LMDS systems hanging from rooftops are subject to phase hits, a severe problem affecting the radio's bit-error rate (BER). Interruptions in the carrier signal stemming from a YIG's vibration sensitivity slows and then drops data transmission. This does not bode well for the LMDS system manufacturers in meeting the industry's five-nines (99.999 percent on-signal disruption) standard for reliability. And when a YIG-based synthesizer is destabilized, it is slow to react and re-establish phase lock. This slow reaction contributes to lost transmission bits, increasing BER.

In outdoor settings such as a rooftop, YIGs are prone to wind, vibration, rain, and lightning, all of which have a detrimental effect.

In contrast, YROs have several distinct advantages over YIG technology. First, YROs are silicon (Si)-based devices that can be inexpensively manufactured to very high standards with high repeatability. Second, YROs can change frequencies very rapidly—orders of magnitude faster than a YIG—providing them with a broader range of applications. Third, since YROs oscillate without the need for expensive housing or cumbersome electronics, they are not prone to many of the physical limitations of YIG technology, such as wind, vibration, rain, and EMI.

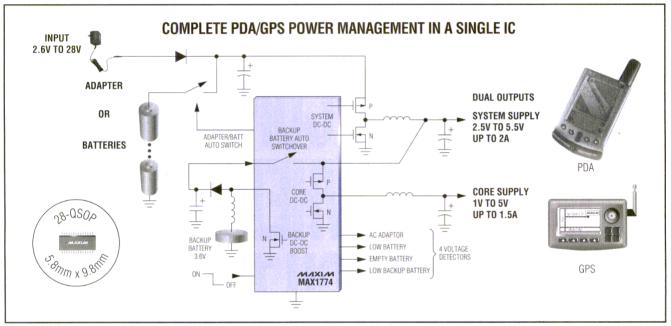
YROs are fundamental-mode devices that combine the size, ease, and speed of tuning that is associated with a VCO and the phase-noise characteristics of a DRO. Depending on frequency and bandwidth, phase noise can vary from -110 to -120 dBc/Hz at 10-kHz offset.

The following discussion provides a sample design for a 3.5-to-4.5-GHz

WORLD'S SMALLEST COMPLETE POWER SUPPLY FOR HANDHELD DEVICES

2 Step-Down DC-DCs, Back-Up Battery Boost, and 4 Voltage Detectors

The MAX1774 is the world's smallest complete power management IC for portable handheld devices like palmtops, e-books, and GPS receivers. Dual high-efficiency supplies save battery life and save space. The MAX1774 detects the AC adapter and automatically switches between battery and wall cube power. When the battery gets low, a compact boost converter supplies backup power from the backup battery. When the backup battery can no longer deliver the load, the MAX1774 signals the system to shut down to prevent data loss or damage. A simpler version without the backup boost and voltage detectors is available in a smaller 16-QSOP package (MAX1775).



Four voltage detectors tell the system when the AC adapter is on, when the main batteries are low and empty, and when the backup battery is low. The MAX1774 automatically switches from battery to adapter power.

- ◆ Two High-Efficiency Step-Down DC-DCs
 - ◆ 2A System Supply (95% Efficient)
 - 1.5A Core Supply (91% Efficient)
- ◆ Step-Up DC-DC for Backup Battery
- ♦ 1.25MHz Switching Reduces Component Sizes
- ◆ 100% Duty Cycle for Longer Battery Life
- ◆ Digital Soft-Start
- ◆ 170µA Quiescent Supply Current
- Evaluation Kits Speed Designs



FREE Power Supplies Design Guide—Sent Within 24 Hours! Includes: Reply Cards for Free Samples and Data Sheets

CALL TOLL-FREE 1-800-998-8800 for a Design Guide or Free Sample 6:00 a.m. – 6:00 p.m. Pacific Time



www.maxim-ic.com

Get Price, Delivery, and Place Orders
Online at www.maxim-ic.com

2001 EDITION! FREE FULL-LINE DATA CATALOG ON CD-ROM





Maxim Integrated Products, 120 San Gabriel Drive, Sunnyvale, CA 94086, (408) 737-7600, FAX (408) 737-7194.

Distributed by Maxim/Dallas Direct!, Arrow, Avnet Electronics Marketing, CAM RPC, Digi-Key, Elmo, Nu Horizons, and Zeus.

Distributed in Canada by Arrow and Avnet Electronics Marketing.

MAXIM is a registered trademark of Maxim Integrated Products. © 2001 Maxim Integrated Products

Congratulations
Microwaves and RF
40 Years of Service to the Industry.

WITH THE WORLD'S MOST COMPREHENSIVE MICROWAVE COMPONENT CATALOG, WHERE ELSE WOULD YOU TURN?

Stop taking wrong turns to catalogs that don't have exactly what you want. With over 600 model-packed pages, Narda's catalog presents you with an astonishing range of quality microwave components.

Looking for wireless components? Turn to over 100 pages of them. Or over 100 pages of electromechanical RF Switches and Passive Components...page after page of Active Components...RF Radiation Safety Products ...and Power Meters/Monitors.

To speed your order, most of our models are in stock and ready to go. And with our huge 150,000 square foot manufacturing facility, we can make and ship any component you order in a hurry.

Wouldn't you like to get exactly the model

you want when you want it?
Call **631-231-1700** now for our catalog and the convenient catalog CD that comes with it.

Once you do, everything will turn out all right.



an Communications company

Enter No. 268 at www.mwrf.com

synthesizer that offers a step size of 1 kHz and spurious response of -80 dBc.

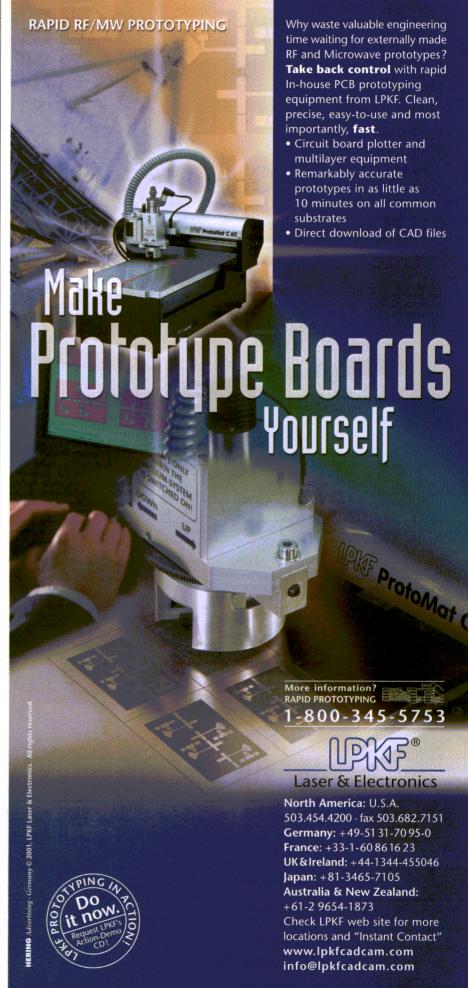
Design Methodology

When designing low-noise, fast-switching synthesizers, the designer must often assess conflicting requirements to create a balanced product. Covering a gigahertz of bandwidth becomes a challenging proposition if the goal is fast switching, particularly if the frequencies covered are in the 5-GHz spectrum. By adhering to a few simple rules, the design process becomes much easier:

- 1. Design in excess margin. Start with 10 dB better phase noise than what is required. This will provide the necessary cushion as the design moves forward.
- 2. Map out an appropriate architecture. This has the largest effect on the design by far, as different architectures accomplish very different roles. Additionally, be sure to analyze the frequency plan for the mixer and other spurious sources.
- 3. Use local voltage regulation for all VCOs. A clean power supply is crucial for a VCO to operate within its specifications. VCOs in reality have three tuning ports: RF $_{\rm out}$, which is subject to load pull (pulling), V $_{\rm cc}$, which is subject to noise modulation (pushing), and, of course, the main tune port. Referring to basic FM modulation theory, noise on the V $_{\rm cc}$ port appears as narrowband FM of the carrier according to the following relationship:

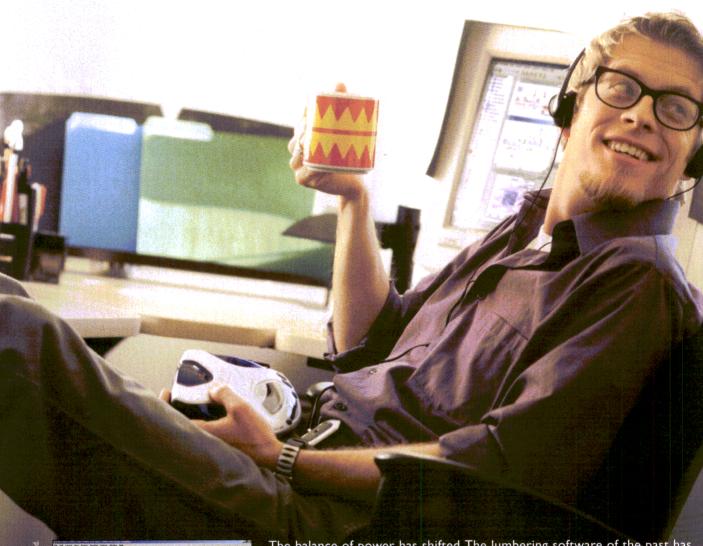
 $L(fm) = 20 \log [KvVnrms \sqrt{2}/(2 fm)]$

For example, assume that a VCO with a 1-MHz pushing specification (a common value) and a phase noise of -100 dBc/Hz at 10-kHz offset has 1- μ VRMS noise on the V_{cc} line. At first glance, this does not appear as excessive noise, but the resulting phase noise at 10 kHz offset will now be degraded to -83 dBc/Hz—which is a significant amount. Additional bypassing would be required to reduce the noise to acceptable levels.





The part of Goliath is now being played by David.



The state of the s

Download a fully-functional 30-day trial (just 20MB) at www.mwoffice.com and start designing today.

The balance of power has shifted. The lumbering software of the past has finally met its match—a more agile, more accurate high frequency design solution. Microwave Office 2001. It can literally double your productivity over legacy design tools. And the precision of its models now makes first-pass success a reality. No EDA software is more powerful or intuitive either.

Simple optimizations are a snap. It's easy to customize. And you get regular timely upgrades. Moreover, our schematic data translators import existing Agilent EEsof designs, so you won't lose any valuable data. For more info, visit www.mwoffice.com or call us at 310-726-3000.

Microwave

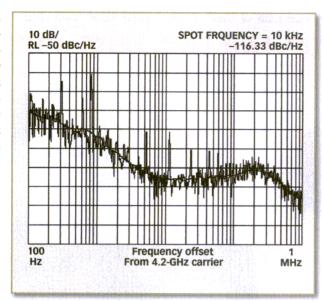
Office 2001

Referring to Fig. 1, the synthesizer contains three loops: a reference loop covering 50 to 150 MHz in 500-Hz steps, a fixed loop covering 1900 to 2100 MHz in 100-MHz steps, and a main loop that uses the other two loops in a mixing/doubling architecture. This architecture minimizes phase noise and spurious response by maintaining a low division ratio.

The reference loop (Fig. 2) provides a lownoise reference that phase noise. steps in small incre-

ments and is essentially free of spurious response. It may be tempting to use a direct-digital-synthesizer (DDS)-based scheme. But for spurious-free performance, a DDS requires extensive filtering and is limited in spurious-free bandwidth due to its sampling-based structure. An alternative approach would be a "mix-and-divide scheme," where successive stages are mixed with fixed carriers and divided down to improve phase noise and spurious response. This is often referred to as "direct analog synthesis."

In the reference loop, a 1000-to-1800-MHz, fractionally based synthesizer is divided down by eight, yielding a 125-to-225-MHz, low-noise source that steps in 8-kHz increments. This is mixed with a 1075-to-2175-MHz synthesizer that steps in 100-MHz steps, yielding a 1200-to-2400-MHz signal that steps in 80-kHz increments. An analysis of this mixing scheme does not show any spurs of consequence (<-65dBc) within ± 5 MHz from the desired carrier, although there are numerous lowand high-order spurs farther out. The higher-order spurs are reduced by using appropriate lowpass filtering, and the resultant signal is then divided down by a factor of 16 (or 32), yielding a 50-to-150-MHz, low-noise signal that steps in 500-Hz increments, with less than



5. This HP 8563E Analyzer plot shows the synthesizer's

-85-dBc spurious response.

This loop (Fig. 3) uses a sampling phase detector (SPD) and three VCOs to generate 1900 to 2100 MHz. A sampling phase detector consists of a steprecovery diode (SRD) capacitively coupled to two back-to-back Schottky diodes, which act as a mixer. The SRD, when properly driven by a 100-MHz source, generates harmonics through several gigahertz. These harmonics mix with the desired carrier (at the Schottky diodes) vielding an intermediate frequency (IF) that is suitable for phase lock. For example, to phase lock the 2100-MHz VCO, the SRD is driven by a 100-MHz signal and generates a 100-MHz comb, which includes a 2100-MHz signal. This 2100-MHz signal is mixed with the VCO's carrier, and the resultant IF signal controls an active loop filter which, in turn, adjusts the VCO's tuning voltage to compensate for phase and frequency fluctuations.

The advantage of using an SPD as opposed to a digital phase detector is the SPD's superior phase-noise characteristics, and the improvement in overall loop gain. A typical SPD-based loop has a noise floor of -155 dBc/Hz at the diodes, and a loop-division ratio of one. This would yield a theoretical noise floor of -127.4 dBc/Hz at 2.1 GHz $([20 \log(2400/100)] - 155)$. Compared



Think Anaren® ... for resistor, termination, and attenuator choices.

You want choices?

Anaren® serves

up plenty in its full line of RF Power resistors, terminations, and attenuators. First, Beryllium Oxide (BeO) or Aluminum Nitride (AlN) — each substrate's thickfilm construction yields a rugged, reliable component that's 100% tested. Second, a plethora of packaging styles, including surface mount, flangeless, flanged, and chip — ideal for a wide range of RF and microwave applications. Finally, power — 5 to 800 watts of output with welded silver contacts for greater conductivity.

Whatever's on your mind, use the reader service number to receive your free Anaren "Thinking Kit." Or email Anaren at rfpresistor@anaren.com.



800-411-6596 > www.anaren.com In Europe, call 44-2392-232392 > ISO 9001 certified

SONET DESIGN SOLUTIONS IT'S WHAT WE DO.

VTDRO

DIELECTRIC RESONATOR OSCILLATORS

- RATES UP TO OC-768
- ULTRA LOW PHASE NOISE
- -115 dBc/Hz @ 100 kHz
- WIDE ELECTRICAL TUNING
- EXCELLENT LINEARITY
- · Low JITTER
- WIDE OPERATING TEMPERATURE RANGE
- Customized Modulation Bandwidth up to 80 MHz



CLOCK & DATA RECOVERY

- · 9.95328 Gb/s & 10.664 Gb/s
- . OTHER DATA RATES TO 12.25 GB/S
- 11 MUI(rms) JITTER GENERATION
- SUPERIOR RESONANCE FILTER CLOCK RECOVERY
- . OPERATES WITH NRZ OR RZ DATA STREAM INPUT
- . COMPLIANCE WITH SONET OC-192 AND SDH STM-64
- WIDE OPERATING TEMPERATURE RANGE

CRO

COAXIAL RESONATOR OSCILLATORS

- RATES UP TO OC-48
- . OPTIMIZED FOR 2.48832 Gb/s
- Phase Noise of -75 dBc/Hz @ 1 kHz
- EXCELLENT FREQUENCY STABILITY
- SURFACE MOUNTABLE
- . SMALL SIZE
- CUSTOMIZED MODULATION BANDWIDTH UP TO 1 MHz

DPLR

CLOCK REGENERATORS

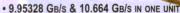
- RATES UP TO OC-768
- FLAT JITTER TRANSFER FUNCTION:
- < 0.1 dB PEAKING
- Low JITTER GENERATION:
- < 10 MUI RMS
- . HIGH JITTER TOLERANCE FOR LOW BIT ERROR RATE
- INTEGER OR NON-INTEGER RELATIONSHIP BETWEEN
 INPUT AND OUTPUT CLOCK
- SEAMLESS TRANSITION FROM MASTER TO SLAVE OPERATION



- GET THE PROPER JITTER TRANSFER
 - MINIMIZE JITTER GENERATION
- GET SEAMLESS TRANSITION FROM MASTER TO SLAVE OPERATION

CR-9095 DUAL CLOCK RECOVERY





- SELECTABLE DATA RATE
- . DATA RATES TO 12.25 Gb/s
- SUPERIOR RESONANCE FILTER CLOCK RECOVERY
- SUPERIOR JITTER PERFORMANCE
- WIDE OPERATING TEMPERATURE RANGE

CALL THE EXPERTS



Enter No. 227 at www.mwrf.com

9 Whippany Rd. • Whippany, NJ 07981

TEL: 973-884-2580 • FAX: 973-887-6245

www.cti-inc.com • e-mail: sales@cti-inc.com



to a digital phase detector, this is a 27dB improvement. The disadvantage of an SPD is the requirement for pre-steering the VCO to aid in acquisition. Unlike a digital phase detector that will lock and acquire more than a ± 2 - Π range, the analog phase detector has limited acquisition capability and requires the assistance of an external circuit.

YROS are

fundamental-

mode devices

size, ease, and

speed of tuning

VCO and the

phase-noise

a DRO.

associated with a

characteristics of

that combine the

Main Loop

The goal of the main loop (Fig. 4) is to generate a spurious-free 3.5-to-4.5-GHz signal. As with the fixed loop, an analog phase detector must be used to satisfy the phasenoise requirements. This, however, brings additional problems in signal acquisition. APA Wireless has developed proprietary patent-pending techniques that fully leverage the superior phase-noise characteristics of analog phase detec-

tors with the wide-tuning and acquisition capabilities of digital phase detectors. Referring to the main loop section shown in Fig. 1, the acquisition circuitry will set the YRO to the exact desired frequency in less than 10 µs, and does so in parallel with the other loops, regardless of step size.

Circuit Description

In order to satisfy the phase-noise requirements at offsets that are far from the carrier, a signal source (VCO or YIG) that can cover wide bandwidths, yet maintain good phase noise must be used. Although a YIG would satisfy this requirement, it lacks the frequency agility needed for sub-100μs switching and requires additional circuitry for phase-lock operation. APA developed its line of YROs to address this issue, with phase noise rivaling YIG solutions but without the driver complexity.

Referring to the block diagram that

is shown in Fig. 3, a 1.75-to-2.25-GHz YRO drives a doubler to achieve a 3.5to-4.5-GHz output. Although a 3.4to-4.5-GHz YRO could have been used, the doubled approach offers the following advantages:

• The divider provides isolation between the fixed-frequency loop and the main output. Without the divider. frequencies close to the desired final frequency would have to be mixed into the main loop. These frequencies would

> appear at the main output, and would be virtually impossible to filter or remove.

> • The divider eases the fixed loop-frequency requirement. Half as many frequencies are needed.

The doubled output is then divided by two, and drives a series of isolation amplifiers, which drive a mixer whose RF port is driven by the fixed loop. The resultant IF signal drives the local-oscillator (LO) port of an ana-

log phase detector whose RF port is driven by the reference loop. In this way, the reference loop provides fine frequency control over 100-MHz bandwidths, with the fixed loop incrementing the coarse frequency in 100-MHz steps.

Since the phase noise of the YRO is -130 dBc/Hz at a 100-kHz offset and the noise floor of the fixed loop is -128dBc/Hz, the loop-bandwidth crossover point for phase noise is set at the 100kHz point. Of course, since the fixed loop sets the noise floor for this architecture, improvements in this area will yield better phase noise, up until the limit that is set by the reference loop (-140)dBc/Hz at 100-kHz offset). The doubled output is filtered in order to remove subharmonics, then drives an automatic-gain-controlled (AGC) final amplifier.

Figure 5 is a phase-noise plot (using an HP 8563E spectrum analyzer) of the output of the previously described synthesizer at 4.2 GHz—clearly at the limits of the analyzer. MRF



Think Anaren® ... for couplers that double up on power.



Want a higher

return on your amplifier investment?

The Anaren® RF Power line of surface mount directional and 90 degree hybrid couplers includes 200-watt versions that yield twice the power of any other components in their class. Designed with continuous-edge plating for better ground path and enhanced connectivity, the RF Power 200- and 100-watt coupler family is constructed from woven, Teflon®-based materials for more stability and low loss. And the couplers are ideal for AMPS. GSM, PDC, DCS, PCS, UMTS, W-LAN, and MMDS applications.

Whatever's on your mind, use the reader service number below to receive your free Anaren "Thinking Kit." Or email Anaren at rfpcoupler@anaren.com.



800-411-6596 > www.anaren.com In Europe, call 44-2392-232392 > ISO 9001 certified Visa/MasterCard accepted (except in Europe)

Enter NO. 405 at www.mwrf.com

RF

Looking for "major savings" on high-performance RF switches?

Switch to ANADIGICS' AWS series from Richardson Electronics!

- High Linearity/Isolation
- Low Loss
- Small Footprint
- Low-cost plastic & chip-scale packages
- GaAs (MOSFET & pHEMT)

Applications

- Transmit/receive switching
- Diversity switching
- Antenna selection
- Filter selection

Call Richardson Electronics to get the best prices on switches.

Call 1-800-737-6937
to find out how
Richardson can
support your wireless
and microwave
programs or visit
www.rfpowernet.com

ANADIGICS Part Number	Alpha Equivalent	Type	Frequency Range (GHz)	Insertion Loss [*] (dB)	Isolation*	IP3 (dBm)	Control Voltage Differential Min/Max (V)	Package
AWS5502	scall-in m	SPDT	DC-2.5	.40	20	+45	3.0/8.0	SOT-26
AWS5503		SPDT	DC-3.0	.55	22	+55	5.0/8.0	MSOP-8
AWS5504	AS139	SPDT	DC-2.0	.35	17	+55	5.0/8.0	SOT-26
AWS5506		SPDT	DC-2.5	.40	20	+45	3.0/8.0	SOT-26
AWS5508	AS166	SP4T	DC-2.0	.80	25	+60	2.5/6.0	MLP-16
AWS5513	AS179	SPDT	DC-2.5	.50	28	+48	2.7/6.0	SOT-363
AWS5516	AS178, AS182	SPDT	DC-2.0	.35	32	+55	2.7/6.0	SOT-26
Specification	s provided above a	re for ANA	DIGICS' products.	Performance a	nt 1GHz.		pterpost countries and some CO Section (SEC) SEC SECTION (SECTION SECTION SECT	







More than 60 locations worldwide to serve you. E-mail: rwc@rell.com, Internet: www.rfpowernet.com, Toll Free: 800-RF Power or 800-737-6937 (U.S. & Canada), Australia: Castle Hill ACN 069 808 108 +61 (2) 9894-7288, Bayswater ACN 19 069 808 108, +61 (3) 9738-0733, Brazil: Sao Paulo +55 (11) 3845-6199, Rio De Janeiro +55 (21) 521-4004, China: Shanghai +86 (021) 6440-0807, Shenzhen +86 755-329-7141, Colombia: Sante Fe de Bogota, DC (57-1) 636-1028, Demmark: Hedenhusene +45 4655-5630, France: Colombias Cedex +33.1.55.66.00, 30, Nozay +33.1.69, 80.71.33, Germany: Puchheim +49 (89) 890 214-0, Hamburg +49 (40) 555 88 410, Italy: Agrate (MI) +39 (039) 653 145, Roma +39 (06) 41.73.37.51, Sesto Fiorention (FL) +39 (055) 42.08.31, Japan: Osaka +81 (6) 6314-5557, Tokyo +81 (3) 5215-1577, Korea: Seoul +82 (2) 539-4731, Malaysia: Selanger +60 (3) 5511-5421, Mexico: Nexico City +52 (5) 674-2228, Guadalajara +52 (3) 645-4641, Philippines: Pasig City +63 (2) 636-8891, Singapore: +65 487-5995, Spain: Barcelona +34 (93) 415 8303, Madrid +34 (91) 528 3700, Sweden: Stockholm +46 8 564 705 90, Taiwan: Taipei +886 (2) 2698-3288, Thailand: Bangkok +66 (2) 749-4402. The Netherlands: Amsterdam +31 (20) 446 7070, United Kingdom: Slough +44 (1753) 733010, Vietnam: Ho Chi Minh City +84 8-8233016. For other international inquiries call Corporate Headquarters: LaFox, IL (630) 208-2200, Fax (630) 208-2550. © 2001 Richardson Electronics MK2080

1-800-RFPOWER

1-800-737-6937

www.rfpowernet.com

rwc@rell.com



Wideband VCO Designs Are Independent Of Circuit Parameters

A set of generalized tuning parameters helps speed the design of various types of wideband voltage-controlled oscillators with either bipolar or FET devices.

oltage-controlled oscillators (VCOs) are important components in a variety of RF and microwave systems, including broadband measurement equipment, wireless and TV applications, as well as military electronic-countermeasures (ECM) systems. In many applications, particularly ECM, system performance improves significantly when VCOs have wide tuning bandwidths using linear varactor tuning,

and high-speed switching characteristics. Only varactors support this high-speed frequency agility while affording small size and more than octave-tuning bandwidths. The recent progress in transistor technology has ensured significant improvement of a VCO's frequency and power characteristics. It is known that the common-base and common-collector connections of a bipolar transistor are the most effective to realize wide VCO frequency-tuning. Varactor properties of fast settling time

and low post-tuning drift make wideband hybrid and

monolithic bipolar VCOs suitable for modern ECM systems, such as frequency-agile local oscillators (LOs) in receiver (Rx) systems and fast-modulation noise sources in active jamming systems.^{2,3}

Gallium-arsenide (GaAs) field-effect transistors (FETs) are another option for designing wideband VCOs. A typical wideband GaAs FET microwave VCO circuit consists of a common-gate transistor with a gate series inductance and two hyperabrupt varactors connected to the gate and source terminals, respectively.²

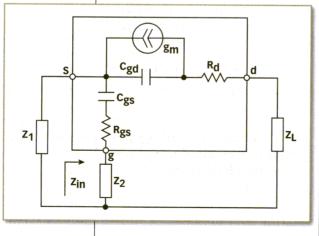
This article offers an analysis of wideband VCO properties in different frequency ranges when bipolar or FET devices are used. The tuning-bandwidth parameters are provided in a generalized form that contributes to faster design procedures for wideband VCOs, regardless of their specific parameters. Also, small-signal circuit analysis and practical examples are presented in the article.

For an analytical evaluation of the

DR. ANDREI GREBENNIKOV

M/A-COM Eurotec Operations Skehard Rd., Blackrock, Cork, Ireland +353-21-4808906, FAX: +353-21-4808357, e-mail: agrebennikov@tycoelectronics.com

1. The equivalent circuit of a common-gate MOSFET VCO shows the device's drain-to-source capacitance, C_{ds} and gate-to-source capacitance, C_{gs}.



Microwave

Sprague-Goodman has passive and active tuning devices to meet microwave designers' needs. A wide variety of tuning elements is offered to work with waveguides, cavities, and dielectric resonators at frequencies too high to use variable capacitors and inductors.

Sapphire **PISTONCAP®**

- O to 4000 at 250 MHz
- · 2 configurations and 6 mounting styles suitable for all RF structures
- Operating temp: -55° to +125°C
- Cap ranges: 0.3-1.2 pF to 0.8-8.0 pF

AIRTRIM® Air Dielectric **Multiturn Trimmers**

- Q: > 5000 at 100 MHz
- · 9 mounting styles including surface mount
- Operating temp: -65° to +125°C
- Cap ranges: 0.35-3.5 pF to 2.0-16.0 pF

Microwave Tuning Elements

Metallic tuning elements

2 to 33 GHz

Dielectric tuning elements

- · Alumina, quartz, sapphire
- 6 to 100 GHz

Dielectric resonator tuners

2 to 18 GHz

LC tuning elements

Resistive tuning elements

• 1 to 18 GHz

Silicon Tuning Varactors

Super Hyperabrupt

UHF - Wireless (4V, 6V, 8V)

• VHF - Wireless (10V)

Hyperabrupt

Microwave (20V)

Abrupt (20V)

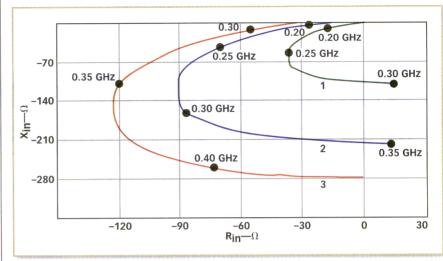
Economical SOT-23 and High Performance Surface Mount Packages

For information on these and our other quality products, visit our website, or phone, fax or write today.



1700 Shames Drive, Westbury, NY 11590 Tel: 516-334-8700 • Fax: 516-334-8771 www.spraguegoodman.com

DESIGN



2. These theoretical impedance curves for the circuit of Fig. 1 illustrate how the input resistance varies with the input inductance, L and load inductance L_L.

tuning range of a metal-oxide-semiconductor-FET (MOSFET) VCO resonant circuit, it is often sufficient to consider the simple device-equivalent circuit, especially when the operating frequencies are not very high. In Fig. 1, the common-gate MOSFET-VCO equivalent circuit is shown where $Z_1 = 1/j\omega C$ is the capacitive source feedback impedance, $Z_2 = j\omega L$ is the inductive gate impedance, and $Z_L = R_L + j\omega L_L$ is the load impedance. Since the device-feedback capacitance C_{gd} is usually much smaller than the device input capacitance Cgs, it is possible to neglect its influence on the VCO characteristic, which simplifies the analytical calculations significantly.

The start-up conditions for this oscillator can be written by:

$$Re Z_{in} < 0 (1)$$

$$Im(Z_{in} + Z_I) = 0 (2)$$

where input impedance Zin is determined through the device small-signal common source Y-parameters by:

$$Z_{in} = I + Y_{11}Z_2 + (Y_{22} + Z_2\Delta Y)Z_L / Y_{11} + Y_{12} + Y_{21} + Y_{22} + \Delta Y(Z_2 + Z_L)$$
(3)

Substituting the small signal Yparameters expressed through the parameters of the MOSFET equivalent circuit into Eq. 3 yields:

$$Z_{in} = (1 - \omega^2 C_{ds} L_L)$$

$$(1 - \omega^2 C_{gs} L) -$$

$$\omega^2 C_{ds} C_{gs} (R_L + R_d) R_{gs} + /$$

$$g_m - \omega^2 C_{ds} C_{gs} (R_L + R_d + R_d) + +$$

$$R_{gs}) + \rightarrow$$

$$j\omega \Big[\Big(1 - \omega^2 C_{gs} L \Big) C_{ds} \Big(R_L + R_d \Big) +$$

$$\Big(1 - \omega^2 C_{ds} L_L \Big) C_{gs} R_{gs} \Big] /$$

$$j\omega \Big[C_{gs} + C_{ds} -$$

$$\omega^2 C_{gs} C_{ds} (L + L_L) \Big]$$
(4)

Figure 2 illustrates the theoretical impedance curves with frequency as the independent variable for different values of the input and output inductances L, L_L , and R_L = 50 Ω

where:

curve 1: L = 200 nH and $L_{L} = 50 \text{ nH}$; curve 2: L = 200 nH and $L_{I} = 0 \text{ nH}$;

curve 3: L = 100 nH and $L_L = 0 \text{ nH}$. An RF MOSFET device with a 5-μm gate length and the small-signal parameters of its equivalent circuit, $g_m = 27$ S, $C_{gs} = 5 \text{ pF}$, $R_{gs} = 25 \Omega$, $C_{ds} = 3.6 \text{ pF}$, $R_d = 70 \Omega$ were chosen. These relationships show that for decreasing values of the inductances L and L_L, the input resistance R_{in} becomes more negative in the frequency range of 200 to 400 MHz. Also, a decrease of the load inductance L_I indicates that the negative-resistance frequency range moves

Customers of Agilent HFSS...

Ansoft is the home of HFSS. With the purchase of Agilent's HFSS, Ansoft has become THE inspiration for true 3D High-Frequency electromagnetic design.

Ever since Ansoft delivered the first commercially available version of HFSS to the microwave market in October 1990 through Hewlett-Packard, we have continued to pioneer the world's leading technology for 3D High-Frequency electromagnetic simulation. We've never stopped innovating and neither should you.

Whether your designs drive next generation technology within the Microwave/RF, Antenna, IC or PCB industry, make HFSS your home.

Enter No. 216 at www.mwrf.com

For more information contact us at

+1-412-261-3200 or send e-mail

to info@ansoft.com

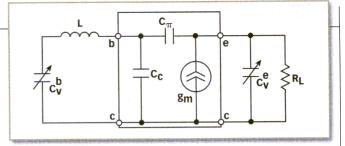
Welcome!



www.ansoft.com

DESIGN

4. This is the equivalent circuit of a bipolar common-collector VCO showing the interterminal capacitance and a current source represented as small-signal transconductance g_m.



in the direction of higher frequencies. The feedback inductance L appears also to have this effect, but in practice, it does not influence the width of the frequency range over which there is negative resistance.

Figure 3 shows the practical realization of this common-gate MOSFET VCO using two hyperabrupt varactors with $K_c = 10$, where K_c is the varactor capacitance ratio, and C_{vmin} = 2 pF. This achieves the output power of 17 ± 5 dBm in the tuning bandwidth of 170 to 390 MHz with varactor biasing in the range of +0.4 to +30 VDC. The variable capacitance connected to the device-source terminal provides the phase-balance condition over the entire varactor-tuning bandwidth. As a result, despite some design simplification, the experimental results are in very good agreement with the theoretical tuningbandwidth evaluation using the device's small-signal parameters.

A Common-Collector VCO

An analytical evaluation of a bipolar VCO resonant circuit begins with the simple equivalent circuit presented in **Fig. 4** where the collector terminal is common and is usually grounded in the

practical realization with a bypass capacitor. The simplified equivalent circuit includes the collector capacitance C_c ; the basemitter capacitance $C\pi$, including diffusion-and junction capacitances; and

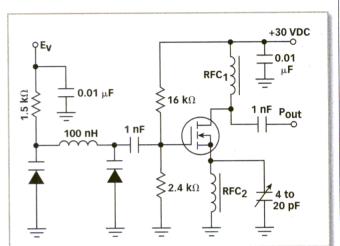
current source described by smallsignal transcon-

ductance g_m . To provide wideband tuning, two varactors— C_v^b and C_v^e —are used in the base and emitter circuits, respectively.

For such a common-collector bipolar VCO, the equation for resonant frequencies in steady-state operation is provided by:

$$\omega^{2}LC_{\nu}^{b}\left(C_{c} + \frac{C_{\pi}C_{\nu}^{e}}{C_{\pi} + C_{\nu}^{e}}\right) = C_{\nu}^{b} + C_{c} + \frac{C_{\pi}C_{\nu}^{e}}{C_{\pi} + C_{\nu}^{e}}$$
(5)

To characterize the VCO band properties, it is convenient to use the generalized functions $K_f(K_{c1} \text{ and } K_{c2})$ where

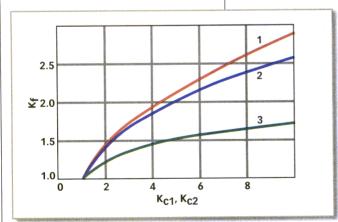


 An actual common-gate VCO uses a pair of hyperabrupt varactors in the gate circuit to obtain the necessary capacitance values to sustain oscillations.

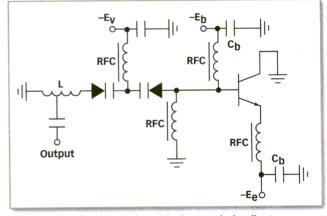
 K_f = the frequency tuning ratio, K_{cl} = C_{vmax}^b/C_{vmin}^b , K_{c2} = C_{vmax}^e/C_{vmin}^c . In a common case, to obtain the results regardless of the particular values of the circuit parameters, the normalized parameters should be used. So, if the following normalized parameters:

 $m_0 = \omega_T C_c / g_{m1}, \, n_0 = 1 + \omega_T R_L C_c, \label{eq:m0}$ and

$$q_1 = C_c/C_{vmin}^b$$
, and $q_2 = C_c/C_{vmin}^e$,

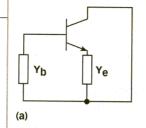


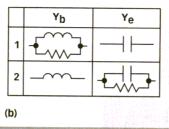
5. Curves 1, 2, and 3 can be used to determine the tuning bandwidth of a common-collector VCO. The largest tuning bandwidth—Curve 1—results from simultaneous varactor tuning of the base and emitter circuits.



6. The implementation of a typical grounded-collector lumped VCO circuit is shown here with back-to-back varactors that are in the base circuit in order to provide tuning over a wide bandwidth.

DESIGN





where g_{m1} is the averaged large-signal transconductance put into operation, and ω_T = the transition frequency, Eq. 5 in a generalized form can be written as:

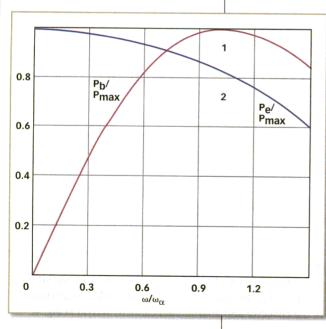
$$K_{f} = \left\{ K_{cl} \frac{\left(l + q_{l}\right)}{\left(q_{l} + K_{cl}\right)} - \frac{\left(m_{0} + q_{2}\right) + \left(m_{0}K_{c2} + q_{2}\right) + \left(m_{0}K_{c2} + q_{2}\right) + \frac{q_{l}K_{c2}\left(l + m_{0}\right) + q_{2}}{q_{l}K_{c2}\left(l + m_{0} + q_{2}\right)} \right\}^{0.5}$$
(6)

In **Fig. 5**, the different functions, K_f , K_{c1} , and K_{c2} for various values of the normalized parameters q₁, q₂, and m₀ = 0.012 are presented. Here, curve 1 is plotted for $q_1 = 1$ and $q_2 = 0.5$ with simultaneous varactor tuning in the base and emitter circuits. Curve 2 is characterized by $q_1 = 1$ and $q_2 = 0.05$ with varactor tuning only in the base circuit when $K_{c2} = 1$. Curve 3 is calculated for $q_1 = 0.1$ and $q_2 = 0.5$ with varactor tuning only in the emitter circuit when $K_{c1} = 1$. A comparison of the curves shows that, for simultaneous varactor changes with $K_c = K_{c1} = K_{c2} = 10$ (in the base and emitter circuits), maximum tuning bandwidth is achieved (curve 1).

7. A common-collector VCO (a) can be designed with different combinations of admittances in the base and emitter circuits (b).

Using varactors in the base circuit only (curve 2) yields a larger tuning bandwidth than in the case of varactor tuning only in the emitter circuit (curve 3). In this case, decreasing q_2 and increasing q_1 can increase the tuning bandwidth. To increase the tuning bandwidth with only an emitter varactor, it is necessary to reduce the parameter q_2 to its optimum value of 1. The change of the parameter n has no essential effect upon tuning bandwidth.

Figure 6 shows a typical fundamental grounded-collector lumped VCO circuit where two back-to-back varactors provide wideband tuning and output power is dissipated in the load conductively connected to a resonant circuit inductance. The RF chokes (RFCs) and bypass capacitors (C_b) form a DC-coupled lowpass filter that is intended to pass power-supply inputs and modulation frequencies, while having high impedance at the fundamental frequency to minimize direct leakage through the bias circuits. Using abrupt varactors with a



illustrate the power versus frequency response of the circuits shown in Fig. 7b, cases 1 and 2. Tuning over a wide frequency range is possible using a variable-series inductor in the base circuit (shown in Fig. 7b, case 2) as shown by curve 2.

8. Curves 1 and 2

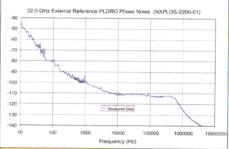
Experience the Nexyn Innovation

QUIET!

No and PRECISE

Per 22 GHz Phase Locked DROs

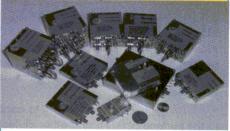
New Products Details on website



Phase Noise at 22 GHz (Typical)

100 Hz - 80 dBc/Hz 1 KHz -100 dBc/Hz 10 KHz -110 dBc/Hz 100 KHz -112 dBc/Hz 1 MHz -127 dBc/Hz

- Free Running/Phase Locked DRO
- Reliable and Rugged Design
- Extremely Low Microphonics
- 10-200 MHz External Reference
- Frequency: 3 to 23 GHz
- Power output: +10dBm
- · Spurious: -80 dBc
- -10 to +65 C (wider range options)
- Internal Ref/Dual Loop options
- Now offering PLO .3 to 3 GHz
- Low Noise crystal reference



<u>Nex</u>yn

Nexyn Corporation 1089 Memorex Dr. Santa Clara, CA 95050

Tel: (408) 982-9339 Fax: (408) 982-9275

Visit our website at www.nexyn.com

Excellent Technical Support Guaranteed Performance and Competitive Pricing (Seeking Sales Reps)



...for materials and processing of antenna circuits!

Materials...



NorCLAD™ PPO based laminate material. dK: 2.55. Dissipation: .0011 @ 3 GHz. NorCLAD costs 10% to 50% less than materials of comparable performance.



POLYGUIDE™ Low cost, low loss substrate used in construction of high performance commercial microwave antenna products. dK: 2.32 ...similar to

other popular laminates. Dissipation: .0002...superior to other comparable constructions. Ideal for moderate temperature commercial applications.

Antenna Design by Seavey Engineering. Material and process by Polyflon.



Pure PTFE substrate electroplated with copper.
Dissipation: .00045 (measured from 1 GHz to 18 GHz). dK; 2.1.

Services...

- Circuit Processing Expert fabrication of high performance circuit boards and panels up to 24"x58", from .003" to .125" thick. Plus, quick turn around of your design.
- **Plating** In-house capability to copper plate directly to the surface of PTFE and other dielectrics.
- **Machining** An array of CNC, custom machining or forming. Our experience in molding, plating, and machining PTFE and other high performance plastics is unsurpassed in the industry.

Only Polyflon can do it all!

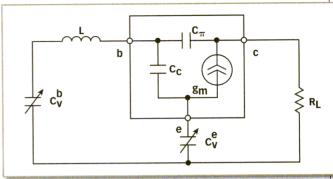


CRANE® POLYFLON

Polyflon Company,
One Willard Road, Norwalk, CT 06851
Tel: (203) 840-7555, Fax: (203) 840-7565
Modem: (203) 840-7564, Email: info@polyflon.com
Internet: http://www.polyflon.com

POLYFLON, NorCLAD, POLYGUIDE and CuFlon are registered trademarks of Polyflon Company.

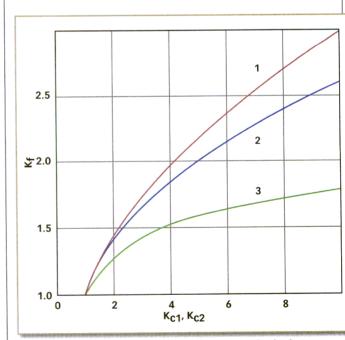
DESIGN



9. This is the equivalent circuit of a common-base VCO showing the interterminal capacitances and the capacitances of the varactors in the base and emitter circuits.

capacitance ratio, $K_c = 3$, in a bias-voltage range of 0 to +5 VDC with minimum capacitance $C_{vmin} \sim 0.6$ pF, it follows from curve 2 in Fig. 5, that it is possible to provide the wideband tuning in a frequency range with $K_f \ge 1.6$. Taking into account that the equivalent device-output capacitance $C_t = 1.5$ pF, the frequency-tuning bandwidth of 5.5 to 8.0 GHz is realized when tank inductance L = 1.9 nH.

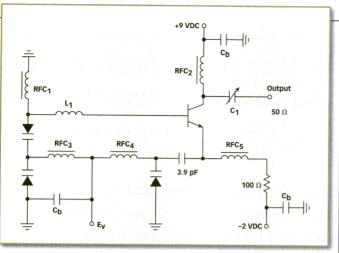
However, for the common-collector VCO, the conductive-load connection is not the only way to realize the maximum output-power level. It is very important to provide minimum flatness over the entire tuning bandwidth. Another approach that is advisable is to connect the load to the emitter terminal, thus decreasing the influence of the load impedance on the resonant circuit that enables the realization of its higher quality factor (Q). **Figure 7a** provides the simplified common-collector VCO schematic and **Fig. 7b** shows two possi-



10. Curves 1, 2, and 3 are plotted for varactors in the base and emitter circuits, base circuit only and emitter circuit only, respectively. The bandwidth can be controlled by the values of the collector and emitter capacitances shown in Fig. 9.

DESIGN

11. An implementation of the circuit of Fig. 9 uses hybrid integrated circuits (ICs) and hyperabrupt varactors in the base and emitter circuits to provide the tuning.



ble combinations of the admittances in the base and emitter circuits. In the first case, the load is connected to the resonant circuit conductively or inductively provided the impedance in the emitter circuit is capacitive. The second combination requires inductive impedance in the base circuit when the load is connected in parallel to the device emitter and collector terminals.

In **Fig. 8**, the calculated functions of the normalized output power versus normalized frequency for these two cases are shown. In case 1, the load is connected to the base circuit and the maximum output power occurs when $\Omega = \Omega_{\alpha}$. In case 2, the output power comes from the device emitter and its level changes negligibly up to $\omega = 0.5~\omega_{\alpha}$. As a result, in the latter, the VCO can tune easily in a very-wide frequency range through simple tuning of the series inductance in the base circuit using a varactor diode in reverse-bias

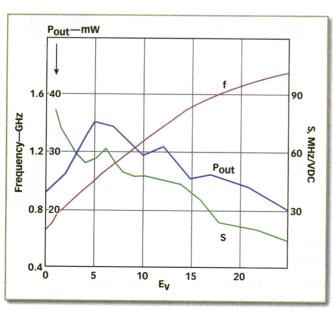
operation. And it should be noted that the series or parallel resistance-capacitance (RC) circuit with constant capacitance and load could realize the capacitive impedance in the emitter circuit.

A Common-Base VCO

In **Fig. 9**, the schematic of the commonbase VCO with varactors in the base and emitter circuits is shown. The resonant frequencies can be found from:

$$\omega^{2}LC_{\nu}^{b}\left[1+\frac{C_{\nu}^{e}}{C_{c}}+\frac{\omega_{T}C_{\nu}^{e}}{g_{ml}}(1+g_{ml}R_{L})\right] = \left(1+\frac{\omega_{T}C_{\nu}^{e}}{g_{ml}}\right)\left(1+\frac{C_{\nu}^{b}}{C_{c}}+\frac{C_{\nu}^{e}}{C_{\nu}}+C_{\nu}^{b}}{G_{c}}g_{ml}R_{L}\right)$$
(7)

12. These curves show the power and frequency performance of the circuit in Fig. 11 as a function of the tuning varactor bias voltage E_v. The curve labeled S is the maximum to-minimum tuning slope (S_{max}/S_{min}) of the circuit.



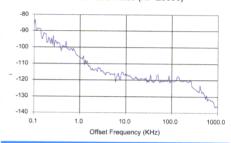
Experience the Nexyn Innovation

QUIET!

Now ing and PRECISE

New Products! Details on website

13.2 GHz Phase Noise (HP E5500)



Phase Noise at 13.2 GHz (Typical)

100 Hz - 86 dBc/Hz 1 KHz -106 dBc/Hz 10 KHz -118 dBc/Hz 100 KHz -122 dBc/Hz 1 MHz -135 dBc/Hz

- Free Running/Phase Locked DRO
- Reliable and Rugged Design
- Extremely Low Microphonics
- 10-200 MHz External Reference
- Frequency: 3 to 23 GHz
- · Power output: +13dBm
- Spurious: -80 dBc
- -10 to +65 C (wider range options)
- Internal Ref/Dual Loop options
- Now offering PLO .3 to 3 GHz
- Low Noise crystal reference



Nexyn Corporation 1089 Memorex Dr. Santa Clara, CA 95050

Tel: (408) 982-9339 Fax: (408) 982-9275

Visit our website at www.nexyn.com

Excellent Technical Support
Guaranteed Performance and
Competitive Pricing
(Seeking Sales Reps)



High Performance Electromagnetic and Network Simulation and Optimization Tools

From: Zeland Software, Inc., 39120 Argonaut Way, PMB 499, Fremont, CA 94538, U.S.A., Phone: 510-623-7162, Fax: 510-623-7135, E-mail: zeland@zeland.com, Web: http://www.zeland.com

Products:

IE3D Planar and 3D Electromagnetic Simulation and Optimization Package

FIDELITY Time-Domain FDTD Full 3D Electromagnetic Simulation Package

MDSPICE Mixed Frequency Domain and Time-Domain SPICE Simulator

COCAFIL Cavity coupled wavguide filter synthesis package

LINMIC Microwave Network Simulator from Jansen Microwave GmbH

Applications:

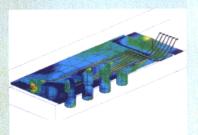
Microstrip, CPW, striplines, suspended-strip lines, coaxial Lines, rectangular waveguides, high speed digital transmission lines, 3D interconnects, decoupling capacitors in digitial circuits, PCB, MCM, HTS circuits and filters, EMC/EMI, wire antennas, microstrip antennas, conical and cylindrical helix antennas, inverted-F antennas, antennas on finite ground planes, and other RF antennas.

Important Announcements:

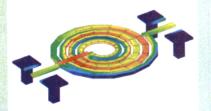
- The IE3D Release 7 has robust and efficient advanced symbolic electromagnetic optimization.
- The FIDELITY Release 3 has complete SAR analysis features for the wireless applications.
- The IE3D with precise modeling of enclosure will be added soon. The IE3D has been known for its
 open structure formulation and its flexibility and capability in modeling 3D and planar structures of
 general shape. The implementation of enclosure will make the IE3D more flexible in the modeling of
 microwave circuits and antennas. Microwave designers will no longer be locked to a uniform grid for
 enclosed structures.

IE3D Simulation Examples and Display

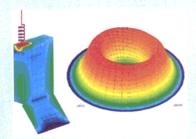
The current distribution on an AMKOR SuperBGA model at 1GHz created by the IE3D simulator



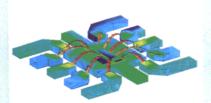
IE3D modeling of a circular spiral inductor with thick traces and vias



The current distribution and radiation pattern of a handset antenna modeled on IE3D

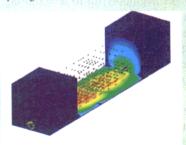


IE3D modeling of an IC Packaging with Leads and Wire Bonds

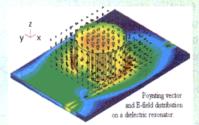


FIDELITY Examples

The near field and Poynting vector display on a packaged PCB structure with vias and connectors



FIDELITY modeling of a cylindrical dielectric resonator and the Poynting vector display



Zeland Software, Inc. provides excellent technical support and services.

Zeland Software, Inc. is also the north American exclusive representative for the LINMIC product from Jansen Microwave GmbH

DESIGN

In generalized form, Eq. 7 can be written as:

$$K_{f} = \left\{ K_{cl} \frac{q_{2} (q_{1} + n_{0}) +}{q_{2} (q_{1} + n_{0} K_{cl}) +} \right.$$

$$\frac{q_{1} (n_{0} + m_{0}) + m_{0}}{q_{1} K_{c2} (n_{0} + m_{0}) + m_{0} K_{cl} K_{c2}}$$

$$\left[\frac{q_{2} + K_{c2} (n_{0} + m_{0})}{q_{2} + n_{0} + m_{0}} \right]^{0.5}$$
(8)

In **Fig. 10**, the functions K_f , K_{c1} , and K_{c2} for various values of the normalized parameters q_1 , q_2 , and $m_0 = 0.012$ and $n_0 = 1.6$ are presented. A comparison of the curves shows that, for the simultaneous varactor change with $K_c = K_{c1} = K_{c2} = 10$ in the base and emitter circuits, a threefold frequency overlapping (curve 1: $q_1 = 1$ and $q_2 = 0.5$) has been achieved. At the same time, the bipolar VCO with varactors only in the base circuit (curve 2: $q_1 = 1$, q_2 = 0.05, and K_{c2} = 1) is characterized by greater sensitivity to the varactor capacitance change than the emitter varactor VCO configuration (curve 3: q_1 = 0.1, $q_2 = 0.5$, and $K_{c1} = 1$). For the purpose of frequency-bandwidth widening, it is advisable to reduce q₂ and to increase q₁. The influence of the parameter n is negligible and cannot be taken into consideration.

In Fig. 11, the practical L-band bipolar VCO electrical circuit manufactured using hybrid-integrated technology is presented. To provide wideband tuning, silicon (Si) hyperabrupt varactors with a minimum capacitance value C_{vmin} = 1.2 pF and capacitance ratio $K_c > 10$ within a reverse biasvoltage range of 0 to +25 VDC were used. The required value of the base inductance L_1 is realized by using the lead inductances of the bipolar transistor and varactors. The experimental results are shown in Fig. 12. The minimum VCO output-power ripple is provided with the tuning of the variable capacitor C_1 in limits of 0.5 to 2.0 pF. The tuning varactor bias voltage $E_{\rm v}$ required to tune from 0.65 to 1.76 GHz is 0 to +25 VDC, and the maximum-to-minimum tuning-slope ratio S_{max}/S_{min} is less than 6:1 across the frequency-tuning range.

REFERENCES

1. R.G. Winch, "Very Broadband Bipolar VCO," *Electronics Letters*, Vol. 17, pp. 871-873, November 1981.
2. K. Adams and C. Oxley. "Broadband FET VCO Design." *Elec*

Lers, Vol. 17, Jpl. of Vol. 9, "Broadband FET VCO Design," Electronic Engineering, Vol. 61, pp. S25-S30, February 1989.

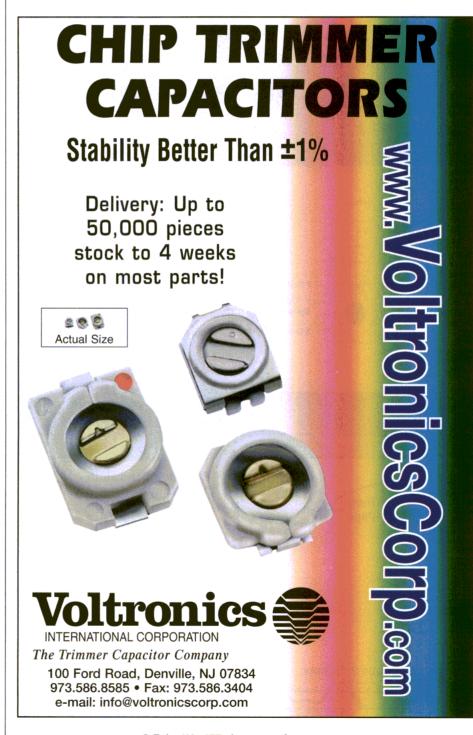
3. R. Beach, "High Speed Linear Oscillators," Microwave Jour-

nal, Vol. 21, pp. 59-65, December 1978

4. A. Shipow, "Linearity in Solid State Microwave Voltage Tuned Oscillators," *Microwave Journal*, Vol. 23, pp. 130-137, February 1983.

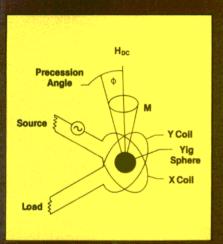
5. H.N. Toussaint and P. Olfs, "Transistor Power Oscillator, Electronically Tunable from 250 to 500 MHz," *Proceedings of the IEEE*, Vol. 56, pp. 226-227, February 1968.

For more Information on this topic, visit us at www.mwrf.com





There are over 1000 various designs available at our facility to choose from



ince 1973, OMNIYIG has been at the forefront of advanced YIG technology manufacturing state-of-the-art YIG components, Detectors and Limiters. The standard products shown here represent a fraction of our total capabilities. We are always on the critical mission of manufacturing YIGs for EW/ECM/JAMMERS/RADARS/INSTRUMENTS/for Airborne/Space/Shipboard.

OMNIYIG's products are built under stringent military specifications (MIL-E-5400) Class II/MIL-STD-883, typical). Our advanced products are designed into some of the world's most sophisticated EW and ECM Programs, including the ALQ-99, ALQ-117, ALR-172, ALR-56C, ALR-62, ALR-64, ALR-67, ALR-69, APR-39, WLR-8, Rapport III, and we are aboard the F-15, F-16, EA6B, EF111, B-1, B-52, C-130 and more.

Rejection Bandwidth 15 MHz min. Band **Pass** 40 dB min. 8 **Band** Reject Spurious 2 dB max. -3 dB B/W-Ins. Loss. 1.5 dB 100 MHz typ. 1.5 dB tvp 0 Fc 8 GHz

YIG MULTIPLIERS

Omniyiq			
Model No.	*Input Output Freq. (GHz)		Output Power
YM 1001	1-2 GHz	2-13	6 dBm
YM 1002	100 MHz	1-12	-33 dBm
YM 1003	200 MHz	1-12	-28 dBm
YM 1004	500 MHz	1-12	-10 dBm
YM 1026	1-2 GHz	2-18	4 dBm
YM 1027	100 MHz	1-18	-40 dBm
YM 1028	200 MHz	1-18	-34 dBm
YM 1029	500 MHz	1-18	-22 dBm
YM 1087	12 GHz	1-12	-30 dBm

*RF input power on all models 0.6 to 1.0 watts.

DUAL 10-STAGE BAND PASS/BAND REJECT FILTERS

Model #

Model No.	M138	M139	
Frequency Range	2-8 GHz Band Pass	8-18 GHz Band Pass	
Insertion Loss 3 dB Bandwidth No. Stages Off Resonance Isolation	4.5 dB 25-50 MHz 4 70 dB	4.5 dB 25-50 MHz 4 70 dB	
	Band Reject	Band Reject	
30 dB Rejection Bandwidth	15 MHz Min.	75 MHz	
3 dB Bandwidth VSWR	125 MHz Max. 2.1	150 MHz 2.5:1	

M139

FAST SWITCHING - 800 MICROSECONDS FULL BAND TRACKING YIG FILTER/YIG OSCILLATOR WITH INTEGRATED ANALOG OR DIGITAL DRIVERS

The newest design at Omniyig is the integrated Fast Switching Yig Tuned Filter/Oscillator build in multioctave frequency ranges. This is achieved by Omniyig's proprietary fast switching magnetic shell design, and integrated tracking capability between oscillator and yig filter. The units are built to meet the MIL-STD-5450 Specification with the extreme temperature ranges between 55°C to +85°C. Some of the RF Specifications are outlined as follows:

Omniyig Model No.	Frequency Range (GHz)	Filter IL (dB)	Oscillator RF Power (dBm)	Frequency Tracking Between Os./Filter (MHz)	Filter 3 dB BW (MHz)
M129YT0	0.5-2.0	5.5	+17	±5	15-30
M120YT0	2-8	5.0	+17	±7	23-40
M121YT0	8-18	5.0	+17	±8	25-45

Additional RF Performance Specifications:

- cy range is typically 160 MHz above the filter bandwidth. The oscillator frequency can also be to any other frequency requirements. tory adjusted to any other
- b) Pulling Figure (1.25:1 VSWR) is less than 3 MHz.
 c) The Second Harmonic is typically 17 dBc and 14 dBc minimum below fundamental frequency.
 For final specification data sheet, call Omniyig's Sales Department at:



STANDARD COMB GENERATORS

Input Freq. (MHz)	Output Freq. Range (GHz)	Output Power (dBm)
100	0.1 to 18.0	-40
200	0.2 to 18.0	-35
500	0.5 to 18.0	-28
1000	1.0 to 18.0	-18
	Freq. (MHz) 100 200 500	Freq. (MHz)

VIG FILTERS

11011	El El IO		
Omniyig Model No.	Frequency Range (GHz)	Ins. Loss (dB)	Bandwidth at 3 dB (MHz)
2-STAGE	MARK WAR	forest in the	Mary Kork
P102	0.5-1.0	4	17-30
L102	1.0-2.0	3	24-35
S102	2.0-4.0	2.5	25-40
C102	4.0-8.0	2.5	25-40
X102	8.0-12.4	2.5	25-40
Ku102	12.4-18.0	2.5	30-45
3-STAGE	******		
P103	0.5-1.0	5	14-25
L103	1.0-2.0	3.5	20-35
\$103	2.0-4.0	3	20-35
C103	4.0-8.0	3	25-40
X103	8.0-12.4	3	25-40
Ku103	12.4-18.0	3.5	30-45
4-STAGE		erte e	
P104	0.5-1.0	6	12-23
L104	1.0-2.0	4.5	20-35
S104	2.0-4.0	4	20-35
C104	4.0-8.0	4	25-40
X104	8.0-12.4	4	25-40
Ku104	12.4-18.0	4	28-45
DUAL 2-ST	TAGE		
P1022	0.5-1.0	3.5	17-30
L1022	1.0-2.0	3	24-35
S1022	2.0-4.0	2.5	25-40
C1022	4.0-8.0	2.5	25-40
X1022	8.0-12.4	2.5	25-40

2.5

12.4-18.0

Ku1022

30-45

YIG BAND REJECT FILTERS



Omniyig Model No.	odel Range		Loss (max.) dB	
P106RX	0.5-1.0	10	1.5	
L106RX	1.0-2.0	10	1.5.	
S106RX	2.0-4.0	15	1.5	
C106RX	4.0-8.0	20	1.5	
X106RX	8.0-12.0	20	1.5	
KU106RX	12.0-18.0	20	1.8	
M102RX	4.0-12.0	8	1.5	
M103RX	4.0-12.0	10	1.5	
M104RX	4.0-18.0	8	2.0	
M105RX	2.0-8.0	10	1.5	
M107RX	8.0-18.0	20	1.5	





THIN FILM YIG BAND **OSCILLATORS**



- 1-4 GHz. RF power output 20-60 mW. 2nd harmonic 16 dB.
- 1.7-4.3 GHz. RF power output 30 mW. 2nd harmonic 20 dB.
- 4-8 GHz. RF power output 10 mW. 2nd harmonic 15 dB.
- 8-12 GHz. RF power output 10 mW. 2nd harmonic 15 dB.
- 12-18 GHz. RF power output 10 mW, 2nd harmonic 12 dB.
- 2-6 GHz. RF power output 15 mW. 2nd harmonic 12 dB.
- 2-8 GHz. RF power output 10 mW. 2nd harmonic 12 dB.
- 8-18 GHz. RF power output 20 mW
- 6-18 GHz. RF power output 20 mW

Contact Omniyig's sales department for comprehensive specifications, price and delivery information.

3350 Scott Blvd., Bldg. #66 Santa Clara, California 95054-3125 (408) 988-0843 TWX 910/338-7356

Enter No. 271 at www.mwrf.com

JECATS of Microwaves & RF

Forty years is a lifetime for some folks, and a considerable period in the history of an electronics industry. For the microwave industry, as chronicled by 40 years of publication by *Microwaves & RF* magazine, that time was spent in wild growth spurts throughout the 1960s through 1980s, until finally reaching a state of "commercial maturity" in the 1990s through 2001. Yet, as this magazine celebrates its 40th year of publication, the industry is poised for further changes, as many companies eye fiber-optic communications as a potential growth market.

In looking back over four decades, the changes that took place to this industry were

dramatic, including a shift from vacuum tubes to solid-state

devices and from military markets to commercial business.

icrowaves & RF started life under the name MicroWaves, and as an insert section within sister publication Electronic Design of Hayden Publishing Co. (which was founded by Jim Mulholland, Jr.). The first full issue of MicroWaves was issued on March 15, 1962, with Robert Ahrensdorf as publisher, Manfred Meisels as editor, and John Weber as sales manager. Meisels, who guided the editorial content of the magazine through its first decade, contributed a news report to that first issue, on fast-tuning hydraulic magnetrons for jam-proof radar systems. In another story, he noted an increase in microwave papers at the IRE Show, an indication that perhaps a separate microwave technical conference was needed.

The cover story (Fig. 1) for that first issue featured an inverted tunable coaxial magnetron from SFD Laboratories, a subsidiary of Varian Associates (Union, NJ). The device yielded 50-W average power and 100-kW peak output power at Ka-band. Transistors were yet to achieve reliable production levels in 1962, and so tubes dominated the market. Tubes were featured in several other product features, including the X-1100 TWT from Eitel McCullough (San Carlos, CA), with 5-W linear output power from 5.9 to 7.5 GHz, and the N1029 TWT from English Electric Valve with similar output power from 5.9 to 7.2 GHz. In these years prior to the adoption of Hertz (Hz) [after Heinrich Hertz] as the unit of measure for frequency, frequency ranges were listed in cycles per second.



Advertisers for that first issue included Varian Associates (Palo Alto, CA) for klystrons, Sylvania (Mountain View. CA) for silicon varactor diodes. Narda Microwave Corp. (Plainview, NY) for ferrite isolators, Philco (Lansdale, PA) for a microwave diode switch, Hughes Aircraft Co., Microwave Tube Div. (Los Angeles, CA) for miniature S-band travelingwave tubes (TWTs) for space applications, Frequency **Engineering Laboratories** (Asbury Park, NJ) for a microwave tube test set, Microwave Electronics Corp. (Palo Alto, CA) for Ku-band TWTs, AMP, Inc. (Elizabeth-

town, PA) for high-frequency connectors, Phelps Dodge Corp. (New York, NY) for coaxial cables,

Polarad Electronics Corp. (Long Island City, NY) for microwave signal generators, Litton Industries, Electron Tube Div. (San Carlos, CA) for a variety of high-power vacuum tubes, Microwave Associates (Burlington, MA) for waveguide components, Airtron (Morris Plains, NJ) for waveguide components, TRAK Electronics Co. (Wilton, CT) for BWO sweepers, ARRA (Westbury, NY),

The first cover story in MicroWaves magazine featured a tunable coaxial magnetron developed by SFD Laboratories, a subsidiary of Varian Associates.

for coaxial variable attenua-

tors, PRD Electronics (Brooklyn, NY) for signal sources and power meters, Microlab (Livington, NJ) for off-the-shelf microwave components, Raytheon Co. (Waltham, MA) for ferrite circulators and vacuum tubes, and RCA Electron Tube Div. (Harrison, NJ) for a unique "coupled-cavity" magnetron.

The following issue



appeared in June 1962, with a semiconductor on the cover: a very-high-frequency (VHF) silicon multiplier varactor

capable of 100 W at 100 MHz on the cover. The model CK303 diffused-junction diode was developed by Raytheon's Semiconductor Div. (Lowell, MA) for solid-state VHF/ultra-high-frequency (UHF) transmitters. In his editorial that issue, Manfred Meisels celebrated the 25th anniversary of the klystron. By August 19,

ARRA, Inc.

ne of the first advertisers in the first issue of *Microwaves & RF* was ARRA, Inc. (Bay Shore, NY) which, after 44 years in business, is still a loyal advertiser (see inside back cover). The small but thriving company features a strong family atmosphere, with approximately 100 employees devoted to the design and production of literally tens of thousands of different custom coaxial and waveguide passive RF components, such as continuously variable attenuators, phase shifters, power dividers/combiners, directional couplers, waveguide attenuators, assemblies, switches, and terminations. The range of applications for these products includes satellites, earth stations, cellular/personal-communications-services(PCS) networks, radar systems, and medical systems.

ARRA was started in 1957 by Harold B. Isaacson. As with many older microwave companies, ARRA was started on a "wing and a prayer" without external financing. By giving his word to pay the monthly rent, and with a handshake between himself and the landlord, Harold secured a room in Westbury, NY to house the fledgling company. ARRA's initial growth was due to Harold's ingenuity, his talent as an electrical engineer, his imagination, and his willingness to work around the clock. When asked of her early involvement with ARRA, Harold's wife Florence notes that she was involved from the very beginning of the company: "I remem-

ber taking dictation for that first letter to Westinghouse, which helped us get our first customer, Westinghouse."

Harold's ability to achieve the highest quality in a timely fashion formed the foundation for the growth of ARRA. He never accepted the word "impossible" or that something could not be done. By providing the drive and inspiration for his employees, Harold was able to expand the company from its initial small space to the landlord's adjoining

two-story building.

1. ARRA, Inc. (Bay Shore, NY) was founded by Harold Isaacson and is run today by Harold's widow, Florence (right) and son Robert (left).



Harold's son, Robert, now runs the day-to-day operations of the company (Fig.1). Even though his father was busy with a startup business, Robert can remember quality time spent with his father. When Robert was six years old, Harold would take Robert and the family dog to the company on weekends and let the inquisitive boy explore his surroundings. One weekend in particular remains strong in Robert's memory, when he sat next to his father, who was working on ARRA products and Robert was working on his model airplane. The model was similar to the one that his father had piloted for



Who will write the next 40 years of technological advancement?

The same guys who wrote the first 40.

Since 1962, *Microwaves & RF* has chronicled the industry's progress, from klystrons to MMICs, with the passion and the unwavering focus of a truly great publication. Congratulations. Your magazine has graced our desktops with 374 issues, and the entire microwaves field is surely better for it.

May you take us through another 374, and beyond. Because true passion never runs out of ink. **Dreams made real**.



Agilent Technologies



ARRA, Inc.

the US Army Air Force. When Robert ran into snags, his father helped him finish his model. "Even though he was there to do his own work, he was able to help me with that plane, to make it the best possible plane that we could put together," recalled Robert.

That philosophy—to do the best possible job—guided the growth of ARRA over the years and even after Harold's untimely death due to Hodgkin's Disease in April 1968. Robert Isaacson was only 11 years old when his father died, but he had already inherited the older Isaacson's values and ethics.

In January 1968, with high hopes, ARRA was relocated to

a 25,000-square-foot rented building in Bay Shore, NY. Harold Isaacson passed away four months after the move, and the future of the company was suddenly in question. The firm was having trouble meeting its



financial obligations but, despite mourning the loss of her husband and employees Tom Cortese having two children to care for, as well as a home mortgage to meet, Florence Isaacson never doubted that she waveguide products for wanted to keep the company going. "It was a labor of love, and I wanted

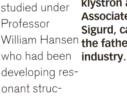
2. Long-time ARRA and Tom Dinnigan are shown preparing some of the company's shipment.

to keep going what Harold had started," Florence says. She devoted herself full-time to solving the company's problems. The first thing she did was to call everyone who was owed money and ensure them that they would be paid as soon as the company solved its cash-flow problems.

Fortunately, each creditor accepted her word, and even thanked her for calling. Many noted that when someone owes money, they are usually difficult to reach, but it is unusual to hear from someone who owes money and to be reassured by them that the debts would be paid. Florence also petitioned the town of Bay Shore to change the name of the street from Ekorb Court (which was "broke" backwards and a developer's idea of humor) to Harold Court. In 1979, Florence ignored advice from lawyers, accountants, and family members and purchased the building.

Florence and Robert attribute much credit for the company's longevity and success over the years to Chief Engineer Ernie Miller, who joined the company as a technician shortly after Harold's death. Miller has been instrumental in designing many of the company's unique coaxial and waveguide components. He is known for his determination and unwillingness to give up or admit that something cannot be done. He is also known for being unable to say "no" to Florence!

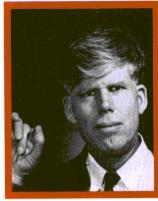
1937, scientist Russell Varian. uraed on by his eneraetic brother Sigurd, developed the first klystron with an operating frequency of 2.3 GHz. While at Stan-Russell had studied under Professor



tures for the production of Xradiation, Hansen, along with Dr. David Webster, head of Stanford's Physics Dept., would team with the Varians to basically start the microwave industry

The second issue also reported on a meeting of the Professional Group on Microwave Theory & Techniques held in Boulder, CO, which featured advances in semiconductors including a 6-GHz paramp from General Motors Defense Systems (Santa Barbara, CA). The meeting also featured a report on a superconducting delay line from Martin-Marietta. The 1200-ft. line exhibited only slight transmission loss at 1 GHz.

One of the more useful articles to appear in that issue was authored by Leo Young of the Stanford Research Institute (Menlo Park, CA), who offered 20 useful Smith chart formulas, including calculations for maximum and minimum conductance and susceptance for a particular reflection



ford University, 2. In many ways, Russell Varian, who developed the klystron and founded Varian Associates with his brother Sigurd, can be thought of as William Hansen the father of the microwave

coefficient. In the same issue, Owen Falor of Raytheon's Spencer Laboratory (Burlington, MA) explained how to select microwave tubes for reliability.

With that June issue, Micro Waves had become a regular monthly magazine, with monthly issues

and supplements through the present. In July, Meisels would write about the Air Force's selection of phasearray technology for nextgeneration radar systems in a news story, and cover the use of optical masers for microwave applications in his editorial. The cover featured a low-noise tunnel-diode amplifier from Micro State Electronics Corp. (Murray Hill, NJ). Based on the company's gallium antimonide tunnel diode, the amplifier achieved a 3.5-dB noise figure at L-band.

In August 1962, a report on the 1962 WESCON show highlighted new tube and parametric amplifier (paramp) developments, but also included a call for papers for the 1963 Professional Group on Microwave Theory & Techniques, to be held May 20-22, 1963 in Santa Monica, CA. The editorial that issue focused on the Telstar communications satellite and how it presented an example of an application other than military for



Xemod 3G QuikPAC™ RF amplifier stages shorten your products' time-to-market.

QuikPACTM surface mount modules can help you shave precious weeks off your 3G amplifier development cycle.

Whether you choose a standard model, a gate-regulated model, or specify your own custom pre-set and compensated bias, QuikPACs eliminate time-consuming stage alignment steps.

They also reduce part counts, allowing you to design simpler, smaller amplifiers that are easier

and more cost-effective to manufacture. And because they're physically interchangeable, you can re-use significant portions of your designs to create entirely new products.

QuikPAC modules are available now in power levels ranging from 25 to 180 Watts. To jump start your 3G amplifier development, call Xemod or visit www.xemod.com—ASAP.



Xemod, Inc. • 3350 Scott Blvd., #49 • Santa Clara, CA 95054 • www.xemod.com • 408-748-7360



ARRA, Inc.

Florence overcame her lack of technical expertise with help from Miller, who possesses more than 33 years of experience and knowledge of ARRA components. Tom Cortese joined the company in 1971, and is now Quality Control Manager (Fig. 2). The company's first salesman, Paul Bleifer, was selling ARRA products for almost two decades until his death in 1977 at the age of 38. The company boasts many loyal employees, with an average time at ARRA of 10.5 years, contributing to the firm's stability, low turnover rate, and continued success.

Florence remembers many times when the dedication and loyalty of her people helped to rescue an otherwise difficult situation. For example, one year before his death, ARRA had qualified Harold's existing design of a 100-dB variable attenuator, but a contract was awarded to a competitor. Several years later the customer, Teledyne, suffered a reliability problem and asked ARRA to bid again. Although this time, ARRA would have to submit its design technique using the competitor's package (since that form factor had been designed into the system). Although this represented a tremendous challenge, "Florence insisted that we could do it," recalls Miller, who was a technician at the time. With Florence's motivation and the perseverance of Miller and the ARRA team, the goal was met and ARRA was awarded several major contracts lasting over a decade. The company is still supplying units for



3. Florence Isaacson's devotion to her husband is symbolized by keeping her late husband's blue 1967 Cadillac because "his hands had been on the steering wheel." The car features a custom cruise control installed by Ernie Miller using a piece of WR229 waveguide as a mount.

the Teledyne system.

At another time, a Marconi order required a special effort. "I gave names to our projects, such as the Duke and the Cyclone, so I would remember them," Florence says. "The Duke was a miniature attenuation trimmer for the Inmarsat satellite. A box of resistors that we needed to complete the job

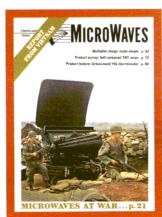
had spilled out on the floor, and it wasn't practical to recover them," Florence recalls. "So I hired a limousine driver to go to New Jersey to pick up another package of resistors from our supplier. We managed to finish the Duke order by the end of the day and meet our delivery date just prior to our Christmas closing," she adds.

"Running ARRA has been good therapy for me," says Florence. "Harold was my hero and the love of my life. We wrote music together—he wrote the music and I wrote the words. In running the company, I feel that we're still writing music together (Fig. 3)."

the microwave industry, and how the industry would benefit from the proper balance of commercial and military markets, rather than focusing on just military business. On the cover, a "centipede" TWT from Sylvania used a slow-wave interaction structure to develop 1.8-MW output power at X-band (8.3 to 10 GHz). An advertisement from Polarad featured a story on the company's mobile calibration laboratory, housed in an air-conditioned van that would travel to different microwave facilities to perform calibration on microwave instruments.

In the design section, Robert O'Nan of Sandia

Corp. (Albuquerque, NM) described the design of super-regenerative microwave receivers (Rxs) and their place in radar systems. Floyd Johnson of Varian Associates explored a procedure for the measure-



ment of very small insertion losses in waveguide, and Harvel Dawirs of the Antenna Laboratory of Ohio State University (Columbus, OH) described how to design impedance-matching transformers using the Smith chart.

The opening advertisement in September, from Varian Associates, was a commemoration of the 25th anniversary of the klystron,

3. The conflict in Vietnam became a proving ground for a number of microwave systems, examined in a special report. with a striking photograph of Russell Varian (1898-1959) by Ansel Adams (Fig. 2). On the cover, a line of frequencv-selective limiters from Watkins-Johnson Co. (Palo Alto, CA) were being promoted as RF-interference (RFI) killers. The C-band limiters, which were made of lithium-ferrite material, could be used from 4.5 to 6.5 GHz. In the design section, Ed Aslan of the FXR Division of Amphenol-Borg Corp. (Woodside, NY) presented guidelines for selecting a swept-signal source.

Through the remainder of that first year, Meisels brought up the theme of millimeter-wave technology,

You'll always get the highest level of reliability with our customized RF power transistors.

It's easy to see why GHz is part of so many avionics, radar and wireless applications, especially compared to ordinary off-the-shelf alternatives. Our customized RF power transistors, fully optimized for your specific project, eliminate endless tuning and rework that can cause productivity to take a nosedive. Plus, ready as we are to help your latest CW applications, we're also committed to providing unending support for pulsed applications. Ready to see more? You'll find us at www.ghz.com or at 408-986-8031, ext. 350. Give us a buzz.



ISO 9001 registered

Copyright © 2001 GHz Technology. All rights reserved.

WE NEVER LET YOU DOWN.



OUR
TRANSISTORS FIT YOUR CIRCUIT,
NOT THE OTHER WAY AROUND.





about the growing number of products for millimeter-wave frequencies, but a lack of applications. A product survey in October by New Products Editor Alan Serchuk offered a roundup of available millimeter-wave tubes. while William Blanchard of Bendix Corp. (Baltimore, MD) offered a nomogram to speed the selection of diffused-junction varactor diodes for multiplier circuits. In November, the theme of new millimeter-wave tubes continued in a special report on tube research, including BWOs with 150-W CW power at 55 GHz from Hughes Research Laboratories (Malibu, CA), An advertisement from Microphase Corp. (Greenwich, CT) presented coaxial filters, couplers, video detectors, and hybrid splitters for use through 10 GHz.

That first year concluded with a spectrum analyzer from General Electric's Light Military Electronics Dept. (Utica, NY) on the cover of the December issue. The instrument operated from 45 MHz to 11 GHz with -40dBm sensitivity, 70-dB total dynamic range, and ± 1 -dB accuracy. Editor Meisels wrote a news story on the development race for GaAs laser-diode devices, including such companies as General Electric and International Business Machines (IBM), while Paul Jensen of Hughes Aircraft Co. (Fullerton, CA) contributed an article on a procedure for designing Cassegrain antennas, and Richard Moore of the University of Kansas (Lawrence, KS) described the acoustic

simulation of radar signal returns for achieving an accurate ultrasonic model of a microwave system.

The cause of millimeter waves was strengthened in 1963 with a January cover story from Westinghouse Electric Corp. (Baltimore, MD) on the model WD4328 tunable varactor-based Ka-band multiplier, which provided coverage from 32 to 38 GHz. A news story detailed plasma tubes as potential alternatives to vacuum tubes, with work being done at Stanford University, Microwave Associates, and Elcon Laboratory (Cambridge, MA). Dick Sparks of Emertron (Silver Spring, MD) reported on microwave phase measurements, and provided a review of the various methods and commercial solutions available for making phase measurements, while Koryu Ishii of Marquette University explained a method for making low-noise measurements with high-noise test equipment, using a novel relative noise-power-measurement technique.

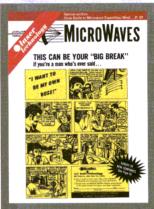
Of significance to future oscilloscope development, the February cover featured a fast coaxial deflection cathode-ray tube (CRT) from Tektronix, Inc. (Beaverton, OR). With a 3-GHz bandwith and 0.13-ns rise time, the tube became the basis for the company's model 519 oscilloscope. That same issue included an article authored by Cliff Moulton of Tektronix (Beaverton, OR) which explained the princi-

4. This cover depicted the trials and tribulations of starting a microwave company. An accompanying special report questioned numerous startup companies on the difficulties and triumphs of their first year in business.

ples of a sampling oscilloscope. The following month,

Murray Feigenbaum of Polarad Electronics Corp. contributed an introduction to spectrum analyzers, explaining how these sensitive Rxs work and the definitions of key operating parameters. An accompanying survey of spectrum analyzers featured products from Polarad, the Panoramic line from Singer Metrics (Bridgeport, CT), and Lavoie.

In May, the magazine explored the world of microwave transistors, including a silicon (Si) device from RCA Semiconductor (Somerville, NJ) with 5 W at 500 MHz and a germanium (Ge) device from Bell Telephone Labs (Murray Hill, NJ) with 1 W at 1 GHz. Research sponsored by the US Army Electronic Research and Development Lab (Fort Monmouth, NJ) would soon be directing the development of a device for 10 W at 500 MHz. At the same time, Fairchild Semiconductor (Mountain View, CA) announced their model 0002 transistor, capable of 1-W output power and 13dB gain at 500 MHz. The transistor consists of four devices on a single wafer interconnected within a metal TO-5 housing. Other manufacturers in the race for



1-GHz transistors included Motorola (Phoenix, AZ) and Texas Instruments (Dallas, TX). Arnold Frisch and Morris Engelson of Pentronix Associates

(Brooklyn, NY) explored five useful measurements that could be performed with a spectrum analyzer, including the analysis of pulsed signals and the measurement of noise figure. This was the first of many articles that Engelson, who would later join Tektronix, would contribute on spectrum analysis.

The remainder of that year included a news report on ultrasonic structures for microwave use, including a YIG rod terminated with coaxial lines capable of coupling in and out signals from 5 to 500 MHz developed by researchers at Bell Telephone Labs; an editorial announcing the first International Microwave Symposium in 1964, in New York City; an article on the application of harmonic generator sources for producing higher-frequency signals by Marion Hines of the Solid State Circuits Div. of Microwave Associates (Burlington, MA); new high-power tubes from Varian and Litton; a solidstate C-band klystron from Fairchild Semiconductor (Mountain View, CA) with single-screw tuning from 5.4 to 5.9 GHz and 10-mW output power; and the introduction of a new magazine department called Laser

NEW MMIC TECHNOLOGY

"At Hittite, our goal has always been clearly defined. We choose to be innovators in our field, rather than followers. And we choose an approach that is revolutionary, rather than merely evolutionary...."



MMDS/WLL
WLAN RFICS
Bluetooth RFICS
UNII & HiperLAN
Cellular Infrastructure
Microwave Systems

Power Amplifiers



DC - 40 GHz Gain Blocks MMW LNA & PA Digital & Analog Attenuators



DC - 15 GHz Low Bit Error Hi Input IP3 Frequency
Dividers
&
Multipliers



DC - 13 GHz Low Phase Noise Single +Supply RF to MMW Mixers



0.7 - 40 GHz Hi LO / RF Isolation Hi Input IP3 Switch & Switch Matrix



DC - 15 GHz Low Insertion Loss Hi Isolation

CONNECTING OUR WORLD
THROUGH INTEGRATED SOLUTIONS!



www.hittite.com

12 Elizabeth Drive Chelmsford, MA 01824 Phone: 978-250-3343 ◆ Fax: 978-250-3373





Technology, recognizing the relationship and importance of laser technology to the microwave industry.

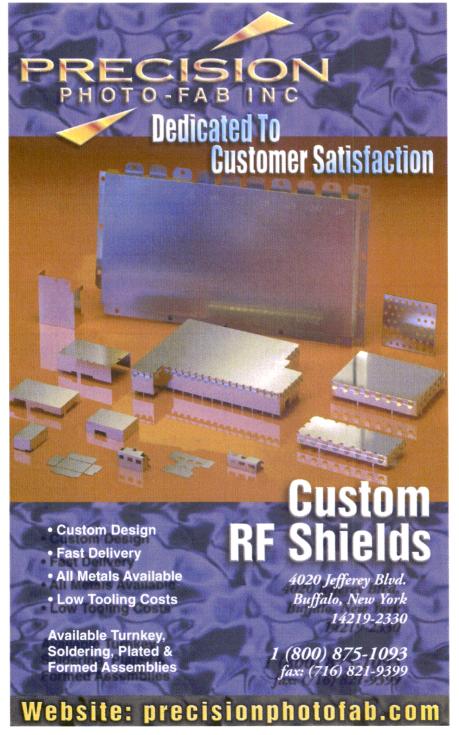
The first issue of 1964 featured the new Laser

Technology section, which would appear on a regular basis within *MicroWaves* for many years. The first installment featured a 240,000-J laser pump from Kemlite

Labs (Chicago, IL). The tube had rise time of 0.3 ms; the 240,000 J was the limit of the capacitor banks. The section also contained a table of laser frequencies, an

article by Richard Daly of TRG (Melville, NY) on measuring laser performance, and an advertisement from Manson Laboratories (Stamford, CT) on a 9-kW pulse modulator with 20-ns rise/fall time. The main cover story that issue was a 1-to-120-dB continuously variable attenuator using coaxial TM mode from Narda Microwave Corp. (Plainview, NY). The component used circular waveguide cutoff sections and symmetrical 3dB hybrids to achieve 1-dB maximum insertion loss from 1 to 2 GHz. In the news, the Naval Research Laboratory (Washington, DC) pushed for the development of microminiature circuitry for VHF/UHF use while, in the design section, Jesse Taub and Harvey Hindin of AIL (Deer Park, NY) addressed the design of quasi-optical components for use at frequencies beyond 300 GHz.

That year saw the continual emergence of solid-state devices, including a 2-GHz Si transistor from Texas Instruments, with 50-mW output power, 12-dB typical gain, and 6-dB typical noise figure at 1 GHz, housed in a TO-18 package. The May cover story offered a YIG-tuned preselector/preamplifier from Watkins-Johnson Co. (Palo Alto, CA), with models covering bands of 1 to 2 GHz, 2 to 4 GHz, 4 to 8 GHz, and 8 to 12 GHz with 80-dB image rejection, 30-MHz bandwidth, and 100-dB gain. That same issue provided a preview of the Professional Technical Group for Microwave Theory and Tech-





niques (PTGMTT) meeting scheduled for May 19-21 at the International Hotel at Kennedy Airport (New York, NY). Additional cover stories featured the model HP 851A/8551A BWO-based spectrum analyzer with 2-GHz bandwidth from 10 MHz to 40 GHz, 60-dB dynamic range, and -100dBm sensitivity from Hewlett-Packard Co., and a complete L-band front end weighing only 2 oz. from Western Microwave Laboratories (Santa Clara, CA), based on high-density solidstate circuitry and dielectricloaded slow-wave structures.

A contributed article from Robert Adams of Sichak Associates (Nutley, NJ) on design opportunities in digital microwave communications, cited that a large share of long-haul communications, particularly for the military would be digital within 10 years. He also noted that digital information would place great demands on the modulation schemes used with microwave transmissions. Also, a news article in July highlighted the acceleration of research on bulkeffect microwave devices, such as hot-carrier and Gunn diodes (named after J.B. Gunn of IBM who discovered the effect of high-voltage fields across a thin slice of ntype GaAs can generate microwave power. This discovery was apparently an accident since Gunn had been plotting the resistance curves of thin material samples and the applied voltage exceeded the oscillation threshold of the material.)

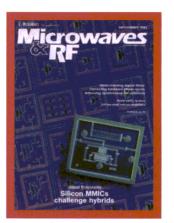
In a ViewPoynt column

 The name MicroWaves was changed to Microwaves & RF for the first time with the November 1982 issue.
 The cover story featured silicon MMICs from Avantek.

that year, Peter Lacy of Wiltron (Mountain View, CA) explained the need for more automated equipment due to the growing sophistication of microwave systems while Bill Bourke, President of Narda Microwave Corp. (Plainview, NY), felt that the growing use of integrated circuits (ICs) would change the requirements for microwave test equipment.

In addition, a study by Hofstra University (Hempstead, NY) predicted that aviation would eventually become the largest commercial market for microwave technology, with annual expenditures of \$130 million by 1970 for air-traffic-control and microwave landing systems. The report also predicted a gradual reduction in defense spending from about \$51 billion in 1964 to approximately \$40 billion by 1970. Statements by former president Dwight D. Eisenhower were cited as evidence for this downward spending trend.

Weinschel Engineering (Gaithersburg, MD) kicked off 1965 with a January cover story on an AGC-stabilized SWR meter capable of measuring VSWR as low as 1.06:1. A news story detailed the Molecular Electronics for Radar Applications (MERA) program sponsored by the Air Force with the intent of developing an all-solid-state, phase-array radar system, a



600-element array, with each element producing 1 W at X-band.

An editorial in February detailed the emergence of miniature coaxial components as a major market area for microwave companies, while the editorial in March would bemoan the lack of a "real" microwave show that was not part of the larger IEEE and WESCON shows. A news story in March would explore the potential growth for microwaves in industrial heating markets, such as processing hops for beer, drying textiles, and producing potato chips. Transistors continued their rise to prominence in an April news story that described the increasing power levels available from microwave transistors, now 1 W at 2 GHz from Texas Instruments and 20 W CW at 400 MHz from RCA. Meanwhile, an advertisement appeared from Fairchild Semiconductor on the model MT-1038, a microwave power transistor with typical efficiency of 50 percent that was capable of 1-W output power at 1 GHz.

In the May ViewPoynt column, Harold Isaacson, founder of ARRA, detailed the changing marketplace in the microwave industry and how there were really two types of competitors: those who made the types of products that your company makes, and the system houses, who must decide whether it makes more sense to purchase a component or to build it themselves. Issacson noted that it was important for microwave companies to make their parts with as much quality and as inexpensively as possible in order to make the decision by the system house one to buy the components from a microwave supplier. Paul Meyerer of Siemens wrote about a new approach to permanent magnet focusing that supported creation of a low-noise magnetic field with much less weight than ellipsoid magnets and that led to the creation of much smaller TWTs.

In August, MicroWaves switched to a smaller trim size $(8.25 \times 11.25 \text{ in.})$ $[20.96 \times 28.58 \text{ cm}]$ and added an antenna-like symbol was added to the left of the logo on the front cover. The news that month covered the gradual shift of millimeter-wave systems from tubes to solid-state devices, while designers Eugene Katz of Grumman Aircraft Engineering (Bethpage, NY) and Heinz Schreiber of Republic Aviation Corp. (Farmingdale, NY) provided design equations for the development of microwave-phase discriminators.

The September cover story unveiled a fundamental transistor oscillator from Fairchild Semiconductor



capable of 200-mW output power at 1.7 GHz without frequency multiplication while the October cover story highlighted YIG technology, with a filter from the Advanced Products Division of Loral Electronic Systems (Bronx, NY), capable of tuning from 1 to 10 GHz with 3dB insertion loss and at least 50-dB rejection of out-of-band signals. The October news section offered a new 7-mm precision connector

specified by the Subcommittee on Precision Coaxial Connectors of the IEEE's Group on Instrumentation and Measurements, capable of low-VSWR operation to 18 GHz. The story also reported plans for a 3.5-mm connector.

In the October ViewPoynt section, Bill Jarvis, President of Wiltron Co. (Palo Alto, CA), discussed how the Vietnam situation was affecting his company, with many inquiries about growth and expanded production capabilities and how there was growing interest in his company's capabilities for producing military-grade test equipment.

In 1966, NASA's projections for deep-space communications required higherpower microwave sources, such as 10 kW CW power in S- and X-bands, Cover stories included the model MA-2016 a miniature UHF TWT from Microwave Associates (Burlington, MA) with 5-W output power from 200 to 400 MHz and weighing only 5.5 lbs.; a pair of Ge transistors with 5.5-dB noise figure at 3 GHz and an \$82.50 price tag, usable to 4 GHz from Texas Instruments; and an X-band sampling scope from HP, with scope displays and time-domain reflectometry possible through 12.4 GHz.

In June 1966, the magazine's first publisher, Bob Ahrensoff, departed in favor of John Weber, who shared publisher's responsibilities with Hayden company president Jim Mulholland Jr. In July of that year, the Depart-



TOME TO YOU!

For PCS, TV,
CELLULAR
and RADAR

3.0 kw

10. kw

Din 7/16

5-1/4 x 5-1/4

(Pk)

Connectors

Fred

Isol/dB mir Ins. Loss dB Max VSWR Power (Av)

		SPECIFICATI	ONS	
	CT-1584-D	CT-1325-N	CT-1615-S	CT-3833-S
q/MHz	170-210	470-860	470-860	2.7-2.9 GHz
	(Full Band)	(4 Units)	(4 Units)	
/dB min	20	20	20	20
Loss				
Max	0.3	0.25	0.3	0.25
VR	1.25	1.25	1.25	1.25

250 w

500 w

2 x 2-5/8

Tabs

100 w

500 w

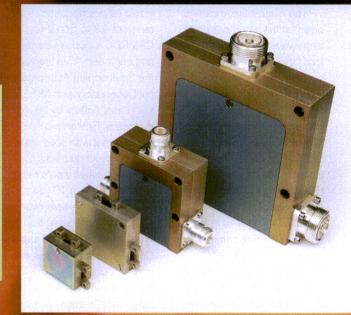
1-1/4 x 1-1/4 x 3/4

Tabs

500 w

1.5 kw

2-3/4 x 2-15/16



With UTE's NEW lineup of isolators and circulators you can pack a lot of high power performance into your designs.

UTE Microwave devices lets you put lots of power thru with minimum loss. Our low loss designs and peak power capabilities help put your products on the cutting edge in critical applications.

Find out more of UTE's total capability - many standard catalog units from stock - special designs to your specs - just visit our website and click www.utemicrowave.com to review our catalog listings. You'll be just a step away from having the technical data - now - and the full support of UTE Engineering.

Contact Len Nilson at: UTE MICROWAVE, INC., 3500 Sunset Ave., Asbury Park, N.J. 07712 PHONE: 732-922-1009 FAX: 732-922-1848 e-mail: info@utemicrowave.com

UTE PRODUCTS:

- Broadband Units
- Common Band Devices
- High Isolation Units
- Multiport Devices
- Drop-In Devices
- Wireless/PCN Devices
- High Power Cellular/Paging
- High Power Industrial/Medical
- TEM/Guide Isolators
- Waveguide Junctions
- High-Power TV Units UHF Devices



Internet: http://www.utemicrowave.com

Enter No. 294 at www.mwrf.com



ment of Defense (DoD) launched MIL-STD-461/462/463, a unified triservice electromagnetic-compatibility (EMC) standard meant to supercede 13 separate documents that were used as EMC standards. The new standard covered conducted emissions, radiated emissions, conducted susceptibility and radiated susceptibility.

The August issue carried news on the world's largest microwave system, at Stanford University, the linear accelerator was two miles long and powered by 240 24-MW S-band klystrons, generating a total of 5760 MW in 2.5-us pulses at 2856 MHz. In September, Boonton Electronics Corp. (Parsippany, NJ) introduced their model 41A microwattmeter, which featured a 70-dB dynamic range from -60 to +10dBm over a frequency range from 1 MHz to 6 GHz. The Business and Defense Services Administration of the Department of Commerce reported that shipments of key microwave components reached \$258 million in 1965, which was up from \$152 million in 1964. Microwave tube shipments increased from 229,000 to 290,000 units, although the dollar volume only increased from \$104 to \$113 million.

In October, a survey of 43 electronic firms conducted by editor Meisels revealed that the average electronic salesman earned \$12,898 per year and brought in \$603,871 of business each year. The average cost was 11.3 cents to sell a dollar's

worth of equipment, and \$48.70 was spent on average for each sales call.

In other news

that year, one story

featured the world's largest radio telescopes, a 500-ft. dish for radio astronomy, being built by the Cambridge Radio Observatory Committee (CAMROC). The dish would have a frequency range of 0.3 to 6.0 GHz. CAMROC includes scientists and engineers from Harvard, the Smithsonian Astrophysical Observatory, and MIT Lincoln Labs. A story by News Editor J.B. Brinton proclaimed that with solid-state devices making steady advances, tubes would need a good market in 10 years, such as in microwave-ovenequipped kitchens. At the time of the story, The Tappan Co. (Mansfield, OH) was the

only producer of home

magnetron in each

microwave oven.

microwave ovens, with a

News in 1967 included a competition between RCA's Missile and Surface Radar Division (Moorestown, NJ) and Sedco Systems (Farmingdale, NY) for the retrofit of the Atlantic Range Instrumentation Ships (ARIS) shipboard monopulse radar system to a phase-array configuration. The Sedco approach is based on the use of waveguide transmission lines while the RCA approach employs coaxial transmission lines but with more phase shifters. That June, a successful Microwave Exposition/67 was held at the New York

6. A chimpanzee graced the January 1983 cover to point out the evolution of millimeter-wave sweep generators from the Millimeter-Wave Products Division of Hughes Aircraft Co. (Torrance, CA). The sweepers operate through 110 GHz.

Coliseum. Donald Cazzens of MITRE Corp.

(Bedford, MA) offered a nomogram for determining the safe distance from highpower microwave sources. WESCON 67 was held that year in San Francisco, CA (August 22-25). Also in the news, Limited Space Charge Accumulation (LSA) diodes showed promise for X-band phased-array radar, with a shift from waveguide to stripline transmission lines, according to papers at a Cornell University conference. And women started appearing in advertising, including a long-legged blonde woman holding a poster for a plug-in VHF-UHF power oscillator from Microdot (Pasadena, CA).

In a ViewPoynt column, the question "What is the biggest problem facing the microwave industry today," was posed to key executives attending the Wescon 67 show. Comments from John Young, General Manager of the Microwave Division of Hewlett-Packard Co., who felt that the training and education were needed by engineers to fully exploit changing technology. Neil Blair, President of Amphenol, felt that it was the industry was still relying on customer business, and lacked large-volume applications. He points



to the astronomical cost of
a television set
if it had been
built by the
microwave
industry. And
William Bourke,
President of
Narda
Microwave
Corp., pointed

to the critical shortage of engineers as the main prob-

Finally that year, the Air Transport Association of America issued a shopping list of requirements for a new collision-avoidance system. The four preferred frequencies for use were at 1575, 1580, 1585, and 1590 MHz. The ATA proposed the entire 1540-to-1660-MHz band to make room for the possible addition of a communications satellite-relay system within the band.

In 1968, the February issue (Fig. 3) featured a dramatic cover of the war/conflict in Vietnam, with a special report on microwave electronics in Vietnam based on a visit there by News Editor Thomas Kilpatrick. Opening with a memo from General William Westmoreland on the reliability of microwave-communications systems in the war effort, the story explained that this was not a conventional war, and that equipment would be used in hostile, jungle environments. The story detailed several systems, including AN/PPS-6 manpack counter-intrusion radar system from General Instrument, and the MPQ-4 counter-mortar radar from

WITH A LITTLE TLC ...

TLC "O" MMIC Chip

The Worlds Most Versatile MMIC Chip

2 to 79 GHz Operation

- MULTIPLIER, VCO, ILO, DRO, MIXER, AMP
 - > 16 dBm @ 38 GHz
 - 8 dBm @ 77 GHz
 - -100 dBc/Hz @ 100 KHz @ 77 GHz

The TLC "O" chip is a general purpose MMIC oscillator with an output buffer amplifier. The center frequency is voltage and mechanically tunable by plucking airbridges. Versatile option allows for higher Q restoration, injection locking, harmonic multiplication, sub-harmonic mix up and down.

The versatility of the TLCO01981 "O" chip oscillator makes it an excellent candidate for use in radar or communication systems from 2 to 79 GHz.

Patents Pending

YOUR PRODUCT COMES TO LIFE



TLC PRECISION WAFER TECHNOLOGY, INC. 1618 WEST RIVER ROAD N. MINNEAPOLIS, MN 55411

(612) 341-2795 FAX (612) 341-2799

Web: www.tlcprecision.com E-mail: sales@tlcprecision.com



General Electric, used to monitor activity at the demilitarized zone (DMZ). The MPQ-4 system could only scan in 25-deg. segments, and must be mechanically shifted to cover larger areas.

Stories that year also covered an international military project called Mallard that was in its \$100 million study phase, with a target date for getting hardware in the field between 1975 and 1977. The project included US, England, Canada, and Australia and administrative offices were in Fort Monmouth, NJ. Another story carried on a plea by the FAA for a low-cost collision-avoidance system for small

aircraft, a potential \$100 million market.

On the first cover that year, a watchspring attenuator from General Microwave (Farmingdale, NY) operated from 50 MHz to 8 GHz. The "watch spring" was a tiny spiral used to form a lowpass filter in a bias line. The component achieved as much as 40-dB attenuation across the operating frequency range. Also on the cover that year, the model 2600 spectrum ana-Ivzer from Polarad Electronic Instrument used backwardwave oscillator (BWO) and cavity oscillators to tune from 10 MHz to 90 GHz. The

7. The "dancing HEMT" cover of November 1985 featured the first commercial GaAs HEMT device, from the Microwave Products Division of Gould, Inc. (San Jose, CA)

> IEEE 1968 show was held March 18-21 that year in New York City.

The MICROWAVE EXPOSI-TION/68 was held June 4-6 in San Francisco, CA. In April, the magazine provided results from a survey of microwave engineers. One-half of those surveyed had BSEE degrees, while one-quarter had Master's level degrees. The typical engineer was less than 40 years

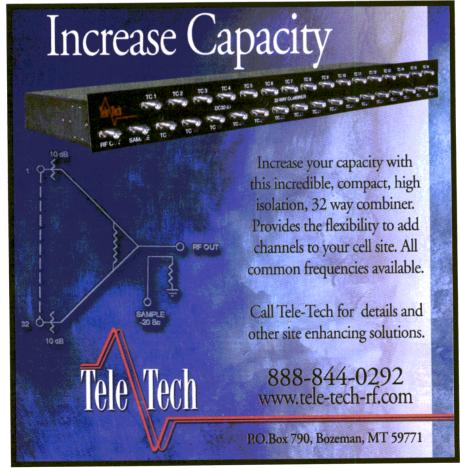


old and had stayed many years at one job. About 43 percent of those surveyed had spent time in military service.

In 1969, January fea-

tured one of the more innovative covers ever produced by MicroWaves-a cartoon of two engineers attempting to start their own company (Fig. 4). The cover was part of a special survey of new microwave companies, why they were started, how difficult was it to get financing, and other key points. The survey included Olektron Corp. (Dudley, MA), Wavecom (Chatsworth, CA), Zeta Laboratories (Mountain View, CA), Microwave Semiconductor (Somerset, NJ), Electromagnetic Sciences, Inc. (Atlanta, GA), California Microwave (Sunnvvale, CA), and Comtech Laboratories (Plainview, NY).

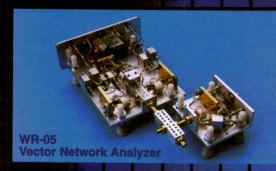
The news story in that issue highlighted a presidential Task Force on Communications Policy panel to assess the state of communications, spurred on by a trail-breaking application from Microwave Communications, Inc. (MCI) of Washington, DC to provide special common-carrier service to businesses with offices in St. Louis, MO and Chicago, IL for less than the cost of service offered by AT&T. The task force felt that the entry of MCI and other common carriers into the market could spur technology developments.



Enter NO. 451 at www.mwrf.com

mmW Test Equipment

Vector Network Analysis Systems Use with popular microwave VNA equipment to achieve millimeter wave vector/amplitude measurement capability. Can be used in either the forward direction only (S11 & S21) with one T/R module and one T module *or* in the forward and reverse direction (S11, S21, S22, S12) with two T/R modules. Systems are available for all waveguide bands from WR-22 to WR-05.

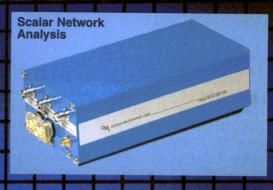


Waveguide VNA Calibration Kits for calibration of the above Vector Network Analysis Systems. Contains all of the components necessary to achieve any of the popular calibration methodologies.

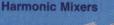




FCC Spurious and Harmonic Test Kit for use with popular Spectrum Analyzers. Each kit contains four mixers providing continuous coverage from 40 to 220 GHz. Each mixer is equipped with an appropriate horn antenna for accomplishing the FCC desired radiated spurious level measurement. Shown with optional diplexer and cable.

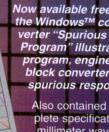


Scalar Network Analysis (SNA) Systems and Multiplier Sources Complete SNA systems containing filtered multipliers with -50 dBc spurs and harmonics. Included are a dual directional coupler and detectors for reference, reflection and transmission. Available for WR-22 through WR-10. Filtered Multiplier Sources are also available without the coupler or detectors. Multiplier Sources are available without filtering for the WR-08 through WR-05 waveguide bands. All of these products are engineered to extend the user's 8 to 20 GHz equipment.





Harmonic Mixers Use with popular Spectrum Analyzers to achieve millimeter wave spectrum analysis. Mixers are available for all waveguide bands from 18 to 325 GHz. LO/IF diplexers are available for most modern spectrum analyzers. Measured conversion loss data supplied with emulation of most modern spectrum analyzers for WR-42 through WR-10.



Now available free at the OML Web Site is the Windows™ compatible, block converter "Spurious Product Prediction Program" illustrated to the left. With this program, engineers can examine their block converter designs for harmful spurious responses.

Also contained on the Web Site are complete specifications for all of the above millimeter wave frequency extension products as well as technical papers addressing many of the more common millimeter wave testing problems.

Contained in these papers are many useful millimeter wave charts and graphs not found elsewhere.

Visit us at www.oml-mmw.com

Oleson Microwave Labs

355 Woodview Drive, Suite 300 • Morgan Hill, CA 95037 • Tel: (408) 779-2698 • Fax: (408) 778-0491



On the February cover, a yttrium-iron-garnet (YIG) filter from Watkins-Johnson Co. offered electrical tuning from 1 to 18 GHz. This was the first YIG filter with that type of bandwidth in a single package, and opened the door for the development of wideband test equipment, including spectrum analyzers. As a followup, the March cover featured a YIG-tuned spectrum analyzer (based on the WJ YIG) from NYTEK Electronics (Sunnyvale, CA) with coverage from 0.7 to 18 GHz. The June cover featured a low-cost version of a precision 7-mm connector from Amphenol RF Division (Danbury, CT), selling for only \$7 each in 1000 quantities. That year, the IEEE Convention was held on March 24-27 in the New York Coliseum.

The first editor of MicroWaves. Manfred Meisels, ended his neardecade-long run at the beginning of 1970, and was replaced by Elmer Ebersol. Howard Bierman joined the staff that year as the new publisher, and would go on to guide the growth of the magazine for the next 10 years. Bierman was former editor of Electronic Design magazine and a graduate of City College of New York. Before year's end, editor Ebersol would leave the magazine and Bierman would become Publisher/Editor.

In the news that year, a story described the Environmental Science Services Administration's use of pulsed Doppler radar for monitoring and analyzing severe storms and other turbulent weather conditions. The news also contained information about a microwave oven developed by Litton Industries for maritime use. With 600-W microwave power at 2450 MHz, A special report detailed an Automatic Microwave Collision Avoidance Radar (AMCAR) system developed by Bentley Associates (Chelmsford, MA). The X-band Doppler radar system detected objects directly in the path of a vehicle and actuated a mechanism that depressed the brakes and pulled back on the accelerator. The July cover featured Fairchild's Xband oscillator, a Gunn device selling for only \$5 in 100,000 quantities. It offered 60-mW CW output power from 8.0 to 12.4 GHz. The November cover showed Hewlett-Packard's model HP 8555A spectrum analyzer, with a frequency range of 10 MHz to 18 GHz and an amplitude range of -130 to +30 dBm. The analyzer's RF section had a hotcarrier diode mixer on a sapphire substrate.

In 1971, RCA Laboratories (Princeton, NJ) announced the development of a GaAs amplifier capable of operating from 3 to 20 GHz with 0.2-mW output power. Communication Transistor Corp. (San Carlos, CA) introduced a VHF transistor with 70-W CW output power, from 130 to 200 MHz, a +12-VDC device. Scientists at Bell Telephone Laboratories

8. This classic remake of the Alexander Graham Bell photograph featured personnel from RF Microdevices and QUALCOMM and was symbolic of the growing reliance of the microwave industry on wireless markets.

> ries discovered the Barrier Injection Transit Time

(BARITT) diode fabricated from a thin slice of Si between two Schottky barrier contacts. The device yielded as much as 57-mW power at 4.9 GHz with 2.3-percent efficiency.

In 1972, Avantek (Santa Clara, CA) developed a fundamental transistor oscillator for use from 4 to 8 GHz, and, without multiplying, the YIGbased source used Si bipolar active devices. Microwave Semiconductor Corp. (Somerset, NJ) unleashed a new transistor structure called the MICROGRID, capable of 5-W CW output power at 4 GHz. Westinghouse announced an L-band transistor amplifier with 1-kW output power at 1250 MHz for 1-ms pulses. Four 25-W transistors were combined to form a 100-W module, then 12 100-W modules were combined to achieve the 1-kW output power. The project was funded in part by the US Air Force Rome Air Development Center (Rome, NY).

In 1973, an impedancematched transistor from Power Hybrids (Torrance, CA) delivered 20-W CW power at 2 GHz, an negativepositive-negative (NPN) planar transistor, while Avantek (Santa Clara, CA) developed a fundamental transistor oscillator for use from 6 to



12 GHz with 5-mW output power. In October that year, Stacy V.
Bearse joined *MicroWaves* as Associate Editor.

In 1974.

the February issue featured news from MIT Lincoln Laboratory (Lexington, MA) on surface-wave pulse-compression filters capable of achieving a 500-MHz bandwidth at 1 GHz. The new type of filter used the reflection of surface acoustic waves (SAWs) to achieve large time-band-

to achieve large time-bandwidth product pulse compression. The cover story in June focused on improving circuit design through computer timesharing, with an article by Nick Kuhn of HP on how to make circuit design a true science by applying graphical techniques with computer analysis.

In 1975, an economic forecast article series on electronic-warfare markets predicted a \$2.17 billion market for electronic countermeasures (ECM). The March cover story, by Algie Lance and Wendell Seal of TRW (Redondo Beach, CA), addressed a new way to measure noise that offered simplicity and accuracy over conventional Y-factor measurements.

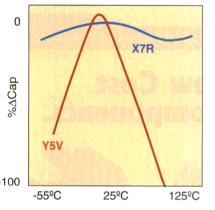
In 1976, the model 451 frequency counter from EIP Microwave (Santa Clara, CA) made news with its capability of measuring the frequency of pulsed signals as narrow

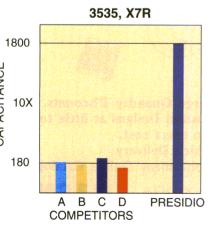
PRESIDIO can make ANY

SINGLE LAYER CAPACITOR

inTRUE 7



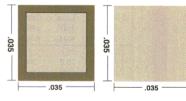




Presidio Components Inc. is the choice of filter bypass application design engineers who know the vastly superior performance numbers that X7R capacitors deliver compared to parts built with Y5V.

As an integral part of our proprietary single layer capacitor product line, we use *true* X7R to produce what our competitors can only make using Y5V or Z5U.

Presidio Components' X7R capacitors offer clear advantages in virtually every possible performance test against any other material. Our parts deliver measurably better temperature stability and high frequency performance. You can also have your choice



Presidio X7R 1800pF Competito

of higher Q, up to 10 times the capacitance, or a much smaller size. We have the flexibility to produce parts that will meet your most demanding requirements.

Call today for a free sample, and prove to yourself the superior performance of Presidio Components' X7R single layer capacitors.

Call us today at 858 578-9390 for our latest free catalog, or visit our website.

www.presidiocomponents.com/mrf







as 100 ns from 925 MHz to 18 GHz. A special report in the December issue pointed to increased interest on the part of the military for integrated components with multiple functions, known then as supercomponents. Ash Gorwara, President of Planar Microwave in Sunnyvale, CA, noted that the mean-time before failure (MTBF) of the supercomponents could be as much as five times better than that of the individual components taken as a group, due, in turn, to the lack of connector failures, usually due to improper torquing of the connectors.

In February 1977, Stacy

Bearse was named Editor-In-Chief. In his first editorial with the new title, he wrote about gigabit logic and its rightful place in a microwave magazine and these devices as important building-block components for future highspeed communications systems. Bearse would eventually become Publisher as part of an almost 16-year career with the magazine, bringing onboard and training future Editors Barry Manz, Mike Kachmar, and Jack Browne.

A news story in June covered a new superconducting device, a Superconducting Quantum Interference Device (SQUID) that was being considered by the National Bureau of Standards as a new RF attenuation standard, while a special report on acousto-optics described the basics of Bragg cell operation and explored the use of this relatively new technology in ESM receiver design. And monolithic devices began to be reported at the International Electron Devices Meeting.

In 1978, a survey of microwave engineers conducted by *MicroWaves* found the average microwave engineer to be male, age 30 to 34 years old, and earning \$20,000 to \$25,000 annually. The typical educational level was

BSEE and the typical position or title was project engineer or senior engineer. Most respondents enjoyed a 7 percent or higher annual salary increase. Of the 314 respondents to the survey, only one was a woman. That same year, Ron Hirsch, president and founder or RHG Electronics Laboratory (Deer Pak, NY) offered an article called "Plain talk on log amps" that demystified the use of intermediate-frequency (IF) logarithmic amplifiers. In the August Calculator Corner, a program offered by Don Sanders of GTE Laboratories (Waltham, MA), transition frequency of a transistor from its S-parameter data

online cata www.pulsarmicrowave.co

Power Dividers

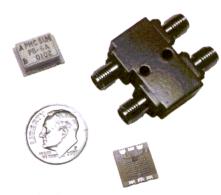
2 W	/AY	SUR	FACE N	TOUNT	00			
Freq. Range (GHz)	nsertion Loss (dB) max.	Iso. (dB) min.	Amp. Balance (dB) max.	Phase Balance (Deg) max.	VSWR max.	Input Power (watts) max.	P/N	Cost Qty. 5-99
800-1000	0.5	20	0.2	2.0	1.40:1	1.0	PB-2	\$4.99
1750-2050	0.5	20	0.2	2.0	1.40:1	1.0	PB-4	\$4.99
2200-2500	0.6	18	0.3	3.0	1.40:1	1.0	PB-5	\$4.99
800-1000	0.6	18	0.2	2.0	1.40:1	10.0	PB-14	\$9.99
1300-1600	0.7	18	0.2	2.0	1.40:1	10.0	PB-10	\$9.99
1700-2000	0.7	18	0.2	2.0	1.40:1	10.0	PB-11	\$9.99
2300-2700	0.7	18	0.3	3.0	1.40:1	10.0	PB-12	\$9.99
3000-3800	0.8	18	0.3	3.0	1.40:1	10.0	PB-13	\$9.99

90° Hybrids

Freq. Range (GHz)	Coupling Loss (dB)	Iso. (dB) min.	Amp. Balance (dB) max.	Phase Balance (Deg) max.	VSWR max.	P/N	Cost (Qty. 5-9)
5.09-5.25	3.2 + 0.2	20	0.2	2.0	1.30:1	QS2-B6-463/2	\$99.99
5.20-5.40	3.2 + 0.2	20	0.2	2.0	1.25:1	QS2-B8-463/2	\$99.99
4.00-8.00	3.3 + 0.3	18	1.4	4.0	1.25:1	QS2-05-463/2	\$99.99
6.10-6.40	3.2 + 0.2	20	0.2	2.0	1.30:1	QS2-B7-463/2	\$99.99
4.50-9.00	3.2 + 0.3	18	1.0	2.0	1.30:1	QS2-B10-463/2	\$99.99
10.80-12.00	3.3 + 0.3	20	0.5	2.0	1.25:1	QS2-B9-463/2	\$99.99
12.50-13.50	3.3 + 0.3	20	0.5	2.0	1.25:1	QS2-B11-463/2	\$99.99

MICROWAVES & RF

Low Cost Components.



- · Large Quantity Discounts.
- Custom Designs at little to no extra cost.
- Quick Delivery.
- · Convenient Online Catalog.

ISO 9001 REGISTERED FIRM



Pulsar Microwave Corporation • 48 Industrial West • Clifton, NJ 07012 • Tel: 800-752-3043 • Fax: 973-779-2727 • sales@pulsarmicrowave.com



was computed. That November, the HP 8566A spectrum analyzer was introduced by HP. With an impressive \$47,500 price tag, the analyzer was the most powerful spectrum analyzer available on the market, with a frequency range of 100 Hz to 22 GHz, 10-Hz minimum resolution bandwidth, and a minimum measurable signal level of -137 dBm.

Computers began to make an impact in 1979. A special report discussed the impact of digital computers on test-and-measurement techniques. How the computer was being used to automate measurement routines and speed productivity

has discussed. That year, the model 560 scalar network analyzer (SNA) was introduced by Wiltron Co. (Mountain View, CA). It had 10-MHz-to-18-GHz coverage and 70-dB dynamic range for less than \$10,000. Tektronix (Beaverton, OR) introduced its model 492 portable spectrum analyzer with coverage from 50 kHz to 21 GHz and optional coverage to 220 GHz with external harmonic mixers. And the MTT-S 1979 International Microwave Symposium was held in Orlando, FL (April 30 to May 2). Approximately 1000 people would attend the conference and exhibition that year.

In 1980, a report by Frank Moncrief, Western Editor, detailed Japan's efforts to advance communications technology. The report explained how Sony hoped to grab a share of the direct-television market for satellites using a small 90cm-diameter disk and a twostage GaAs preamplifier at bands of 12 and 14 GHz. The cover featured Dr. Koii Kobayashi, Chairman of the Board and CEO of NEC. In February of that year, Walter ("Hap") Bojsza joined the staff of MicroWaves as Associate Editor, Hewlett-Packard Co. introduced the HP 8350A sweeper with plug-in modules for frequen-

cy coverage to 26.5 GHz. Narda advertised their model 7000A, a lightweight automatic microwave multimeter capable of measuring power, insertion loss, gain, VSWR, and generating signals with interchangeable RF heads for different frequency ranges. And the 1980 International Microwave Symposium was held that year in Washington, DC (May 26-30). Also, in 1980, Associate Editor Hap Bojsza assembled a masterful profile of Raytheon's maverick Bill Brown that explored Brown's theories on microwave power transmission from space.





The February 1981 cover story featured Comsat's plans to put a dish on every roof in the hopes of supporting a widespread market for direct-broadcast-satellite (DBS) services. Uplink frequencies occupied the 17.3to-18.1-GHz band while downlink signals occupied the 12.1-to-12.7-GHz band. In the August issue, a special report heralded the coming of optical components and high-speed optical communications systems, and how microwave companies could play in this potentially large market. That year, the staff of MicroWaves would grow by two, with the addition of Associate Editors Jack

Browne and Barry Manz.

MicroWaves underwent a dramatic transformation in November 1982, with an increase in circulation and a change in name to Microwaves & RF. The name change signified more dedicated coverage of lowerfrequency issues from 10 MHz to 2 GHz. That November issue featured a cover story (Fig. 5), written by Craig Snapp of Avantek, on the company's Si monolithicmicrowave-integrated-circuit (MMIC) technology, and amplifiers with flat gain past 2 GHz. The following issue would feature a masterful interview by Associate Editor Barry Manz with two of the

pioneers of the microwave industry-Dean Watkins and Dick Johnson-founders of Watkins-Johnson Co.

In 1983, Hughes Aircraft Co. cleverly portrayed a chimpanzee on the January cover to highlight an evolutionary line of new millimeter-wave sweepers. (Fig. 6). That same year. Hewlett-Packard Co. introduced the 8902A measuring Rx capable of making power measurements down to -127dBm at frequencies from 150 kHz to 1300 MHz. In July, the news section offered a story about a unique industry-university alliance between Raytheon Co. and the University of

Massachusetts (Amherst. MA) where Raytheonemployed students could earn a master's degree in microwave engineering. The program, which began in 1980, continues to this day. That June, Carl Sagan spoke to the MTT-S awards banquet audience in Boston, MA. Later that year. Wiltron's Bill Oldfield introduces the K connector, for coaxial coverage to 45 GHz, and Avantek introduced a YIG oscillator with coverage from 26 to 40 GHz and 10mW output power. And by the end of that year, Hewlett-Packard Co. would shake up the entire industry with the introduction of the

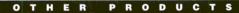
SURFACE MOUNT ISOLATORS / CIRCULATORS







- **Available in Frequencies** Starting at 400 MHz
- **High Volume Production** Capacity
- Can Be Delivered on Tape and Reel



- Isolators/Circulators
- **MMDS/WLL Tranceivers**
- **Power Dividers**
- **Receiver Multicouplers**

Transmitter Combiners

1991-2001

HARVARD, MA

ISO 9001 CERTIFIED

Visit our web site at http://www.rec-usa.com to see our product search engine.

12 Lancaster County Road • Harvard, MA 01451 • 978/772-7774 Tel. • 978/772-7775 FAX

Enter NO. 445 at www.mwrf.com



HP 8510A vector network analyzer (VNA). By the end of 1984, the company would make another big splash with its Modular Measurement System (MMS) line of customerconfigurable modular instruments, a project that had been in development for more than 10 years.

In the decade that would follow, the microwave industry would begin to wean away from its dependence on military markets, and start to cultivate commercial business. But the transition was slow and painful for many companies, and a great deal of consolidation would take place in

the latter half of the 1980s. For example, by 1986
Anzac Adams Russell had acquired RHG Electronics
Laboratories (Deer Park, NY). Shortly thereafter,
Anzac, in turn, was acquired by M/A-COM. During the 1990s, M/A-COM would be acquired by AMP, Inc. (Harrisburg, PA) and AMP, in turn, was acquired by Tyco Electronics.

In November 1985, Gould's Microwave Products Division (San Jose, CA) would introduce an alternative to the GaAs FET (Fig. 7), in the form of a high electron-mobility transistor (HEMT). Offering lower noise and higher gain than equivalent-sized MESFETs, the HEMT would eventually make its mark on the industry, especially in low-noise, higher-frequency applications.

In January 1986. Hewlett-Packard Co. bought new hope to RF engineers planning to start their own company, with the introduction of the HP 8753A. This first RF vector analyzer, priced for the masses. brought 3-GHz coverage with performance specifications similar to its "big brother," the HP 8510A. In March that year, a "Technology Closeup" highlighted the current explosion in GaAs developments, in the form of

analog and digital ICs.

After several years as Chief Editor, Barry Manz would leave the staff of Microwaves & RF during 1987 to start his own company, Manz Communications (Montville, NJ). Michael Kachmar, who had joined the staff years earlier as Copy Editor, would take the reins as Chief Editor at the end of 1987, a position he would hold until 1990. Along the way, the staff added Ron Schneiderman as News Editor and Victor Perrote as Associate Editor to handle the Design Features section. And beginning with the May 1990 Continued on page 202

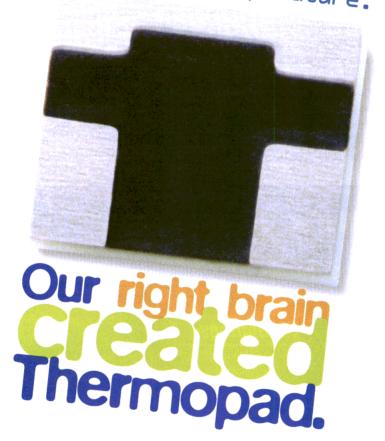
Expanding New Horizons **Products Capabilities** • 0.1 to 20GHz, 80dB, High Speed, Successive Detection Log Video Amplifiers Connectorized or Drop-in, MIL-STD-883 Available Low Noise Amplifiers 0.1 to 20GHz, up to 40dB, Low Noise (4dB), +/-2dB Flatness Phase Shifters/Modulators • 0.1 to 20GHz (Octave/Multioctave), Analog or Digital Control, High Speed, +/-90 Degrees Threshold Detectors • 0.1 to 20GHz, High Speed and Sensitive, Hard or Soft Limiting Limiter/Detectors 0.1 to 20GHz, High Speed and Sensitive Detectors 0.1 to 20GHz, High Speed and Sensitive Also Available: Frequency Discriminators and Reciever Front Ends Planar Monolithic Industries, Inc. 7311 G Grove Road , Frederick, MD , 21704 TEL: 301.662.4700 FAX: 301.662.4938 Area Sales Reps Wanted

Right Brain Components.



Our left brain

figured you could use a totally passive attenuator that will compensate for changes in your amplifier gain over temperature.



Our Thermopad® surface mount attenuators provide temperature

compensation. Replace complicated active control circuits that are expensive, less reliable, produce distortion and eat up valuable PC board space. Thermopads can be used in place of a standard chip attenuator to combine level setting and temperature compensation in one chip, reducing your component count, increasing reliability and saving you money.

Call us at 856-429-7800, and ask about Thermopad,

another brainstorm from EMC. Or visit **www.emct.com**



EMCTECHNOLOGY, INC. Right Brain Components.

application notes

The digital radio Rx revisited

LAST MONTH'S APPLICATION Notes column reported on an Analog Devices paper explaining the underlying concepts of a multichannel digital radio Rx. This month, that subject is further explored with another one of the company's reports. This one is on the design aspects of an IF-sampling digital Rx, "Designing a Super-Heterodyne Multi-Channel Digital Receiver."

This Rx has one RF front end rather than several; a single IF-sampling ADC rather than several; and a special filter bank that contains devices, such as digital decimating Rxs. The note details the subtle differences between a full super-heterodyne Rx and an IF sampling type.

Proceeding through each stage at a time, the note covers the factors involved in component selection. The LNA and band-select filter are similar to those of a single-channel Rx, but the mixer must be selected carefully. It must be a low loss, low noise figure type with high intercept points. This is because increasing input signal levels can gradually degrade the IM performance.

IF filtering is an important consideration in an IF-sampling Rx, since that device must prevent aliasing of unwanted signals by the ADC. The choices are the traditional SAW filter and the conventional LC filter. A problem with SAW filters is that multichannel types can exhibit higher insertion losses than the single-channel variety. Conventional LC filters can introduce phase distortion, but have better insertionloss characteristics than SAWs.

IF amplifiers and the IF-sampling ADCs are key components of the design. For the amplifiers, IF gain blocks are the clear choice over optical amplifiers, which are too noisy and lack the spurious performance necessary for IF sampling. A gain block, however, can introduce harmonics, which must be filtered out to prevent interaction with ADC harmonics. Advances in semiconductor technology have led to much improved IF-sampling ADCs, but harmonic performance and two-tone IMD are factors that can impair Rx performance.

A number of possible Rx designs for various digital wireless systems are offered at the end of the note. The standards include CDMA, PHS/PACS, GSM, and even AMPS, which is still a factor in multimode radio designs. Similar to the earlier note, this one is included in the company's CD-ROM, "Advanced Signal Processing for Wireless."

Analog Devices, Inc. Three Technology Way, Norwood, MA 02062; (781) 329-4700, Internet: www.analog.com.

Enter No. 194 at www.mwrf.com

Stick to the basics for lownoise designs

ONE OF AN engineer's worst nightmares is when noise problems prevent the completion of a design and delay the introduction of a product. But according to an 11-page brochure from Washington Laboratories Ltd. entitled "The 10 Basic Steps to Successful EMC Design," many fundamental design mistakes are routinely made. The brochure states that "Most of the reasons for equipment failure during EMC testing can be traced to less than a dozen common, predictable design flaws. Most designers can improve their EMC performance by observing relatively uncomplicated design guidelines." That being said, Part One of the brochure explains the first five steps in avoiding the pitfalls that lead to noise problems.

Three areas contribute to most problems: circuit boards, cables, and enclosures. At the board level, it is imperative to control the flow of current to get control of the noise. The current generated by a noise source must be returned to the 0-VDC reference point of that source through the lowest impedance path possible.

The note claims that 80 percent of EMC

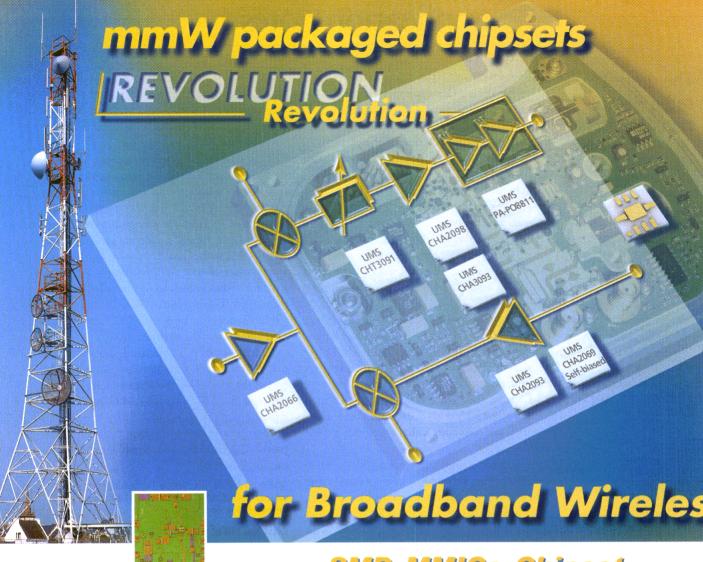
problems involve a system's cables. Using shielded cables is mandatory, but the type of shield and how it is grounded can make a difference in EMC performance. For example, the pigtail ground should be avoided at high frequencies since it has inductance which can contribute considerable impedance to the ground path.

With reference to enclosures, the note points out that potential EMC problems must be addressed first at the circuit-board level and then at the enclosure. The point is that doing the job properly from the bottom up yields greater margin, better performance, and fewer delays in the qualification process.

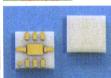
The least-expensive method of noise control is the careful location of components to minimize coupling between high-frequency circuits, I/O, and the outside world. The application note is the first of two parts, both of which can be obtained by contacting the company.

Washington Laboratories Ltd., 7560 Lindbergh Dr., Gaithersburg, MD 20879; (800) 839-1649, e-mail: info@wll.com, Internet: www.wll.com

Enter No. 195 at www.mwrf.com











Engineered Solutions

SMD MMICs Chipset 26 - 28GHz Radiolink

Function	P/N	Operating Frequency	Gain	Gain Control	Noise Figure	P-1dB	Bias	
LNA (*)	CHA2066-XXF(**)	10-16GHz	15dB		2.5dB	9dBm	4V, 45mA	
LNA (*)	CHA2069-RAF	18-31GHz	19dB	_	3dB	9dBm	4.5V, 55mA	
LNA	CHA2093-RBF	20-30GHz	14dB	_	3dB	12dBm	4V, 45mA	
Attenuator	CHT3091a-RCF	DC-40GHz	-	-4,21dB	4. · · ·	14dBm	0V,-5V, 0mA	
Buffer	CHA2098a-RBF	20-40GHz	18dB		_	15dBm	3.5V, 150mA	
MPA	CHA3092-RBF	20-33GHz	21dB	_	_	18dBm	3.5V, 300mA	
MPA	PA-PO-8811-TBF(***)	24-30GHz	25dB	_	_	24dBm	5V, 460mA	

*self biased, **XX tbd, ***New eng samples available

united monolithic semiconductors



succeeding together

Call 1-800-737-6937 to find out how Richardson can support your wireless and microwave programs or visit www.rfpowernet.com/ums.asp



More than 60 locations worldwide to serve you. E-mail: nwc@rell.com, Internet: www.rfpowemet.com, Toll Free: 800-RF Power or 800-737-6937 (U.S. & Canada), Australia: Castle Hill ACN 19 069 808 +61 (2) 9894-7288, Bayswater ACN 19 069 808 108, +61 (3) 9738-0733, Brazil: Sao Paulo +55 (11) 3845-6199, Rio De Janeiro +55 (21) 521-4004, China: Shanghai +86 (21) 6440-0807, Shenzhen +86 755-329-1 Colombia: Sante Fe de Bogota, DC (57-1) 636-1028, Denmark: Hedenhusene +45 4655-5630, France: Colombes Cedex +33.1.55.66.00.30, Nozay +33.1.69.80.71.33, Germany: Puchheim +49 (89) 890 214 Hamburg +49 (40) 555 88 410, Italy: Agrate (MI) +39 (039) 653 145, Roma +39 (06) 41.733.751, Sesto Fiorentino (FL) +39 (055) 42.08.31, Japan: Osaka +81 (6) 6314-5557, Tokyo +81 (3) 5215-1577. Korea: Seoul: (2) 539-4731, Malaysia: Selangor +60 (3) 5511-5421, Mexico: Mexico City +52 (5) 674-2228, Guadalajara +52 (3) 645-4641, Philippines: Pasig City +63 (2) 636-8891, Singapore: +65 487-5995, Spain: Barcell +34 (93) 415 8303, Madrid +34 (91) 528 3700, Sweden: Stockholm +46 8 564 705 90, Taiwan: Taipei +886 (2) 2698-3288, Thailand: Bangkok +66 (2) 749-4402, The Netherlands: Amsterdam +31 (20) 446 7070, Unit Kingdom: Slough +44 (1753) 733010, Vietnam: Ho Chi Minh City +84 8-8233016. For other international inquiries call Corporate Headquarters: LaFox, IL (630) 208-2200, Fax (630) 208-2500.

1-800-RF POWER

1-800-737-6937

www.rfpowernet.com

rwc@rell.co

PRODUCT

LDMOS Delivers 500 W For IFF Systems

A high-efficiency, Class AB linear LDMOS high-power FET is well-suited for boosting the short-duration pulsed signals found in IFF Tx systems.

aterally-diffused-metal-oxide-semiconductor (LDMOS) field-effect transistors (FETs) have been the devices of choice for high-power commercial base-station linear amplifiers for several years. These powerful transistors have been designed into a multitude of linear power amplifiers (PAs) used within the 500-to-2500-MHz frequency range. The high gain, good efficiency, and excellent Class AB linearity of

LDMOS FETs make them suitable for a wide variety of RF and microwave highpower applications. Typically, these high-power transistors have been associated with commercial applications, such as cellular base stations. But the devices also provide the type of performance benefits wellsuited for many military applications as well.

In a military Identification Friend or Foe (IFF) system, for example, configuring an entire PA (including the 500-W output devices) using high-gain, Class AB linear transistors provides significant system advantages. These

RON OLSON

Vice-President-Engineering

Zeta, an Integrated Defense
Technologies Co., 2811 Orchard Pkwy.,
San Jose, CA 95134; (408) 433-0205, email: rono@seta-dit.com, Internet:
www.zeta-idt.com.

MIKE MALLINGER

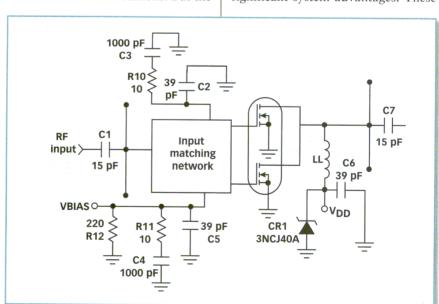
Vice-President

GHz Technology, Inc., 3000 Oakmead Village Dr., Santa Clara, CA 95051; (408) 986-8031, FAX: (408) 986-8102, e-mail: mmallinger@ghz.com, Internet: www.ghz.com.

LEE MAX

Technical Consultant

6284 Squiredell Dr., San Jose, CA 95129; (408) 252-3807.



1. This amplifier circuitry was used to optimize the performance of a high-power LDMOS device for IFF applications.

PRODUCT — technology

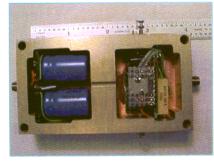
advantages include IFF Mode S and Mode 5 capability, reduced cost and size, increased reliability, and improved thermal performance.

Designers of military IFF PAs have looked longingly at the proliferation of +28-VDC continuous-wave (CW) microwave LDMOS FETs and waited patiently for a device and circuit that was optimized for their IFF high-voltage (greater than +35-VDC), highpower (greater than 500-W), and 1030/1090-MHz, pulsed applications. Fortunately, an LDMOS FET has been developed by GHz Technology (Santa Clara, CA) with the performance and reliability needed for these IFF systems. What follows is an examination of the device and its associated circuitry under a variety of low-duty-cycle, and extended-length message formats.

Since the emergence of high-power LDMOS FETs for 900-MHz cellular base-station PAs, RF circuit designers have envisioned LDMOS transistors for L-band

avionics applications. These Class AB

devices offer at least 4 dB more gain and 15 dB more dynamic range than the Class C commonbase bipolar transistors used in the present distance-measuring equipment (DME), Joint Tactical Information Distribution (JTIDS), Tactical Air Navigation (TACAN), and IFF systems. This significant improvement in single-stage gain and



2. Charge storage for the LDMOS' DC drain circuit and the gate DC bias circuit are mounted under the RF PCB.

plify and reduce the cost of traditional avionics transmitter (Tx) subsystems. For example, the linear LDMOS devices will not require the pulse-shaping circuits commonly used with Class C devices.

In new multimode IFF-enhanced data systems, even greater performance, reliability, and cost benefits are available by using LDMOS FETs. These new systems use amplitude modula-

ulation (PM).
Furthermore, they must support substantially higher data rates.
Only LDMOS-based Txs can provide the high linearity and thermal capability necessary to fully meet the requirements of next-generation avionics systems.

tion (AM) and phase mod-

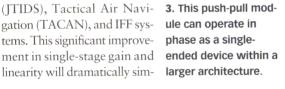
Unfortunately, device and circuit designers have struggled to achieve an LDMOS device/circuit combination suitable for the higher-voltage pulse requirements of L-band avionics applications. RF power-circuit designers have been stymied by several unexpected device problems associated with LDMOS in avionics applications.

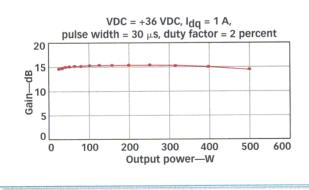
Some of the major problems encountered when using standard LDMOS FETs in an avionics application are:

- The fragility of the devices when used in pulse applications with fast rise and fall times.
- The inherent threshold drift in LDMOS FETs increases dramatically as the DC operating voltage is increased.
- The internal balance of an LDMOS die becomes significantly worse as the DC operating voltage is increased.
- RF power devices that contain aluminum (Al) bond wires have displayed poor reliability in high-power pulsed applications due to bond-wire failures.

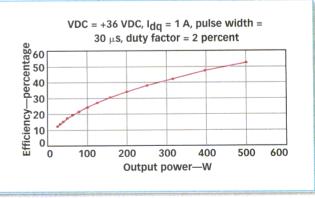
Engineering development staffs at GHz Technology and Zeta (San Jose, CA) carried out an extensive investigation focused on identifying the causes of these LDMOS problems in IFF applications. That research was followed by a device/circuit-development program that provided realistic solutions, including a single Class AB LDMOS FET device which is capable of more than 500 W of peak output power.

As PA designers started to use LDMOS FETs in pulse applications or systems with high-speed digital modulation, unexplainable failures often occurred. It was later found that large voltage spikes were appearing on the drain of the





4. In short-pulsed applications, the high-power LDMOS device provides more than 15-dB gain with over 500-W output power.



5. The efficiency is better than 50 percent for the high-power LDMOS device in short-pulsed applications.

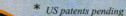




Harmonic Load Pull System 1.8 - 18 GHz
Compact, user friendly operation

Experience the cutting-edge precision and *state of the art* features included in every Focus product:

- Prematching* and Harmonic* coaxial tuners, 0.2 50 (65) GHz
- Fundamental waveguide tuners, 26.5 110 GHz
- Advanced Load Pull and Noise measurement software
- VNA TRL calkits, 0.1 50 GHz
- Manual tuners (with prematching options), 0.4 50 GHz
- Modular, low loss, high power test fixtures*



Harmonic Source & L/P Software
Intuitive operation with unique options

Focus Microwaves offers complete measurement solutions for high power, harmonic & noise testing; on-wafer or in fixture. Over 400 systems in operation worldwide.

L/P Tuners, TRL Calkit & Transistor Test Fixture
A complete measurement solution

Phone: +1.514.335.6227 Fax: +1.514.335.6287 www.focus-microwaves.com

LDMOS FET due to the very-fast fall times of the DC drain current. These short-duration voltage spikes were triggering and "turning on" the parasitic bipolar transistor inherent in the LDMOS FET structure, creating a self-destructive device condition.

In IFF systems, fall times are generally controlled between 50 and 200 ns. However, to minimize the risk of LDMOS self-destruction due to fast DC-drain-current spikes, the GHz/Zeta team took several steps. The first involved increasing the drain breakdown voltage capa-

bility of the LDMOS die. In the second step, the value of the inductor was used to deliver the DC current to the drain of the LDMOS FET (inductor L1 in Fig. 1) in the amplifier circuit was minimized as much as possible, consistent with the RF circuit impedance requirements. In the third step, a fast, high-peak-current Zener diode (diode CR1 in Fig. 1) was added to the drain DC feed network to clip voltage spikes at +5 VDC above the operating DC drain voltage.

Threshold drift with operating time has historically been a problem for PA designers using LDMOS FETs. Device suppliers have been reducing the drift of their devices to the point where today's newest LDMOS FETs have minimal threshold drift when operating at +26 to +28 VDC. However, when LDMOS FETs operate at the higher DC voltages of pulsed avionics applications (above +35 VDC), the threshold drift increases. Two primary techniques for managing the threshold drift in an IFF system are: 1. preconditioning the devices (typically 72-to-168-h system burn-in) and 2. using a selfadjusting bias circuit that periodically samples the quiescent current of the device and adjusts the DC voltage on the gate of the LDMOS FET to hold the quiescent current at its initial value.

As seen in **Fig. 2**, the charge storage for the DC drain circuit and the gate DC bias circuit are mounted under the RF printed-circuit board (PCB) using the backside ground plane to shield the sensitive bias circuitry from RF interference (RFI).

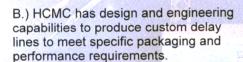
Balancing the die is the single biggest challenge for the device and circuit designers when trying to extract the maximum performance from this high-voltage RF metal-oxide semiconductor field-effect transistor (MOSFET). As seen in **Fig. 3**, there is approximately an inch (side to side) of die in this very-large push-pull LDMOS FET.

The GHz device team has incorporated a variety of balancing techniques on die and in the assembly of the device inside the package. The Zeta circuit-design team has developed proprietary circuit techniques that force extraordinary

State-of-the-art Quality Crafted, Full Service — Cable

Manufacturing

A.) HCMC manufactures and stocks fully tested standard straight semi-rigid and flexible assemblies which can be hand formed. We also provide cable assemblies to customer specification.



C.) Utilizing our manufactured cable HCMC is providing miniature interconnect components to meet customer specified requirements for surface mount applications on printed circuits and microwave substrates.

Haverhill Cable and Manufacturing Corp.



Semi-Rigid Coaxial Cable Specialists

TEL (978) 372-6386 • **FAX (978) 373-8024**P. O. BOX 8222, Haverhill, MA 01835

www.haverhillcable.com

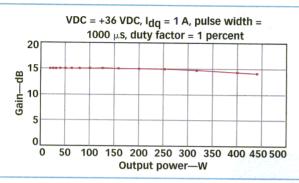
A.



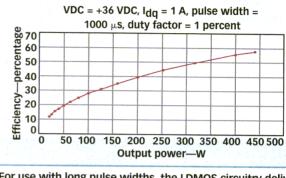


Enter NO. 421 at www.mwrf.com

PRODUCT— technology



6. For use with high-data-rate IFF modulation, LDMOS amplifier circuitry was developed to handle pulse widths of 1 ms at a 1-percent duty cycle.



For use with long pulse widths, the LDMOS circuitry delivered approximately 15-dB gain and more than 50-percent efficiency.

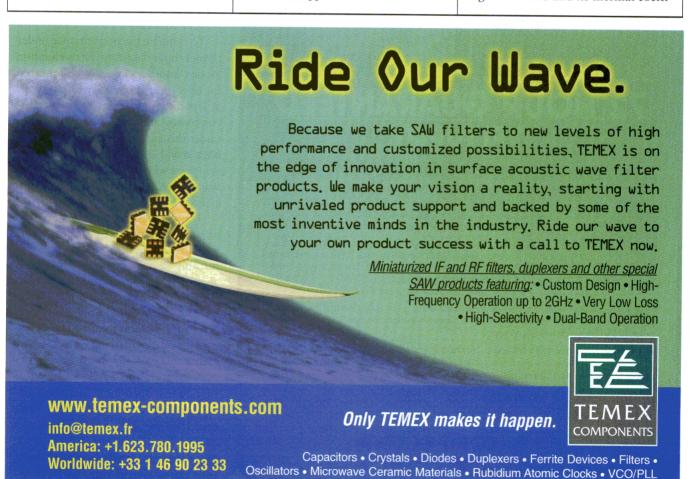
balance across the die. These techniques allow the entire push-pull device to operate in phase as a large single-ended device (Fig. 3).

A wear-out mechanism that is frequently overlooked in active-device studies is the failure of the bond wires. Under certain conditions, bond wires can actually fatigue and break. As the

device is driven with RF energy, current flows through the bond wires. The bond wires then increase in temperature and expand in length. The bond wire is attached at both ends. Therefore, each time the wire expands, the connection point at the bond foot is flexed. This does not present a problem under CW operation or for applications that do not have

a time-varying waveform. However, amplifiers for pulse applications such as radar and avionics, as well as many modern modulation formats, produce a range of time-varying waveforms.

Al bond wires are at far greater risk of failure than gold (Au) bond wires. Electrical and thermal resistance of Al is higher than Au and its thermal coeffi-



PRODUCT — technology

cient of expansion is much higher than Au. Therefore, an Al bond wire will flex significantly more at the bond foot than an equivalent-size Au bond wire. Since Al work hardens readily (Au does not), multiple flexing of the Al wire at the bond foot causes the wire to fatigue

and break. It typically requires at least 10 million cycles to produce this type of Al bond-wire failure. Unfortunately, documented examples [an ultrahigh-frequency (UHF) radar amplifier and a very-high-frequency (VHF) TV Tx] have shown that this type of design-

defect failure can occur in less than a month of normal operation.

The exact level of risk for a particular application is uniquely dependent on the construction of the specific microwave power device and the operating conditions of the system. However, Au-metallized LDMOS FETs that use Au bond wires are likely to be significantly more reliable than the Al metal systems that some device manufacturers currently use in their highpower cellular base-station LDMOS FETs.

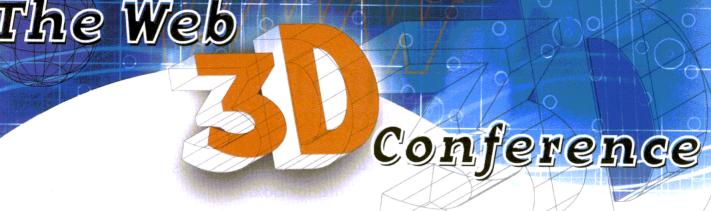
As seen in **Figs. 4 and 5**, the LDMOS FET pulse-amplifier circuit has very high gain, excellent dynamic range, and exceptional efficiency. With a standard 30- μ s pulse width at 2-percent duty cycle, the 1-dB compression point is 500 W. The LDMOS amplifier circuit also exhibits more than 15-dB gain with a gain flatness of ± 0.5 dB over a 13-dB output-power dynamic range (i.e., P_{out} versus P_{in}), and better than 50-percent efficiency.

To estimate the performance under the new high-data-rate IFF modulation modes, another circuit was optimized for operation at a pulse width of 1 ms at 1-percent duty cycle. The device/circuit combination operated so well, even under this extremely long pulse width (Figs. 6 and 7), that the 1-dB compression point was well over 400 W, the gain was approximately 15 dB, and the efficiency exceeded 50 percent.

The GHz/Zeta team has created device/circuit techniques that enable the single-device amplifier to operate comfortably at peak output-power levels above 500 W. With this much linear Class AB peak power out of a single IFF device/circuit, high-data-rate, multi-killowatt IFF systems using modern complex modulation schemes can be configured with simple low-level modulators, followed by an all-LDMOS FET-based, open-loop, high-gain, linear PA. GHz Technology, Inc., 3000 Oakmead Village Dr., Santa Clara, CA 95051; (408) 986-8031, FAX: (408) 986-8102, e-mail: mmallinger@ghz.com, Internet: www.ghz.com. MRF

Enter No. 51 at www.mwrf.com





OCTOBER 3-4, 2001 HILTON SANTA CLARA | SANTA CLARA, CALIFORNIA

Technology, content, and demand have converged, bringing the first wave of compelling 3D content to the Web. Jon Peddie Associates' first annual Web 3D Conference will examine the next challenging threshold of Internet communications.

Join leading industry figures from Viewpoint, Nvidia, Pulse and more — with Keynotes by Roger Chandler of Intel Architecture Labs, Kevin Lynch of Macromedia and Alex St. John of WildTangent – for two days of intensive discussion to learn the latest in opportunities, tools and applications.





For more information on The Web 3D Conference or to register at the advance rate, visit www.jpa.com or call 415.331.6800.

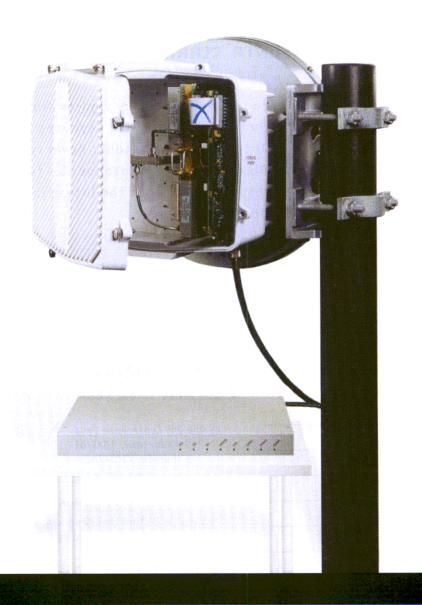
or fax to 201.393.6297 or call 888.947.3734

Media and relevant 3rd party businesses?

. Primary	Information	2. Please select your conference level				
ame			BEFORE 9/12/01	AFTER 9/12/01		
tle		O One Day Conference Pass O Wednesday, 10/3/01 O Thursday, 10/4/01	\$380	\$475		
dress		O Two Day Conference Pass	\$716	\$895		
		3. Payment Information				
		Payment in US funds must accompany your registration.				
У	State	US Government purchase orde	ers will be accepted	(Tax ID#:36-287538		
		Total Fee: \$				
untry	Postal Code	Check #: (Make check payable to Penton Media, Inc.)				
one	Fax	Credit Card: O VISA O M				
mail		Card Number:	Exp	o. Date:		
		Name of Cardholder:				
like many of our customers, you wish to be contacted e-mail, please check YES below for the reasons we		Cardholder Signature: I agree to pay the above in accordance with my cardholder agreement				
y contact y	ou:	Mail completed form to: Pen	ton Media. Inc.			
Yes O No	May we send you an e-mail regarding this event?	Attn: Linda Wilczynski 611 Route 46 West				
Yes O No	May we send you an e-mail from Penton	Has	brouck Heights, NJ	07604		



We make the GaAs MMIC building blocks for your outdoor box.



Mimix Broadband provides high performance GaAs MMICs for broadband wireless access. Learn more about us at mimixbroadband.com.



RF SubsystemEnables Cable Telephony

This RF transceiver provides an integrated solution for modern cable-telephony network interface units with a migration strategy to future VoIP systems.

able services are rapidly expanding to include upstream (from the customer to the service provider) and downstream (from the service provider to the customer) communications, including Internet access through cable modems and cable telephony. In many applications, the cable system's customer-premises equipment (CPE) is evolving beyond the cable modem and set-top box to a res-

idential home gateway that mounts outside the home. This home gateway contains the network-interface unit (NIU), which is the hub for all up and downstream communications at the residence, including cable-television

(CATV), cable-modem, and cable-telephony functions. In the past, the original equipment manufacturers (OEMs) of these cable home gateways were required to have inhouse RF transceiver expertise to develop custom solutions based on a propri-

etary technology. A commercial-offthe-shelf (COTS) solution with significant price/performance advantages could open up the market and speed the development of cable broadband services such as cable telephony.

The MT4950 RF-NIU Subsystem (see figure) from Microtune (n. Inc.

(Plano, TX) is standardsbased solution that, when integrated into an NIU, enables voice, video, and data ser-

vices across the broadband cable network. It is a standards-based product that is designed to migrate to future voice-over-Internet-Protocol (VoIP) implementations.

Based on a hybrid circuit-switched/

intellectual-property (IP) architecture, the RF subsystem supports circuit-switched and Data Over Cable Service Interface Specification (DOCSIS)-based implementations. The basic building blocks of the product include the company's RF single-

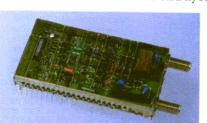
conversion tuner and a new higher performance MicroStreamer MT1540 upstream amplifier, RF automatic gain control (AGC), and intermediate-frequency (IF) circuitry, along with the functions of a network bias tap, high-voltage safety capacitors, primary lightning protection, cutoff relay, and net-

KEVIN LYNAUGH

Advanced Development Engineering Manager Microtune, Inc., 2201 10th St., Plano,

TX 75054; (972) 673-1600, FAX: (972) 673-1602, E-mail:

sales@microtune.com, Internet: www.microtune.com.



The MT4950 is an integrated transceiver subsystem that enables voice, video, and data services across a broadband CATV network.

work coupler. These functions are integrated into a single, cost-effective RF subsystem. A built-in DC-to-DC converter allows the system to be biased from a single +5-VDC supply.

Power consumption is a critical concern for cable-telephony systems due to the requirements of backup power to ensure lifeline telephone service. In order to minimize power consumption, a variant of the RF-NIU subsystem is designed using an IF amplifier structure, which provides fixed IF gain and corrects gain variations that occur with the fluctuations in temperature experienced in an outdoor environment (-40 to +75°C).

The MT4950 features an 88-to-862-MHz downstream range and a 5-to-42-MHz (or 5-to-65-MHz) upstream range. Band selection and tuning is performed using an I²C bus, and the transmit amplifier is controlled using a three-wire bus. The MT4950 is equipped

with two F connectors for cable and television connections.

Housed in a 2 × 4-in. (5.08 × 10.16-cm) package, the RF-NIU subsystem features maximum insertion loss of 2 dB from 88 to 862 MHz and 2.5 dB from 862 to 1000 MHz. Return loss is better than 15 dB from 5 to 862 MHz. Integrated into the MT4950, the MT1540 upstream amplifier, part of the company's MicroStreamer device family, offers +67-dBmV linear output power. The generous output power provides enough margin to overcome losses incurred from the system coupler and diplexer. Upstream harmonics are better than −47 dBc from 10 to 88 MHz.

Since it is mounted outside of the home, the NIU and home gateway have to be equipped with primary lightning and surge protection, stipulated in the US by standards developed by Underwriters' Laboratory (UL) and the IEEE. The RF-NIU transceiver subsystem is

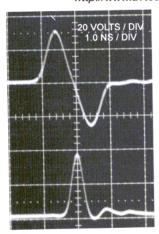
designed with safety capacitors, a highcurrent bias tap, as well as creepage and clearance spacing in order to meet these safety regulations.

Microtune will work with OEMs and cable-equipment suppliers to customize the RF-NIU transceiver subsystem to specific price/performance targets. The MicroStreamer MT1540 Upstream Amplifier is also available as a stand-alone component. It is designed for operation from a single +5-VDC supply and features a selectable transmit-disable function that can be accessed through an external control pin. P&A: \$35.00 (MT4950) (10,000 qty.) and \$2.00 (upstream amplifier alone) (10,000qty.). Microtune, Inc., 2201 10th St., Plano, TX 75074; (972) 673-1600, FAX: (972) 673-1602, e-mail: sales@microtune.com, Internet: www. microtune.com. MRF

Enter No. 52 at www.mwrf.com

MONOCYCLE GENERATORS AND IMPULSE GENERATORS

Data sheets and pricing on the Web! http://www.avtechpulse.com



We have expanded our line RF monocycle impulse generators for SAW. ultra-sonics and short pulse The radar applications. monocycle generators span the frequency and amplitude range of 20 MHz to 5 GHz and 10 Volts to 750 Volts while the impulse generators range from 10 Volts, 130 ps to 1000 Volts, 8 ns. Call or fax for a copy of our new 113 page catalog (Cat. No. 10). Our product information is now also available on the Web. Call World Wide Avtech for all your pulse generator and pulsed laser diode driver requirements



Enter No. 407 at www.mwrf.com



Enter NO. 414 at www.mwrf.com



Accelerating Tomorrow's Designs

Santa Clara Convention Center Santa Clara, CA

Conference: September 24-26, 2001

Test-Drive Showcase: September 25-26, 2001

Test-drive the new design tools that will move you ahead of the competition

Not another trade show

NOT Just Another Tradeshow

EDA: Front to Back features a unique test-drive showcase. You will be able to select from a wide range of educational sessions presented by vendors. Each "Test-Drive" Demo is equipped with a maximum of 6 computer workstation/PCs to demonstrate to a

small group of designers. You'll see the software in action and try it out for yourself in an intimate classroom-like setting.

This is the hands-on revolutionary forum that puts you in the driver's seat... Open the door, turn the key and Register Now!

Don't Miss one of the industry's most pervasive leaders, Mark Santoro of Juniper Networks, present his keynote address.

Tuesday, Sept 25, 8:30 AM

Each conference track consists of instruction training classes on the prime areas of design:

- Field Programmable Gate Arrays (FP)
- System Design (SD)
- Functional Verification (FV)
- Functional Design (FD)
- Physical Design (PD)
- Analog/Mixed Signal Design (MS)
- Design For Test (DT)
- Design Languages (DA, DB, DC, DD, DE, DF)
- DSP Design (DS)

Log onto www.edafronttoback.com

for registration, special events, exhibitors and technical conference details.







Planet FL





Hospitality Sponsor:



a Penton

Associate Sponsor:









PLLs Shine With Sapphire Technology

The use of CMOS-on-sapphire technology has led to a line of low-power PLLs capable of low-phase-noise operation in +3-VDC systems operating to 3 GHz.

apphire is more than a gem. As a true insulator at high frequencies, with superb thermal conductivity, it is a nearideal substrate material. Peregrine Semiconductor (San Diego, CA) has been able to produce sapphire substrates cost-effectively for use in a line of PLLs with excellent phase noise and low current consumption. The PLLs include integer-N and fractional-N models for use through 3 GHz.

The company's patented Ultra-Thin-Silicon (UTSi) CMOS-on-sapphire process is a variation of SOI technology that supports the integration of analog, RF, and digital active devices. In addition, Si is optically transparent, making it a suitable platform for the integration of fiber-optic components. The company, with UTSi design centers in the US and France, also boasts an advanced 6in. (15.24-cm), 0.5-µm wafer-fabrication facility in Sydney, Australia. Last year, the firm announced a series of high-performance components, including a high-linearity mixer, a series of switches, and lines of PLLs. The PLLs are noteworthy for their low phase noise and low power consumption.

For example, model PE3236 is a 2.2-GHz integer-N PLL with a divide-by-10/11 dual-modulus prescaler. It has an internal phase detector and can be programmed through serial, parallel, or hard-wire connections. The main divider handles input signals from 200 to 2200 MHz at levels of -5 to +5 dBm, while the reference divider oper-

ates at a maximum frequency of 100 MHz. The PLL draws 30-mA current at +3 VDC. It is supplied in a 44-

pin PLCC package. The model PE3240 PLL offers similar performance to the PE3236, but is supplied in a 20-lead TSSOP or 24-lead BCC package.

The model PE3336 integer-N PLL extends the frequency of operation to 3 GHz. It includes the internal phase detector and divide-by-10/11 prescaler, and is pin-compatible with the PE3236 PLL, but works with divider frequencies from 200 to 3000 MHz and reference frequencies to 100 MHz. For lower-frequency applications, the model PE3238 integer-N PLL offers the phase detector and divide-by-10/11 prescaler, but with a main divider frequency range of 200 to 1500 MHz. The maximum reference frequency is 100 MHz.

The company also offers the model PE3291 dual (1200- and 550-MHz) fractional-N PLL and the model PE3293 dual (1800- and 550-MHz) fractional-N PLL. Peregrine Semiconductor, 6175 Nancy Ridge Dr., San Diego, CA 92121; (858) 455-0660, FAX: 455-0770, Internet: www.peregrine-semi.com.

Enter No. 53 at www.mwrf.com

JACK BROWNE
Publisher/Editor

Miniature

Wideband

- Low Cost
- Optimized & Octave Bandwidths
- 0.58" x 0.80"



MICROWAVE CORPORATION

Enter No. 290 at www.mwrf.com

sit our web site at http://www.synergymwave.com

ontact Synergy's Sales and Application team.

Of McLean Blvd., Paterson, New Jersey 07504
hone: (973) 881-8800 Fax: (973) 881-8361

mail: sales@synergymwave.com

Gall-For Speakers



February 25 - March 1, 2002 San Jose Convention Center San Jose, CA www.WirelessPortable.com

Take a position as a leader in one of the fastest growing forums for professional dialogue in electronics engineering and design. We're looking for industry experts to propose a session for the upcoming Wireless Symposium & Exhibition Spring 2002 Conference. Much of the rapid growth of the wireless and portable industry has been due to the ongoing interchange of professional expertise. Your participation helps to further that growth. It's also a great opportunity to meet your peers, showcase your ideas, and build your career. Your ideas are valued!

About the Wireless Symposium & Exhibition

The conference will take place February 19-21, 2002 at the San Jose Convention Center, San Jose, CA. For over nine years the Wireless Symposium & Exhibition has been a place for engineers to investigate new technologies and techniques. It has become the preeminent technical conference for designers and engineers of portable and wireless products.

Acceptance Guidelines

Sessions are selected based on content originality, quality and timeliness. We do not imitate programs found at other conferences. If you are planning to present the same topic within the next 12 months, please indicate where so your program can be adjusted appropriately. We do not accept canned topics, or overtly commercial content. Each session must be one-of-a-kind and intended to inform, not sell attendees. All submitted material becomes the property of Penton Media, Inc.

About Penton Media

Wireless Symposium & Exhibition is managed and produced by Penton Media, Inc., publishersof Microwaves & RF, EE Product News, Wireless Systems Design, Internet World, Electronic Design, Boardwatch, and Netronics.

Penton Media, Inc., 611 Route 46 West, Hasbrouck Heights, NJ 07604 Phone: 201-393-6060 Fax: 201-393-6297.

Submission Guidelines

To be considered as a speaker, please submit the following information:

- **1.** Your name, title, company or organization, address, phone, fax and email address.
- 2. A short professional biography (50 words maximum).
- Proposed session title and a 150-word abstract. This material must be included or your submission will not be considered.

Please indicate what type of session you are proposing. We offer three types of sessions at the Wireless/Portable Symposium & Exhibition:

- Paper Presentation Session: Led by a "Session Chair" and includes a number of papers on a general theme. Each speaker/author makes a 20-30 minute presentation based on their paper.
- Mini-Tutorial "Expert" Session: Presented by an expert instructor on one concise topic, a case study, a narrow discipline, or "tips and tricks".
 1 to 1.5 hours in length.
- Full-Day Workshop Tutorial Session: 1 or 2 day session presented by an expert instructor.
- **4.** If you will be speaking elsewhere within the next twelve months, please indicate where.

Submit your session proposal by September 7, 2001 to Betsy Tapp, Conference Manager, via fax 201-393-6297 or e-mail btapp@penton.com.











SAW Filter Screens PS Receive Signals

Based on SAW technology, this compact filter provides the out-of-band rejection needed for sensitive GPS receivers, without adding excessive in-band insertion loss.

ocation services such as the Global Positioning System have proven invaluable in military theaters, but they are also rapidly gaining acceptance in commercial applications such as in-vehicle systems. In support of this growth, SAWTEK, Inc. (Orlando, FL) has developed a tiny surface-acousticwave bandpass filter to combine high rejection of unwanted signals with low insertion loss for desired GPS signals.

> The model 855969 filter (see figure) provides the critical function of RF filtering in a GPS receiver. In order to minimize signal-recovery errors in the receiver, the filter should exhibit minimal signal loss. At the same time, since

a variety of voiceand data-transmission systems operate in the frequency bands surrounding GPS, the filter must also keep these signals from entering the front-end electronics of the GPS receiver where they could cause unde-

sired mixing and IMD effects.

these goals with simultaneous low insertion loss and high out-of-band signal rejection. The tiny filter is designed to oper-MHz. It has a bandwidth of 2.4 MHz around that center frequency, with maximum in-band insertion loss of 1.8

dB. The typical insertion loss is only 1.3 dB. It also achieves as much as 50-dB out-ofband rejection of potential interfering signals such as cel-

lular and personal-communicationsservices (PCS) transmissions. The typical rejection is achieved in the critical 824-to-869-MHz and 1640-to-1926-MHz frequency ranges.

The SAW GPS RF receive filter mea-

sures $3.0 \times 3.0 \times$ 1.2 mm and is supplied in a surfacemount package for ease of installation in crowded printedcircuit boards. It is 94-percent smaller than ceramic filters with similar bandwidth, which should help designers of GPS

receivers for embedded applications. It is designed for use at 50 Ω , with an impedance-matched, single-ended source of load ports. SAWTEK, Inc., P.O. Box 609501, Orlando, FL 32860-9501; (800) 332-8638, (407) 886-8860, FAX: (407) 886-7061, e-mail: info@sawtek.

com, Internet: www.sawtek.com.

Enter No. 54 at www.mwrf.com

JACK BROWNE

Publisher/Editor

The tiny model 855969 SAW filter is

designed to pass GPS RF signals at

1575.42 MHz while rejecting out-of-

band signals by at least 50 dB.

Simulator TacklesTricky EM Problems

The latest version of this EM simulation and optimization package includes flexible simulation engines, a menu-based interface, and a versatile optimizer.

lectromagnetic (EM) simulation has become a well-established tool for the prediction of current flow and field patterns in planar and three-dimensional (3D) structures. The IE3D EM simulation and optimization package from Zeland Software (Fremont, CA) is now in Version 8 with a set of capabilities and features for solving the most demanding EM problems in 3D structures and multilayer high-

frequency circuits.

Version 8 of IE3D for Windows is a full-wave, method-of-moments (MoM) simulator that can be used to model the current distribution in a variety of transmission media, including microstrip, stripline, coplanar waveguide, suspended stripline, coaxial lines, rectangular waveguide, high-speed digital transmission lines, interconnections, and filters. The software features a straightforward menu-driven graphical user interface (GUI), and can model a wide range of dielectric materials, handling lossy and high-dielectric-constant layers as thin as 0.1 mm. This latest version of the EM simulator includes advanced iterative matrix solvers (AIMS) for large layouts. The new version can speed up simulations and reduce random-access-memory (RAM) requirements by a factor of 10 for large integrated circuits (ICs) and antenna designs compared to previous versions.

The EM simulator handles models within an enclosure, under open-boundary conditions (such as an antenna) or

under periodic-boundary conditions. The software automatically generates a nonuniform mesh around a modeled

structure using rectangular and triangular cells. It also automatically generates edge cells for high accuracy when modeling the current distribution along the edges of conductors. In fact, the software can exactly model current on four sides of a metallic strip.

Rather than assuming models with infinite ground planes, IE3D allows operators to solve antenna and circuit problems with finite ground planes, as well as circuits with differential feed structures. The software enables the modeling of conductor thickness, rather than assuming an infinitely thin conductor and neglecting electrical thickness effects.

The IE3D software simplifies the creation of 3D models through its built-in library of circles, rings, spheres, rectangles, circular spirals, cylindrical and conical via holes, and helices. IE3D can import GDSII files, AutoCAD DXF files, and CalTech Intermediate Form (CIL) layout files. It can save files in these formats, in a proprietary 3D Text file format, and in a FIDELITY file format used by the firm's 3D simulation tools

JACK BROWNE
Publisher/Editor

PRODUCT — technology

for modeling 3D structures with nonuniform dielectric constant. The IE3D program places no limits on the number of ports that can be defined, and enables flexible de-embedding of circuit parameters. Results are provided in the form

The FM

simulator handles

models within an

enclosure, under

open-boundary

periodic-bound-

ary conditions.

conditions or

of S-parameters, although S-parameter data can be optionally converted into Simulation-Program-with-Integrated-Circuit-Emphasis (SPICE) netlists for use with a SPICE simulator. IE3D offers full-color visual displays of S-, Y-, and Z-parameters, with two-dimensional (2D) and 3D displays of current dis-

VIA (Vendor Instant Access).

tribution, radiation patterns, and nearfield EM radiation patterns. In addition to simulators, operators can define the shape of a circuit as a set of optimization variables and then apply the builtin GeneticEM optimizer to achieve a design that has desired performance levels.

Release 8 of IE3D is supplied on a compact-disc-read-only memory (CD-ROM) with full documentation and a

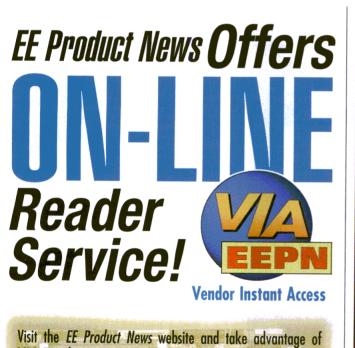
series of sample files. The software includes the Intelli-Fit curve-fitting scheme that can be used to extract the frequency response of a complicated structure with multiple resonances. It incorporates periodic Green's functions for analysis of phasearray designs. The software suite includes a simple-to-use circuit sim-

ulator that helps to perform functions including finding the characteristic impedance of a transmission line, creating S-parameters for a suitable transmission line, and extracting the S-param-

eters from a section of a circuit. In addition to the standard package (with no limit to the number of unknowns in a simulation), a version of the software is also available with an upper limit of 1000 unknowns.

In addition to IE3D, the company offers MDSPICE, a wideband SPICE simulator. The S-parameter-based simulator yields precise time-domain waveforms on extremely long transmission lines and electrically long interconnections. The software, written for Windows NT operating systems, features nonlinear modeling for analog and digital circuits. P&A: \$17,000 (standard IE3D package), \$10,000 (limited IE3D version), and \$10,000 (MDSPICE): stock. Zeland Software, Inc., 39120 Argonaut Way, PMB 499, Fremont, CA 94538; (510) 623-7162, FAX: (510) 623-7135, e-mail: ze land@zeland.com, Internet: www. zeland.com. MRI

Enter NO. 55 at www.mwrf.com



With VIA, you can request information from vendors appearing in EE Product News by e-mail, mail, phone,

www.eepn.com

fax, or by linking directly to the vendor's website!

The wireless market is heating up...make sure your products don't.

From phone to FET channel, increase reliability with TAS - the complete Thermal Analysis System.

To download a demo of TAS or to learn more about Harvard Thermal's engineering services please visit our web site at:

WWW.HarvardThermal.com

Harvard Thermal, Inc. 249 Ayer Road, Harvard, MA 01451 Tel: 978-772-3800 • Fax: 978-772-9765 www.HarvardThermal.com

www.HarvardThermal.com

Enter NO. 420 at www.mwrf.com



Continued from page 181

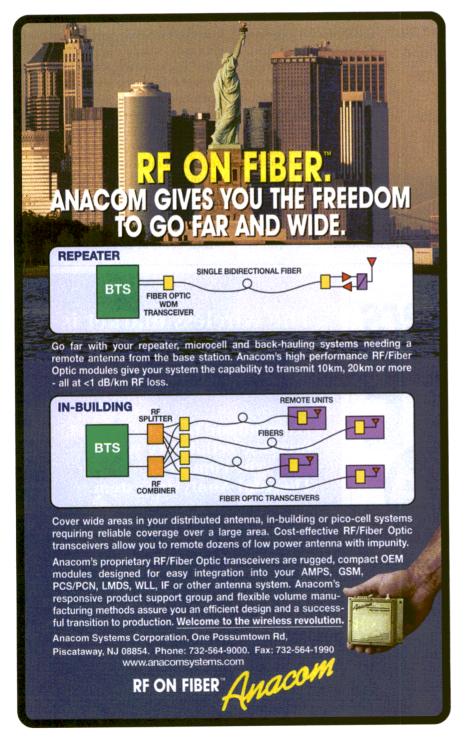
issue, Jack Browne would assume the role of Chief Editor, a position that he has held to this day.

In May 1988, a technology assessment offered by Alan Conrad of Configuration Analysis Management (Danbury, CT) would point to the need for speed in signal-processing applications. Alan ("Pete") Conrad remains affiliated with the magazine to the present, now serving as Special Projects Editor. In July of

that year, Sciteq Electronics (San Diego, CA) launched a direct digital synthesizer capable of 20-ns switching speed across a 250-MHz bandwidth, using digital control of a digital-to-analog converter (DAC) to create analog output signals.

The 1990s were marked by the growth of commercialism to an industry accustomed to military customers. The cellular telephone replaced the radar system for many companies and numerous IC suppliers, such as RF Microdevices (Fig. 8), Analog Devices, and Maxim Integrated Components, were able to meet the needs of these emerging wireless markets. Since these markets stressed fast delivery times, microwave companies became more concerned with higher-speed test equipment and modeling software. The late 1980s and early 1990s were also marked by the growing sophistication of computer-aideddesign (CAD) tools with two companies-EEsof, Inc. (Westlake Village) and Compact Software (Paterson, NJ)-each making major contributions to the development of software tools for the personal computer (PC) during the late 1980s and early 1990s. As the PC has grown in processing power and speed, so have developers of EM simulation tools, including Ansoft (Pittsburgh, PA) and Sonnet Software (Liverpool, NY).

The beginning of 2000 saw a carryover of the economic good fortune enjoyed by many high-frequency companies during the 1990s. But 2001 has seen an economic downturn and a slowdown for many companies. Fortunately, as the 40-year history of this magazine has shown, this is truly a cyclical business with large and small cycles. Ironically, the military markets that were all but abandoned during the commercial gold rush of the 1990s are now the focus of a number of companies seeking growth markets. And the opticalcommunications market may yet become one of the largest segments of the "microwave" industry. MRF



JACK BROWNE

Publisher/Editor



System Speeds Assembly Of RF Power Devices

This automated system provides preheating of device packages, precision handling and placement of components, and consistent eutectic attachment of semiconductors.

ower RF transistors are generally assembled by hand, with all of the inconsistencies of die placement and bond-wire attachment associated with human handling. But the HotRail Radio Frequency Assembly (RFA) Cell from Palomar Technologies (San Diego, CA) is an automated assembly system that can do away with the inconsistencies found with hand assembly of power devices and amplifiers.

The fully automatic, in-line multichip system provides void-free assembly and programmable steady-state heat control for eutectic die attach, with placement precision of ± 10 to $12~\mu m$.

The system (see figure) is designed to

dramatically increase the throughput of high-power device and amplifier assembly lines. The system can handle wafers from 3 to 8 in. (7.62 × 20.32 cm) in diameter and can handle components in 2- and 4-in. (5.08 × 10.16-cm) waffle and gel packs and in tapeand-reel formats.

The system incorporates an eight-

position turret head that is for a wide range of vacuum tools. The system enables loading of a large quantity of parts at one time, while the component-assembly system can eject and attach fragile die, including 3-mil-thick GaAs devices. The system can be equipped with a vacuum tool for moving components

larger than 2 in. (5.08 cm) on a side.

Parts are preheated as they enter the hitch-feed conveyor assembly to gradually reach the required eutectic temperature. A clamping mechanism holds the headers in place at the required

eutectic temperature to achieve precision side-by-side placement of die for wire-bonding attachment and consistent wire-loop profiles. The temperatures of the preheat, eutectic, and cool-down zones can be independently programmed by an operator. Palomar Technologies, 2230 Oak Ridge Way, Vista,

CA 92083-8341; (760) 931-3406, FAX: (760) 931-3444, Internet: www.palomartech nologies.com.

Enter No. 57 at www.mwrf.com



The HotRail RFA assembly system couples high-capacity input and output magazine handlers with precision component-assembly capability. It can handle wafers from 3 to 8 in. (7.62 \times 20.32 cm) in diameter.

MICROWAVES & RF

SPICE-Based SoftwareFine-Tunes Designs

With its hierarchical format, this powerful program allows engineers to integrate complex circuit designs with analog and digital components to nearly unlimited nested depths.

imulation Program with Integrated-Circuit Emphasis (SPICE)-based programs are still among the most widely used of computer-aided-engineering (CAE) tools for high-frequency, high-speed circuit design. The latest version of Orcad PSpice A/D from Cadence Design Systems (Portland, OR) builds on the tradition of SPICE simulation by simplifying the design of mixed analog/digital circuitry and

adding new tuning and optimization capabilities. The latest version of PSpice features more than 16,000 component models, including active devices and passive circuit elements.

The first version of PSpice was introduced in 1985 by MicroSim Corp., which was later acquired by Orcad, which was, in turn, acquired by Cadence Design Systems. The popular program has been continuously enhanced and structured to accommodate the latest hardware and operating systems.

Orcad PSpice A/D permits users to simulate mixed analog/digital circuits of any size. Simulation results for analog and digital functions can be viewed in a common plot window using a common time axis. The program automat-

ically recognizes analog-to-digital and digital-to-analog connections within a design. Using a companion program known as the Orcad PSpice Optimizer, designers can fine-tune designs according to prescribed performance parameters and automate the optimization process according to a number of different component values.

The program seamlessly supports hierarchical designs containing components, circuit models, or subsystems that are reused extensively. Figure 1 illustrates a simple active-filter hierarchical block diagram. Each block, in turn, contains a bandpass resistance-capacitive (RC) biquad active filter (Fig. 2). Clicking within either of the hierarchical blocks and selecting "descend" reverts the active-filter block diagram of Fig. 1 to the simpler structure of Fig. 2. Component values can be changed, performance parameters can be redefined, and probes can be inserted at different locations before quickly re-running a simulation and almost instantly generating a new set of tuned or optimized results

ALAN CONRAD Special Projects Editor

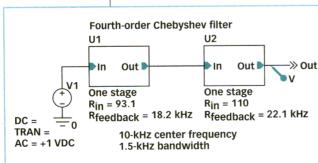


Fig. 1. This hierarchical block diagram represents a simple active fourth-order Chebyshev filter design in the latest version of PSpice A/D from Cadence Design Systems.

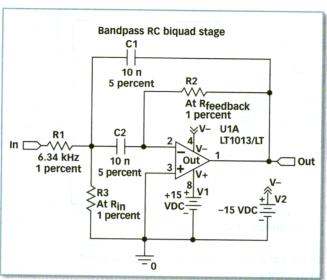
PRODUCT — technology

that reflect the effects of the changes.

The software allows operators to define specific measurements and plot configurations, or select from a wide variety of standard PSpice plots, such as bode plots, bandwidth plots, group-delay plots, Nyquist plots, and log-linear plots. Plotting functions can be used to display Bode plots of phase and magnitude on separate Y-axes of a single plot or on stacked plots with a common frequency axis.

An interactive stimulus editor allows users to define waveform parameters of sine, pulse, exponential pulse, and single-

frequency frequency-modulation (FM) waveforms or create freehand linear (PWL) signals by dragging the mouse. Designers can explore circuit behavior



2. This bandpass RC biquad stage is contained within the hierarchical block diagram of the active filter.

using basic DC, AC, noise, and transient analyses, as well as view node voltages, pin currents, and power consumption or noise of individual devices.

Designs can include specific local temperature effects on individual devices for more accurate analyses and track circuit behavior variations, as components change with parametric, Monte-Carlo, or worst-case analyses. They also display Fourier transforms of time-domain signals or inverse transforms of frequency-domain signals. Users can vary component values over multiple runs and quickly view results as a family of waveforms with parametric, Monte-Carlo (Fig. 3), and worst-case analyses while plotting waveform characteristics such as rise time versus tem-

perature or supply voltage, using parametric analysis.

The program allows users to monitor the progress of a transient analy-

max

SUBSTRATES

Tungsten Carbide Aluminum Nitride

(fused & natural)

Other dielectrics

CAPABILITIES

Alumina Beryllia

Quartz

Titanates

Metals

ULTRA-PRECISION SUBSTRATES

Surface finish tolerances to

First time. Every time

Consistency, Quality, Responsive

service. Peace of mind. These are

For precision substrates fabricated to

fine tolerances and "exact duplicate"

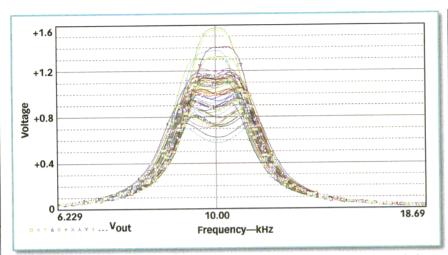
repeatability, look to the industry

the reasons Accumet customers

return to us again and again.







3. In these Monte Carlo-simulation results, all component parameters are varied 1 percent over 25 design/simulation iterations.

sis and, if necessary, extend it beyond the original end time without restarting the simulation. Users can increase simulation speed by specifying looser tolerances and time steps during noncritical periods of transient analysis. Users can modify simulation run times without restarting the simulation in the event of convergence problems. The user can pause the analysis in progress, change run-time simulation settings, and continue.

Designers can maximize a circuit's performance with a PSpice optimizer that operates in conjunction with PSpice A/D. The optimization routine tunes the values of up to eight user-specified circuit parameters. Optimization specifications can be set as goals or constraints. Optimizer reports include the margins of each constraint and sensitivity of each specification with respect to each parameter.

Orcad PSpice runs under Windows 95 or higher operating system, Windows NT 4.0 with service pack three or later, and with a Pentium or equivalent processor with 32-MB random-access memory (RAM) and 50-MB available hard-disk memory. Cadence Design Systems, Inc., PCB Systems Div., 13221 SW 68th Pkwy., Ste. 200, Portland, OR 97223; (503) 671-9500, FAX: (503) 671-9501, e-mail: pcbinfo@cadence.com, Internet: www.cadence.com. MRE

Enter No. 59 at www.mwrf.com



Switches and Power Dividers

JFW Industries continues to redefine high performance RF switches and power dividers at competitive prices. With over 1,500 individual models currently available and custom design capabilities, JFW has the switching and power divider solutions that you need. Recent innovations include 2 and 4 way dividers optimized for cellular and PCS applications with a guaranteed minimum isolation of 40 dB, as well as

1P2T and 1P4T solid-state switches designed specifically for 3 G applications up to 3 GHz. For more information, please contact us or visit the Switch and Power Divider sections on our web site at www.jfwindustries.com/rfswitches.htm

www.jfwindustries.com/dividers.html

JFW Industries, Inc.

Specialists in Attenuation and RF Switching

TEL (317) 887-1340 • Toll Free 1 (877) 887-4539 • Fax (317) 881-6790 5134 Commerce Square Dr. • Indianapolis, Indiana 46237

Internet- http://www.jfwindustries.com E-mail- sales@jfwindustries.com ISO 9001 Certified

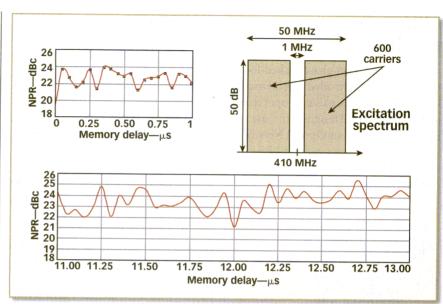
Enter NO. 426 at www.mwrf.com

DESIGN

Continued from page 92

equal-amplitude, random-phase, uniform-frequency spacing and a central, 1-MHz notch that is 50 dB deep. The block diagram of the simulation is roughly similar to that of ref. 5 with appropriate filtering adjustments. A greater number of carriers would have been required to fully satisfy the statistical requirements of this noise simulation. As previously mentioned, though, the "mem.model" greatly increases the computer RAM consumption and, therefore, severely limits the number of sources that can be treated.

Before looking at NPR results, it is of prime importance to see what kind of manifestation arises at the output of the "mem.model" from the combined influences of distortion and memory effects. Displaying the output-signal envelope versus time for different values of the memory delay τ does not reveal any clear modification with respect to the input excitation. As expected, noise resembles noise. It is more appropriate to examine how the corresponding power behaves. This was performed by adding a "SIGPWR" test at the output of the "mem.model." Indeed. this function made it possible to determine the total output power Pout total over the entire band of the NPR excitation. Figure 9 shows the result of this investigation versus the memory delay τ for a total input power of 0 dBm. This representation is limited to small intervals of τ due to the fact that the value of $P_{\rm out\,tot}$ versus τ is nearly constant except for 0 μs, 12 μs, and all of its multiples, where it exhibits steep negative impulses of approximately 1-dB amplitude. A relatively simple interpretation of this behavior can be provided. The 12-us period of P_{out total} versus τ can be viewed as a direct manifestation of the beat period relating to the basic 83.33-kHz frequency spacing of the 600 carriers that synthesize the random-excitation process. On the other hand, the fact that these periodic impulses are steep and negative must be interpreted according to a statistical approach. Indeed, for $\tau =$ $0 \mu s$ and each multiple of $12 \mu s$, the situation can be considered memoryless



10. This figure shows the NPR variations versus the memory delay τ obtained from simulation on a "MAR3" module, with the previously discussed excitation spectrum and 0-dBm total input power.

and distortion occurs instantaneously at each peak of the input signal. Compression of Pout total is then maximum. But as soon as τ differs from these particular values, the random nature of the signal predominates, which results in less compression and an unvarying value of Pout total. This interpretation is corroborated by the width of the impulses shown in Fig. 9. The 0.1-us width appears to agree well with the theoretical autocorrelation time constant of the narrowband, quasi-white-noise process involved in this simulation, which is the reciprocal value of the noise bandwidth (here it is 50 MHz).

The foregoing development clarifies the NPR behavior versus the memory delay τ . NPR, which is defined as the ratio of the carrier-power density outside the notch to the IM power density within the notch, is performed in the simulation block diagram through two, 500-kHzwide bandpass filters followed by adequate calculation. Figure 10 shows a typical example of the NPR behavior versus τ for a total input power of 0 dBm, as stated previously. NPR, similar to P_{out total}, exhibits fluctuations around an averaged value (approximately 23 dBc). Nevertheless, the magnitude of these fluctuations is substantially larger than those of Pout total. The most prob-

able explanation for this observation is that the NPR calculation is based on a noise-to-noise ratio and, moreover, is performed on small-analysis bandwidths compared to the total bandwidth of interest. As a consequence, the periodic impulses for $\tau = 0$ µs and the multiples of 12 µs are now nearly imperceptible. Note that these results are based on only five successive simulation runs. Of course, one can reduce the uncertainty of the results by increasing the number of runs. But this requires more computing time. A more suitable improvement lies in a future extension of computer RAM to increase the number of carriers to several thousand. MRE

REFERENCES

- 1. R. Hassun, "Comparing Analog and Digital Techniques For Measuring Noise Power Ratio," *Microwave Journal*, pp. 88-98, March 1997
- 2. G.L. Heiter, "Characterization of Non Linearities in Microwave Devices and Systems," *IEEE Transactions*, No.12, pp. 797-805, December 1973.
- J.C. Pedro and N. Borges de Carvalho, "On the Use of Multitone Techniques for Assessing RF Components' Intermodulation Distortion," *IEEE Transactions*, No.12, pp. 2393-2402, December 1999.
- 4. T. Reveyrand et al., "A Novel Experimental Noise Power Ratio Characterization Method for Multicarrier Microwave Power Amplifiers," 55th ARFTG Conference, Boston, pp. 22-26, June 2000.
- 5. P. Delemotte and Y. Crosnier, "Predict NPR For RF Modules Using System Simulation," *Microwaves & RF*, pp. 55-63, July
- 6. W. Bosch and G. Gatti, "Measurement and Simulation of Memory Effects in Predistortion Linearizers," *IEEE Transactions*, No.12, pp. 1885-1890. December 1989
- 7. V. Meghdadi *et al.*,"Modeling of Solid State Power Amplifiers (SSPA) and Validation By Means of a System Simulator," *Ann.Telecom.*, Vol. 53, Nos. 1-2, pp. 4-14, 1998.



VCXO Works To 622.08 MHz

A LOW-PROFILE, non-phase-locked-loop (PLL) voltage-controlled crystal oscillator (VCXO) is capable of operating at 622.08 MHz. Designed for use in PLLs of Synchronous Optical Network (SONET)/synchronous-digital-hierarchy (SDH) systems, this +3.3-VDC oscillator is based on a fundamental-mode



crystal. The VCXO also minimizes jitter [<1 ps root-mean square (RMS)]. The unit is housed in a low-profile, nonhermetic 1.0×1.2 -in. (2.54×3.04 -cm) package with FR4 substrate and grounded metal cover. P&A: \$117.00 each.

Connor-Winfield Corp., 2111 Comprehensive Dr., Aurora, IL 60505; (630) 851-4722, FAX: (630) 851-5040, e-mail: info@conwin.com, Internet: www.conwin.com.

Enter No. 77 at www.mwrf.com

Load Provides Amplifier Stability

THE ZXFV201 IS a high-speed, current-mode amplifier that meets the requirements of video and high-speed signal-processing applications. The unit operates over the -40 to $+85^{\circ}\text{C}$ temperature range and provides a bandwidth of 300 MHz, a slew rate of 400 V/ μs , and an output-drive rating of 40 mA. The device maintains stability with up to 400 pF of capacitive load. Differential gain and phase are low at 0.01 percent and 0.01 deg., respectively. Power-supply requirements are ± 5 VDC at a current of 7 mA per amplifier. P&A: \$2.00 each (1000 qty.).; 4 to 6 wks.

Zetex, Inc., 47 Mall Dr., Commack, NY 11725; (631) 543-7100, FAX: (631) 864-7630, Internet: www.zetex.com.

Enter No. 78 at www.mwrf.com

Gain Block Boasts 2.9-dB Noise Figure

THE SGA-7489 IS a silicon-germanium (SiGe) 50-Ω cascadable gain block featuring high output third-order intercept point (IP3) [+36 dBm at 850 MHz], high gain (22 dB at 850 MHz), and a noise figure of 2.9 dB from a single positive supply voltage. The unit is also an intermediate-frequency (IF) amplifier, with an output IP3 of +38 dBm and P1dB of +23 dBm at 100 MHz. Housed in a standard surface-mount SOT-89 package with backside metallization, this amplifier requires only DC blocking, bypass capacitors, and a bias inductor for external components. P&A: \$1.95 each (10,000 qty.).

Standford Microdevices, Inc., 522 Almanor Ave., Sunnyvale, CA 94086; (800) 764-6642, (408) 616-5464, FAX: (408) 739-0970, Internet: www.stanfordmicro.com. Enter No. 79 at www.mwrf.com

FET Operates To 500 MHz

THE L2721 IS a 15-W, 11-dB gain, 500-MHz, low-cost laterally-diffused-metaloxide-semiconductor (LDMOS) field-effect transistor (FET). It is assembled in a two-lead surface-mount package. It is not internally matched and will operate from DC to above the frequency of test. The FET is intended to operate from +12- to +16-VDC power supplies. It is suitable for narrowband or wideband circuits.

Polyfet RF Devices, 1110 Avenida Acaso, Camarillo, CA 93012; (805) 484-4210, FAX: (805) 484-3393, Internet: www. polyfet.com.

Enter No. 80 at www.mwrf.com

Connectors Target 50-Ω Coaxial Cables

THE RFD-1605-2 and RFD-1630-2 series of 7/16 DIN male and female connectors is silver (Ag)-plated machined brass connectors with Teflon insulation that features the versatile combination head

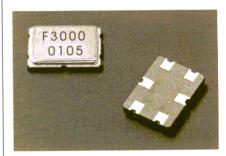
configuration. Since the ferrule stud backnut or cable-clamp assembly screws into the connector body, users have the ability to decide whether to create a straight or right-angle connector, offering maximum flexibility. The cable center conductor is soldered through either the side or the end opening of the connector body. The series is suitable for most $50-\Omega$ coaxial cables.

RF Connectors, 7610 Miramar Rd., San Diego, CA 92126; (800) 233-1728, (858) 549-6340, FAX: (858) 549-6345, e-mail: rfi@rfindustries.com, Internet: www.rfindustries.com.

Enter No. 81 at www.mwrf.com

Filters Span O to +85°C

THE F3000 FUNDAMENTAL-mode family of monolithic crystal filters is available in two- and four-pole configurations in a variety of bandwidth and rejection characteristics. Typical operating temperature ranges are from 0 to +70°C for indoor applications to -40 to +85°C for outdoor, power-pole environments. The filters are offered in a true surface-mount-device (SMD) ceramic package



measuring $7.0 \times 5.0 \times 1.4$ mm. Applications include cellular telephone, base stations, communications receivers (Rxs), local-area network (LAN), widearea network (WAN), wireless, and remote-meter reading. P&A: \$2.88 (10,000 qty.); stock to 10 wks. (prototypes) and 10 to 12 wks. (production qty.).

Tellurian Technologies, Inc., 1801 Hicks Rd., Suite B, Rolling Meadows, IL 60008; (847) 934-4141, FAX: (847) 934-4175, email: info@telliantech.com.

Enter No. 82 at www.mwrf.com

Sleeves Cover Antenna Elements

ANT SKINS ARE low-cost antenna sleeves in lengths that cover the 400-MHz-to-2.4-GHz frequency range. The sleeves provide the ruggedness of whip antennas, but are hollow to cover a low-cost internal element such as a wire, rod, or flexible shaft. The sleeve is designed to support a range of mounting options. P&A: less than \$0.50 (in production quantities).

Antenna Factor, 575 SE Ashley Pl., Grants Pass, OR 97526; (541) 956-0931, FAX: (541) 471-6251, Internet: www.anten nafactor.com.

Enter No. 83 at www.mwrf.com

Oscillator Boasts Low Jitter

THE PE1100BV SERIES is a line of differential positive-emitter-coupled-logic (PECL) output oscillators. The series uses a true crystal design for jitter of 3 ps root



mean square (RMS) maximum for >70 MHz. With a frequency range spanning 10 to 170 MHz, the parts have an input voltage of +3.3 VDC \pm 10 percent or +5 VDC \pm 10 percent.

Pletronics, Inc., 19013 36th Ave. W., Suite H, Lynnwood, WA 98036; (425) 776-1880, FAX: (425) 776-2760, e-mail: ple-sales@pletronics.com, Internet: www.pletronics.com.

Enter No. 84 at www.mwrf.com

Filter Features 50-dB Rejection

MODEL NBR MR1004X is a multioctave band-reject filter. Covering 7 to 18

GHz, insertion loss is 2 dB typical, bandwidth is 180 MHz at 3 dB typical, and rejection bandwidth is 20 MHz minimum. Rejection is 50 dB, passband spurious and ripple is 5 dB, limiting level is +10 dBm minimum, and linearity is ±10 MHz. Coil resistance

is 110 μH typical.

OMNIYIG, 3350 Scott Blvd., Bldg. 66, Santa Clara, CA 95054; (408) 988-0843, FAX: (408) 727-1373, e-mail: Omniyig@ix.netcom.com, Internet:

www.Omniyig.com.

Enter No. 85 at www.mwrf.com



Enter No. 413 at www.mwrf.com

QUIET DROS – CLEAR COMMUNICATION



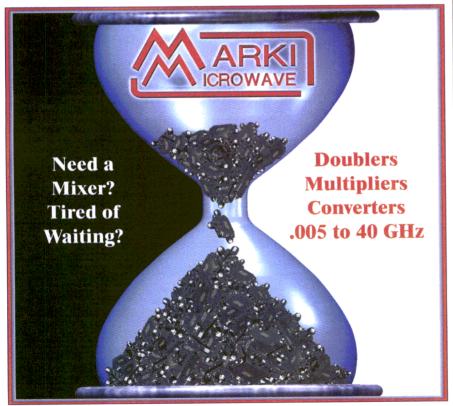
The desire for low noise Dielectric Resonator Oscillators to enhance clear communication, spectral purity, continues. Typical phase noise @ 100 KHz offset of -126 dBc/Hz for 10 GHz, -115 for 18 GHz, and -108 for 38 GHz are being measured on our production DROs. Harmonics measure between -50 dBc and -80 dBc. Spurious are less

than -90 dBc with -120 dBc available by request. Designs under way promise to reduce phase noise even more significantly. Check the Lucix Website for outstanding features of our DROs, such as low power consumption, very small size, high output power, ultra stability. Tell us your special needs. At Lucix, we Listen.



800 Avenida Acaso, Unit E Camarillo, CA 93012 Phone: 805-987-6645 805-987-6145 Fax:

Enter No. 429 at www.mwrf.com



Website: MarkiMicrowave.com

Phone: (408) 778-4200 Fax: (408) 778-4300

Email: Mixers@MarkiMicrowave.com

Enter No. 430 at www.mwrf.com

new products

Monitor Detects Gamma Rays To 0.02 MeV

GAMMA-SCOUT IS a handheld radiation monitor. It features a Geiger-Müller tube detector and a large liquid-crystal display (LCD) mounted in an ergonomic, rugged, impact-resistant Novodur housing. Gamma-Scout measures alpha, beta, and gamma rays to 4.00, 0.20, and 0.02 MeV, respectively. The onboard memory and serial port make this device suitable for field-measurement and data-logging applications. An ultralong-life 10-year battery is included. P&A: \$329.95 each.

Scientifics, Dept. A011-C999, 60 Pearce Ave., Tonawanda, NY 14150; (800) 728-6999, (716) 874-9091, FAX: (800) 828-3299, e-mail: cons_order@edsci.com, Internet: www.scientificsonline.com. Enter No. 86 at www.mwrf.com

Switch Targets DC To 3 GHz

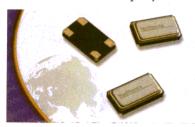
THE SW-456 IS a single-pole, doublethrow (SPDT) gallium-arsenide (GaAs) switch that is suitable for low-power switching applications ranging from DC to 3 GHz. The switch operates on positive or negative control voltages that are as low as +2.3 VDC, offers insertion loss of less than 0.4 dB, and an isolation that is greater than 15 dB at 1 GHz. The SW-456 provides switching between two RF inputs and two RF outputs. The switch can be used in low-power time-division-multiple-access (TDMA), code-division-multiple-access (CDMA), as well as wideband-CDMA (WCDMA) wireless systems at personal-communications-services (PCS), digital communications services (DCS), and cellular frequencies, along with many other low-power DC-to-3-GHz systems. P&A: \$0.40 each (10,000 qty.).

M/A-COM, Inc., 1011 Pawtucket Blvd., Lowell, MA 01853; (978) 442-5000, FAX: (978) 442-5350, Internet: www.macom.com.

Enter No. 87 at www.mwrf.com

TCVCXO Spans $-30 \text{ To } +80^{\circ}\text{C}$

THE S6800 SERIES IS a surface-mount temperature-controlled voltage-controlled crystal oscillator (TCVCXO) that delivers frequency stability of ± 2.5 PPM maximum versus temperature, ± 0.3 PPM maximum versus supply voltage, ±1.0 PPM maximum per year versus



time, and ± 0.3 PPM maximum versus load. With a supply voltage of +3 VDC ±5 percent, the \$6800 yields a frequency control range of ± 5 to ± 12 PPM from a pull voltage of +0.5 to +2.5 VDC. Available in standard wireless frequencies of 12.80, 13.00, 14.40, 19.20, and 19.68 MHz, the unit operates within the temperature range of -30 to +80°C. The S6800 series is especially applicable within tight environments such as Personal Computer Memory Card International Association (PCMCIA) cards and handheld wireless devices.

SaRonix, 141 Jefferson Dr., Menlo Park, CA 94025; (650) 470-7700, FAX: (650) 462-9894, e-mail: saronix@saronix.com, Internet: www.saronix.com.

Enter No. 88 at www.mwrf.com

Amplifier Suits Custom Space Applications

A FIVE-CHANNEL AMPLIFIER has been specifically designed for custom space applications. Each independent channel that is used features a dedicated RF input/output (I/O), along with DC-bias connections. Each channel's RF performance is tailored differently to meet the application requirements. All components were manufactured and screened according to MIL-PRF-38534 Class K requirements.

Cougar Components, 198 Union Blvd., No.

200, Lakewood, CO 80228; (408) 522-3838, FAX: (303) 985-5177.

Enter No. 89 at www.mwrf.com

Duplexer Unaffected By Temperature

A CERAMIC MONOBLOCK duplexer component that suits the wideband-codedivision-multiple-access (WCDMA) market provides additional benefits for integrated-circuit (IC) and cell-phone manufacturers, as well as consumers in the WCDMA field. This standard is important in the current market because it allows the world to use one cellular standard, improves efficiency throughout the network, and promises increased functionality, including high-speed Internet, streaming video, location awareness, and m-commerce. Ceramic duplexers, versus other technologies, are unaffected by temperature, vibration, or mechanical shock.

Murata Electronics North America, Inc., 2200 Lake Park Dr., Smyrna, GA 30080: (800) 831-9172, (770) 436-1300, FAX: (770) 436-3030.

Enter No. 90 at www.mwrf.com

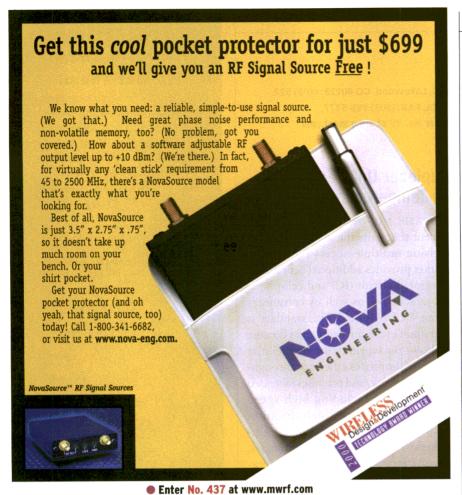
Filter Thwarts PCS Interference

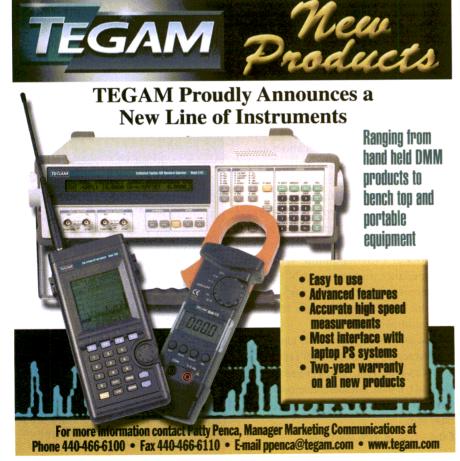
MODEL 14042 BANDPASS filter is used to prevent personal-communications-services (PCS) interference at the ENG receive site. It passes the entire ENG band (channels 1 through 10, from 1990 to 2500 MHz). The unit provides stopband rejection of 25 dB minimum at 1910 MHz and 2580 MHz, with a passband insertion loss of 1 dB maximum. With 50- Ω impedance and standard N female connectors, it is designed for indoor use, but can be provided as a temperature-compensated unit.

Microwave Filter Co., Inc., 6743 Kinne St., East Syracuse, NY 13057; (800) 448-1666. (315) 438-4700, FAX: (888) 411-8860, (315) 463-1467, e-mail: mfcsales@microwavefilter.com, Internet: www.microwavefilter.com.

Enter No. 91 at www.mwrf.com



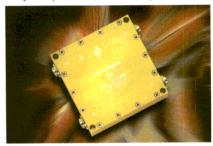




new products

Demodulator Uses Diplexer At I/Q Ports

AN IN-PHASE/QUADRATURE (I/Q) DEMOD-ULATOR uses a diplexer at the in-phase (I) and quadrature (Q) ports to meet high local-oscillator (LO) and intermediatefrequency (IF) rejection requirements.



All of the components and processing meet MIL-PRF-38534, Class K and MIL-M-28837 requirements. Designs can be specified for space, military, performance, as well as commercial applications.

Cougar Components, 198 Union Blvd., No. 200, Lakewood, CO 80228; (408) 522-3838. FAX: (303) 985-5177.

Enter No. 92 at www.mwrf.com

Synthesizers Span 0.5 to 23 GHz

THE MFS SERIES of low-power microwave frequency synthesizers is suitable for applications requiring wider operating temperatures for use alongside smaller power supplies. With a frequency range of 0.5 to 23 GHz, switching speed is less than 50 ms, output-power range is +12 to +18 dBm, spurious output is -70 dBc, and harmonics are -20 dBc. DC power is +12/+18 VDC at 250 mA and +8/+18 VDC at 550 mA. The compact devices employ a single-module design implemented with complementary-metal-oxide-semiconductor (CMOS) application-specific integrated circuits (ASICs), advanced monolithic microwave ICs (MMICs), and a dedicated microprocessor.

Elcom Technologies, Inc., 11 Volvo Dr., Rockleigh, NJ 07647; (201) 767-8030, FAX: (201) 767-6266, e-mail: sales@elcom-tech.com, Internet: www.elcom-tech.com.

Enter No. 93 at www.mwrf.com

Inductor Ranges From 1 to 1000 µH

THE 1008PS SERIES of surface-mount power inductors is suitable for applications requiring magnetic shielding. Inductance values span 1 to 1000 µH with saturation current ratings up to



3 A. Applications include notebook computers, personal-computer (PC) cards, wireless communications, and handheld devices. The unit features a footprint of 3.7×3.7 mm. A specially designed ferrite cover provides magnetic shielding.

Coilcraft, 1102 Silver Lake Rd., Cary, IL 60013; (847) 639-6400, FAX: (847) 639-1469, e-mail: info@coilcraft.com, Internet: www.coilcraft.com.

Enter No. 94 at www.mwrf.com

Synthesizers Offer -115-dBc Phase Noise

THE DFS SERIES of dual-output, rugged frequency synthesizers is suitable for microwave and millimeter-wave radios up to 38 GHz. Phase noise is -115dBc typical at 100 kHz in Ku-band operation. The frequency range is from 0.5 to 23 GHz in-band, switching speed is less than 25 ms, and output-power range is from +12 to +18 dBm. Spurious output is -70 dBc, while harmonics are -20 dBc and frequency stability is less than ± 3 PPM from -35 to 70° C. The DFS series has a tuning bandwidth up to 1000 MHz and step sizes ranging from 25 kHz to 10 MHz. DC power consumption for the synthesizers is less than 4 W.

Elcom Technologies, Inc., 11 Volvo Dr., Rockleigh, NJ 07647; (201) 767-8030, FAX: (201) 767-6266, e-mail: sales@elcomtech.com, Internet: www.elcomtech.com.

Enter No. 95 at www.mwrf.com

Connectors Target Board-To-Board Stacking

THE SCX ULTRAMINIATURE coaxial connector series is suitable for board-to-board stacking arrangements with a 0.375-in. (0.953-cm) overall mated pair length and 0.165-in. (0.419-cm) maximum height in low-profile R/A configuration. An air dielectric interface is maintained for constant 50- Ω characteristic impedance. VSWR is 1.25:1 maximum per mated pair up to 20 GHz using a quick-disconnect, snap-in mating scheme with detent locking. The cable-mount connectors are designed for a full-crimp assembly with standard crimp tools or solder termination. Other connector types include a blindmate/float-mount board-to-board mounting version, as well as low-profile right-angle configurations for tight right-angle packaging constraints.

Sabritec, 17750 Gillette Ave., Irvine, CA 92614; (949) 250-1244, FAX: (949) 250-1009, Internet: www.sabritec.com.

Enter No. 96 at www.mwrf.com

Oscillators Span 1 To 125 MHz

THE PrO S8002C ceramic series is a line of surface-mount-device programmable oscillators. Operating voltages are +3.0. +3.3, and +5.0 VDC while the frequency range is 1 to 125 MHz. Operating at +3.0 and +3.3 VDC, period jitter root mean square (RMS) is kept to a noise-free level of 50 ps maximum 33+ to 90 MHz, 100 ps maximum 5+ to 33 MHz, and 167 ps maximum 1 to 5 MHz. Operating at +5 VDC, jitter is kept to 17 ps typical 42 ps maximum 33+ to 125 MHz and 33 ps typical 100 ps maximum from 1 to 33 MHz. In all cases, the oscillators contain a unique internal programming feature that allows a distributor to supply the specified frequency in one to two days.

SaRonix, 141 Jefferson Dr., Menlo Park. CA 94025; (650) 470-7700, FAX: (650) 462-9894, e-mail: saronix@saronix.com, Internet: www.saronix.com.

Enter No. 97 at www.mwrf.com

ANTENNAS!



6-Foot Diameter X-Band Weather Radar Antenna

Seavey Engineering

ANTENNA DEVELOPMENT & MANUFACTURING

offers:

- Wide Standard Product Line Catalog (Available Online!)
- Design/Development
- Antenna Testing Services
- Manufacturing
- Consulting Services

Products Available For:

- LAN
- PCN/PCS
- Mobile Satellite Satellite Audio
- Cellular
- Military Satcom

- Surveillance
- Inmarsat
- Satellite Uplinks Navigation

Seavey Engineering Associates, Inc.

28 Riverside Drive Pembroke, MA 02359 Phone (781) 829-4740 Toll Free (866) 829-4740 Fax (781) 829-4590

E-Mail: info@seavevantenna.com

Visit our Web site www.seaveyantenna.com

CONTACT US FOR YOUR SPECIAL **ANTENNA** REQUIREMENTS



25 years ago, who'd have the

Congratulations
Congratulations
Microwaves & RF Magazine
on 40 years.

t that this would lead to this?



We did.

We're Avnet's RF and Microwave Division, your one source for RF and microwave semiconductors and components. For over 25 years, we've been bringing OEMs the industry-leading RF and microwave components on which cutting edge products are built ... plus superior service.

Our extensive field-based technical staff applies years of RF expertise to your design, component and application requirements. Our value-added services span parametric testing and hi-rel processing, to custom hybrid development and thin-film assembly services. And when your needs go beyond traightforward component selection, we offer complete integrated materials services and design ervices, helping you navigate the entire supply chain, from design to production.

you're looking for a partner who brings an innovative RF and microwave product and service approach the market, look no further than Avnet. Who knows where we'll take your next product?

366) Avnet RF or (866) 286-3873 www.em.avnet.com/rfm



MICROWAVES & RF ENGINEERING CARFERS

RATES

Effective January 1, 2001 \$225 per column inch Commissionable to agencies

DEADLINES

Space reservation:

5th of month preceding issue date

Ad material to:

Penton Media Inc., Classified Dept. 611, Route 46 West, Hasbrouck Heights, NJ 07604

SALES STAFF

Loree Poirier (216) 931-9201

Fax: (216) 931-9441

e-mail: Lpoirier@penton.com



A World of Possibilities A Window of Opportunity

The number of opportunities in today's market is overwhelming... However, identifying the best and timing it right is the challenge. NES has strategic alliances with the people who are creating technology, not just using it. If you're looking for the inside track on tomorrow's best opportunities (not yesterday's), then you should be talking to us!

National Engineering Search ®

is the leading search firm placing Engineers nationwide. Our clients range from the Fortune 500 to new emerging technology companies. Contact us today for tomorrow's best opportunities!

> 800.248.7020 Fax: 800.838.8789

mrf@nesnet.com
See many of our opportunities on-line:

IMMEDIATE OPPORTUNITIES: Communications (Data, PCS, Cellular, Networks, Satcom, GPS), Digital Imaging, CATV, Medical, Computers, Defense Consumer Electronics

Skills in any of the following:
High Speed Digital & Analog
Design, Mixed Signal, ASIC,
FPGA, MMIC, AD/DA, BICMOS
Synthesizers, WCDMA, GSM,
Spread Spectrum, VHF/JHF,
Antennas, Embedded Software

nesnet.com

What are you Worth?
See our On-Line Salary Survey!



If you would like to place an ad in the Classified Section of Microwaves &RF!

Customer Service Department at...

- PH 201-393-6083
- FAX 201-393-0410

In most cases, advertisements contained in Microwaves &RF employment section indicate that the companies are equal opportunity employers. The Federal Civil Rights Act of 1964, and other laws, prohibit discrimination in employment based on race, color, religion, national origin, sex or for any reason other than lack of professional qualification for the position being offered. It should be noted that employment advertisements in Microwaves & RF are published for the readers convenience and in no way, to the best of our knowledge, promote unlawful discrimination.

new literature

Varactor Diodes

A 12-PAGE engineering bulletin (SG-950) offers detailed descriptions of 11 series of diodes that provide designers with a wide selection of capacitance versus voltage characteristics, including super hyperabrupt, wideband hyperabrupt, microwave hyperabrupt, high-quality-factor (Q) abrupt, and microwave abrupt. Product descriptions include features, specifications, outline drawings, applications, and C-V curves. The listings include common cathode models.

Sprague-Goodman Electronics, Inc.; (516) 334-8700, FAX: (516) 334-8771, e-mail: info@spraguegoodman.com.

Enter No. 60 at www.mwrf.com

DAQ Equipment

AN EIGHT-PAGE brochure offers devices that are suitable for test-and-measurement applications. Products for data acquisition (DAQ), DC sourcing and measurement, optic testing, telecommunications, audio measurements, microwave switching, and device characterization are presented. Specifications include inputs, outputs, frequency, resolution, continuity, resistance, current, and temperature.

Keithley Instruments, Inc.; (888) 534-8453, Internet: www.keithley.com.

Enter No. 61 at www.mwrf.com

EMI Reduction

A BOOKLET ENTITLED "Applications Guide to EMI/RFI/ESD" offers information on electromagnetic interference (EMI), RF interference (RFI), and electrostatic distortion (ESD) and solutions for design engineers. The guide includes a checklist of products available to provide EMI reduction and ESD suppression, a selector-guide flowchart to assist designers in specifying the correct devices, and a snapshot of international EMI/ESD regulatory standards. The guide provides the top 10 printed-circuit-board (PCB) EMI rules used in the design of low-noise boards, while also explaining actual

proven circuit solutions for EMI reduction and ESD suppression. Theories and step-by-step instructions on how to solve various PCB problems are presented.

AVX Corp.; (843) 946-0414, FAX: (843) 946-0626, e-mail: lit@avxcorp.com.

Enter No. 62 at www.mwrf.com

Logic Analyzers

TEST EQUIPMENT IS available from an 18-page catalog. Pulse generators, logic analyzers, plotters, TV and video devices, meters, RF signal generators, inductance-capacitance-resistance (LCR) analyzers, spectrum analyzers, precision sources, and oscilloscopes are specified. Frequency counters, RF measurement equipment, impedance analyzers, network analyzers, power supplies, audio analyzers, semiconductors, signal generators, as well as data-acquisition (DAQ) equipment are offered from a variety of manufacturers. Pricing and ordering information is included.

Test Equipment Connection Corp.; (800) 615-8378, (407) 804-1299, FAX: (800) 819-TEST, (407) 804-1277, Internet: www.TestEquipmentConnection.com.

Enter No. 63 at www.mwrf.com

Test Equipment

TEST EQUIPMENT IS the subject of a 56-page catalog. Oscilloscopes, arbitrary function generators, probes, DC power supplies, waveform generators, data-acquisition (DAQ) equipment, pulse generators, spectrum and network analyzers, as well as cable are presented. Reconditioned equipment offerings include power supplies, spectrum analyzers above and below 1 GHz, RF measurement equipment, signal generators, counters, logic analyzers, and meters. A section on new equipment is included.

TestEquity, Inc.; (800) 884-3457, FAX: (800) 272-4329, Internet: www.test equity.com.

Enter No. 64 at www.mwrf.com

GPIB Programmers

A 200-PAGE catalog contains information on a selection of AC and DC power supplies. Electronic loads, battery testers, power-supply controllers, general-purpose-interface-bus (GPIB) programmers, and rack assemblies for power supplies are presented. Oscilloscopes and signal generators are offered, along with electrical safety testers, jitter meters, as well as test-and-measurement instruments.

IFR; (800) 835-2352, (316) 522-4981, e-mail: info@ifrsys.com, Internet: www.ifrsys.com.

Enter No. 65 at www.mwrf.com

Proprietary-Bus Systems

A REFERENCE GUIDE outlines a company's line of VME, VXI, cPCI, PXI, and proprietary-bus-systems products. A range of system chassis, enclosures, power supplies, and turnkey solutions for telecommunications, test-and-measurement, military, and related applications is presented. Modified and custom products are offered. Services include printed-circuit-board (PCB) design and assembly, component and software integration, and functional testing.

Tracewell Systems, Inc.; (800) 848-4525, (614) 846-6175, FAX: (614) 846-4450, Internet: www.tracewellsystems.com.

Enter No. 66 at www.mwrf.com

Network Enclosures

A SIX-PAGE brochure illustrates the advantages of the isoNet line of network enclosures. Options that are described include lift-off-style ventilated doors and side panels, multivendor-compatible mounting rails, cable-management features and accessories, power-distribution strips, and a variety of cooling accessories.

Crenlo, Inc.; (507) 289-3371, FAX: (507) 287-3405, e-mail: sales@emcor-crenlo.com, Internet: www.emcor-cren-

●Enter No. 67 at www.mwrf.com

MMIC Products

AN 818-PAGE designer's guide includes 39 monolithic-microwave-integrated-circuit (MMIC) product data sheets. Wireless application selection guides, application notes, and major trade-journal article reprints are featured.

More than 135 products spanning the DC-to-40-GHz frequency range are detailed.

Hittite Microwave Corp.; (978) 250-3343, FAX: (978) 250-3373, e-mail: sales@hit tite.com, Internet: www.hittite.com.

Enter No. 68 at www.mwrf.com



Custom Thin Film Circuits to Your Strictest Specifications



Thin Film Concepts, Inc. can solve critical circuit manufacturing problems that most of our competitors try



to avoid. We utilize all sputtered ceramics, high resolution lithography, and ion-beam

milling to produce circuits with micron dimensional tolerances for today's high frequency applications.

TFC is also one of the largest custom metallizers of optical cable assemblies for hermetic packaging.

Give us a call to discuss your critical requirements.

THIN FILM CONCEPTS, INC. One Westchester Plaza Elmsford, NY 10523 P: 914-592-4700 • F: 914-592-0067 www.thinfilmconcepts.com

Enter NO. 454 or visit www.mwrf.com

Vector ator or • 9.1 Bandwidth • 2-18 GHz Simultaneous Phase & **Amplitude Control** FREQUENCY (GHz) · Linear Control Slope · Size: 3.5" x 4.25" x 0.71" Flatness vs Frequency ±20°/3 dB Resolution < 0.1°/0.06 dB FREQUENCY (GHz) Send For Our New Catalog 2 Emery Avenue Randolph, NJ 07869 USA 973-361-5700 Fax: 973-361-5722 www.gtmicrowave.com e-mail: gtmicrowav@aol.com

Enter NO. 418 or visit www.mwrf.com

new literature

Subracks/Accessories

A 124-PAGE catalog details a range of subracks and accessories for CompactPCI, VME64x, and other platforms. Accessories, including side plates, injector/ejector handles, front panels, and drive bays are covered.

Pentair Electronic Packaging; (888) 550-9543, Internet: www.pentairep.com/schroff.

Enter No. 69 at www.mwrf.com

Card Cages

A FOUR-PAGE brochure provides charts and illustrations detailing the R10 and Bord-Pak® card cages. Mechanical specifications are included. Customization and ordering information are provided.

Buckeye ShapeForm; (800) 728-0776, FAX: (614) 445-8224, Internet:

www.buckeyeshapeform.com.

Enter No. 70 at www.mwrf.com

Optics/Lasers

THE 2001 REFERENCE catalog for technical scientists, educators, and engineers contains 100 pages featuring more than 1500 science, laboratory, and optical products. Science-discovery items, optics, biomedical instruments, scales, solar equipment, and magnets are offered. SCIENTIFICS; (800) 728-6999, (716) 874-9091, FAX: (800) 828-3299, e-mail: cons_order@edsci.com, Internet: www.scientificsonline.com.

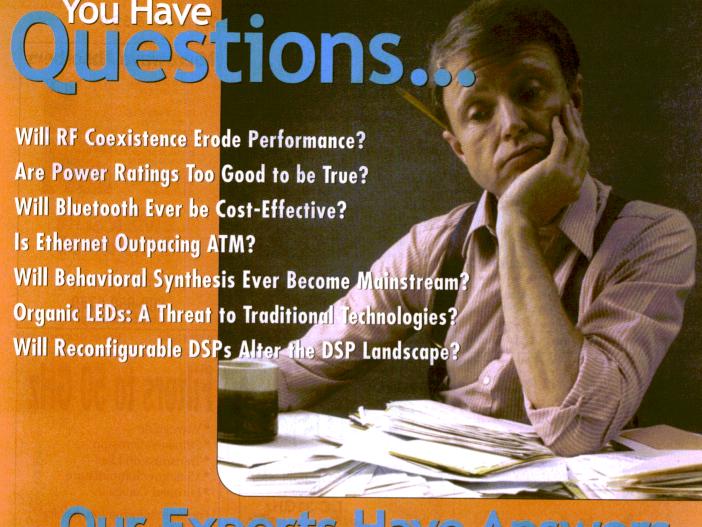
●Enter No. 71 at www.mwrf.com

Cable Ferrites

AN RF-INTERFERENCE (RFI) cable-ferrite catalog features 126 products for round and flat cables. Expanded universal wideband styles, low- and high-frequency specific-purpose styles, and 2.45-GHz Bluetooth microwave series are offered.

FerriShield, Inc.; (212) 268-4020, FAX: (212) 268-4023, Internet: www.fer rishield.com.

Enter No. 72 at www.mwrf.com



... Our Experts Have Answers































Subscribe to PlanetEE's free e-newsletters today at www.PlanetEE.com and receive expert analysis, insightful commentary, product updates, news, design tips, tutorials, and more. You have design questions...our experts have answers. Go to www.PlanetEE.com to sign up for Bluetooth Alert* Power Alert* EDA Alert* Netronics Alert* Communications Alert* Display Alert* and DSP Alert*.





netronics Microwaves & RF Wireless



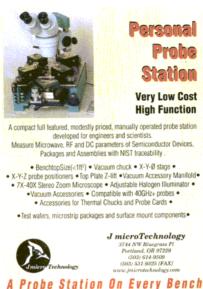
MICROWAVES & RF DIRECT CONNECT

TO ADVERTISE, CALL JOANNE REPPAS (201) 666-6698



SECTOR MICROWAVE

Enter No. 550 at www.mwrf.com



J MICROTECHNOLOGY

Enter No. 551 at www.mwrf.com

Microwave Absorbers

- Custom parts in lossy foam or elastomer systems
- Die cut or water-iet cut to meet tolerance requirements
- Liquid absorber applied in-house for hot-spot interference problems
- · Reduce fabrication costs with automated mold-inplace technology







Specialists In Solving Cavity Resonant Interference Problems From 0.8-40 GHz

> 800-650-5740 www.eccosorb.com

EMERSON & CUMING

Enter No. 552 at www.mwrf.com

SWITCHES WAVEGUIDE, COAX, DUALS



A Full spectrum of Switches for the 21" Century...



2P3T(1: 2 Redundancy) 561-842-3550

Fax 561-842-2196 e-mail: switches@logus.com web; www.logus.com

LOGUS MICROWAVE Enter No. 554 at www.mwrf.com

Filters to 50 GHz

- Waveguide
- Stripline/Microstrip
- Transmission Line
- Miniature/Subminiature
- Lumped Constant.

For more information, ask for our RF Catalog.

M£ MICROWAVE FILTER COMPANY

6743 KINNE STREET, E. SYRACUSE, NY 13057 315-438-4700 '800-448-1666 'FAX: 315-463-1467 E-MAIL: mfcsales@microwavefilter.com http://www.microwavefilter.com

MICROWAVE FILTER CO

Enter No. 555 at www.mwrf.com

HIGH PERFORMANCE TECHNOLOGY RF POWER AMPLIFIERS IMHz - 2 GHz . IW - 2 KW

Small, Ultra High Efficiency Modules Low Cost Amplifier Systems T/R Subsystems



Blding A, 570 West Clearwater Loop Post Falls, Idaho 83854 USA 208-457-0292 • Fax 208-457-0296 www.lcfamps.com E-mail: info@lcfamps.com

LCF ENTERPRISES

Enter No. 553 at www.mwrf.com

Cast Components



- stock items in under 3 days
- Economical just try us
- High Spec. satisfied customers & ISO9001 accredition speaks for itself

To find out about our large range of components in 2.5 - 40 GHz just

Micro Metalsmiths

t.watson@micrometalsmiths.co.uk Website: www.micrometalsmiths.com

220

MICRO METALSMITHS

Enter No. 556 at www.mwrf.com

Microwave Isolators/Circulators



Frequency coverage 450 Mb Low Insertion Loss <0.3 dB; Hig MHz to 26.5 GHz High Isolation >23 dB Excellent VSWR 1.25:1

- Drop-in Packages
- Reflection sensing tabs
- Surface Mount Packages Four port custom designs
- Connector options
- Coaxial packages Multi-junction for higher isolation
- Volume Discount Application Support
- TQM Organization Just in Time delivery
- MIL-I-45208 Qualified Custom designs
- Cellular/Comm. ontimized

Low Cost / High Volume Production Capability



NOVA MICROWAVE

Enter No. 557 at www.mwrf.com

MICROWAVES & RF

AUGUST 2001

3 CK RELICENTED

TO ADVERTISE, CALL JOANNE REPPAS (201) 666-6698



POLYFET RF DEVICES

Enter No. 558 at www.mwrf.com

PLDROs, PLCROs **Surface Mount DROs** PLDRO Modules YIG SYNTHESIZERS



Princeton Microwave Technology 3 Nami Lane, Unit C-10, Mercerville, NJ Tel: 609-586-8140 Fax: 609-586-1231 www.Pmmt.net email: PmmT@aol.com

PRINCETON MICROWAVE

Enter No. 559 at www.mwrf.com

Sector Microwave A Quarter Century of Switch Innovation Let Sector Solve Your Switching Needs www.sectormicrowave.com 999 Grand Blvd., Deer Park, L.I., N.Y. 11729 (631) 242-2300 • FAX: (631) 242-8158 smi

SECTOR MICROWAVE INC.

Enter No. 560 at www.mwrf.com

AVCOM PSA-86A Portable 6 GHz Spectrum Analyzer



The new AVCOM PSA-86A/002 is a cost effective tool for broadband measurements in the 5-6 GHz ISM bands. Frequency coverage is 5.1-6.1 GHz, resolution BW is adjustable from 3 MHz to 75 KHz. Battery, line, or vehicle power, and weighs only 18 lbs.

Call for more details.

AVCOMRAMSEY

500 Southlake Blvd. • Richmond, VA 23236 Phone: 804-794-2500 Fax: 804-794-8284 www.avcomramsey.com sales@avcomramsey.com

AVCOM-RAMSEY TECHNOLOGY Enter No. 561 at www.mwrf.com

IMPEDANCE CONVERTERS



Model A65 Series uses a specially designed and tuned broadband transformer for converting 50/75 ohms. 75/93 ohms, 50/93 ohms with negligible loss (.5 dB max for the 1-1000 MHz version).

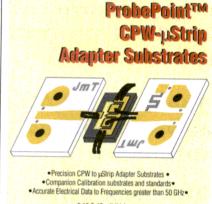
Available with a number of connector configurations.

WIDE BAND ENGINEERING CO., INC.

P.O. Box 21652, Phoenix, AZ 85036 PHONE/FAX (602) 254-1570 http://www.wbecoinc.com

WIDE BAND ENGINEERING

Enter No. 562 at www.mwrf.com



• 5,10,& 15 mil thickness • · Compatible with 40GHz+ probes ·

J microTechnology 3744 NW Bluegrass Pl Portland, OR 97229 (503) 614-9509 (503) 531-9325 [FAX]

Test Tooling for the Untestable

J MICROTECHNOLOGY

Enter No. 563 at www.mwrf.com



Discover a new planet





SECTOR MICROWAVE INC

Enter No. 564 at www.mwrf.com

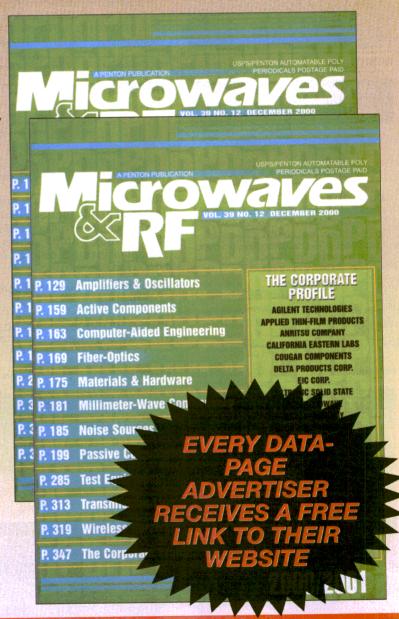
THE DIRECTORY FOR THE NEXT CENTURY

PRODUCT DATA DIRECTORY ISSUE

- The most comprehensive listings (1500) of high-frequency suppliers.
- The most (55,000) one-year-qualified subscribers.
- The most complete (450) product categories.

PLUS

New Reference
 Directory for specifiers.



The 2000/2001 Product Data Directory Issue is now available!
Copies are \$100 (plus \$6.00 P&H) in the U.S. or \$125 (plus \$7.50 P&H) all other countries.
For more information, call Dawn Prior at (201) 393-6286.

INFOCENTER

Advertiser	Website, E-Mail Address	Page
Accumet Engineering	www.accumet.com; e-mail: sales@accumet.com	
Advanced Control Component	S	
Advanced reciliology Group in	If www advischer com: a-mail: fmhanusate@1-	
Agriefit rechnologies	www.agilent.com	27 22 22 444 00
Amount communications, inc.,		
Amitron	www.amwave.com	
Amnlifier Research	www.amitron.comwww.amplfiers.com/ampmicro.cfm	
Amplifier Research	www.ampirriers.com/ampmicro.cfm www.arkalmus.com	
Milacolli Systems Coro	www.anacomsystoms.com	
Milaren Microwave, Inc	Www.anaren.com	143 145 001
Milatech Electronics	www.ana-tech.com; o-mail; calos@ana 44	
Anritsu Co	WWW US apritsu com/ademailers/MC26004	
MIII ILSU CO	WWW IIS apritsu com/Discover	
AIII ILSU CO	WWW IIS anritsu com/bluetooth	
Alisoit Corp	www.ancoft.com	
Innlied Wave Persanch	www.aplac.com; e-mail: sales@aplac.com	
irra. Inc.	www.mwoffice.comwww.arra.com; e-mail: sales@arra.com.	1
tmel Corn	www.arra.com; e-mail: sales@arra.com www.atmel.com	
vcom-Ramsey Technologies, I	nc www.avcomramsey.com; e-mail: sales@avcomrai	
whet Electronics Marketing	www.em.avnet.com/rfm	42 42 244 2
vtech Electrosystems Ltd	www.avtechpulse.com	42-43, 214-2
liley Technologies, Inc	www.hlilev.com	***
oonton Electronics Corp	www.boonton.com; e-mail: sales@boonton.com .	
alifornia Eastern Lab	www.cel.com	
dscade Microtech	www.cascademonarch.com	_
Olicraft	www.coilcraft.com	
viiiiiuiiications rechniques	www.cit-inc.com.o-mail:salos@sti-inc.com	70.4
Jilipex Corp	WWW COMPRYCOLD COM: 0-mail: compoy@p3+	40
Dilibuter Simulation Technolog	IV	
niiputei Simulation lechnolog	V WWW CSt-america com: e-mail: info@cst-america	/
milecticul Microwave Co	e-mail: sales@connecticutmicrowave.com	44
Jugar Components	www.cougarcorp.com; e-mail: cougaramps@couga	arcorp.com 5
inning corp	e-mail: mwsales@cuningcorn.com	
-! V	D —	
gi-key	www.digikev.com	
ow-key microwave	www.dow-key.com	
icommun rechnologies, Incdi	mt www.ductech.com; e-mail; sales@ductech.com	10.4-10
A Front-to-Back		
gleware Low Technologies Com Technologies Company Com		
gjeware AA Front-to-Back com Technologies cetromagnetic Tech/EFI IC Technology, Inc. erson & Cuming Microwave Pr celics Semiconductor, Inc. K Corp.		
gleware AA Front-to-Back com Technologies ctromagnetic Tech/EFI IC Technology, Inc erson & Cuming Microwave Pr celics Semiconductor, Inc K Corp cus Microwave.		
gleware AA Front-to-Back com Technologies ectromagnetic Tech/EFI (C Technology, Inc. ererson & Cuming Microwave Pr celics Semiconductor, Inc. K Corp. Cus Microwave Y Microwave Inc.		
gleware A Front-to-Back com Technologies ctromagnetic Tech/EFI C Technology, Inc. nerson & Cuming Microwave Pr celics Semiconductor, Inc. K Corp. cus Microwave Y Microwave Inc tists Compound Semiconductor		
gleware A Front-to-Back com Technologies ctromagnetic Tech/EFI C Technology, Inc. nerson & Cuming Microwave Pr celics Semiconductor, Inc. K Corp. cus Microwave Y Microwave Inc tists Compound Semiconductor		
gyeware AA Front-to-Back com Technologies ctromagnetic Tech/EFI IC Technology, Inc IC Technology, Inc K Corp cus Microwave Y Microwave Inc itsu Compound Semiconducto ture Electronics, Inc.		77 199 199 199 199 199 199 199 199 199 1
ugware AA Front-to-Back com Technologies cetromagnetic Tech/EFI (C Technology, Inc. erson & Cuming Microwave Pr celics Semiconductor, Inc. K Corp. cus Microwave Y Microwave Inc iitsu Compound Semiconducto ture Electronics, Inc.		
ugware AA Front-to-Back com Technologies ctromagnetic Tech/EFI IC Technology, Inc IC Technology, Inc K Corp Cus Microwave Y Microwave Inc itisus Compound Semiconducto ture Electronics, Inc AT Technology, Inc Inc Inc Inc		
gleware A Front-to-Back .com Technologies .ctromagnetic Tech/EFI (C Technology, Inccross & Cuming Microwave Pr celics Semiconductor, Inccus Microwave Y Microwave Inc .itsu Compound Semiconducto ture Electronics, Inca-Tronics, Inc.		
y Front-to-Back com Technologies ctromagnetic Tech/EFI C Technology, Inc. cerson & Cuming Microwave Predicts Editor Semiconductor, Inc. K Corp. cus Microwave its Compound Semiconducto ure Electronics, Inc. Z Technology, Inc. a-Tronics, Inc. Microwave, Inc.		
greware A Front-to-Back com Technologies ctromagnetic Tech/EFI C Technology, Inc. cerson & Cuming Microwave Prelics Semiconductor, Inc. K Corp. cus Microwave C Microwave Inc tistu Compound Semiconducto ure Electronics, Inc. Z Technology, Inc. a-Tronics, Inc. Microwave, Inc. bour Industries, Inc.		7 7 999 999 999 999 999 999 999 999 999
y Evrore seek of the seek of t		
greware A Front-to-Back com Technologies ctromagnetic Tech/EFI C Technology, Inc. erson & Cuming Microwave Prelics Semiconductor, Inc. K Corp. us Microwave of Microwave Inc tists Compound Semiconducto ure Electronics, Inc. Z Technology, Inc. a-Tronics, Inc. bour Industries, Inc. vard Thermal, Inc. ererbill Cable & Mfg Corp. otek, Inc.		7 7 99 91 91 91 91 92 92 92 92 92 92 92 92 92 92 92 92 92
greware A Front-to-Back com Technologies ctromagnetic Tech/EFI C Technology, Inc. erson & Cuming Microwave Prelics Semiconductor, Inc. K Corp. us Microwave of Microwave Inc tissu Compound Semiconducto ure Electronics, Inc. Z Technology, Inc. a-Tronics, Inc. bour Industries, Inc. vard Thermal, Inc. ererbill Cable & Mfg Corp. otek, Inc.		7 7 99 91 91 91 91 92 92 92 92 92 92 92 92 92 92 92 92 92
yewhere - general services and		77 99 19. 18. 18. 22(2. 40 10. 10. 10. 10. 10. 10. 10. 10. 10. 10
yieware A Front-to-Back com Technologies ctromagnetic Tech/EFI C Technology, Inc. erson & Cuming Microwave Prelics Semiconductor, Inc. K Corp. Lus Microwave If Microwave Inc et Succession of Semiconducto ure Electronics, Inc. Z Technology, Inc. a-Tronics, Inc. Microwave, Inc. bour Industries, Inc. vard Thermal, Inc. vard Thermal, Inc. vard Thermal, Inc. ite Microwave et Corp.		7 7 99 91 91 91 91 91 91 91 91 91 91 91 91
greware A Front-to-Back com Technologies ctromagnetic Tech/EFI C Technology, Inc. erson & Cuming Microwave Predicts Semiconductor, Inc. K Corp. cus Microwave of Microwave Inc tists Compound Semiconducto cure Electronics, Inc. Z Technology, Inc. a-Tronics, Inc. Microwave, Inc. bour Industries, Inc. vard Thermal, Inc. vard Thermal, Inc. ite Microwave ite Microwave et Microwave et Microwave et Corp. rad Ltd.www.interadltd.com;		77 99 1.1 199 18.1 22(4 44 65-64 66-68-68-68-68-68-68-68-68-68-68-68-68-6
yeware - yew		77 99 19. 18. 22(2: 40 40 10. 16. 16. 16. 16. 16. 16. 16. 16. 16. 16
greware to-Back. om Technologies ctromagnetic Tech/EFI C Technology, Inc. erson & Cuming Microwave Prelics Semiconductor, Inc. K Corp. us Microwave. Microwave Inc. itsu Compound Semiconducto ure Electronics, Inc. Z Technology, Inc. a-Tronics, Inc. Microwave, Inc. bour Industries, Inc. vard Thermal, Inc. errhill Cable & Mfg Corp. otek, Inc. ite Microwave et Corp. ad Ltdwww.interadltd.com; rnatlonal Crystal Mfg.		77 99 19. 18. 22(2: 40 40 10. 16. 16. 16. 16. 16. 16. 16. 16. 16. 16
gleware A Front-to-Back com Technologies ctromagnetic Tech/EFI C Technology, Inc. erson & Cuming Microwave Prelics Semiconductor, Inc. K Corp. cus Microwave cus Microwave inc itsu Compound Semiconducto cure Electronics, Inc. Z Technology, Inc. a-Tronics, Inc. Microwave, Inc. bour Industries, Inc. vard Thermal, Inc. vard Thermal, Inc. ite Microwave et Corp. ite Microwave et Corp. rad Ltd.www.interadltd.com; rational Crystal Mfg. rnet World		77 99 91 199 188 224 40 61 656 655 656 655
ygeware A Front-to-Back com Technologies ctromagnetic Tech/EFI C Technology, Inc. erson & Cuming Microwave Prelics Semiconductor, Inc. K Corp. cus Microwave C Microwave Inc itsu Compound Semiconducto ure Electronics, Inc. Z Technology, Inc. a-Tronics, Inc. Microwave, Inc bour Industries, Inc. vard Thermal, Inc. vard Thermal, Inc. ite Microwave et Corp. rad Ltd.www.interadItd.com; rad Ltd.www.interadItd.com; raret World crotechnology		
ygeware A Front-to-Back com Technologies ctromagnetic Tech/EFI C Technology, Inc. erson & Cuming Microwave Predics Semiconductor, Inc. K Corp. Lus Microwave Lits Compound Semiconductor Lits Lompound Lits Lompound Lits Lits Lits Lits Lits Lits Lits Lits		7 7 99 91 91 91 92 92 92 92 92 92 92 92 92 92 92 92 92
ygeware A Front-to-Back com Technologies ctromagnetic Tech/EFI C Technology, Inc. erson & Cuming Microwave Predics Semiconductor, Inc. K Corp. Lus Microwave Lits Compound Semiconductor Lits Lompound Lits Lompound Lits Lits Lits Lits Lits Lits Lits Lits		7 7 99 91 91 91 92 92 92 92 92 92 92 92 92 92 92 92 92
greware A Front-to-Back com Technologies ctromagnetic Tech/EFI C Technology, Inc. erson & Cuming Microwave Prelics Semiconductor, Inc. K Corp. cus Microwave C Microwave C Microwave Inc C Microwave C Technology, Inc. C Technology, Inc. C Technology, Inc. C Technology C Microwave C C Microwave C C		
gleware A A Front-to-Back com Technologies cetromagnetic Tech/EFI C Technology, Inc. eerson & Cuming Microwave Pr celics Semiconductor, Inc. K Corp. cus Microwave. Y Microwave Inc eitsu Compound Semiconducto ture Electronics, Inc. Z Technology, Inc. ea-Tronics, Inc. Microwave, Inc. bour Industries, Inc. vard Thermal, Inc. vard Thermal, Inc. erhill Cable & Mfg Corp. otek, Inc. ite Microwave et Corp. rrad Ltd.www.interaditd.com; rrational Crystal Mfg. rret World crotechnology Technology Technology Industries, Inc.		
gleware A Front-to-Back com Technologies ctromagnetic Tech/EFI C Technology, Inc. derson & Cuming Microwave Precilics Semiconductor, Inc. K Corp. cus Microwave. Y Microwave Inc ditsu Compound Semiconducto ture Electronics, Inc. Z Technology, Inc. da-Tronics, Inc. ditsu Compound Semiconducto ture Electronics,		
gleware A Front-to-Back Com Technologies Cetromagnetic Tech/EFI C Technology, Inc. Lerson & Cuming Microwave Predicts Company Cus Microwave Cu		
greware A A Front-to-Back com Technologies ctromagnetic Tech/EFI C Technology, Inc. uerson & Cuming Microwave Predicts Semiconductor, Inc. K Corp. cus Microwave. Y Microwave Inc itsu Compound Semiconducto ture Electronics, Inc. Z Technology, Inc. ua-Tronics, Inc. Microwave, Inc. bour Industries, Inc. vard Thermal, Inc. vard Thermal, Inc. ite Microwave et Corp. rad Ltd.www.interaditd.com; rrational Crystal Mfg. rret World crotechnology Technology. Industries, Inc. Microwave/Dover Triangle Loss, Inc. Microwave/Dover Iriangle Loss, Inc. Microwave/Loss, Inc. Mic		
ygeware on the control of the contro		
ygware or growth of the state o		
ygeware - ygeware - AA Front-to-Back .com Technologiesctromagnetic Tech/EFI (C Technology, Incerson & Cuming Microwave Predicts Semiconductor, Inc K Corpcus Microwavey Microwave Inciitsu Compound Semiconductoture Electronics, Inc Z Technology, Inca-Tronics, Incward Thermal, Incvard Thermal, Incvard Thermal, Inctite Microwavetite Microwavet		
ygware - ygware - ygware - ygware - ygware - ya Front-to-Back om Technologies om Technologies om Technology onerson & Cuming Microwave Precilics Semiconductor, Inc K Corp own Microwave y Microwave y Microwave own microwave y Microwave own microwave o		
ygware oggeter og general og gene		
ygware oggeter og general og gene		
ygware ygware AA Front-to-Back com Technologies cetromagnetic Tech/EFI IC Technology, Inc. erson & Cuming Microwave Pr celics Semiconductor, Inc. K Corp. cus Microwave. Y Microwave Inc eitsu Compound Semiconducto ture Electronics, Inc. Z Technology, Inc. ea-Tronics, Inc. Microwave, Inc. erbour Industries, Inc. ervard Thermal, Inc. eite Microwave et Corp. erad Ltd.www.interadltd.com; ernational Crystal Mfg. errnet World crotechnology Industries, Inc. Microwave/Dover Triangle hiey Instruments IUSA, Inc. ar, Inc. Enterprises. Is Microwave Is Microwave Laser & Electronics Laser &		
ygware - ygw		
greware A A Front-to-Back com Technologies cetromagnetic Tech/EFI C Technology, Inc. erson & Cuming Microwave Predicts Semiconductor, Inc. K Corp. cus Microwave. Y Microwave Inc elitsu Compound Semiconductor ure Electronics, Inc. Z Technology, Inc. ea-Tronics, Inc. Microwave, Inc. bour Industries, Inc. vard Thermal, Inc. vard Thermal, Inc. eth Microwave et Corp. eth Microwave et Corp. rad Ltd.www.interaditd.com; rrational Crystal Mfg. rret World crotechnology Technology. Industries, Inc. Microwave/Dover Triangle hely Instruments USA, Inc. enterprises. s Microwave h Microwave h Microwave h Microwave Laser & Electronics C Corp. ech, Inc. i Microwave, Inc.		
gleware A. A Front-to-Back com Technologies com Technologies ctromagnetic Tech/EFI (C Technology, Inc derson & Cuming Microwave Precelics Semiconductor, Inc K Corp cus Microwave y Microwave Inc itsu Compound Semiconductor ture Electronics, Inc Z Technology, Inc ia-Tronics, Inc microwave, Inc chour Industries, Inc rebour Industries, Inc rehill Cable & Mfg Corp otek, Inc ite Microwave et Corp rad Ltd.www.interadltd.com; rnational Crystal Mfg rnet World crotechnology Industries, Inc Microwave/Dover Inley Instruments IUSA, Inc ar, Inc Enterprises s Microwave b Microwave Laser & Electronics c Corp ech, Inc i Microwave, Inc y Microwave, Inc i Microwave, Inc cech, Inc i Microwave, Inc		
greware A. A Front-to-Back com Technologies com Technologies ctromagnetic Tech/EFI (C Technology, Inc derson & Cuming Microwave Predicts Semiconductor, Inc K Corp cus Microwave Y Microwave lnc Y Microwave lnc Y Technology, Inc a-Tronics, Inc Microwave, Inc "bour Industries, Inc "bour Industries, Inc "bour Industries, Inc "bour Industries, Inc "bour Industries, Inc "bour Industries, Inc "bour Industries, Inc "browave, Inc Indicrowave, Inc "bricrowave, Inc Indicrowave, Inc Indicrowave, Inc Indicrowave, Inc Indicrowave, Inc Interowave, Inc Inter		
greware A Front-to-Back com Technologies com Technologies ctromagnetic Tech/EFI C Technology cerson & Cuming Microwave Predicts Semiconductor, Inc K Corp cus Microwave y Microwave Inc itsu Compound Semiconductor ture Electronics, Inc Z Technology, Inc a-Tronics, Inc Microwave, Inc bour Industries, Inc vard Thermal, Inc vard Thermal, Inc ite Microwave et Corp rad Ltd.www.interaditd.com; or rational Crystal Mfg rnet World crotechnology Industries, Inc Microwave/Dover Microwave/Dover Triangle hely Instruments USA, Inc ar, Inc Enterprises s Microwave h Microwave Laser & Electronics Corp Laser & Electronics Corp i Microwave, Inc y Microwave, Inc i Microwave, Inc.		

Advertiser	Website, E-Mail Address	Pag
Micro Lambda, Inc.	www.micro-lambda.com; e-mail: microlambda,aol.com	
micro metalsmiths i th	www.micrometalsmiths.com	
MICLODINASE COLD.	www Microphaeo com	
microsemi corp	www.microsemi.com	
microtecii, iiic.	WWW Microtech-inc.com	
MICTOWAVE FIITER COInc.	www microwayofiltor com: o-mail: mfeesles@i	
Microwave Solutions,, Inc.,	e-mail: sales@microwayesolutions.com	
microwaves video systems, inc.		0.5
Milmena	www.midatlanticrf.com; e-mail: info@midatlanticrf.com	
millix bi odubaliu	WWW mimixhroadhand.com	
MINI-Systems, Inc.	www Mini-SystomsIns.com	
mitted	www.miteg.com	
modular components National	WWW.MCn-MMpc.com: e-mail: sales@mcn-mmpc.com	
Narda An La2 Communications	N —	
National Semiconductor	wireless.national.com	
Nexyn Corp	WWW DEXVD COM	151
Nova Engineering, Inc.	www.nova-eng.com	
NOVA MICTOWAVE, INC.	WWW DOVAMICTO COM A-mail: novamic@mcn com	
Numeritz rechnologies,lic		
Omnivia Inc		
ommyrg, mc		156-
Palomar Technologies	www.palomartechnologies.com	
Pidnal Monolithics Industries		
I DIVIET UL DEVICES	WWW.DOIVTET.com	
rolylloli co./crane	www notyton com: o-mail: info@notyton	
Power Systems Tech Div/Comtect	h www.comtochast.com	
Frecision Filoto-Fab	WWW precisionphotofab com	
FILITURE COLOR MICTOWAVE LECT INC	www.presidiocomponents.com www.PmmT.net; e-mail: PmmT@aol.com	
rrogrammed rest sources, inc.		
ruisai microwave corp	WWW.DUISarmicrowave.com; e-mail; sales@microwave.com	
quest microwave, inc	www.questmw.com; e-mail: circulators@questmw.com	
Richardson Electronics	www.rec-usa.com	68- . 146, 1
Sawtek, Inc. Seavey Engineering Sector Microwaves Ind, Inc. Seven Associates Sonnet Software, Inc. Spectrum Control, Inc. Spectrum Elektrotechnik GmbH Sprague-Goodman Electronics Stanford Microdevices Storm Products, Inc.	www.sawtek.com www.seaveyantenna.com; e-mail: info@seaveyantenna.com www.sectormicrowave.com www.seni-rigidcables.com www.sonnetusa.com; e-mail: info@sonnetusa.com www.spectrumcontrol.com www.spectrum-et.com; e-mail: specelek@compuserve.com www.spectrum-et.com; e-mail: specelek@compuserve.com www.spraguegoodman.com www.starnfordmicro.com www.starnfordmicro.com/microwave www.startedege.com/mwrf www.synergymwave.com; e-mail: sales@synergymwave.com	13 220, 2
aconic Advanced Dielectric	www.4taconic.com	
ecdia, Inc	www.tecdia.com	60-6
ele Tech Corp	WWW tele-tech-rf com	47
	www.teledynewireless.com; e-mail: switches@teledyne.com. www.temex-components.com; e-mail: info@temex.fr	
HEI HIAX/ CDF	WWW thermayedt com	
IIII FIIII CONCEDTS	www.thinfilmconcents.com	
LC Precision water	WWW ticnrecision com	
E, IIIC	www.tte.com	1
TE Microwave	www.uel.co.jp; e-mail: eletro@ube.com	113
ector Fields, Inc	www.vari-l.com	170
	www.voltronics.com; e-mail: info@voltronicscorp.com www.gore.com/electronics www.weinschel.com; e-mail: sales@weinschel.com www.whening.com; e-mail: widehand@whening.com	120
L. Gore & Associates, Inc. einschel Corp. ide Band Engineering ireless Developer ireless Systems 2002 J Communications	www.wj.com; e-mail: sales@wj.com	18
inschel Corp ide Band Engineering ireless Developer ireless Developer ireless Systems 2002 Communications	www.wj.com; e-mail: sales@wj.com	18
L. Gore & Associates, Inc. einschel Corp. ide Band Engineering ireless Developer ireless Systems 2002 J Communications	www.wj.com; e-mail: sales@wj.com	18

GROUP PUBLISHER (201) 393-6225 e-mail:croth@penton.com

DIRECT CONNECTION ADS Joanne Reppas (201) 666-6698 e-mail: irepfran@aol.com

CLASSIFIED ADVERTISING Loree Poirier (216) 931-9201 FAX: (216) 931-9441

e-mail: lpoirier@penton.com NORTHERN CA, NORTHWEST **Gene Roberts** Regional Sales Manager

Penton Media, Inc. San Jose Gateway 2025 Gateway Place, Suite 354 San Jose, CA 95110 (408) 441-0550 ext. 112 FAX: (408) 441-6052 e-mail: groberts@penton.com

NEW YORK, NEW ENGLAND, MIDWEST, MID-ATLANTIC, CANADA Paul Barkman Regional Sales Manager Penton Media, Inc. 611 Route #46 West Hasbrouck Heights, NJ 07604 (908) 704-2460 FAX: (908) 704-2486 e-mail: pbarkman@penton.com

SOUTHWEST, SOUTHEAST, SOUTHERN CA Mary Bandfield Regional Sales Manager Penton Media, Inc. 501 N. Orlando Avenue Winter Park, FL 32789 (407) 381-5850 FAX: (407) 382-9805 e-mail: mbandfield@penton.com

> ISPAFI Igal Elan, General Manager Elan Marketing Group 2 Habonim Street Ramat Gan, Israel 52462 Phone: 011-972-3-6122466 011-972-3-6122467 011-972-3-6122468 FAX: 011-972-3-6122469

TAIWAN, R.O.C. Charles C.Y. Liu, President Two-Way Communications Co., Ltd. 11F/1, No. 421 Sung Shan Road Taipei 110, Taiwan, R.O.C. Phone: 886-2-727-7799 FAX: 886-2-728-3686

> CZECH REPUBLIC Robert Bilek Production International Slezska 61, 13000 Praha 3 Czech Republic Phone: 011-42-2-730-346 FAX: 011-42-2-730-346

> > ITALY Cesare Casiraghi Via Napo Torriani 19/c 1-22100 Como - Italy Phone: 39-31-261407 FAX: 39-31-261380

INDIA Shivaji Bhattacharjee Information & Education Services 1st Floor, 30-B Ber Sarai Village, Near LLT, Hauz Khas, Behind South Indian Temple New Delhi, 110016 India FAX: 001-91-11-6876615 FAX: 81-3-3261-6126

7 Penton

Paulo Andrade Ilimitada-Publicidade Internacional LDA Av Fng. Duarte Pacheco Empreedimento das Amoreiras-Torre 2 Piso 11-Sala 11 1070 Lishoa, Portugal Phone: 351-1-3883176 FAX: 351-1-3883283

Emmanual Archambeauld Defense & Communication 10 Rue St. Jean, 75017 Paris, France Phone: 33-4294-0244 FAX: 33-4387-2729

Luis Andrade, Miguel Esteban Publicidad Internacional Sepulveda, 143-38 08011 Barcelona, Spain Phone: 011-34-93-323-3031 FAX: 011-34-93-453-2977

GERMANY, AUSTRIA, SWITZERLAND Friedrich K. Anacker Managing Director InterMedia Partners Deutscher Ring 40 42327 Wuppertal, Germany Phone: 011-49-202-271-690 FAX: 011-49-202-271-6920

Jo Young Sang Rm. 521 Midopa Bldg. 145 Dan Ju-Dong Chongno-Gu Seoul 110-071 Korea Phone: 027397840 FAX: 027323662

SCANDINAVIA **Paul Barrett** I.M.P. Hartswood Hallmark House 25 Downham Road, Ramsden Heath Billericay Essex, CM 11 1PV United Kingdom Phone: 44-1268-711-560 FAX: 44-1268-711-567

HOLLAND, BELGIUM William J.M. Sanders, S.I.P.A.S. Rechtestraat 58 1483 Be De Ryp, Holland Phone: 31-299-671303 FAX: 31-299-671500

FUROPEAN OPERATIONS Paul Barrett, Mark Whiteacre, David Moore Phone: 44-1268-711-560 FAX: 44-1268-711-567 John Maycock Phone: 44-1142-302-728 FAX: 44-1142-308-335 Hartswood, Maycock Media Hallmark House 25 Downham Road, Ramsden Heath Billericay Essex, CM 11 PV. U.K.

Hiro Morita Japan Advertising Communications, Inc. Three Star Building 3-10-3 Kanda Jimbocho Chiyoda-ku, Tokyo 101, Japan Phone: 81-3-3261-4591

looking back



FORTY YEARS AGO, the model SFD-307 inverted coaxial magnetron from SFD Laboratories, a subsidiary of Varian Associates (Union, NJ), provided 50-W average power and 100-kW peak power from 33.5 to 35.5 GHz.

→next month

Microwaves & RF September Editorial Preview Issue Theme: Amplifiers & Oscillators

News

At one time, the microwave industry was highly dependent upon the military for its business. With the explosion in wireless markets during the 1990s, however, military customers were often left behind. But in the quest for a more balanced microwave economy, the industry is returning to the military for business. What are the future trends facing the military and what do they require from their suppliers? Do not miss this Special Report, written by Fred Levien of The Levien Group, on the current state of military electronics.

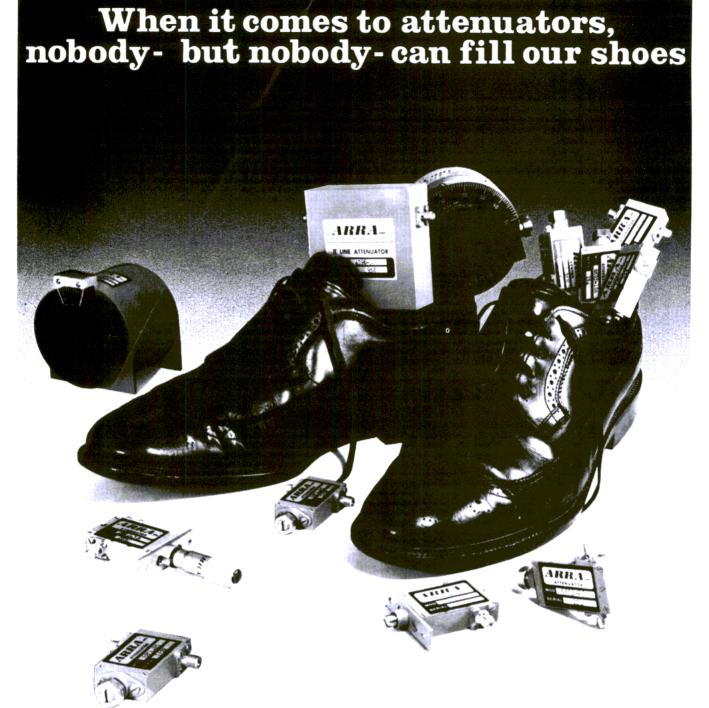
Design Features

In September, the Design Features section offers a variety of contributed articles in support of the issue theme, including a technique for modeling and verifying timing jitter in oscillators, a review of tunable oscillator-design fundamentals, and methods for making triggered measurements with a sampling power meter.

September also examines the use of harmonic-balance techniques for modeling nonlinear circuits, such as oscillators and high-power amplifiers, and marks the opening of a three-part article series on the design of LNAs. Finally, an author from Analog Devices will explore various LO architectures for the 5-to-6-GHz unlicensed frequency band.

Product Technology

The September Product Technology section will feature a novel new integrated V-connector design for reliable higher-frequency operation, especially for optical components operating at OC-768 rates. Additional product features will examine a line of Darlington HBT-based amplifiers for applications through 5 GHz, a connector system with interchangeable transition pins and tabs, a precision jitter analyzer from a leading supplier of digital oscilloscopes, and an amazing design-kit collection of 90 small-signal amplifiers and a test fixture that sells for only \$10.



After all, who knows more about variable attenuators than ARRA? We've got them all ...and then some!

- High Power: 500 W average, 10 kW peak
- Miniature size, in bands 1.0 to 18.0 GHz
- Direct Reading to 120-dB attenuation
- Absorptive PIN Diode extremely broadband
- Remote Control broadband, direct reading
- Computer Programmable TTL-compatible decimal, binary, or BCD

Write today for *New Catalog No. 98*. Or call (631) 231-8400 with your special requirements. Customer specials have been our way of life for over 40 years.

... the last word in variable attenuators



15 Harold Court, Bay Shore, NY 11706 • 631-231-8400 FAX: 631-434-1116 • E-Mail: sales@arra.com

Visit our website at www.arra.com



Funny. "Global coverage" has been on our minds, too. North America. Europe. Asia. Anaren® serves the world's premier

wireless OEMs through a well-connected, worldwide sales and distribution network. Add in our savvy engineers — who know international wireless markets and protocols like the back of their calculators — and you have an experienced RF team that provides unfettered, single-source service, regardless of your location or your application. Take the first step to being our global partner: get your free Anaren "Thinking Kit." To reply, use the reader service number.



Combiners and Dividers



Attenuators







Circulators and Isolators

Splitter/Combiner Assemblies

Backplanes and Custom Products



Think Anaren® ... for resistor, termination, and attenuator choices.

Anaren® serves up plenty in its full line of RF Power resistors, terminations, and attenuators. First, Beryllium Oxide (BeO) or Aluminum Nitride (AlN) — each substrate's thick-film construction yields a rugged, reliable component that's 100% tested.

Second, a plethora of packaging styles, including surface mount, flangeless, flanged, and chip — ideal for a wide range of RF and microwave applications. Finally, power — 5 to 800 watts of output with welded silver contacts for greater conductivity.

Whatever's on your mind, use the

reader service number to receive your free

Anaren "Thinking Kit." Or email Anaren at

rfpresistor@anaren.com.

You want choices?